



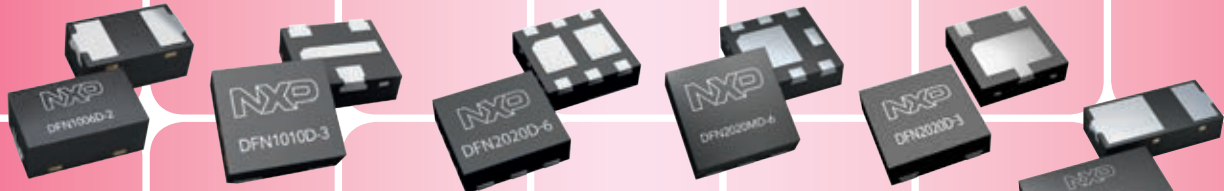
Discrete semiconductors selection guide 2015

Bipolar transistors, diodes, ESD protection, filtering and signal conditioning, MOSFETs, and thyristors



The next generation of packaging

DFN / DSN packages – high performance on a smaller footprint

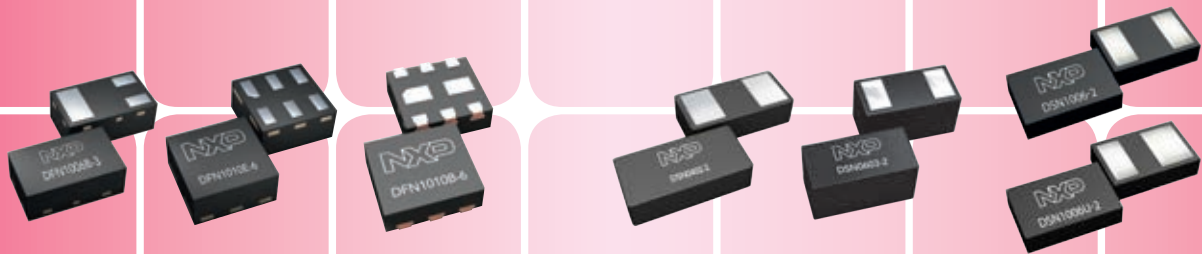


100% solderable side pads

- ▶ Improved electro-thermal behaviour
- ▶ For visual solder inspection

Heat sink at die pad

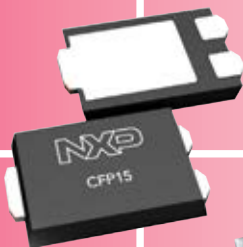
- ▶ For high power on a small footprint
- ▶ Enabling smaller designs



Smallest packages

- ▶ Outline down to 0.4 x 0.2 mm
- ▶ Height down to 0.12 mm
- ▶ For ultra-compact and slim designs

True power packages for smart efficiency – with solid wireless-clip design



The miniaturization of power

- ▶ Only 1 mm in height
- ▶ Excellent electro-thermal behavior
- ▶ For high-temperature use (175 °C)



**FlatPower: CFP15 (SOT1289)
SOD128 / SOD123W**

- ▶ Same performance as SMA / SMB on a much smaller footprint

LFPAK56/56D (SOT669 / SOT1205)

- ▶ Same performance as DPAK, on a much smaller footprint

Discretes semiconductors selection guide 2015

Bipolar transistors

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Benefit from interactive features in the online edition of this selection guide: A click on a product type takes you to the corresponding product information page on the NXP website. There you'll find data sheets and other design-support documents. To access the online selection guide, go to www.nxp.com/discrete_selection_guide

Our extensive package range provides maximum flexibility

	Miniaturization										>> Medium Power				
2 Pins	 DSN0402 (SOD992) 0.4 x 0.2 x 0.12	 DSN0603-2 (SOD962) 0.6 x 0.3 x 0.3	 DSN1006-2 (SOD993) 1.0 x 0.6 x 0.3	 DSN1006U-2 (SOD995) 1.0 x 0.6 x 0.3	 DFN1006D-2 (SOD882D) 1.0 x 0.6 x 0.37	 DFN1006-2 (SOD882) 1.0 x 0.6 x 0.48	 SOD523 1.2 x 0.8 x 0.6	 DFN1608D-2 (SOD1608) 1.6 x 0.8 x 0.37	 SOD323F 1.7 x 1.25 x 0.7	 SOD323 1.7 x 1.25 x 0.95	 SOD123F 2.6 x 1.6 x 1.1	 SOD123W 2.6 x 1.7 x 1.0	 SOD128 3.8 x 2.6 x 1.0	 CFP15 (SOT1289) 5.8 x 4.3 x 0.78	 D2PAK (SOT404) 11.0 x 10.0 x 4.3
3 Pins	 DFN1006B-3 (SOT883B) 1.0 x 0.6 x 0.37	 DFN1006-3 (SOT883) 1.0 x 0.6 x 0.48	 DFN1010D-3 (SOT1215) 1.1 x 1.0 x 0.37	 SOT663 1.6 x 1.2 x 0.55	 SOT323 2.0 x 1.25 x 0.95	 SOT23 2.9 x 1.3 x 1.0	 DFN2020-3 (SOT1061) 2.0 x 2.0 x 0.62	 DFN2020D-3 (SOT1061D) 2.0 x 2.0 x 0.62	 SOT89 4.5 x 2.5 x 1.5	 DPAK (SOT428) 6.6 x 6.1 x 2.3					
4/5 Pins	 WLCSP4*	 WLCSP5*	 SOT665 1.6 x 1.2 x 0.55	 SOT353 2.0 x 1.25 x 0.95	 SOT143B 2.9 x 1.3 x 1.0	 LPAK33 (SOT1210) 3.3 x 3.3 x 0.85	 LPAK56 (SOT669) 4.9 x 4.45 x 1.0	 SOT223 6.5 x 3.5 x 1.65							
6 Pins	 DFN1010E-6 (SOT1202) 1.0 x 1.0 x 0.35	 DFN1010B-6 (SOT1216) 1.0 x 1.0 x 0.37	 DFN1010-6 (SOT891) 1.0 x 1.0 x 0.48	 DFN1410-6 (SOT886) 1.45 x 1.0 x 0.48	 SOT666 1.6 x 1.2 x 0.55	 SOT363 2.0 x 1.25 x 0.95	 DFN2020-6 (SOT1118) 2.0 x 2.0 x 0.62	 DFN2020D-6 (SOT1118D) 2.0 x 2.0 x 0.62	 DFN2020MD-6 (SOT1220) 2.0 x 2.0 x 0.62	 SOT457 2.9 x 1.5 x 1.0	 LPAK56D (SOT1205) 4.9 x 4.45 x 1.0				
≥ 7 Pins	 DFN2110-9 (SOT1178) 2.1 x 1.0 x 0.48	 DFN2111-7 (SOT1358) 2.1 x 1.1 x 0.5	 DFN2510A-10 (SOT1176) 2.5 x 1.0 x 0.48	 DFN2520-9 (SOT1333) 2.5 x 2.0 x 0.48	 DFN2521-12 (SOT1156-1) 2.5 x 2.1 x 0.5	 DFN3525-16 (SOT763) 3.5 x 2.5 x 0.5	 DFN4020-14 (SOT1334) 4.0 x 2.0 x 0.48	 DFN4040-32 (SOT1318-1) 4.0 x 4.0 x 0.5	 DFN5050-32 (SOT617-3) 5.0 x 5.0 x 0.85						

* The exact position of the balls and package dimensions vary.

The partner for excellence, experience, and innovation



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Our commitment: quality and reliability

AEC-Q101

- ▶ Our product-qualification strategies begin with a baseline of AEC-Q101, and then exceed this standard.
- ▶ NXP has more than 15 years of experience qualifying small-signal discretes for automotive, and we've generated an impressive track record of reliability.



- ▶ All our processes and manufacturing plants are subject to regular international and internal audits, including the following:
 - ▶ ISO9001
 - ▶ ISO/TS 16949 for automotive sites
 - ▶ ISO14001
 - ▶ OHSAS18001



- ▶ NXP's Design for Excellence (DfX) program ensures that each new development builds on past learning and that best practices are always employed. The result is continual product improvement.



- ▶ Our "Zero Defects" culture is supported by a dedicated team of technical experts, specializing in product quality, failure analysis, and process engineering, and working at all stages of development and production. Failure analysis is supported by a determination to find root causes and to eliminate failure modes through widespread adoption of quality-analysis tools and methodologies (e.g. Six-Sigma, Safe-Launch).

Rigorous attention to detail and commitment to quality have yielded a very low product failure rate of a single-digit part per billion (ppb).



Bipolar transistors

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High power transistors double	10

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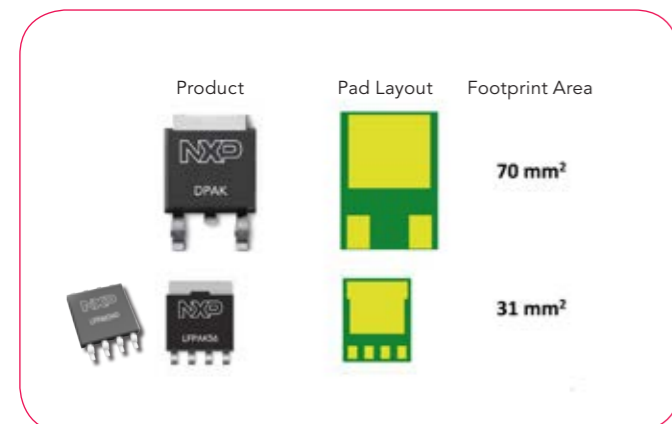
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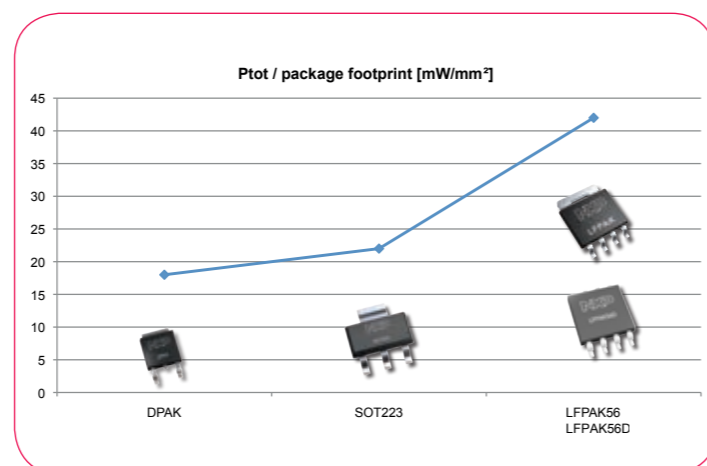
Bipolar transistors in LFPAK56 and LFPAK56D

Miniaturization of power

Same power dissipation but half the size



55 % package size reduction while retaining the same power performance

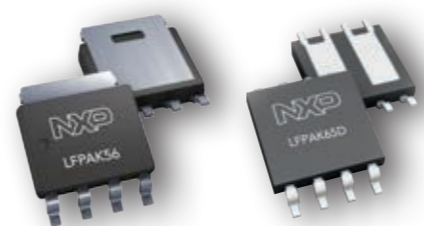


Reduced PCB area requirements compared to SOT223 and DPAK

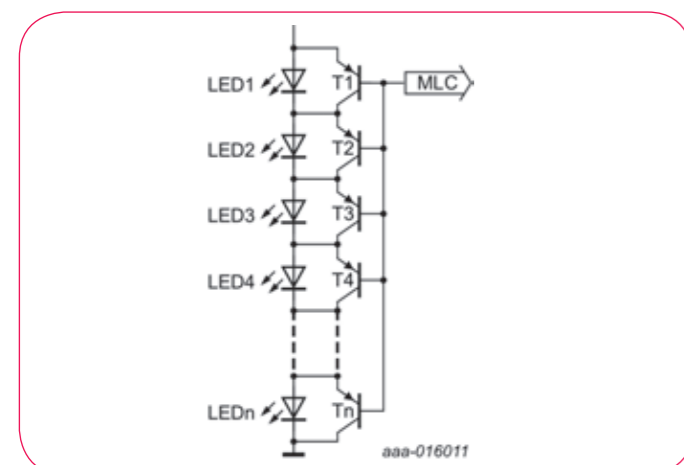
In the spotlight

Bipolar transistors in LFPAK56 and LFPAK56D power packages

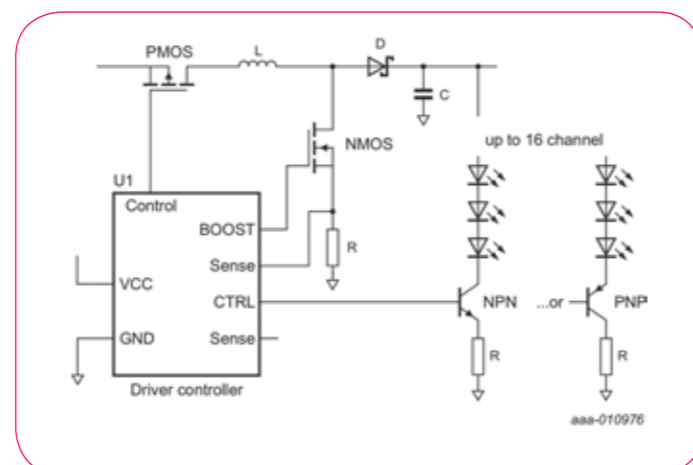
- High thermal power dissipation up to 3 W
- V_{ceo} up to 100 V
- All types in LFPAK56D and 18 types in LFPAK56 AECQ 101 qualified (I_C = 3 up to 15 A)
- 2 types in LFPAK56D with current gain matching of 5 and 10 %
- Reduced PCB area requirements compared to transistors in DPAK
- Suitable for high-temperature applications up to 175 °C
- Designed for reliability, solid copper clip, wire-free
- High energy efficiency due to less heat generation
- Ultra-thin packages of only 1 mm height



Dimming transistor in matrix headlamp



Backlight unit (PHPT61002NYC/PYC)



LFPAK56 (SOT669)
Single package
4.8 x 6 x 1.1

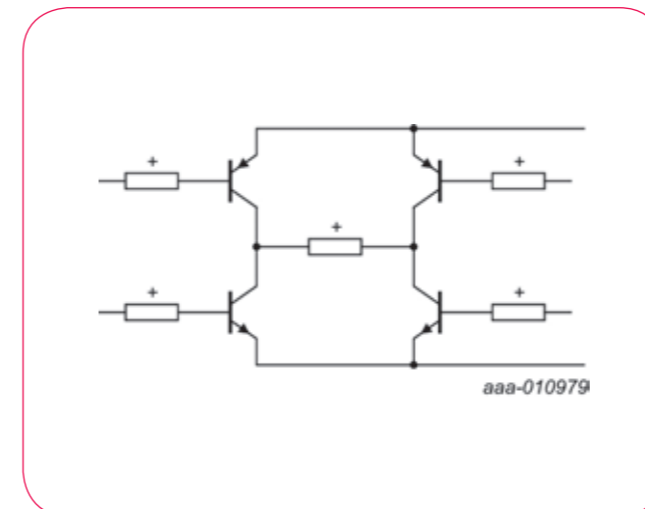
Applications

- ▶ Power management
- ▶ Loadswitch
- ▶ Linear-mode voltage regulator
- ▶ Backlight units
- ▶ Motor drive
- ▶ LED lighting
- ▶ Relay replacement
- ▶ IGBTdrive

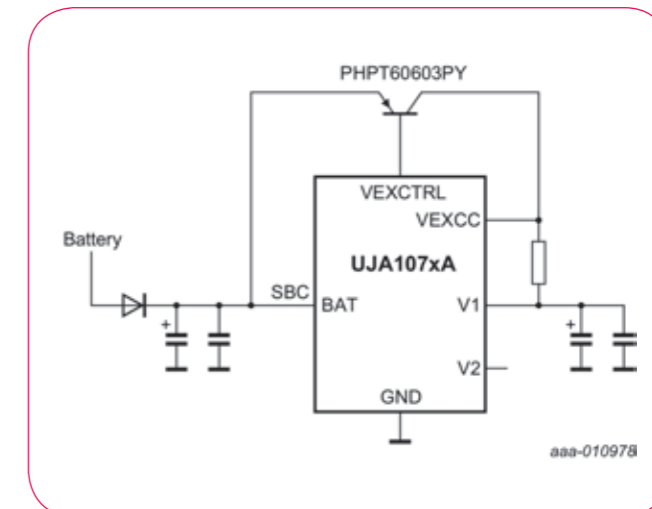


LFPAK56D (SOT1205)
Dual package
4.8 x 6 x 1.1

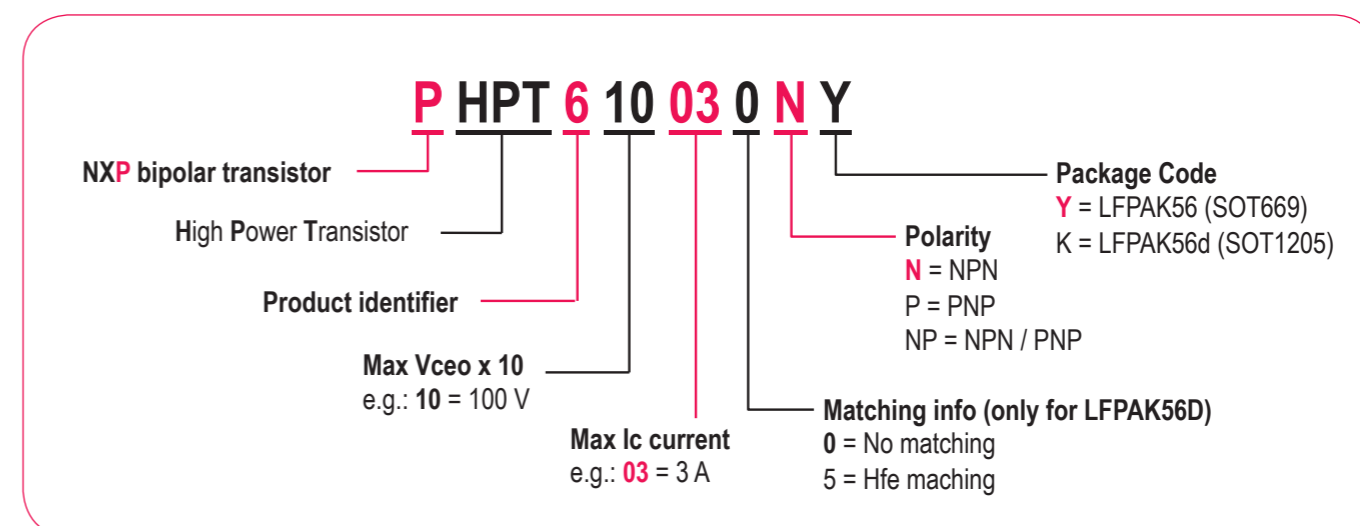
Motor drive (2x PHPT60603NY/PY) or a double LFPAK56D (PHPT610030NK/PK)



IVN – System Basis Chip (PHPT60603PY) External pass transistor, linear regulator



Nomenclature for high-power transistors



High-power transistors (single)

Package													LFPAK56 (SOT669)
Size (mm)													4.8 x 6 x 1.1
V_{CE0} (V)	I_C (A)	I_{CM} (A)	h_{FE} typ	@ I_C (A)	@ V_{CE} (V)	R_{CEsat} typ. @ $I_C/I_B=10$	V_{CEsat} typ (mV); $I_C = 0.5$ A; $I_B = 0.05$ A	V_{CEsat} max (mV)	@ I_C (A)	@ I_B (A)	Polarity		
60	3	8	200 / 400	0.5	2	60	50	270	3	0.3	NPN	PHPT60603NY	
			200 / 400	0.5	2	80	70	360	3	0.3	PNP	PHPT60603PY	
150 / 250	0.5		10	75	50	330	3	0.3	NPN	PHPT61003NY			
150 / 220	0.5		10	110	70	360	2	0.2	PNP	PHPT61003PY			
100	3	6	150 / 250	0.5	10	80	50	300	2	0.2	NPN	PHPT61002NYC	
	150 / 220		0.5	10	125	70	400	2	0.2	PNP	PHPT61002PYC		

High-current, high-power transistors

Package							LFPAK56 (SOT669)
Size (mm)							4.8 x 6 x 1.1
V_{CE0} (V)	I_C (A)	h_{FE} typ	@ I_C (A)	@ V_{CE} (V)	Polarity		
40	6	200/400	0.5	2	NPN	PHPT60406NY	
40	6	200/400	0.5	2	PNP	PHPT60406PY	
40	10	200/400	0.5	2	NPN	PHPT60410NY	
40	10	200/400	0.5	2	PNP	PHPT60410PY	
40	15	200/400	0.5	2	NPN	PHPT60415NY	
40	15	200/400	0.5	2	PNP	PHPT60415PY	
60	6	200/400	0.5	2	NPN	PHPT60606NY	
60	6	150/250	0.5	2	PNP	PHPT60606PY	
60	10	200/400	0.5	2	NPN	PHPT60610NY	
60	10	150/250	0.5	2	PNP	PHPT60610PY	
100	6	150/250	0.5	10	NPN	PHPT61006NY	
100	6	150/220	0.5	10	PNP	PHPT61006PY	
100	10	150/250	0.5	10	NPN	PHPT61010NY	
100	10	150/220	0.5	10	PNP	PHPT61010PY	

High-power transistors (double)

Package													LFPAK56D (SOT1205)
Size (mm)													4.8 x 6 x 1.1
V_{CE0} (V)	I_C (A)	I_{CM} (A)	h_{FE} typ	@ I_C (A)	@ V_{CE} (V)	R_{CEsat} typ. @ $I_C/I_B=10$	V_{CEsat} typ (mV); $I_C = 0.5$ A; $I_B = 0.05$ A	V_{CEsat} max (mV)	@ I_C (A)	@ I_B (A)	Polarity	h_{FE1}/h_{FE2}	
100	3	6	150	0.5	10	80	50	300	3	0.2	2XNPN	-	
						125	70	400	3	0.2	2XPNP	-	
						80 / 125	50 / 70	300 / 400	3	0.2	NPN/PNP	-	
						80	50	300	3	0.2	2XNPN	0.95	
						125	70	400	3	0.2	2XPNP	0.9	

Low V_{CEsat} (BISS) transistors single NPN

In the spotlight


New low V_{CEsat} transistors up to 2 A in DFN1010D-3: 2 A on 1.1 mm² footprint

High I_C performance on ultra-small footprint

V_{CE} 30 and 60 V

Leadless DFN1010D-3 (SOT1215) SMD package with solderable sidepads (1.1 x 1.0 x 0.37)

AEC-Q101 qualified



types in **bold** represent new products

Package											SOT23	SOT323 (SC-70)	SOT363 (SC-88)	DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)	DFN1010D-3 (SOT1215)
Size (mm)											2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37	1.1 x 1.0 x 0.37
P_{tot} (mW)											480	350	430	250	250	750
V_{CE0} (V)	I_C (A)	I_{CM} (A)	h_{FE} min/typ	@ I_C (A)	@ V_{CE} (V)	R_{CEsat} typ (mΩ); $I_C/I_B = 10$	V_{CEsat} typ (mV); $I_C = 0.5$ A; $I_B = 0.05$ A	V_{CEsat} max (mV)	@ I_C (A)	@ I_B (A)						
15	0.5	1	200 / 325	0.01	2	360	-	250	0.5	0.05					PBSS2515M	PBSS2515MB
			200 / 425	0.01	2	300	200	250	0.5	0.05						
20	1	3	350 / 470	0.1	2	220	110 ²⁾	250	1	0.05	PBSS4120T					
			220 / 330	0.1	2	80	45	310	3	0.3	PBSS4320T					
	4.3	8	300 / 550	0.5	2	36	21	220	4	0.2	PBSS4021NT					
			230 / 380	0.5	2	175	90	235	1	0.1						PBSS4130QA
30	1	3	300 / 450	0.5	2	240	120 ²⁾	270	1	0.05	PBSS4130T					
			300 / 450	0.5	2	120	70	320	2	0.2	PBSS4230T					
	2.6	5	230 / 380	0.5	2	135	75	350	2	0.2						PBSS4230QA
			300 / 500	0.5	2	76	80	320	3	0.3	PBSS4032NT ³⁾					
40	0.5	1	200 / 550	0.01	2	380	200 ²⁾	250	0.5	0.05					PBSS2540M	PBSS2540MB
			200 / 350	0.01	2	380	190	250	0.5	0.05						
	2.0	3	300 / 440	0.5	5	240	130	500	1	0.1				PBSS4140U		
			300 / 510	0.5	5	230	120	500	1	0.1	PMMT491A					
			300 / 420	0.5	5	150	130	500	1	0.1	PBSS4140T					
	3.0	8	300 / -	0.5	5	280	140	510	2	0.2						
			350 / 470	0.1	2	120	70	320	2	0.2					PBSS4240Y	
			300 / 450	0.5	2	120	70	320	2	0.2	PBSS4240T					
50	2	5	300 / 495	0.5	2	100	60	260	2	0.2	PBSS4350T					
60	1.0	1.5	150 / 240	0.5	2	170	90	235	1	0.1					PBSS4160QA	
			200 / 420	0.5	5	230	120	280	1	0.1				PBSS4160U		
	3.8	8	200 / 350	0.5	5	200	110	250	1	0.1	PBSS4160T					
			150 / 240	0.5	2	125	75	350	2	0.2					PBSS4260QA	
100	1.0	3.0	150 / 400	0.25	10	160	80	200	1	0.1					PBSS8110Y	
			150 / 300	0.25	10	165	70	200	1	0.1	PBSS8110T					

¹⁾ $I_C / I_B = 20$ ²⁾ V_{CEsat} (max) ³⁾ Optimized for high-speed switching

Low V_{CEsat} (BISS) transistors single PNP

In the spotlight

Low V_{CEsat} transistors up to 2 A in DFN1010D-3: 2 A on 1.1 mm² footprint

High I_c performance on ultra-small footprint

V_{CE} 30 and 60 V

Leadless DFN1010D-3 (SOT1215) SMD package with solderable sidepads (1.1 x 1.0 x 0.37)

AEC-Q101 qualified

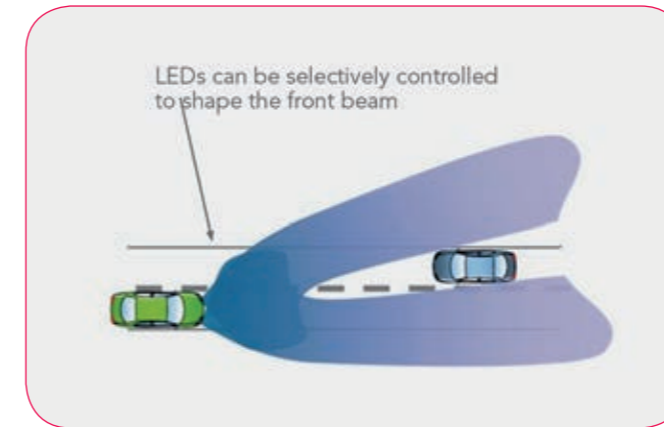


Package		SOT23	SOT323 (SC-70)	SOT363 (SC-88)	DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)	DFN1010D-3 (SOT1215)				
Size (mm)		2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37	1.1 x 1.0 x 0.37				
P_{tot} (mW)		480	350	430	250	250	750				
V_{CEO} (V)	I_c (A)	I_{CM} (A)	h_{FE} min/typ	@ I_c (A)	@ V_{CE} (V)	R_{CEsat} typ (mΩ); $I_c/I_b = 10$	V_{CEsat} typ (mV); $I_c = 0.5$ A; $I_b = 0.05$ A	V_{CEsat} max (mV)	@ I_c (A)	@ I_b (A)	Product
15	0.5	1	200 / 260	0.01	2	300	150	250	0.5	0.05	PBSS3515M, PBSS3515MB
20	2.0	1	300 / 450	0.1	2	250	125 2)	250	1	0.05	PBSS5120T
		3	225 / -	0.5	2	115	80 2)	225	2	0.2	PBSS5220T
		5	220 / 420	0.5	2	75	50	210	3	0.2	PBSS5320T
30	1	1.5	180 / 295	0.5	2	160	85	240	1	0.1	PBSS5130QA
		2	300 / 450	0.1	2	160	70	350	2	0.2	PBSS5230T
40	1.0	2	180 / 295	0.5	2	125	70	330	2	0.2	PBSS5230QA
		2.4	200 / 320	0.5	2	110	95	330	2	0.2	PBSS4032PT ³⁾
50	2.0	0.5	200 / 380	0.01	2	440	220	350	0.5	0.05	PBSS3540M, PBSS3540MB
		1	200 / 380	0.01	2	440	230	350	0.5	0.05	
		2	300 / 520	0.1	5	230	130	500	1	0.1	PBSS5140U
		3	300 / 800	0.1	5	250	130	500	1	0.1	PMMT591A
		4	300 / 510	0.1	5	230	130	500	1	0.1	PBSS5140T
60	1.0	1	300 / -	0.1	2	200	110 2)	350	2	0.2	PBSS5240Y
		2	300 / 450	0.1	2	150	70	350	2	0.2	PBSS5240T
		3	200 / -	0.5	2	150	90 2)	300	2	0.1	PBSS5250T
		5	200 / 360	0.5	2	90	55	270	2	0.2	PBSS5350T
100	1.0	1.5	120 / 185	0.5	2	225	125	330	1	0.1	PBSS5160QA
		2	150 / 250	0.5	5	255	135	340	1	0.1	PBSS5160U
		3	150 / 250	0.5	5	220	120	330	1	0.1	PBSS5160T
100	3.0	1.7	120 / 185	0.5	2	205	105	500	1-Jul	0.17	PBSS5260QA
		2.7	200 / 300	0.5	2	80	49	360	3	0.3	PBSS4041PT
100	1.0	1	150 / -	0.25	5	170	93	320	1	0.1	PBSS9110Y
		2	150 / 350	0.5	5	170	95	320	1	0.1	PBSS9110T

¹⁾ $I_c / I_b = 20$ ²⁾ V_{CEsat} (max) ³⁾ Optimized for high-speed switching

DFN2020D-6 with solderable sidepads Innovation for LED lighting in automotive

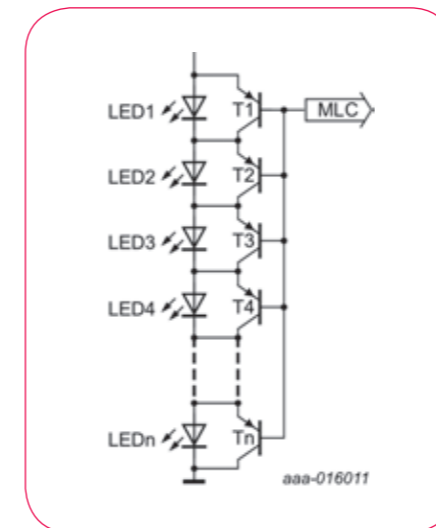
Matrix light sketch



PBSS5160PAPS in DFN2020D-6

- ▶ Industry first low V_{CEsat} transistor in DFN2020 with 100 % solderable sidepads
- ▶ Enables individual dimming in the LED front light matrix solution
- ▶ Offers automatic optical inspection of solder joints
- ▶ Saves PCB space by replacing two DFN2020D-3 or two SOT89 packages

Dimming transistor application



Key package benefits

- ▶ AEC-Q101 qualified
- ▶ Suitable for AOI of solder joints
- ▶ Leadless SMD plastic package with solderable side pads
- ▶ Exposed heat sink for excellent thermal and electrical conductivity
- ▶ Package size of only 2 x 2 mm and a height of only 0.62 mm
- ▶ Single version available in DFN2020D-3

Low V_{CEsat} double transistors portfolio on DFN2020D-6

V_{CEO} (V)	I_c (A)	Polarity	h_{FE} min	@ I_c (A)	@ V_{CE} (V)	V_{CEsat} typ (mV); $I_c = 0.5$ A; $I_b = 0.05$ A	V_{CEsat} max (mV)	@ I_c (A)	@ I_b (A)	Product
60	1	NPN / NPN	150	0.5	2	90	120	0.5	0.05	PBSS4160PANS
		PNP / PNP	120	0.5	2	125	180	0.5	0.05	PBSS5160PAPS
		NPN / PNP	150 / 120	0.5	2	90 / 125	120 / 180	0.5	0.05	PBSS4160PANPS

Medium-power low V_{CEsat} (BISS) transistors single PNP

types in **bold** represent new products

Package												SOT223 (SC-73)	SOT89 (SC-62)	SOT457 (SC-74)	DFN2020-3 (SOT1061)	DFN2020D-3 (SOT1061D)
Size (mm)												6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.5 x 1.0	2.0 x 2.0 x 0.62	2.0 x 2.0 x 0.62
P_{tot} (mW)												1700	1650	750	1300	1300
V_{CEO} (V)	I_C (A)	I_{CM} (A)	h_{FE} min/typ	@ I_C (A)	@ V_{CE} (V)	R_{CEsat} typ ($I_C/I_B = 10$) (m Ω)	V_{CEsat} typ ($I_C = 0.5$ A; $I_B = 0.05$ A) (mV)	V_{CEsat} max (mV)	@ I_C (A)	@ I_B (A)						
12	5.3	10.6	250 / 400	0.5	2	28 ¹⁾	20	210	5.3	0.265						
	5.7	11.4	250 / 400	0.5	2	30 ¹⁾	20	245	5.7	0.285	PBSS301PZ					
	6	7	220 / 335	0.5	2	33 ¹⁾	20	300	6	0.3						PBSS5612PAS
20	3	5	200 / -	0.5	2	85	80 ²⁾	400	3	0.3						
			220 / 450	0.5	2	90	50	300	3	0.3						
	3.5	8	250 / 400	0.5	2	55	35	375	4	0.2						
	4	15	250 / 400	0.5	2	50	35	280	4	0.4						
	5	10	300 / 430	0.5	2	34	45	270	5	0.5						
	5.1	10.2	250 / 370	0.5	2	32 ¹⁾	25	230	5.1	0.255						
	5.5	11	250 / 370	0.5	2	34 ¹⁾	25	265	5.5	0.275	PBSS302PZ					
	6	7	230 / 345	0.5	2	39 ¹⁾	25	350	6	0.3						
30	2.7	5	200 / 350	0.5	2	88	87	395	3	0.3						
			200 / 380	0.5	2	80	50	320	3	0.3						
	3	5	200 / 320	0.5	2	75	45	320	3	0.3						
	4.2	10	200 / 350	0.5	2	58	70	345	4	0.4						
	4.4	10	200 / 350	0.5	2	58	70	400	4	0.2	PBSS4032PZ ³⁾					
	5.1	10.2	250 / 400	0.5	2	32 ¹⁾	25	230	5.1	0.255						
	5.3	10.6	250 / 400	0.5	2	35 ¹⁾	25	265	5.3	0.265	PBSS303PZ					
	6	7	200 / 335	0.5	2	39 ¹⁾	25	350	6	0.3						
	6.6	20	250 / 400	0.5	2	22	16	240	7	0.35	PBSS4021PZ					
	2.7	5	200 / 350	0.5	2	88	87	395	3	0.3						
40	2.0	3.0	215 / -	0.5	5	340	170	500	2	0.2						
			200 / 310	0.5	2	55	46	300	4	0.4						
	4	10	250 / 370	0.5	2	45	33	375	5	0.5						
	5	10	250 / 350	0.5	2	55	40 ¹⁾	160	2	0.2	PBSS5540Z					
	2.0	5	200 / -	0.5	2	160	90 ²⁾	320	2	0.2						
	3.0	5.0	200 / 300	0.5	2	120	70	300	2	0.2						
	3.0	5.0	200 / 375	0.5	2	120	70	390	3	0.3						
	3.0	5.0	200 / 300	0.5	2	120	70	300	2	0.2	PBSS5350Z					
3	6	180 / 265	0.5	2	70	55	290	3	0.3							
60	4.2	8.4	200 / 295	0.5	2	53 ¹⁾	35	310	4.2	0.21						
			200 / 295	0.5	2	59 ¹⁾	35	375	4.5	0.225	PBSS304PZ					
	4.5	9	200 / 295	0.5	2	59 ¹⁾	35	375	4.5	0.225						
	5	6	170 / 260	0.5	2	35 ¹⁾	35	450	5	0.25						
	5	15	200 / 300	0.5	2	40	30	300	5	0.5						
	5.7	15	200 / 300	0.5	2	29	22	285	6	0.3	PBSS4041PZ					
80	3	5	155 / 225	0.5	2	71	55	290	3	0.3						
			180 / 265	0.5	2	65 ¹⁾	40	420	4	0.2						
	4.0	10	200 / 300	0.5	2	50	35	380	5	0.5						
	4.0	8	200 / 280	0.5	2	43	36	240	4	0.4						
	4.5	9	200 / 280	0.5	2	69 ¹⁾	36	450	4.5	0.225	PBSS305PZ					
100	1.0	3.0	150 / 350	0.5	5	170	100	320	1	0.1						
			150 / 350	0.5	5	170	90	320	1	0.1						
			150 / -	0.5	5	170	90	320	1	0.1	PBSS9110Z					
	2	3	175 / 275	0.5	2	88	65	250	2	0.2						
	2.7	4	180 / 295	0.5	2	110 ¹⁾	45	450	2.7	0.135						
3.7	7.4	200 / 300	0.5	2	52	45	300	4	0.4							
4.1	8.2	200 / 300	0.5	5	57	45	325	4.1	0.41	PBSS306PZ						

¹⁾ $I_C / I_B = 20$ ²⁾ V_{CEsat} (max) ³⁾ Optimized for high-speed switching

Low V_{CEsat} (BISS) load switches

Package				SOT457 (SC-74)	SOT363 (SC-88)
Size (mm)				2.9 x 1.5 x 1.0	2.0 x 1.25 x 0.95
P_{tot} (mW)				750 ¹⁾	300 ²⁾
V_{CEO} (V)	I_C (A)	V_{CEsat} max (mV); $I_C = 0.5$ A; $I_B = 0.05$ A	R1, R2 (k Ω)		
15	0.5	250	2.2		
			4.7		PBLS1501Y
			10		PBLS1502Y
			22		PBLS1503Y
20	1	150	2.2		PBLS2001D
			4.7		PBLS2002D
			10		PBLS2003D
			22		PBLS2004D
20	1.8	70	2.2	PBLS2021D	
			4.7	PBLS2022D	
			10	PBLS2023D	
			22	PBLS2024D	
40	0.5	350	2.2		PBLS4001Y
			4.7		PBLS4002Y
			10		PBLS4003Y
			22		PBLS4004Y
	1	170	2.2		PBLS4005Y
			4.7		PBLS4001D
			10		PBLS4002D
			22		PBLS4003D
60	1	180	2.2		PBLS6001D
			4.7		PBLS6002D
			10		PBLS6003D
			22		PBLS6004D
	1.5	100	2.2	PBLS6021D	
			4.7	PBLS6022D	
			10	PBLS6023D	
			22	PBLS6024D	

¹⁾ Device mounted on a ceramic PCB, Al₂O₃, standard footprint

²⁾ Device mounted on an FR4 PCB, single-sided copper, tin-plated, and standard footprint

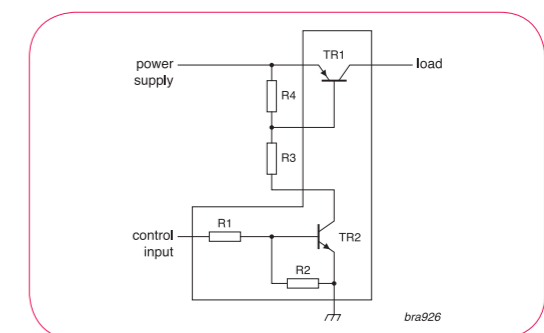
Key features and benefits

- ▶ Very small input current drives high load current
- ▶ High efficiency and low voltage drop due to low V_{CEsat} (BISS) pass transistor
- ▶ Replaces expensive P-MOSFETs
- ▶ Inherent reverse-current blocking
- ▶ Automotive qualified according to AEC-Q101

Key applications

- ▶ Fan driver
- ▶ Battery-charge switch
- ▶ Supply-line switch
- ▶ High-side load

Low V_{CEsat} (BISS) load switch – the optimal choice for supply-line and high-side switches



High-voltage low V_{CEsat} (BISS) transistors

types in **bold** represent new products

Package				SOT223 (SC-73)	SOT89 (SC-62)	SOT23
Size (mm)				6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.3 x 1.0
P _{tot} (mW)				1700	1300	250
Polarity	V _{CESM} ¹⁾	V _{CEO} (V)	I _C (A)			
NPN	-	150	1	PBHV8115Z	PBHV8115X	PBHV8115T
			2	PBHV8215Z		
		180				PBHV8118T
	500	600	0.5	PBHV8560Z		
			400	PBHV8540Z	PBHV8540X	PBHV8540T
		500	0.15			PMBTA45
PNP	-	140	4	PBHV9414Z		
			1	PBHV9115Z	PBHV9115X	PBHV9115T
		150	2	PBHV9215Z		
		600	0.5	PBHV9560Z		
			0.1	PBHV3160Z		
	500	400	0.25	PBHV9040Z	PBHV9040X	PBHV9040T
			0.5	PBHV9540Z		
		500	0.15	PBHV3160Z		PBHV9050T
			0.25	PBHV9050Z		

¹⁾ Collector-emitter peak voltage

In the spotlight

High-voltage low V_{CEsat} (BISS) transistors in SOT223, SOT23 & SOT89

- Voltage V_{CEO} up to 600 V
- Current I_C up to 4 A (continuous), 10 A (peak)
- V_{CEsat} down to 33 mV
- AEC-Q101 qualified

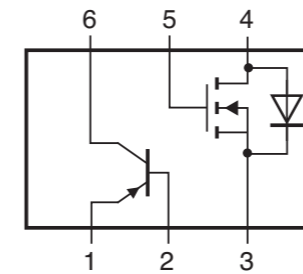


Low V_{CEsat} (BISS) RETs

Package					SOT23	
Size (mm)					2.9 x 1.3 x 1.0	
P _{tot} (mW)					250	
V _{CEO} (V)	I _C (mA)		R1 (kΩ)	R2 (kΩ)	NPN	PNP
40	600	R1 = R2	1	1	PBRN113ET	PBRP113ET
			2.2	2.2	PBRN123ET	PBRP123ET
		R1 ≠ R2	1	10	PBRN113ZT	PBRP113ZT
			2.2	10	PBRN123YT	PBRP123YT

Low V_{CEsat} (BISS) transistor PNP – N-channel MOSFET combination

Package											DFN2020-6 (SOT1118)
Size (mm)											2.0 x 2.0 x 0.62
P _{tot} (mW)											1300
V _{CEO} (V)	I _C (A)	h _{FE min}	h _{FE max}	@ I _C (mA)	@ V _{CE} (V)	R _{CEsat} typ (mΩ)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{Dson} typ (mΩ)	
40	2	300	800	100	5	240	30	0.7	0.66	390	PBSM5240PF
		100	-	100	5	240	30	0.7	0.66	390	PBSM5240PFH



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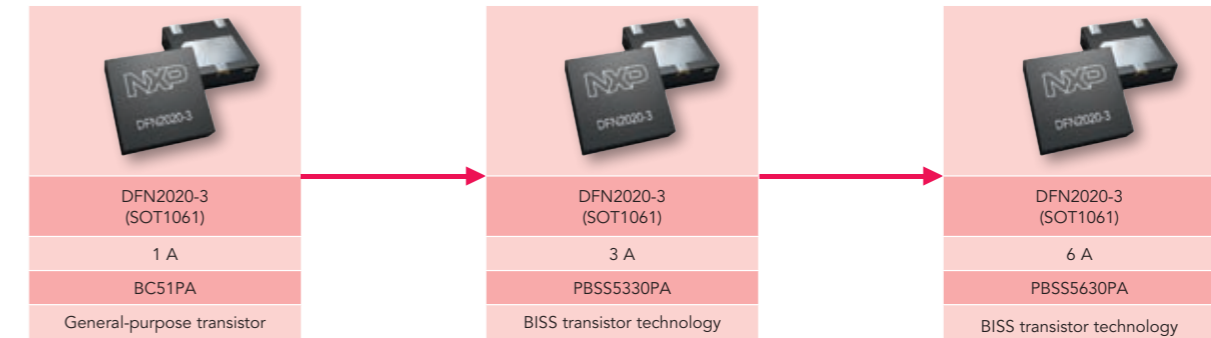
Combination of low V_{CEsat} transistor with N-channel MOSFET in the very small and ultrathin leadless package DFN2020-6 (SOT1118)

Advantages of low V_{CEsat} (BISS) technology



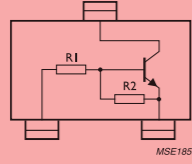
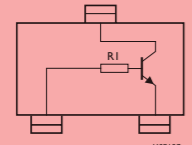
Our BISS (Breakthrough In Small-Signal) transistors show lowest V_{CEsat} values due to an innovative mesh-emitter technology and further technology improvement. They also reduce board space due to improved collector-current capabilities as shown below.

Improved collector-current capabilities



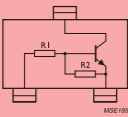
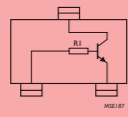
▶ 17.87 mm² footprint






RETs 100 mA single - Part 1

Package				SOT23		SOT323 (SC-70)		
								
Size (mm)				2.9 x 1.3 x 1.0		2.0 x 1.25 x 0.95		
P _{tot} (mW)				250		200		
V _{CEO} (V)	I _C (mA)	Configuration	R1 (kΩ)	R2 (kΩ)	NPN	PNP	PNP	
50	100		1	1		PDTA113ET		PDTA113EU
			2.2	2.2	PDTC123ET	PDTA123ET	PDTC123EU	PDTA123EU
			4.7	4.7	PDTC143ET	PDTA143ET	PDTC143EU	PDTA143EU
			10	10	PDTC114ET	PDTA114ET	PDTC114EU	PDTA114EU
			22	22	PDTC124ET	PDTA124ET	PDTC124EU	PDTA124EU
			47	47	PDTC144ET	PDTA144ET	PDTC144EU	PDTA144EU
			100	100	PDTC115ET	PDTA115ET	PDTC115EU	PDTA115EU
			1	10		PDTA113ZT		PDTA113ZU
			2.2	10	PDTC123YT	PDTA123YT	PDTC123YU	PDTA123YU
			2.2	47	PDTC123JT	PDTA123JT	PDTC123JU	PDTA123JU
		4.7	10	PDTC143XT	PDTA143XT	PDTC143XU	PDTA143XU	
		4.7	47	PDTC143ZT	PDTA143ZT	PDTC143ZU	PDTA143ZU	
		10	47	PDTC114YT	PDTA114YT	PDTC114YU	PDTA114YU	
		22	47	PDTC124XT	PDTA124XT	PDTC124XU	PDTA124XU	
		47	10	PDTC144VT	PDTA144VT	PDTC144VU	PDTA144VU	
		47	22	PDTC144WT	PDTA144WT	PDTC144WU	PDTA144WU	
		2.2	-	PDTC123TT	PDTA123TT	PDTC123TU	PDTA123TU	
		4.7	-	PDTC143TT	PDTA143TT	PDTC143TU	PDTA143TU	
		10	-	PDTC114TT	PDTA114TT	PDTC114TU	PDTA114TU	
		22	-	PDTC124TT	PDTA124TT	PDTC124TU	PDTA124TU	
47	-	PDTC144TT	PDTA144TT	PDTC144TU	PDTA144TU			
100	-	PDTC115TT	PDTA115TT	PDTC115TU	PDTA115TU			
								




RETs 100 mA single - Part 2

Package				DFN1006-3 (SOT883)		DFN1006B-3 (SOT883B)		
								
Size (mm)				1.0 x 0.6 x 0.48		1.0 x 0.6 x 0.37		
P _{tot} (mW)				250		250		
V _{CEO} (V)	I _C (mA)	Configuration	R1 (kΩ)	R2 (kΩ)	NPN	PNP	PNP	
50	100		1	1		PDTA113EM	PDTA113EMB	
			2.2	2.2	PDTC123EM	PDTA123EM	PDTC123EMB	PDTA123EMB
			4.7	4.7	PDTC143EM	PDTA143EM	PDTC143EMB	PDTA143EMB
			10	10	PDTC114EM	PDTA114EM	PDTC114EMB	PDTA114EMB
			22	22	PDTC124EM	PDTA124EM	PDTC124EMB	PDTA124EMB
			47	47	PDTC144EM	PDTA144EM	PDTC144EMB	PDTA144EMB
			100	100	PDTC115EM	PDTA115EM	PDTC115EMB	PDTA115EMB
			1	10		PDTA113ZM		PDTA113ZMB
			2.2	10	PDTC123YM	PDTA123YM	PDTC123YMB	PDTA123YMB
			2.2	47	PDTC123JM	PDTA123JM	PDTC123JMB	PDTA123JMB
		4.7	10	PDTC143XM	PDTA143XM	PDTC143XMB	PDTA143XMB	
		4.7	47	PDTC143ZM	PDTA143ZM	PDTC143ZMB	PDTA143ZMB	
		10	47	PDTC114YM	PDTA114YM	PDTC114YMB	PDTA114YMB	
		22	47	PDTC124XM	PDTA124XM	PDTC124XMB	PDTA124XMB	
		47	10	PDTC144VM	PDTA144VM	PDTC144VMB	PDTA144VMB	
		47	22	PDTC144WM	PDTA144WM	PDTC144WMB	PDTA144WMB	
		2.2	-	PDTC123TM	PDTA123TM	PDTC123TMB	PDTA123TMB	
		4.7	-	PDTC143TM	PDTA143TM	PDTC143TMB	PDTA143TMB	
		10	-	PDTC114TM	PDTA114TM	PDTC114TMB	PDTA114TMB	
		22	-	PDTC124TM	PDTA124TM	PDTC124TMB	PDTA124TMB	
47	-	PDTC144TM	PDTA144TM	PDTC144TMB	PDTA144TMB			
100	-	PDTC115TM	PDTA115TM	PDTC115TMB	PDTA115TMB			
								

RETs 100 mA double

Package					DFN1010B-6 (SOT1216)	SOT363 (SC-88)		SOT666				
												
Size (mm)					1.1 x 1.0 x 0.37	2.0 x 1.25 x 0.95		1.6 x 1.2 x 0.55				
P _{tot} (mW)					350	300		300				
V _{CEO} (V)	I _C (mA)	Configuration	R1 (kΩ)	R2 (kΩ)	NPN / PNP	NPN / NPN	NPN / PNP	PNP / PNP	NPN / NPN	NPN / PNP	PNP / PNP	
50	100	R1 = R2	2.2	2.2			PUMH20	PUMD20	PUMB20	PEMH20	PEMD20	PEMB20
			4.7	4.7			PUMH15	PUMD15	PUMB15	PEMH15	PEMD15	PEMB15
			10	10			PUMH11	PUMD3	PUMB11	PEMH11	PEMD3	PEMB11
			22	22			PUMH1	PUMD2	PUMB1	PEMH1	PEMD2	PEMB1
			47	47	PQMD12		PUMH2	PUMD12	PUMB2	PEMH2	PEMD12	PEMB2
			100	100			PUMH24	PUMD24	PUMB24	PEMH24	PEMD24	PEMB24
			2.2	47			PUMH10	PUMD10	PUMB10	PEMH10	PEMD10	PEMB10
			4.7	10			PUMH18	PUMD18	PUMB18	PEMH18	PEMD18	PEMB18
			4.7	47			PUMH13	PUMD13	PUMB13	PEMH13	PEMD13	PEMB13
			10	47			PUMH9	PUMD9	PUMB9	PEMH9	PEMD9	PEMB9
		22	47			PUMH16	PUMD16	PUMB16	PEMH16	PEMD16	PEMB16	
		47	22			PUMH17	PUMD17	PUMB17	PEMH17	PEMD17	PEMB17	
		47 / 2.2	47 / 47				PUMD48			PEMD48		
		2.2	-				PUMH30	PUMD30	PUMB30	PEMH30	PEMD30	PEMB30
		4.7	-				PUMH7	PUMD6	PUMB3	PEMH7	PEMD6	PEMB3
		10	-				PUMH4	PUMD4	PUMB4	PEMH4	PEMD4	PEMB4
		22	-				PUMH19	PUMD19	PUMB19	PEMH19	PEMD19	PEMB19
		47	-				PUMH14	PUMD14	PUMB14	PEMH14	PEMD14	PEMB14

RETs 500 mA

Package					SOT457 (SC-74)	SOT23	SOT323 (SC-70)			
										
Size (mm)					2.9 x 1.5 x 1.0	2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95			
P _{tot} (mW)					750	250	200			
V _{CEO} (V)	I _C (mA)	Configuration	R1 (kΩ)	R2 (kΩ)	NPN / NPN	NPN / PNP	NPN	PNP		
50	500	R1 = R2	1	1			PDTD113ET	PDTB113ET	PDTD113EU	PDTB113EU
			2.2	2.2			PDTD123ET	PDTB123ET	PDTD123EU	PDTB123EU
			4.7	4.7			PDTD143ET	PDTB143ET	PDTD143EU	PDTB143EU
			10	10			PDTD114ET	PDTB114ET	PDTD114EU	PDTB114EU
			10	10			PDTD144ET	PDTB144ET	PDTD144EU	PDTB144EU
		R1 ≠ R2	1	10	PIMN31	PIMC31	PDTD113ZT	PDTB113ZT	PDTD113ZU	PDTB113ZU
			2.2	10			PDTD123YT	PDTB123YT	PDTD123YU	PDTB123YU
			4.7	10			PDTD143XT	PDTB143XT	PDTD143XU	PDTB143XU
			2.2	-			PDTD123TT	PDTB123TT		
			2.2	-						

types in **bold** represent new products

Single transistors NPN

Package						SOT23	SOT323 (SC-70)	DFN1010D-3 (SOT1215)	DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)
Size (mm)						2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	1.1 x 1.0 x 0.37	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37
P _{tot} (mW)						250	200	750	250	250
V _{CE0} (V)	I _C (mA)	h _{FE} min	h _{FE} max	f _T min (MHz)						
25	100	450	1200	100						
30	100	110 - 200	450 - 800	100		BC848B				PMST5089
		350	900	100						BC848W
32	100	110 - 420	220 - 800	100		BCW31 / 32 / 33				PMST5088
		180 - 380	310 - 630	250		BCW60B / C / D				
45	100	110 - 420	220 - 800	100		BC847 / A / B / C	BC847W / AW / BW / CW	BC847AQA / BQA / CQA	BC847AM / BM / CM	BC847AMB / BMB / CMB
		120 - 380	220 - 630	100		BCX70G / H / J / K				
		110 - 200	220 - 450	100		BCW71 / 72				
50	100	210 - 290	340 - 460	100 - 150		PMBT6429	2PD601ART 2PD601ARL 2PD601ASL	2PD601ARW / SW		
		250	650	100		PMBT6428				
60	100	110 - 200	220 - 450	100		BCV71 / 72				
65	100	110 - 200	220 - 450	100		BC846 / A / B	BC846W / AW / BW			BC846BMB
80	100	20	80	60		BSS64				
50	150	120 - 200	240 - 400	80		NXP3875Y / G				
	150	120 - 270	270 - 560	100			2PC4081Q / R / S		2PC4617QM / RM	2PC4617QMB / RMB
	200	210	340	100		2PD601BRL				
45	500	100 - 250	250 - 600	100		BC817 / -16 / -25 / -40	BC817W / -16W / -25W / -40W	BC817 / -25QA / -40QA		
		100	600	100		BCX19				
50	500	85 - 170	170 - 340	140 - 180		2PD602AQL 2PD602ARL 2PD602ASL	2PD1820AR / S			
60	500	50	-	100						PMSTA05

Single transistors PNP

Package						SOT23	SOT323 (SC-70)	DFN1010D-3 (SOT1215)	DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)
Size (mm)						2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	1.1 x 1.0 x 0.37	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37
P _{tot} (mW)						250	200	750	250	250
V _{CE0} (V)	I _C (mA)	h _{FE} min	h _{FE} max	f _T min (MHz)						
80	500	100	-	50		PMBTA06	PMSTA06			
30	100	125 - 220	500 - 800	100		BC858B	BC858W			
		120 - 215	260 - 500	100		BCW29 / 30				
32	100	180 - 380	310 - 630	100		BCW61B / C / D				
		210 - 290	340 - 460	70 - 80		2PB709ART 2PB709ARL 2PB709ASL	2PB709ARW / SW			
45	100	180 - 380	310 - 630	100		BCX71H / J / K				
		120 - 215	260 - 500	100		BCW69 / 70				
		125 - 420	250 - 800	100		BC857 / A / B / C	BC857W / AW / BW / CW	BC857AQA / BQA / CQA	BC857AM / BM / CM	BC857AMB / BMB / CMB
60	100	120	260	150		BCW89				
65	100	125 - 200	250 - 475	100		BC856 / A / B	BC856W / AW / BW			
100	100	30	-	50		BSS63				
50	150	120 - 270	270 - 560	100			2PA1576Q / R / S		2PA1774QM / RM / SM	2PA1774QMB / RMB / SMB
	200	210	340	100		2PB709BRL				
25	500	290	460	100		2PB709BSL				
		100	600	80		BCX18				
45	500	100 - 250	250 - 600	80		BC807 / -16 / -25 / -40	BC807W / -16W / -25W / -40W	BC807 / -25QA / -40QA		
		100	600	80		BCX17				
50	500	85 - 170	170 - 340	100 - 140		2PB710ARL 2PB710ASL	2PB1219AQ / R / S			
60	500	100	-	50						PMSTA55
80	500	100	-	50						PMSTA56

Double transistors

types in **bold** represent new products

Package						SOT457 (SC-74)	SOT363 (SC-88)	SOT666	DFN1010B-6 (SOT1216)
Size (mm)						2.9 x 1.5 x 1.0	2.0 x 1.25 x 0.95	1.6 x 1.2 x 0.55	1.0 x 1.0 x 0.37
P _{tot} (mW)						750	300	300	350
Polarity	V _{CE0} (V)	I _C (mA)	h _{FE} min	h _{FE} max	f _T min (MHz)				
NPN	40	100	120	450	100			PUMX1	PEMX1
	45	100	200	450	100		BC847DS	BC847BS	BC847BV
	65	100	110	-	100			BC846S	
			200	450	100		BC846DS	BC846BS	
50	150	120	560	100			PUMX2		
PNP	45	500	160	400	80		BC817DS		
	40	100	120	450	100		PIMT1	PUMT1	PEMT1
	45	100	200	450	100			BC857BS	BCC857BV
	65	100	110	-	100			BC856S	
NPN / PNP	45	500	160	400	80		BC807DS		
			200	450	100			BC856BS	
	40	100	120	450	100			PUMZ1	PEMZ1
	45	100	200	450	100			BC847BPN	BC847BVN
50	100	120	560	100			PIMZ2	PUMZ2	
65	100	200	450	100			BC846BPN		
12	500	200	-	250 / 100				PEMZ7	
45	500	160	160	100 / 800			BC817DPN		

Single and double switching transistors

Package							SOT223 (SC-73)	SOT89 (SC-62)	SOT23	SOT323 (SC-70)	SOT363 (SC-88)	SOT666	DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)	
Size (mm)							6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.6 x 1.2 x 0.55	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37	
P _{tot} (mW)							1700	1300	250	200	300	300	250	250	
Configuration							single	single	single	single	double	double	single	single	
Polarity	V _{CE0} (V)	I _C (mA)	h _{FE} min	h _{FE} max	f _T min (MHz)	t _{off} (ns)									
NPN	12	100	40	120	400	20			BSV52						
	40	200	100	300	180	1200			PMBS3904	PMSS3904					
					300	250									
	15	600	40	120	500	20			PMBT2369	PMST2369					
	40	200	100	300	300	250			MMBT3904						
									PMBT3904	PMST3904	PMBT3904YS	PMBT3904VS	PMBT3904M	PMBT3904MB	
	30	600	100	300	250	250			PMBT2222	PMST2222					
	40	600	100	300	300	250			PZT4401	PXT4401	PMBT4401	PMST4401			
									MMBT2222A						
	40	800	100	300	300	250			PZT2222A	PXT2222A	PMBT2222A	PMST2222A			
PNP	40	100	100	300	150	700			PMBS3906	PMSS3906					
	40	200	100	300	250	300			MMBT3906						
									PMBT3906	PMST3906	PMBT3906YS	PMBT3906VS	PMBT3906M	PMBT3906MB	
	40	600	100	300	200	350	300			PZT4403	PXT4403	PMBT4403	PMST4403		
						365	300					PMBT2907			
	60	600	100	300	200	300						PMST2907A			
365	300									BSR16					
NPN / PNP	40	200	100	300	300 / 250	250 / 300			PZT2907A	PXT2907A	PMBT2907A				

Medium-power general-purpose transistors

types in **bold** represent new products

Package						SOT223 (SC-73)	SOT89 (SC-62)	DFN2020-3 (SOT1061)	DFN2020D-3 (SOT1061D)
Size (mm)						6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.0 x 2.0 x 0.62	2.0 x 2.0 x 0.62
P _{tot} (mW)						1700	1300	1300	1300
Polarity	V _{CEO} (V)	I _C (A)	h _{FE} min	h _{FE} max	f _T min (MHz)				
NPN	20	2	85 - 160	375	40	BCP68 / -25	BC868 / -25	BC68PA / BC68-25PA	BC68PAS / BC68-25PAS
	45	1	63 - 100	160 - 250	100	BCP54 / -10 / -16	BCX54 / -10 / -16	BC54PA / BC54-10PA / BC54-16PA	BC54PAS / BC54-10PAS / BC54-16PAS
	60	1	63 - 100	160 - 250	100	BCP55 / -10 / -16	BCX55 / -10 / -16	BC55PA / BC55-10PA / BC55-16PA	BC55PAS / BC55-10PAS / BC55-16PAS
			100	300	100	BSP41	BSR41		
80	1	63 - 100	160 - 250	100	BCP56 / -10 / -16	BCX56 / -10 / -16	BC56PA / BC56-10PA / BC56-16PA	BC56PAS / BC56-10PAS / BC56-16PAS	
		40 - 100	120 - 300	100	BSP43	BSR43			
PNP	20	2	85 - 160	250 - 375	40	BCP69 / -16 / -25	BC869 / -16 / -25	BC69PA / BC69-16PA / BC69-25PA	BC69PAS / BC569-16PAS / BC69-25PAS
	45	1	63 - 100	160 - 250	115 ¹⁾ - 145 ¹⁾	BCP51 / -10 / -16	BCX51 / -10 / -16	BC51PA / BC51-10PA / BC51-16PA	BC51PAS / BC51-10PAS / BC51-16PAS
	60	1	63 - 100	160 - 250	100	BCP52 / -10 / -16	BCX52 / -10 / -16	BC52PA / BC52-10PA / BC52-16PA	BC52PAS / BC52-10PAS / BC52-16PAS
			40 - 100	120 - 300	100	BSP31	BSR30 / 31		
80	1	63 - 100	160 - 250	115 ¹⁾ - 145 ¹⁾	100	BCP53 / -10 / -16	BCX53 / -10 / -16	BC53PA / BC53-10PA / BC53-16PA	BC53PAS / BC53-10PAS / BC53-16PAS
		40 - 100	120 - 300	100	BSP32 / 33	BSR33			

¹⁾ Typical value

In the spotlight

Medium-power transistors in DFN2020-3 and DFN2020D-3 (with solderable sidepads)

Excellent electrical performance on a small 2 x 2 mm footprint

80% board space reduction (DFN2020 vs. SOT89)

100% solderable sidepads (DFN2020D-3)

V_{CEO} ranging from 20 to 80 V

High collector-current capability I_C up to 2 A

AEC-Q101 qualified



Package						SOT223 (SC-73)	SOT89 (SC-62)	SOT457 (SC-74)	SOT23	SOT323 (SC-70)
Size (mm)						6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.5 x 1.0	2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95
P _{tot} (mW)						1700	1300	750	250	200
Polarity	V _{CEO} (V)	I _C (mA)	h _{FE} min	h _{FE} max	f _T min (MHz)					
NPN	80	100	20	-	60					BSS64
	140	300	60	250	100					PMBT5550 PMST5550
	160	300	80	250	100					PMBT5551/BSR19A PMST5551
	250	100	50	-	60	BF722	BF622			BF822
	300	100	50	-	60	BF720	BF620			BF820 BF820W
			40	-	50	PZTA42	PXTA42			PMBTA42 PMSTA42
350	100	40	-	70	BSP19	BST39				
400	300	50	200	20	PZTA44			PMBTA44		
PNP	100	100	30	-	50					BSS63
	250	100	50	-	60	BF723			BF823	
			50	-	60			BF623	BF821	
300	100	40	-	50	PZTA92	PXTA92			PMBTA92 PMSTA92	
2 x NPN	300	100	40	-	50					PMBTA42DS

For high-voltage transistors with increased performance please refer to our high-voltage low V_{CEsat} (BISS) transistor portfolio on page 18.

LED driver

Package		SOT457
Size (mm)		2.9 x 1.5 x 1.0
P _{tot} (mW)		750
V _s supply voltage [V]		LED drive current [mA] @ V _s =10V
40		10
		20
		50
		NCR401U
		NCR402U
		NCR405U

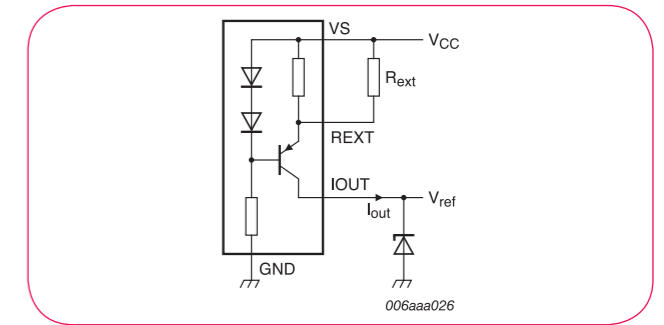
Key features and benefits

- ▶ Single-chip constant-current source with reduced component count
- ▶ Very small footprint for smaller designs

Key applications

- ▶ Constant-current LED driver
- ▶ Generic constant-current source
- ▶ Active bias control for audio amplifiers

Voltage reference



Constant-current source

Package		SOT353 (SC-88A)					
Size (mm)		2.0 x 1.25 x 0.95					
P _{tot} (mW)		335					
Type		PSSI2021SAY					
Description	maximum supply voltage	maximum supply current	typical stabilized output current	minimum stabilized output current	maximum stabilized output current	typical load stability of stabilized output current	typical output current change over ambient temperature
Parameter	V _s max (V)	I _s max (mA)	I _{out} typ (μA)	I _{out} min (mA)	I _{out} max (mA)	ΔI _{out} /I _{out} typ (%)	ΔI _{out} /(I _{out} ·ΔT _{amb}) ¹⁾ typ (μA/K)
Value	75	2.2	15	0.015	50	0.5	0.15

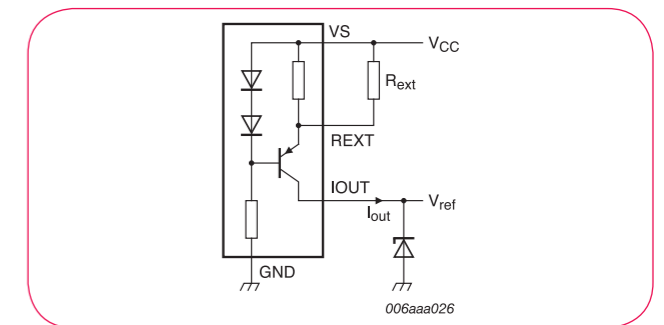
Key features and benefits

- ▶ Single-chip constant-current source with reduced component count
- ▶ Output current set by an external resistor
- ▶ Very small footprint for smaller designs

Key applications

- ▶ Constant-current LED driver
- ▶ Generic constant-current source
- ▶ Active bias control for audio amplifiers

Voltage reference



Darlington transistors

Package					SOT223 (SC-73)	SOT89 (SC-62)	SOT23
Size (mm)					6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.3 x 1.0
P _{tot} (mW)					1700	1300	250
Polarity	V _{CE0} (V)	I _C (mA)	h _{FE} min	f _T min (MHz)			
NPN	30	500	10000	125	PMBTA13		
			20000		PZTA14	PXTA14	PMBTA14
	45	1000	2000	200	BCV29		
			2000		BSP50	BST50	BCV27
	60	500	10000	220	BCV49		
			2000		BSP51	BST51	BCV47
80	1000	2000	200	BSP52	BST52		
PNP	30	500	20000	125	PMBTA64		
			2000		BCV28		
	45	1000	2000	200	BSP60		
			2000		BSP60	BST60	BCV26
	60	500	10000	220	BCV48		
			2000		BSP61	BST61	BCV46
80	1000	2000	200	BSP62	BST62		

Schmitt triggers

Package							SOT143B
Size (mm)							2.9 x 1.3 x 1.0
P _{tot} (mW)							250
Polarity	V _{CE0} (V) TR1	V _{CE0} (V) TR2	I _C (mA)	h _{FE} min	h _{FE} max	V _{CEsat} typ (mV)	
NPN	30	6	100	110	800	250	BCV63 / B
PNP	30	6	100	220	475	250	BCV64B

Low-noise transistors

Package					SOT23	SOT323 (SC-70)		
Size (mm)					2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95		
P _{tot} (mW)					250	200		
Polarity	V _{CE0} (V)	I _C (mA)	Noise figure max (dB)	h _{FE} min	h _{FE} max	f _T min (MHz)		
NPN	30	100	4	200	450	100	BC849B	BC849BW
				420	800	100	BC849C	BC849CW
	45	100	4	200	450	100	BC850B	BC850BW
				420	800	100	BC850C	BC850CW
PNP	30	100	4	220	475	100	BC859B	BC859BW
				420	800	100	BC859C	BC859CW
	45	100	4	220	475	100	BC860B	BC860BW
				420	800	100	BC860C	BC860CW

Matched-pair transistors

types in **bold** represent new products

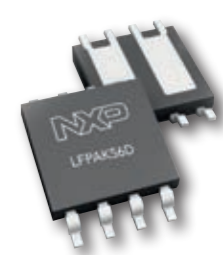
Package								SOT143B	SOT457 (SC-74)	SOT353 (SC-88A)	SOT363 (SC-88)	SOT666	LFPAK56D (SOT1205)
Size (mm)								2.9 x 1.3 x 1.0	2.9 x 1.5 x 1.0	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.6 x 1.2 x 0.55	4.9 x 4.45 x 1.0
P _{tot} (mW)								250	750	300	300	300	1250
Polarity	V _{CE0} (V)	I _C (mA)	h _{FE} min	h _{FE} max	h _{FE1} /h _{FE2}	V _{BE1} - V _{BE2} (mV)							
NPN	30	100	110	800	0.7 ¹⁾	n.a.	BCV61/A/B/C ¹⁾						
							n.a.						
	45	100	200	450	0.9 ¹⁾	2	2	BCM847DS		BCM847BS		BCM847BV	
								PMP4501G		PMP4501Y		PMP4501V	
								PMP4201G		PMP4201Y		PMP4201V	
	100	3000	150	400	0.98	2	PHPT610035NK						
Configuration													
PNP	30	100	100	800	0.7 ¹⁾	n.a.	BCV62/A/B/C ¹⁾						
							n.a.						
	45	100	200	450	0.95	2	2	BCM857DS		BCM857BS		BCM857BV	
								PMP5501G		PMP5501Y		PMP5501V	
								PMP5201G		PMP5201Y		PMP5201V	
	65	100	200	450	0.9	2	BCM856DS						
100	3000	150	220	0.9	n.a.	PHPT610035PK							
Configuration													

¹⁾ I_{C1} / I_{E2}

In the spotlight

New transistors in LFPAK56D (SOT1205) power package

- High thermal power dissipation up to 3 W
- V_{ce0} up to 100 V
- All types AECQ-101 qualified (I_C = 3 A)
- 2 types with current gain matching of 5 and 10%
- Reduced PCB size requirements
- High-temperature applications up to 175 °C
- For LED lighting, motor drive, linear regulators, backlight units, PowerMOS, and IGBT drive



Key features

- ▶ Current gain matching to 10, 5, or 2%
- ▶ Base-emitter voltage matching to 2 mV
- ▶ Choice of standard double transistor pinout or application-optimized pinout
- ▶ Common-emitter configuration for 5-pin type
- ▶ Range of small, very small, and ultra-small packages

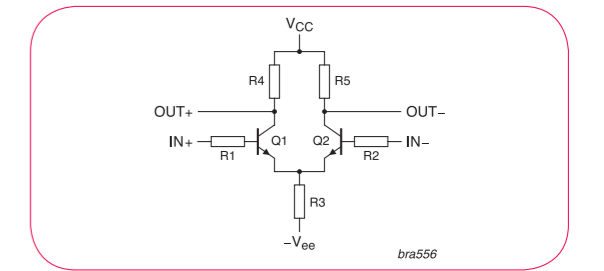
Key benefits

- ▶ Improved performance of current mirror and differential amplifier circuits
- ▶ Drop-in replacement for standard double transistors (BCM series)
- ▶ Simplified board layout (PMP series)
- ▶ Eliminates the need for costly additional trimming

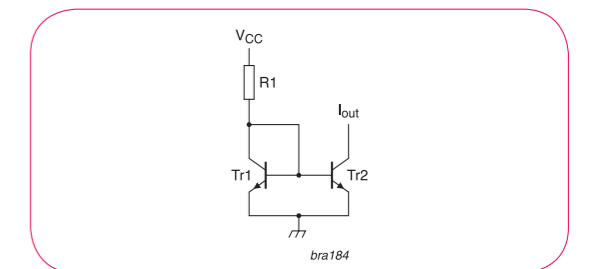
Key applications

- ▶ Current mirrors
- ▶ Differential and instrumentation amplifiers
- ▶ Logarithmic amplifiers
- ▶ Comparators


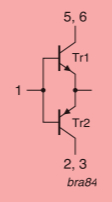

Differential amplifier



Current mirror



MOSFET driver

V_{CE0} (V)	I_C (mA)	I_{cm} [A]	Type	Package	Remark	Configuration
30	0.1	0.2	BCV65	SOT143B 	General-purpose transistors	
40	0.6	1	PMD2001D	SOT457 	Switching transistors with reduced storage time	
	1	2	PMD3001D		Low V_{CEsat}	

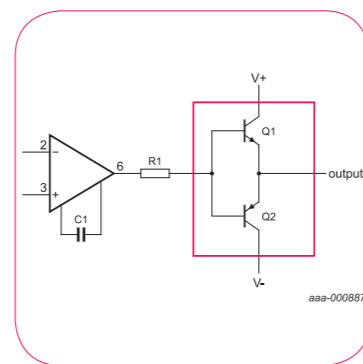
Key features and benefits

- ▶ Three different configurations
- ▶ Types available with standard, switching, and low V_{CEsat} (BISS) transistors
- ▶ Small footprint

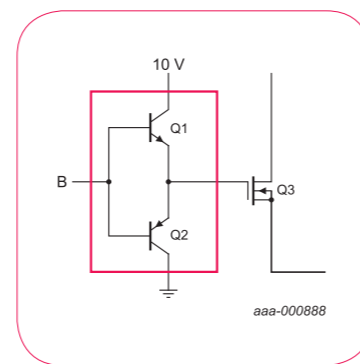
Key applications

- ▶ Power management
 - (Half) bridge push-pull driver
 - Isolated DC/DC converters
 - Secondary synchronous rectification
- ▶ Peripheral driver
 - (Half) bridge push-pull driver
 - Motor driver
 - Brushless DC motor driver
 - Op-amp output current booster



Op-amp booster



MOSFET driver for faster switching, lower losses



Medium-frequency transistors

						SOT23	SOT323 (SC-70)
Package							
Size (mm)						2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95
P_{tot} (mW)						250	200
Polarity	V_{CE0} (V)	I_C (mA)	$h_{FE min}$	$h_{FE max}$	f_t typ (MHz)		
NPN	15	100	40	-	500	BF570	
	20	25		85	>275	BF520	BF520W
		30	65	225	260	BF519	
		40	25	67	220	380	BF840
PNP	30	25	25	50	250	BF824	BF824W
	40		50	-	>325	BF550	



Diodes

Schottky barrier diodes and rectifiers

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Switching diodes

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Power diodes

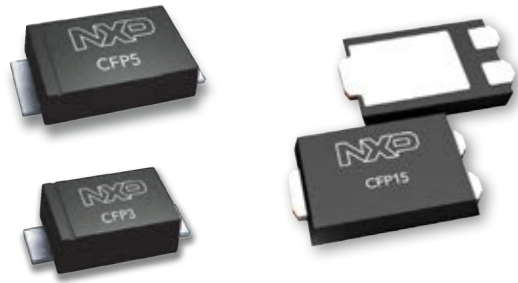
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NXP's FlatPower packages CFP3, CFP5, and CFP15

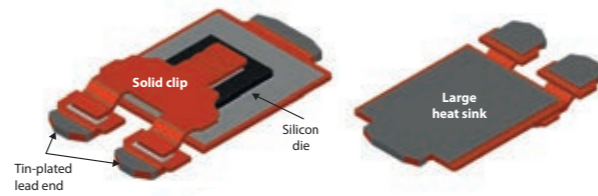
The medium-power solution for shrinking designs

Small SMD FlatPower packages in three different versions



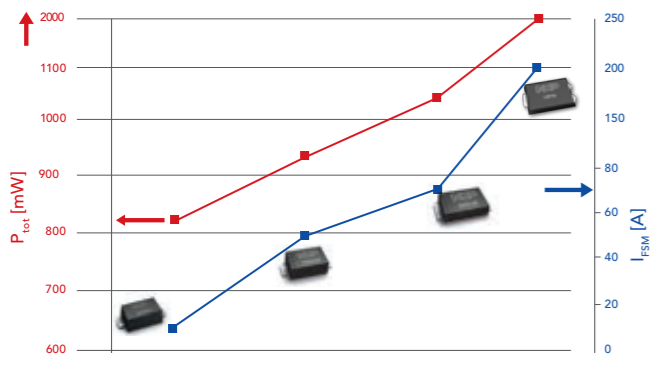
- ▶ Flat geometry, of down to 0.78 mm height
- ▶ Halogen-free mold compound
- ▶ AEC-Q101 qualified

Robust design inside the FlatPower packages

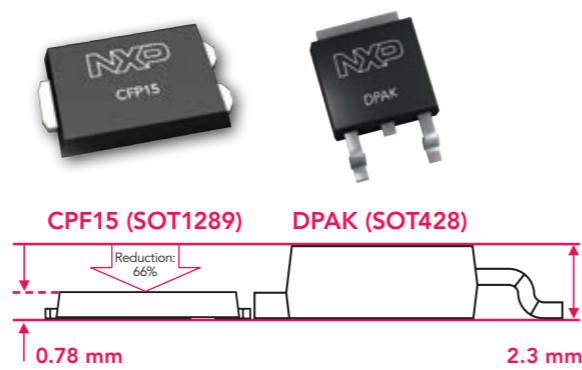


- ▶ High-power capability due to clip-bond technology and heatsink
- ▶ Automatic optical inspection of solder joint due to tin-plated lead ends
- ▶ Benchmark flat design of only 0.7 mm height

Power dissipation (@ 1 cm²), and I_{FSM} per package



Package height comparison: CFP15 - DPAK



The new NXP CFP15 package delivers a 66% reduction in height compared to a conventional DPAK.

Schottky diodes

- Enabling superior high P_{tot} and I_{FSM}
- ▶ Huge portfolio of Schottky diodes available
 - ▶ 20 to 100 V, 1 to 15 A, very low V_F
 - ▶ Junction temperature up to 175 °C

TVS diodes

- Can replace SMA and SMB products
- ▶ Complete TVS series available
 - ▶ 3.5 to 64 V, 400 and 600 W
 - ▶ Junction temperature up to 185 °C

NXP offers more than 200 products in FlatPower packages, to support a wide range of applications for medium-power rectification and surge protection.

Medium-power low V_F Schottky rectifiers single ≥ 1 A - FlatPower packages

types in **bold** represent new products

I _F max (A)	V _R max (V)	V _F max (mV) @ I _F max	I _R max (mA) @ V _R max	Package	CFP15 (SOT1289)	CFP5 (SOD128)	CFP3 (SOD123W)	
					5.8 x 4.3 x 0.78	3.8 x 2.5 x 1.0	2.6 x 1.7 x 1.0	
					Size (mm)			
					P _{tot} (mW) @ 1 cm ²	2150	1050	950
					Optimization			
1	20	340	1	Low V _F			PMEG2010ER	
		450	0.05	Low I _R			PMEG2010BER	
	30	360	1.5	Low V _F		PMEG3010EP	PMEG3010ER	
		450	0.05	Low I _R		PMEG3010BEP	PMEG3010BER	
	40	490	0.05	Low V _F		PMEG4010EP	PMEG4010ER	
				Low V _F		PMEG4010ETP	PMEG4010ETR	
	60	530	0.06	Low V _F		PMEG6010EP	PMEG6010ER	
		530		Low V _F			PMEG6010ETR	
	100	660	0.0003	Low I _R			PMEG6010ELR	
		770	0.00015	Low I _R			PMEG10010ELR	
2	30	360	3	Low V _F		PMEG3020EP		
		420	1.5	Low V _F		PMEG3020CEP	PMEG3020ER	
		450	0.1	Low I _R		PMEG3020BEP		
		520	0.05	Low I _R		PMEG3020DEP	PMEG3020BER	
	40	490	0.1	Low V _F		PMEG4020EP	PMEG4020ER	
				Low V _F		PMEG4020ETP	PMEG4020ETR	
	60	530	0.2	Low V _F		PMEG6020EP	PMEG6020ER	
		530		Low V _F		PMEG6020ETP	PMEG6020ETR	
	100	680	0.0007	Low I _R		PMEG6020AELP	PMEG6020AELR	
		760	0.0003	Low I _R			PMEG6020ELR	
3	30	770	0.00015	Low I _R		PMEG10020AELP	PMEG10020AELR	
		830	0.00015	Low I _R			PMEG10020ELR	
	40	360	5	Low V _F		PMEG3030EP		
		450	0.15	Low I _R		PMEG3030BEP		
	60	490	0.2	Low V _F		PMEG4030EP		
		490		Low V _F		PMEG4030ETP		
	100	540	0.1	Low I _R			PMEG4030ER	
		530	0.2	Low V _F		PMEG6030EP		
	150	475	0.4	Low V _F		PMEG6030EVP		
		530	0.2	Low V _F		PMEG6030ETP		
200	690	0.001	Low I _R		PMEG6030ELP			
	770	0.00045	Low I _R		PMEG10030ELP			
4.5	60	530	0.4	Low V _F		PMEG6045ETP		
	30	360	8	Low V _F		PMEG3050EP		
45		450	0.25	Low I _R		PMEG3050BEP		
	60	490	0.3	Low V _F		PMEG4050EP		
75		490	0.3	Low V _F		PMEG4050ETP		
	100	490	0.6	Low V _F		PMEG045V050EPD		
150		560	0.4	Low V _F		PMEG060V050EPD		
	200	490	0.6	Low V _F		PMEG045V1000EPD		
300		540	0.5	Low I _R		PMEG45U10EPD		
	450	560	0.7	Low V _F		PMEG45A10EPD		
600		560	0.7	Low V _F		PMEG060V100EPD		
	800	490	0.03	Low I _R		PMEG045T150EPD		
1000		490	1	Low V _F		PMEG045V150EPD		
	1500	500	1	Low V _F		PMEG050V150EPD		

Medium-power low V_F Schottky rectifiers single ≥ 100 mA - DSN packages

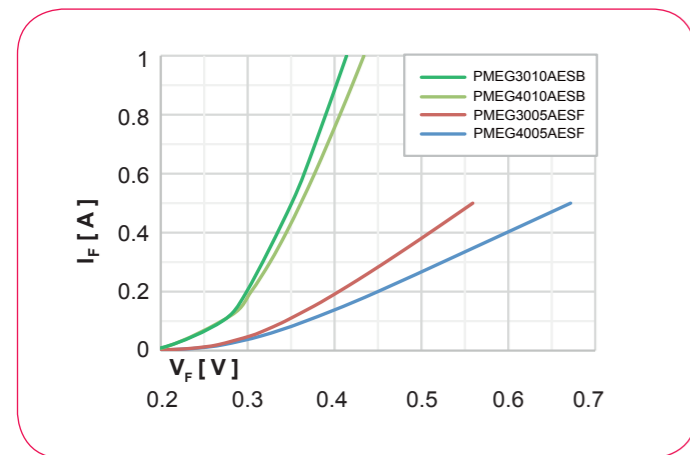
types in **bold** represent new products

I_F max (A)	V_R max (V)	V_F max (mV) @ I_F max	I_R max (mA) @ V_R max	Package	DSN0603-2 (SOD962)	DSN1006-2 (SOD993)	DSN1006U-2 (SOD995)	
					Size (mm)	0.6 x 0.3 x 0.3	1.0 x 0.6 x 0.28	1.0 x 0.6 x 0.28
					P_{tot} (mW) @ 1 cm ²	525	tbd	tbd
Optimization								
0.1	12	250	2	Low V_F	PMEG1201AESF			
				Low I_R	PMEG2002AESF			
0.2	20	420	0.045	Low V_F	PMEG2002AESF			
				Low I_R	PMEG2002ESF			
	30	470	0.08	Low V_F	PMEG3002AESF			
				Low I_R	PMEG3002ESF			
	40	525	0.08	Low V_F	PMEG4002AESF			
				Low I_R	PMEG4002ESF			
0.5	20	550	0.045	Low V_F	PMEG2005AESF			
				Low I_R	PMEG2005ESF			
	30	620	0.035	Low V_F	PMEG3005AESF			
				Low I_R	PMEG3005ESF			
	40	630	0.08	Low V_F	PMEG4005AESF			
				Low I_R	PMEG4005ESF			
1	30	typ. 415	typ. 0.3	Low V_F		PMEG3010AESB	PMEG3010AESA	
				Low V_F		PMEG4010AESB		

Forward characteristic survey of Schottkys in DSN1006-2

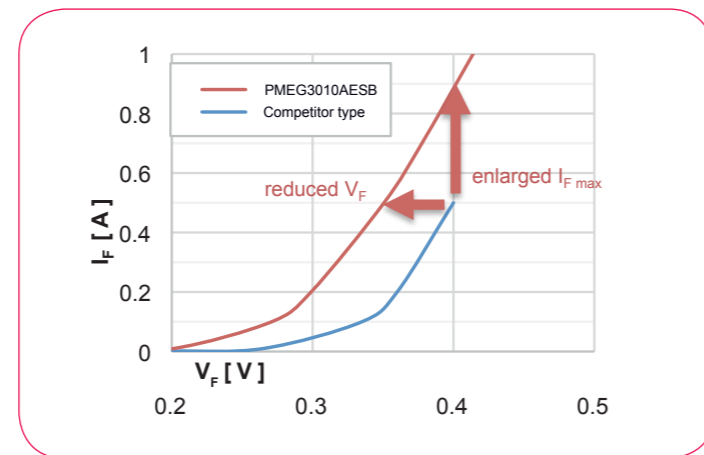
$V_R: 30V, I_F: I_A$ (typical data)

Selected DSN Schottky rectifier



This diagram shows the broad variety of the DSN portfolio

PMEG3010AESB versus competitor type



NXP type has higher forward current specified and has benchmark low V_F

In the spotlight

PMEG3010AESB and PMEG4010AESB, low V_F Schottky rectifier

30 / 40 V, 1A Schottky rectifier in CSP DSN1006-2 (SOD993) package

Low V_F typ = 415 / 435 mV @ 1 A

High surge capability up to 8 A

Ideal for shrunk designs and 'small power' applications

Ideal for LED backlighting in mobile applications



Medium-power low V_F Schottky rectifiers single ≥ 200 mA - Leadless (DFN) packages

types in **bold** represent new products

I_F max (A)	V_R max (V)	V_F max (mV) @ I_F max	I_R max (mA) @ V_R max	Package	DFN2020-3 (SOT1061)	DFN2020D-3 (SOT1061D)	DFN1608D-2 (SOD1608)	DFN1006-2 (SOD882)	DFN1006D-2 (SOD882D)	
					Size (mm)	2.0 x 2.0 x 0.62	2.0 x 2.0 x 0.62	1.6 x 0.8 x 0.37	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37
					P_{tot} (mW) @ 1 cm ²	960	960	780	565	660
Optimization										
0.2	30	480	0.05	low V_F				PMEG3002AEL	PMEG3002AELD	
				low I_R				PMEG4002EL	PMEG4002ELD	
				low V_F				PMEG6002EL	PMEG6002ELD	
0.5	20	390	0.2	low V_F					PMEG2005BELD	
				low V_F			PMEG2005EPK			
	30	440	1.5	low V_F				PMEG2005AEL	PMEG2005AELD	
				low I_R				PMEG2005EL	PMEG2005ELD	
	40	500	0.03	low V_F				PMEG3005EL	PMEG3005ELD	
				low I_R						
1	20	375	1.9	low V_F	PMEG2010EPA	PMEG2010EPAS				
				low V_F				PMEG2010EPK		
				low V_F						PMEG2010BELD
1.5	40	600	0.02	low I_R				PMEG4010EPK		
				low V_F				PMEG2015EPK		
				low I_R				PMEG4015EPK		
2	20	420	0.9	low V_F	PMEG2020EPA	PMEG2020EPAS				
				low V_F				PMEG2020EPK		
	30	470	2.5	low V_F	PMEG3020EPA	PMEG3020EPAS				
				low V_F	PMEG4020EPA	PMEG4020EPAS				
	40	535	0.1	low V_F					PMEG4020EPK	
				low V_F	PMEG6020EPA	PMEG6020EPAS				
60	575	0.25	low V_F							

Features and benefits

- ▶ 33% lower V_F on same footprint
- ▶ Low profile of 0.37 mm
- ▶ Solderable side pads
- ▶ Visual solder inspection

Applications

- ▶ Handheld equipment
- ▶ Smartphone backlight units
- ▶ Battery chargers
- ▶ Shrunk PCB designs

Differentiated portfolio

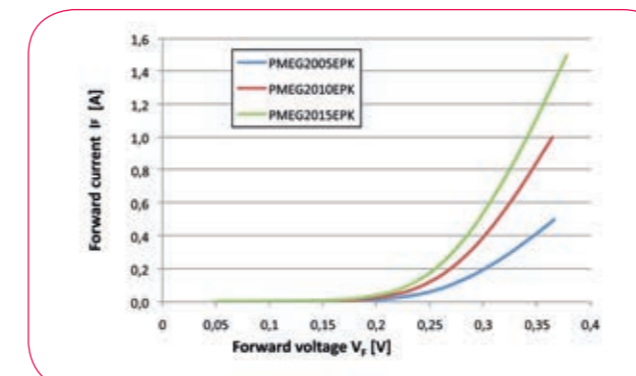
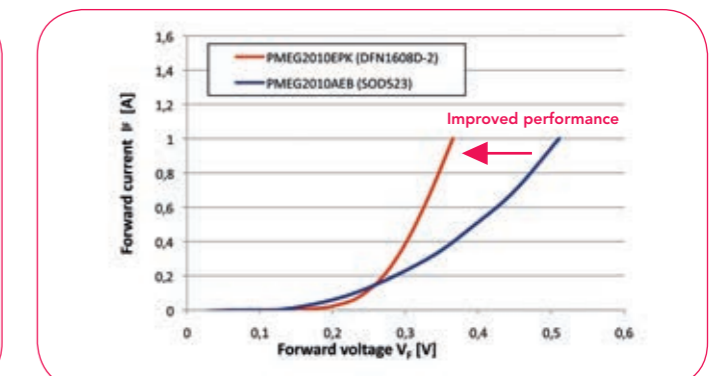


Diagram shows the variety of characteristics in DFN1608D-2 (SOD1608)

with best performance



PMEG2010EPK shows significant V_F improvement compared to the SOD523 device

Medium-power low V_F Schottky rectifiers single ≥ 200 mA - Leaded packages

I_F max (A)	V_R max (V)	V_F max (mV) @ I_F max	I_R max (mA) @ V_R max	Package	SOT457 (SC-74)	SOT23	SOD123F	SOT323 (SC-70)	SOD323F (SC-90)	SOD323 (SC-76)	SOT666	SOD523 (SC-79)	
					Size (mm)	2.9 x 1.5 x 1.0	2.9 x 1.3 x 1.0	2.6 x 1.6 x 1.1	2.0 x 1.25 x 0.95	1.7 x 1.25 x 0.7	1.7 x 1.25 x 0.95	1.6 x 1.2 x 0.55	1.2 x 0.8 x 0.6
					P_{tot} (mW) @ 1 cm ²	540	420	830	400	830	570	570	500
					Optimization								
0.2	30	480	0.05	low V_F						PMEG3002EJ		PMEG3002AEB	
	40	600	0.01	low I_R						PMEG4002EJ		PMEG4002EB	
	60	600	0.1	low V_F						PMEG6002EJ		PMEG6002EB	
0.5	20	390	0.2	low V_F		PMEG2005ET	PMEG2005EH			PMEG2005EJ	PMEG2005AEA	PMEG2005AEV	
		480	0.03	low I_R								PMEG2005EB	
	30	430	0.15	low V_F		PMEG3005ET	PMEG3005EH			PMEG3005EJ	PMEG3005AEA	PMEG3005AEV	
		500	0.5	low V_F									PMEG3005EB
		470	0.1	low V_F		PMEG4005ET	PMEG4005EH			PMEG4005EJ	PMEG4005AEA	PMEG4005AEV	
40	550	1.1	low V_F		BAT720		1PS70SB20						
1	20	430	0.2	low V_F		PMEG2010AET	PMEG2010AEH						
		500	0.2	low V_F		PMEG2010ET	PMEG2010EH			PMEG2010EJ	PMEG2010BEA	PMEG2010BEV	
		550	0.07	low I_R						PMEG2010AEJ	PMEG2010EA BAT760	PMEG2010EV BAT960	
		620	1.5	low V_F								PMEG2010AEB	
	30	450	1	low V_F		1PS74SB23							
		520	0.1	low I_R				PMEG3010CEH		PMEG3010CEJ			
		560	0.15	low V_F			PMEG3010ET	PMEG3010EH		PMEG3010EJ	PMEG3010BEA	PMEG3010BEV	
680	0.5	low V_F									PMEG3010EB		
570	0.05	low I_R				PMEG4010CEH		PMEG4010CEJ					
600	0.02	low I_R											
40	640	0.05	low V_F			PMEG4010ET	PMEG4010EH		PMEG4010EJ	PMEG4010BEA	PMEG4010BEV		
60	650	0.35	low V_F		PMEG6010AED								
	660	0.05	low I_R				PMEG6010CEH		PMEG6010CEJ				
1.5	20	660	0.2	low I_R			PMEG2015EH		PMEG2015EJ	PMEG2015EA	PMEG2015EV		
	30	500	1	low V_F			PMEG3015EH		PMEG3015EJ		PMEG3015EV		
2	10	460	3	low V_F			PMEG1020EH		PMEG1020EJ	PMEG1020EA	PMEG1020EV		
	20	525	0.2	low V_F			PMEG2020EH		PMEG2020EJ	PMEG2020AEA			
	30	620	1	low V_F			PMEG3020EH		PMEG3020EJ				
3	10	530	3	low V_F			PMEG1030EH		PMEG1030EJ				

In the spotlight

Schottky Rectifier in SOD123F and SOD323F

Broad portfolio base of 36 types, 20 / 60 V, 0.2 - 3 A

Optimized either for low V_F or low I_R

High surge capability up to 10 A

High thermal capability due to flat-lead design

AEC-Q101 qualified

Ideal for DC/DC conversion, free-wheeling, reverse polarity protection



Medium-power low V_F Schottky rectifiers dual ≥ 200 mA

types in bold represent new products

I_F max (A)	V_R max (V)	V_F max (mV) @ I_F max	I_R max (mA) @ V_R max	Optimization	Package	SOT223 (SC-73)	SOT23	DFN2020-3 (SOT1061)	DFN2020D-3 (SOT1061D)	SOT666	
						Size (mm)	6.5 x 3.5 x 1.65	2.9 x 1.3 x 1.0	2.0 x 2.0 x 0.62	2.0 x 2.0 x 0.63	1.6 x 1.2 x 0.55
						P_{tot} (mW) @ 1 cm ²	1500	250	1000	1001	300
0.2	30	480	0.03	low V_F							PMEG3002TV
	60	600	0.1	low V_F							PMEG6002TV
0.5	20	390	0.2	low V_F						PMEG2005CT	
		480	0.03	low I_R						PMEG2005EB	
	30	430	0.15	low V_F						PMEG3005CT	
1	25	470	0.1	low V_F						PMEG4005CT	
		500	0.5	low V_F						PMEG3005EB	
		450	1.0	low V_F		BAT120S					
	40	500	0.05	low V_F		BAT120C					
		540	0.06	low V_F		BAT120A					
2.0	60	650	0.35	low V_F						PMEG4010CPA	PMEG4010CPAS
		550	0.07	low I_R						PMEG6010CPA	PMEG6010CPAS
	30	650	0.35	low V_F		BAT160S					
		660	0.05	low I_R		BAT160C					
20	420	1.0	low V_F						PMEG2020CPA	PMEG2020CPAS	

Diodes

Low V_F (MEGA) Schottky rectifier nomenclature

PMEG 40 10 A E T P

NXP MEGA Schottky rectifier

Max. reverse voltage in V
e.g. 40 = 40 V

Cont. forward current in A
e.g. 10 = 1.0 A

Variant number (optional)













Internal configuration:
A = CA
C = CC
E = single
P = double, parallel
R = tripple, antiparallel
S = series
V = tripple
W = CA and CC
X = 2 x series
Y = 2 x CC
Z = 2 x CA

Variant number (optional)
L = low I_R
T = high temperature
V = low I_R and low V_F

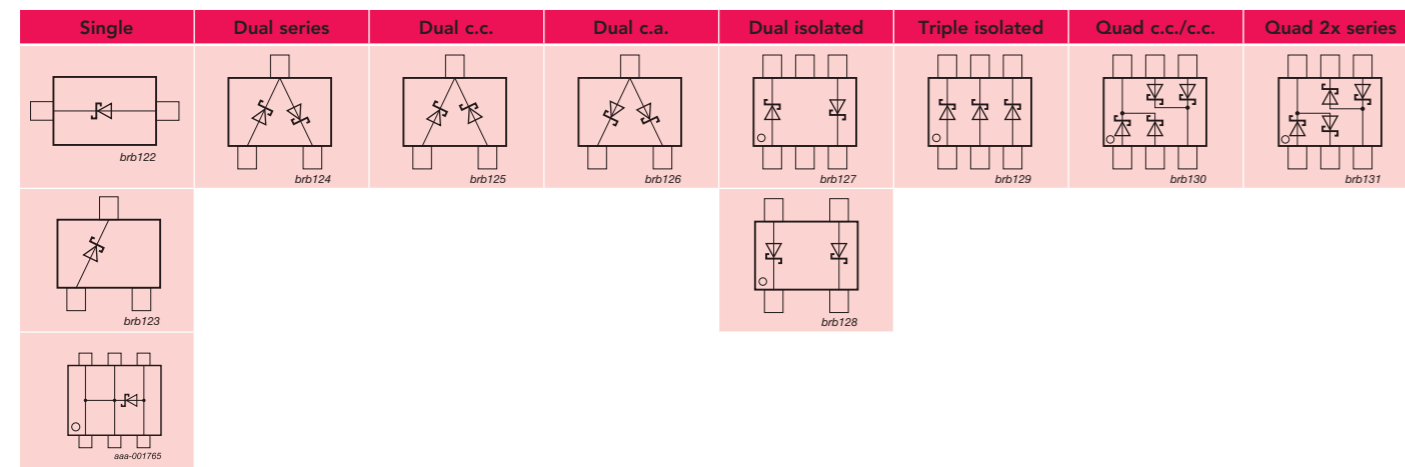
Package indicator:
A = SOD323
B = SOD523
D = SOT457
H = SOD123
J = SOD323F
L = DFN1006-2 (SOD882)
LD = DFN1006D-2 (SOD882D)
P = SOD128
PA = DFN2020-3 (SOT1061)

PAS = DFN2020D-3 (SOT1061D)
PD = CFP15 (SOT1289)
PK = DFN1608D-2 (SOD1608)
R = SOD123W
SA = DSN1006U-2 (SOD995)
SB = DSN1006-2 (SOD993)
SF = DSN0603-2 (SOD962)
T = SOT23
V = SOT666








General-purpose Schottky diodes ≤ 250 mA

I _F max (mA)	V _R max (V)	V _F max (mV)	@ I _F (mA)	I _R max (μA)	@ V _R (V)	Package	SOD80C (MiniMelf)	SOD68 (DO-34)	SOT23	SOT143B		SOD123F	SOT323 (SC-70)	SOT363 (SC-88)	SOD323F (SC-90)	SOD323 (SC-76)	SOT666	SOD523 (SC-79)	DFN1006-2 (SOD882)/DFN1006-3 (SOT883)					
																								
							3.5 x 1.5 x 1.5	3.04 x 1.6 x 0.55	2.9 x 1.3 x 1.0	2.9 x 1.3 x 1.0		2.6 x 1.6 x 1.1	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.7 x 1.25 x 0.7	1.7 x 1.25 x 0.95	1.6 x 1.2 x 0.55	1.2 x 0.8 x 0.6	1.0 x 0.6 x 0.48					
P _{tot} (mW)	300	500	250	250		830	250	300	550	400	300	500	250											
70	70	750	10	0.1	50	single			BAS70			BAS70H	BAS70W			1PS76SB70		1PS79SB70	BAS70L					
						dual series			BAS70-04			BAS70-04W												
						dual c.c.			BAS70-05			BAS70-05W												
						dual c.a.			BAS70-06			BAS70-06W												
						dual isolated							BAS70-07						BAS70-07S			BAS70-07V		
						triple isolated																BAS70VV		
quad 2x series													BAS70XY											
120	40	370	1	0.5	30	single						BAS40H	BAS40W				RB751V40		RB751S40	RB751CS40				
						dual series			BAS40-04			BAS40-04W									1PS79SB40		BAS40L	
						dual c.c.			BAS40-05			BAS40-05W												
						dual c.a.			BAS40-06			BAS40-06W												
						dual isolated							BAS40-07									BAS40-07V		
						quad c.c./c.c.													1PS88SB48			BAS40-05V		
quad 2x series													BAS40XY											
200	30	300	10	30	10	single													1PS79SB31					
						dual series			BAT754															
						dual c.c.			BAT754S															
		dual c.a.			BAT754C																			
		triple isolated			BAT754A																			
		quad 2x series																						
	400	10	2	2	25	single	BAS85	BAT85	BAT54			BAT54H	BAT54W			BAT54J	1PS76SB10		1PS79SB10	BAT54L				
						dual series			BAT54S			BAT54SW												
						dual c.c.			BAT54C			BAT54CW												
	dual c.a.			BAT54A			BAT54AW																	
	dual isolated							BAT74										BAT74V						
	triple isolated																	BAT54VV						
quad c.c./c.c.																	BAT54CV							
quad 2x series														BAT54XY										
500	200	30	10	10	single														RB521S30	RB521CS30L				
					dual series																			
					dual c.c.																			
600	200	1	10	10	single														RB520S30	RB520CS30L				
					dual series			BAT721																
					dual c.c.			BAT721S																
dual c.a.			BAT721C																					
triple isolated			BAT721A																					
quad 2x series																								
300	10	15	30	30	single															1PS76SB21				
					dual series																			
					dual c.c.																			
					dual c.a.																			
					triple isolated																			
					quad 2x series																			
360	10	0.5	25	25	single															1PS79SB30				
					dual series																			
					dual c.c.																			
					dual c.a.																			
420	30	0.5	25	25	single																			
					dual series																			
					dual c.c.																			
					dual c.a.																			
450	10	5	40	40	single	BAS86	BAT86																	
					single																			
250	100	850	250	4	75	single						BAT46WH												
						single																		

Diodes



Low-capacitance Schottky diodes

I _F max (mA)	V _R max (V)	V _F max (mV) @ I _F (mA)	C _d max (pF) @ V _R = 0 V	Package	SOT23	SOT323 (SC-70)	SOT363 (SC-88)	SOD323 (SC-76)	SOT666	SOD523 (SC-79)	DFN1006-2 (SOD882)	
												
					2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.7 x 1.25 x 0.95	1.6 x 1.2 x 0.55	1.2 x 0.8 x 0.6	1.0 x 0.6 x 0.48	
P _{tot} (mW)	250	250	300	400	300	500	250					
30	4	450	1	1	single	BAT17			1PS76SB17		1PS79SB17	
					triple isolated					1PS66SB17		
					dual series	PMBD353 PMBD354 ¹⁾						
	15	340	1	1	single		1PS70SB82			1PS66SB82		1PS10SB82
					triple isolated			1PS88SB82				
					dual series			1PS70SB84				
dual c.c.			1PS70SB85									
dual c.a.			1PS70SB86									

¹⁾Diodes have matched capacitance

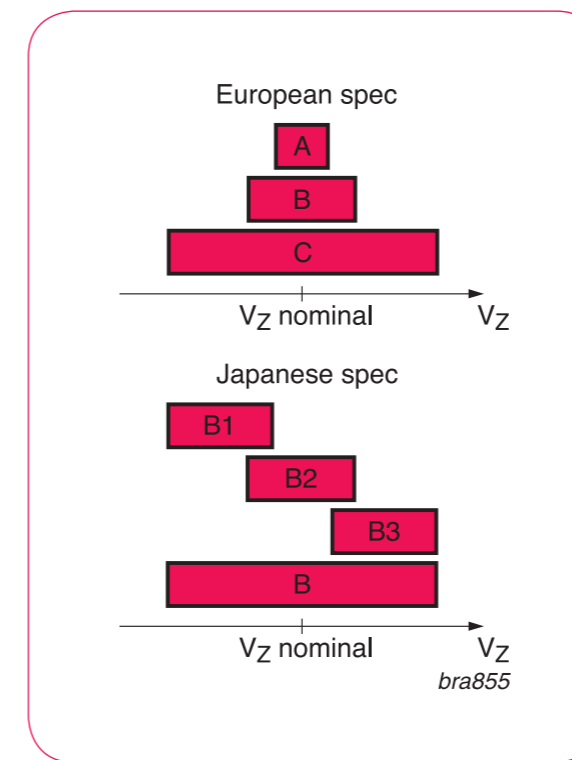
General-purpose Zener diodes

I_f max (mA)	P_{ZSM} (W)	V_Z nom (V)	V_Z tolerance	Note	Configuration	Series	Package	Size (mm)	P_{tot} (mW)
500	-	3.3~24	C	Europe	Single	1N47xxA series	SOD66 (DO-41)	4.8 x 2.6 x 0.81	1000
	60	3.6~75				BZV85 series			
250	-	2.1~36	About 2%	Special	Single	NZX series	SOD27 (DO-35)	4.25 x 1.85 x 0.56	400
	40	2.4~75	B, C	Europe		BZX79 series			
400	40	2.4~75	C	Europe	Single	BZV90 series	SOT223 (SC-73)	6.5 x 3.5 x 1.65	1500
250	40	2.4~75	C	Europe	Single	BZV49 series	SOT89 (SC-62)	4.5 x 2.5 x 1.5	1000
250	40	2.4~75	B, C	Europe	Single	BZV55 series	SOD80C (MiniMelf)	3.5 x 1.5 x 1.5	400
						BZB84 series			
200	40	2.4~75	B, C	Europe	Dual c.a.	BZB84 series	SOT23	2.9 x 1.3 x 1.0	250
						BZX84 series			
250	30	5~6.8	0.2 V	Ave	Single	PLVA600A series	SOT23	2.9 x 1.3 x 1.0	250
						PLVA2600A series			
250	-	3.0~30	About 2.5%	Special	Single	NZH series	SOD123F	2.6 x 1.6 x 1.1	830
						BZT52H series			
200	40	2.7~24	B2	Japan	Dual isolated	PZUxDB2 series	SOT353 (SC-88A)	2.0 x 1.25 x 0.95	300
200	40	2.4~15	C	Europe	Dual c.a.	BZB784 series	SOT323 (SC-70)	2.0 x 1.25 x 0.95	350
200	30	100	C	Europe	Back-to-back	BZB100A	SOD323 (SC-76)	1.7 x 1.25 x 0.95	300
						PDZ-B series			
250	40	2.4~75	B, C	Europe	Single	BZX384 series	SOD323 (SC-76)	1.7 x 1.25 x 0.95	300
						PZUxBA series			
200	40	2.4~36	B, B1, B2, B3	Japan	Single	BZX100A	SOD323F (SC-90)	1.7 x 1.25 x 0.7	550
						PZUxB series			
250	40	2.4~75	B, C	Europe	Single	BZX84J series	SOD323F (SC-90)	1.7 x 1.25 x 0.7	550
200	40	2.4~15	C	Europe	Dual c.a.	BZB984 series	SOT663	1.6 x 1.2 x 0.55	350
200	40	2.4~75	B, C	Europe	Single	BZX585 series	SOD523 (SC-79)	1.2 x 0.8 x 0.6	300
200	40	2.4~75	B, C	Europe	Single	BZX884 series	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48	250
						PZUxBL series			
250	40	2.4~30	B	Europe	Single	TDZxJ series	SOD323F	1.7 x 1.25 x 0.7	500

Notes:
 Japan: B selection: app. 5% V_Z tolerance, B1, B2, B3 selections: app. 2% V_Z tolerance in sequential intervals
 Europe: A selection: app. 1% V_Z tolerance, B selection: app. 2% V_Z tolerance, C selection: app. 5% V_Z tolerance; the selections are in overlapping intervals
 Ave: low-voltage avalanche regulator diodes
 Dual c.a.: dual common anode

Zener diodes specifications

Differences in Zener specifications



Japanese spec (PZU, PDZ)

y =	B-series ± 5%	B1-series ± 2%	B2-series ± 2%	B3-series ± 2%
	V_Z (V)	V_Z (V)	V_Z (V)	V_Z (V)
PZU2.4y	2.3 - 2.6	-	-	-
PZU2.7y	2.5 - 2.9	2.5 - 2.75	2.65 - 2.9	-
PZU3.0y	2.8 - 3.2	2.8 - 3.05	2.95 - 3.2	-
PZU3.3y	3.1 - 3.5	3.1 - 3.35	3.25 - 3.5	-
PZU3.6y	3.4 - 3.8	3.4 - 3.65	3.55 - 3.8	-
PZU3.9y	3.7 - 4.1	3.7 - 3.97	3.87 - 4.1	-
PZU4.3y	4.01 - 4.48	4.01 - 4.21	4.15 - 4.34	4.28 - 4.48
PZU4.7y	4.42 - 4.9	4.42 - 4.61	4.55 - 4.75	4.69 - 4.9
PZU5.1y	4.84 - 5.37	4.84 - 5.04	4.98 - 5.2	5.14 - 5.37
PZU5.6y	5.31 - 5.92	5.31 - 5.55	5.49 - 5.73	5.67 - 5.92
PZU6.2y	5.86 - 6.53	5.86 - 6.12	6.06 - 6.33	6.26 - 6.53
PZU6.8y	6.47 - 7.14	6.47 - 6.73	6.65 - 6.93	6.86 - 7.14
PZU7.5y	7.06 - 7.84	7.06 - 7.36	7.28 - 7.6	7.52 - 7.84
PZU8.2y	7.76 - 8.64	7.76 - 8.1	8.02 - 8.36	8.28 - 8.64
PZU9.1y	8.56 - 9.55	8.56 - 8.93	8.85 - 9.23	9.15 - 9.55
PZU10y	9.45 - 10.55	9.45 - 9.87	9.77 - 10.21	10.11 - 10.55
PZU11y	10.44 - 11.56	10.44 - 10.88	10.76 - 11.22	11.1 - 11.56
PZU12y	11.42 - 12.6	11.42 - 11.9	11.74 - 12.24	12.08 - 12.6
PZU13y	12.47 - 13.96	12.47 - 13.03	12.91 - 13.49	13.37 - 13.96
PZU14y	-	-	13.7 - 14.3	-
PZU15y	13.84 - 15.52	13.84 - 14.46	14.34 - 14.98	14.85 - 15.52
PZU16y	15.37 - 17.09	15.37 - 16.01	15.85 - 16.51	16.35 - 17.09
PZU18y	16.94 - 19.03	16.94 - 17.7	17.56 - 18.35	18.21 - 19.03
PZU20y	18.86 - 21.08	18.86 - 19.7	19.52 - 20.39	20.21 - 21.08
PZU22y	20.88 - 23.17	20.88 - 21.77	21.54 - 22.47	22.23 - 23.17
PZU24y	22.93 - 25.57	22.93 - 23.96	23.72 - 24.78	24.54 - 25.57
PZU27y	25.1 - 28.9	-	-	-
PZU30y	28 - 32	-	-	-
PZU33y	31 - 35	-	-	-
PZU36y	34 - 38	-	-	-







European spec (BZV, BZX, BZB, 1N47)

y =	C-series ±5%	B-series ±2%	A-series ±1%
	V_Z (V)	V_Z (V)	V_Z (V)
BZX84-y2V4	2.2 - 2.6	2.35 - 2.45	2.37 - 2.43
BZX84-y2V7	2.5 - 2.9	2.65 - 2.75	2.67 - 2.73
BZX84-y3V0	2.8 - 3.2	2.94 - 3.06	2.97 - 3.03
BZX84-y3V3	3.1 - 3.5	3.23 - 3.37	3.26 - 3.34
BZX84-y3V6	3.4 - 3.8	3.53 - 3.67	3.56 - 3.64
BZX84-y3V9	3.7 - 4.1	3.82 - 3.98	3.86 - 3.94
BZX84-y4V3	4 - 4.6	4.21 - 4.39	4.25 - 4.35
BZX84-y4V7	4.4 - 5	4.61 - 4.79	4.65 - 4.75
BZX84-y5V1	4.8 - 5.4	5 - 5.2	5.04 - 5.16
BZX84-y5V6	5.2 - 6	5.49 - 5.71	5.54 - 5.66
BZX84-y6V2	5.8 - 6.6	6.08 - 6.32	6.13 - 6.27
BZX84-y6V8	6.4 - 7.2	6.66 - 6.94	6.73 - 6.87
BZX84-y7V5	7 - 7.9	7.35 - 7.65	7.42 - 7.58
BZX84-y8V2	7.7 - 8.7	8.04 - 8.36	8.11 - 8.29
BZX84-y9V1	8.5 - 9.6	8.92 - 9.28	9 - 9.2
BZX84-y10	9.4 - 10.6	9.8 - 10.2	9.9 - 10.1
BZX84-y11	10.4 - 11.6	10.8 - 11.2	10.8 - 11.11
BZX84-y12	11.4 - 12.7	11.8 - 12.2	11.88 - 12.12
BZX84-y13	12.4 - 14.1	12.7 - 13.3	12.87 - 13.13
BZX84-y15	13.8 - 15.6	14.7 - 15.3	14.85 - 15.15
BZX84-y16	15.3 - 17.1	15.7 - 16.3	15.84 - 16.16
BZX84-y18	16.8 - 19.1	17.6 - 18.4	17.82 - 18.18
BZX84-y20	18.8 - 21.2	19.6 - 20.4	19.8 - 20.2
BZX84-y22	20.8 - 23.3	21.6 - 22.4	21.78 - 22.22
BZX84-y24	22.8 - 25.6	23.5 - 24.5	23.76 - 24.24
BZX84-y27	25.1 - 28.9	26.5 - 27.5	26.73 - 27.27
BZX84-y30	28 - 32	29.4 - 30.6	29.70 - 30.30
BZX84-y33	31 - 35	32.3 - 33.7	32.67 - 33.33
BZX84-y36	34 - 38	35.3 - 36.7	35.64 - 36.36
BZX84-y39	37 - 41	38.2 - 39.8	38.61 - 39.39
BZX84-y43	40 - 46	42.1 - 43.9	42.57 - 43.43
BZX84-y47	44 - 50	46.1 - 47.9	-
BZX84-y51	48 - 54	50 - 52	50.49 - 51.51
BZX84-y56	52 - 60	54.9 - 57.1	-
BZX84-y62	58 - 66	60.8 - 63.2	-
BZX84-y68	64 - 72	66.6 - 69.4	-
BZX84-y75	70 - 79	73.5 - 76.5	74.25 - 75.75














NZX-series in SOD27

	V_Z (V)	V_Z (V)	V_Z (V)
NZX2V1B	2.0 - 2.2	NZX6V2D	6.1 - 6.4
NZX2V4A	2.3 - 2.5	NZX6V2E	6.3 - 6.6
NZX2V4B	2.4 - 2.6	NZX6V8A	6.4 - 6.7
NZX2V7A	2.5 - 2.7	NZX6V8B	6.6 - 6.9
NZX2V7B	2.6 - 2.8	NZX6V8C	6.7 - 7
NZX2V7C	2.7 - 2.9	NZX6V8D	6.9 - 7.2
NZX3V0A	2.8 - 3	NZX7V5A	7 - 7.3
NZX3V0B	2.9 - 3.1	NZX7V5B	7.2 - 7.6
NZX3V0C	3 - 3.2	NZX7V5C	7.3 - 7.7
NZX3V3A	3.1 - 3.3	NZX7V5D	7.5 - 7.9
NZX3V3B	3.2 - 3.4	NZX7V5X	7.07 - 7.45
NZX3V3C	3.3 - 3.5	NZX8V2A	7.7 - 8.1
NZX3V6A	3.4 - 3.6	NZX8V2B	7.9 - 8.3
NZX3V6B	3.5 - 3.7	NZX8V2C	8.1 - 8.5
NZX3V6C	3.6 - 3.8	NZX8V2D	8.3 - 8.7
NZX3V9A	3.7 - 3.9	NZX9V1A	8.5 - 8.9
NZX3V9B	3.8 - 4	NZX9V1B	8.7 - 9.1
NZX3V9C	3.9 - 4.1	NZX9V1C	8.9 - 9.3
NZX4V3A	4 - 4.2	NZX9V1D	9.1 - 9.5
NZX4V3B	4.1 - 4.3	NZX9V1E	9.3 - 9.7
NZX4V3C	4.2 - 4.4	NZX10A	9.5 - 9.9
NZX4V3D	4.3 - 4.5	NZX10B	9.7 - 10.1
NZX4V7A	4.4 - 4.6	NZX10C	9.9 - 10.3
NZX4V7B	4.5 - 4.7	NZX10D	10.2 - 10.6
NZX4V7C	4.6 - 4.8	NZX11A	10.4 - 10.8
NZX4V7D	4.7 - 4.9	NZX11B	10.7 - 11.1
NZX5V1A	4.8 - 5	NZX11C	10.9 - 11.3
NZX5V1B	4.9 - 5.1	NZX11D	11.1 - 11.6
NZX5V1C	5 - 5.2	NZX12A	11.4 - 11.9
NZX5V1D	5.1 - 5.3	NZX12B	11.6 - 12.1
NZX5V6A	5.2 - 5.5	NZX12C	11.9 - 12.4
NZX5V6B	5.3 - 5.6	NZX12D	12.2 - 12.7
NZX5V6C	5.4 - 5.7	NZX12X	11.44 - 12.03
NZX5V6D	5.5 - 5.8	NZX13A	12.4 - 12.9
NZX5V6E	5.6 - 5.9	NZX13B	12.6 - 13.1
NZX6V2A	5.7 - 6	NZX13C	12.9 - 13.4
NZX6V2B	5.8 - 6.1	NZX14A	13.2 - 13.7
NZX6V2C	6 - 6.3	NZX14B	13.5 - 14

Controlled-avalanche switching diodes







V_R max (V)	V_F max (V)	@ I_F (mA)	I_R max (nA) @ V_R max	I_{FSM} max (A)	I_{FRM} max (mA)	C_d max (pF)	t_{rr} max (ns)	Package	SOT23	SOT143B	
											
									Size (mm)	2.9 x 1.3 x 1.0	2.9 x 1.3 x 1.0
									P_{tot} (mW)	250	250
60	1	200	100	9	600	2.5	6			BAS56	
90	1	200	100	10	600	35	50			BAS29	
										BAS31	
										BAS35	

Low-leakage current-switching

V_R max (V)	V_F max (V)	@ I_F (mA)	I_R max (nA) @ V_R max	t_{rr} max (µs)	Package	SOD80C (MiniMelf)	SOD68 (DO-34)	SOT23	SOD123F	SOT323 (SC-70)	SOD323 (SC-76)	SOD523 (SC-79)			
															
						Size (mm)	3.5 x 1.5 x 1.5	3.04 x 1.6 x 0.55	2.9 x 1.3 x 1.0	2.6 x 1.6 x 1.1	2.0 x 1.25 x 0.95	1.7 x 1.25 x 0.95	1.2 x 0.8 x 0.6		
						P_{tot} (mW)	300	500	250	830	250	400	500		
75	1	10	5	3					BAS116H		BAS416	BAS716			
												BAS116			
												BAV199		BAV199W	
												BAW156			
												BAV170			
125	1	100	1	1.5 typ		BAS45AL	BAS45A								

Hyperfast power diodes

types in **bold** represent new products

	V_{RRM} (V)	$I_{F(AV)}$ (A)	V_F (typ) @ 150C (V)	@ I_F (A)	t_{rr} (typ) @ 25C (ns)	SOD59 (TO220AC)	SOD113 (2-pin SOT186A)	SOD142 (2-pin TO247)	SOT429 (3-pin TO247)	SOT78 (TO220AB)	SOT404 (D ² PAK)	
												
Hyperfast diodes for Continuous Current Mode PFC	500	5	1.15	5	16	BYC5D-500	BYC5DX-500					
			1.4		19	BYC5-600	BYC5X-600					
			13		BYC5-600P	BYC5X-600P				BYC5B-600		
		8	1.4	19	BYC8-600	BYC8X-600				BYC8B-600		
			20	BYC8D-600	BYC8DX-600							
			19	BYC8-600P	BYC8X-600P				BYC8B-600P			
	600	10	1.3	10	19	BYC10-600	BYC10X-600					BYC10B-600
			1.4	18	BYC10D-600	BYC10DX-600						
			19	BYC10-600P	BYC10X-600P				BYC10B-600P			
		2 x 5	1.4	5	19					BYC10-600CT		
		15	1.4	15	22	BYC15-600	BYC15X-600					
		20	1.2	20	19	BYC20-600	BYC20X-600					
30	1.4	30	29	26	BYC20D-600P	BYC20DX-600P						
				25	BYC20X-600P							
					BYC30X-600P	BYC30W-600P	BYC30WT-600P					

In the spotlight

Hyperfast recovery power diodes

- Comprehensive package offerings
- Low leakage current (platinum doped series)
- Low reverse recovery current
- Low thermal resistance


Reduces switching losses in associated MOSFET or IGBT



Power Schottky diodes

	V_{RRM} (V)	$I_{F(AV)}$ (A)	V_F (typ) @ 125C (V)	@ I_F (A)	SOT78 (TO220AB)	SOT186A (isolated TO220AB)
						
Power Schottky diodes for SMPS output rectification	100	2 x 10	0.59	10	NXPS20H100C	NXPS20H100CX
			0.62	10	NXPS20S100C	NXPS20S100CX
			0.59	10	NXPS20H110C	

Casco diodes

	V_{RRM} (V)	$I_{F(AV)}$ (A)	V_F (typ) @ 150C (V)	@ I_F (A)	t_{rr} (typ) @ 25C (ns)	SOD113 (2-pin SOT186A)
						
Casco diodes for Continuous Current Mode PFC	600	8	2	8	12.5	BYC58X-600


In the spotlight

Power Schottky diodes

- Negligible switching losses
- High junction temperature capability
- Low leakage current

Optimized design to give low V_F and high T_{jmax}

Integrated guard ring for voltage stress protection





ESD protection, filtering and signal conditioning

Ultra low-capacitance ESD protection devices 53

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Safeguard your SoC – upgrade to the 6th generation of ESD protection devices

The best system-chip protection available in the market

- ▶ Extremely deep snap-back
- ▶ Low dynamic resistance of $\pm 0.27 \Omega$
- ▶ Extremely low diode switching times



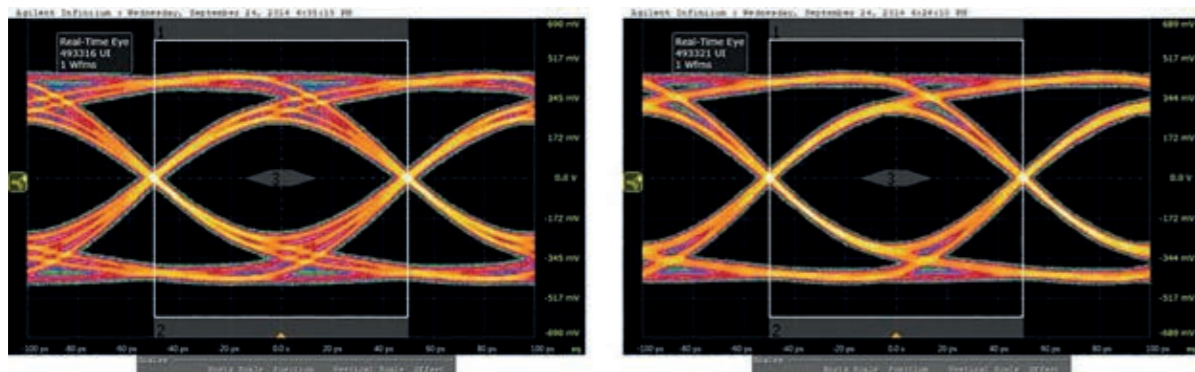
Extremely low clamping voltage
Absorbing highest ESD pulses
THE key for reliable system protection

- ▶ Low capacitance of 0.3 pF unidirectional, fully supporting SuperSpeed USB 10 Gbps
- ▶ Flexible package options: Choose small, RF-optimized DFN2510A-10 / DFN2111-7 or tiny DSN0603 (0201 inch) form factor

NXP's 6th generation of ESD protection devices

The solution for future-proof designs in computing and mobile applications

PUSB3FR4: USB3.1 eye diagram @ 10 Gbps



PUSB3FR4 on standard FR4 testboard

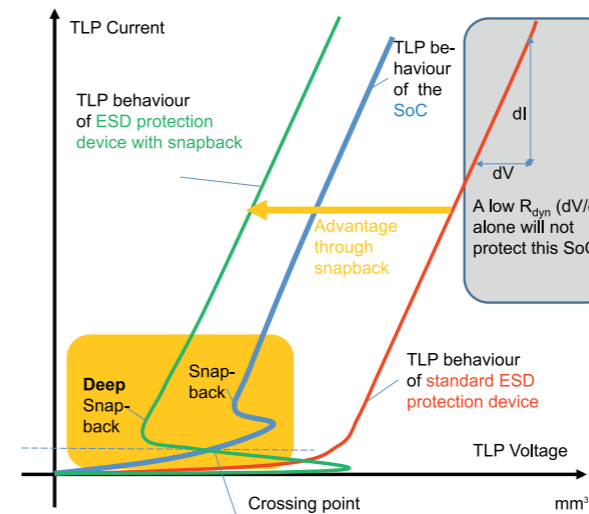
Standard FR4 testboard without ESD protection

PUSB3FR4 is ready for the new SuperSpeed USB 10 Gbps standard

6th generation ESD protection devices – selection guide

Type	V _{RWM} (V)	Uni- or bidirectional	C _{line, typ} (pF)	ESD rating max (kV)	R _{dyn, TLP} (Ω)	Number of protected lines	Package	Size (mm)
PUSB3FR4	5	uni	0.29	15	0.27	4 lines	DFN2510A-10	2.5 x 1.0 x 0.48
PUSB3FR6	5	uni	0.29	15	0.27	6 lines	DFN2111-7	2.1 x 1.1 x 0.48
PESD5V0R1BSF	5	bi	0.18	10	0.5	1 line	DSN0603	0.6 x 0.3 x 0.3
PESD5V0H1BSF	5	bi	0.22	15	0.36	1 line	DSN0603	0.6 x 0.3 x 0.3
PESD5V0C1BSF	5	bi	0.26	20	0.35	1 line	DSN0603	0.6 x 0.3 x 0.3
PESD5V0C1USF	5	uni	0.35	20	0.18	1 line	DSN0603	0.6 x 0.3 x 0.3

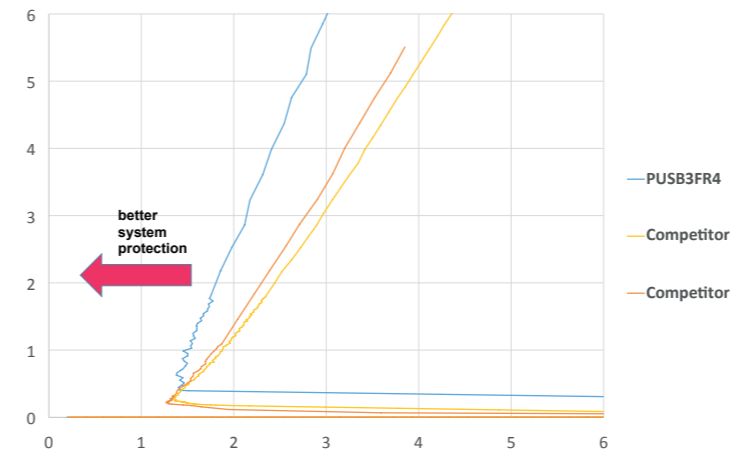
How to achieve the best SOC protection



- ▶ Sensitive SoCs react quickly to transients (ESD pulses and TLP measurements)
- ▶ Standard protection devices react at higher TLP voltages and do not offer sufficient protection
- ▶ Devices with deep snapback protect the most sensitive SoCs against ESD pulses according to IEC61000-4-2

ESD protection, filtering and signal conditioning

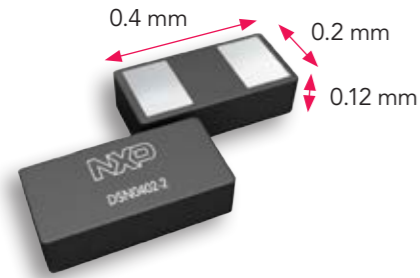
PUSB3FR4: Transmission Line Pulse (TLP) measurement



The PUSB3FR4 absorbs the most pulse energy and safeguards the SoC. The same SoC was damaged at half the IEC voltage using competitor products.

Tiny but mighty – DSN0402

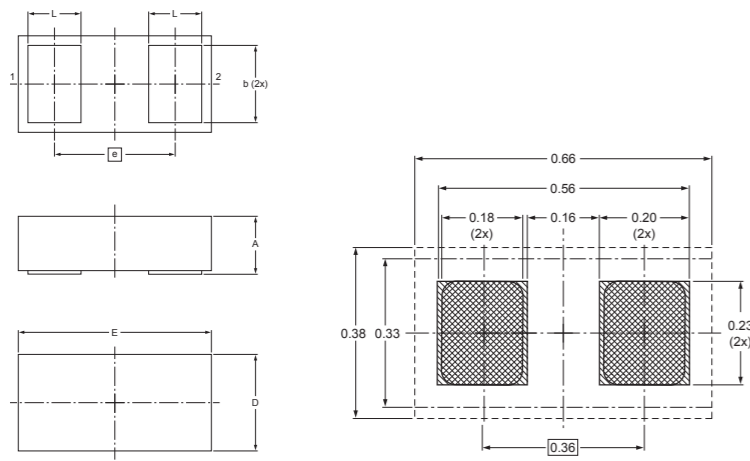
Reliable ESD protection on minimal space



DSN0402-2 (SOD992) features and benefits

- ▶ Ultra-small dimensions: 0.4 x 0.2 mm (02001 inch)
- ▶ 45% less package area compared to DSN0603-2
- ▶ Only 120 μm in height
- ▶ Coated sidewalls enable easier soldering
- ▶ Polarity marking
- ▶ Halogen and antimony free; RoHS compliant

DSN0402-2 package outline and reflow soldering footprint



Dimensions (mm are the original dimensions)

Unit	A	E	D	L	b	e
max	0.14	0.42	0.22	0.12	0.17	
nom	0.12	0.40	0.20	0.11	0.16	0.25
min	0.10	0.38	0.18	0.10	0.15	

Reliable ESD protection for all interfaces and applications

- ▶ Uni- and bidirectional configuration
- ▶ Standard and ultra-low capacitances down to 0.25 pF
- ▶ High ESD robustness up to 25 kV
- ▶ Ultra-low leakage currents

Standard capacitance

Type	V_{rwm} (V)	Config	C_d typ (pF)	C_d max (pF)	V_{esd} (kV)	I_{rm} typ (nA)	I_{rm} max (nA)
PESD5V0V1BSH	5 V	Bi	5 pF	6 pF	25 kV	1 nA	25 nA
PESD5V0V1USH	5 V	Uni	10 pF	12 pF	20 kV	1 nA	100 nA

Ultra-low capacitance

Type	V_{rwm} (V)	Config	C_d typ (pF)	C_d max (pF)	V_{esd} (kV)
PESD5V0F1BSH	5 V	Bi	0.25 pF	0.3 pF	8 kV
PESD5V0F1USH	5 V	Uni	0.4 pF	0.6 pF	8 kV

Ultra low-capacitance ESD protection devices

Ultra low-capacitance ESD protection devices – Part I

types in **bold** represent new products

Unidirectional	Bidirectional	Number of protected lines	V_{rwm} (V)	$C_{d, typ}$ (pF)	$C_{d, max}$ (pF)	ESD rating ⁽¹⁾ max (kV)	Configuration	Type	Package	Size (mm)	
1	0	1	5	0.4	0.6	8		PESD5V0F1USH	DSN0402-2 (SOD992)	0.4 x 0.2 x 0.12	
			5	0.35	0.41	20		PESD5V0C1USF	DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3	
			5.5	0.45	0.6	10		PESD5V0F1USF			
			5	0.95	1.15	8		PESD5V0X1ULD	DFN1006D-2 (SOD882D)	1.0 x 0.6 x 0.37	
				1.55	1.75	15		PESD5V0X1UALD			
			16	0.83	0.98	8		PESD16VX1UL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48	
				5	0.95	1.15		8	PESD5V0X1UB	SOD523 (SC-79)	1.2 x 0.8 x 0.6
			1.55		1.75	15		PESD5V0X1UAB			
				80	0.6	0.75		30		NUP1301U	SOT323
			NUP1301							SOT23	
5.5	1	1.5	8		PRTR5V0U1T		2.9 x 1.3 x 1.0				
0	1	0	5	0.3	0.4	8		PESD5V0F1BSH	DSN0402-2 (SOD992)	0.4 x 0.2 x 0.12	
				0.18	0.24	10		PESD5V0R1BSF			
					0.22	0.27		15	PESD5V0H1BSF		
			0.26	0.32	20	PESD5V0C1BSF		DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3		
				5.5	0.25	0.3		10	PESD5V0F1BSF		
			18		0.28	0.45			PESD5V0F1BSRF		
			24	0.25	0.4	PESD18VF1BSF					
			5	0.4	0.55	10		PESD24VF1BSF			
								PESD5V0F1BLD	DFN1006D-2 (SOD882D)	1.0 x 0.6 x 0.37	
			3.3	1.3	1.6	9		PESD5V0F1BRLD	DSN0603-2 (SOD962)	1.0 x 0.6 x 0.37	
									PESD3V3X1BL		
			5.5	0.4	0.55	10		PESD5V0F1BL			
								0.49	0.6	8	PESD5V0X1BCL
			5	0.85	0.95	15		PESD5V0X1BCAL			
								0.9	1.3	9	PESD5V0X1BL
			18	0.35	0.5	10		PESD18VF1BL			
24	0.3	0.45					10	PESD24VF1BL			

⁽¹⁾ according to IEC 61000-4-2 (contact discharge)

In the spotlight

Ultra low-capacitance ESD protection in DSN0603-2: PESD5V0H1BSF

Bidirectional protection for one data line in DSN0603-2

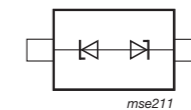
Ultra-low line capacitance of 0.22 pF

Ultra-low clamping

Minimized capacitance variation over voltage

High ESD robustness = 15 kV

Ultra-small package DSN0603-2 (0.6 x 0.3 x 0.3 mm)



ESD protection, filtering and signal conditioning

Ultra low-capacitance ESD protection devices – Part 2

types in **bold** represent new products

Number of protected lines		V _{rev} (V)	C _{line typ} (pF)	C _{line max} (pF)	ESD rating ⁽¹⁾ max (kV)	Configuration	Type	Package	Size (mm)	
Unidirectional	Bidirectional									
1	5	5	0.55	0.7	10		PESD5V0X2UMB	DFN1006B-3 (SOT883B)	1.0 x 0.6 x 0.37	
							PESD5V0X2UM	DFN1006-3 (SOT883)	1.0 x 0.6 x 0.48	
							PESD5V0X2UAMB	DFN1006B-3 (SOT883B)	1.0 x 0.6 x 0.37	
							PESD5V0X2UAM	DFN1006-3 (SOT883)	1.0 x 0.6 x 0.48	
	0.9	1.3	9		PESD5V0X1BQ	SOT663	1.6 x 1.2 x 0.55			
					PESD5V0X1BT	SOT23	2.9 x 1.3 x 1.0			
2	1	5.5	1	1.5	8		PRTR5V0U2X	SOT143B	2.9 x 1.3 x 1.0	
							PRTR5V0U2AX			
							PRTR5V0U2F	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48	
	1.8	-	12	-	-					
	0	5.5	2	0.7	-	8		IP4234CZ6	SOT457 (SC-74)	2.9 x 1.5 x 1.0
								IP4282CZ6	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
								IP4359CX4/LF	WLCSP4	0.76 x 0.76 x 0.61
IP4369CX4									0.76 x 0.76 x 0.47	

⁽¹⁾ according to IEC 61000-4-5 (contact discharge)

In the spotlight

Lowest capacitance ESD protection in DFN1006B-3: PESD5V0X2UAMB

Unidirectional double protection for two signal lines

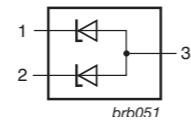
Ultra-low line capacitance of 0.8 pF

Very low package height of 0.37 mm typ

High ESD robustness of 15 kV

AEC-Q101 qualified

Ideal for high-speed data lines, portable electronics, and communication systems



Ultra low-capacitance ESD protection devices – Part 3

types in **bold** represent new products

Number of protected lines		V _{rev} (V)	C _{line typ} (pF)	C _{line max} (pF)	ESD rating ⁽¹⁾ max (kV)	Configuration	Type	Package	Size (mm)
Unidirectional	Bidirectional								
4	0	5.5	1	-	8		IP4220CZ6	SOT457 (SC-74)	2.9 x 1.5 x 1.0
							IP4221CZ6-S	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
							IP4221CZ6-XS	DFN1010-6 (SOT891)	1.0 x 1.0 x 0.48
							IP4233CZ6	SOT363 (SC-88)	2.0 x 1.25 x 0.95
							PRTR5V0U4D	SOT457 (SC-74)	2.9 x 1.5 x 1.0
							PRTR5V0U4Y	SOT363 (SC-88)	2.0 x 1.25 x 0.95
							IP4285CZ9-TBB	DFN2110-9 (SOT1178)	2.1 x 1.0 x 0.48
							PUSB2X4D	SOT457 (SC-74)	2.9 x 1.5 x 1.0
							PUSB2X4Y	SOT363 (SC-88)	2.0 x 1.25 x 0.95
							IP4283CZ10-TBR	DFN2510A-10 (SOT1176)	2.5 x 1.0 x 0.48
IP4284CZ10-TBR	DFN2510A-10 (SOT1176)	2.5 x 1.0 x 0.48							

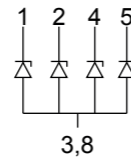
⁽¹⁾ according to IEC 61000-4-5 (contact discharge)

ESD protection,
filtering and signal
conditioning

In the spotlight

PUSB3FR4 - ESD protection in very small DFN2510A-10 package for USB3.0

- Protects four very fast data lines of sensitive system chips
- Best system chip protection in the 0.3 pF class
- Very small DFN2510A-10 package (2.5 x 1.0 x 0.48 mm)
- Capacitance < 0.3 pF



Ultra low-capacitance ESD protection devices – Part 4

types in **bold** represent new products

Number of protected lines		V _{revm} (V)	C _{line typ} (pF)	C _{line max} (pF)	ESD rating ^[1] max (kV)	I _r max (μA) @ V _{revm}	Configuration	Type	Package	Size (mm)
Unidirectional	Bidirectional									
4	0	5.5	0.55	-	8	-		IP4292CZ10-TBR	DFN2510A-10 (SOT1176)	2.5 x 1.0 x 0.48
			0.5	-	10					
		3.3	0.27	-	15					
5	4	5	0.5	0.65	8	0.1		PESD5V0F5UF	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
								PESD5V0F5UV	SOT666	1.6 x 1.2 x 0.55
0	6	5.5	0.27	0.35	10	0.1		PUSB3TB6	DFN2111-7 (SOT1358)	2.1 x 1.1 x 0.48
6	0	3.3	0.25	-	15	0.1		PUSB3FR6		

^[1] according to IEC 61000-4-2 (contact discharge)

Low-capacitance ESD protection devices – Part 1

types in **bold** represent new products

Number of protected lines		V _{revm} (V)	C _{line typ} (pF)	C _{line max} (pF)	P _{pp} ^[1] max (W)	ESD rating ^[2] max (kV)	I _r max (μA) @ V _{revm}	Configuration	Type	Package	Size (mm)
Unidirectional	Bidirectional										
1	0	5	10	12	-	20	100		PESD5V0V1USH	DSN0402-2 (SOD992)	0.4 x 0.2 x 0.12
		3.3	34	40	45	30	0.3		PESD3V3L1UL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48
		5	25	30	42	26	0.1		PESD5V0L1UL	DFN1006D-2 (SOD882D)	1.0 x 0.6 x 0.37
		5	25	30	42	26	0.1		PESD5V0L1ULD	SOD523 (SC-79)	1.2 x 0.8 x 0.6
		3.3	34	40	45	30	0.3		PESD3V3L1UA	SOD323 (SC-76)	1.7 x 1.25 x 0.95
		5	25	30	42	26	0.1		PESD5V0L1UA	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48
		5	12	15	10	30	0.1		PESD5V0L1USF	DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3
		5	4	5	8	14	0.1		PESD5V0V1USF	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48
		3.3	2.6	3.1	-	9	0.1 (@ 3 V)		PESD3V3U1UL	SOD523 (SC-79)	1.2 x 0.8 x 0.6
		5	2	2.6	-	9	0.1		PESD5V0U1UL	SOD323 (SC-76)	1.7 x 1.25 x 0.95
		3.3	2.6	3.1	-	9	0.1 (@ 3 V)		PESD3V3U1UB	SOD323 (SC-76)	1.7 x 1.25 x 0.95
		5	2	2.6	-	9	0.1		PESD5V0U1UB	SOD323 (SC-76)	1.7 x 1.25 x 0.95
		3.3	2.6	3.1	-	9	0.1 (@ 3 V)		PESD3V3U1UA	SOD323 (SC-76)	1.7 x 1.25 x 0.95
		5	2	2.6	-	9	0.1		PESD5V0U1UA	SOD323 (SC-76)	1.7 x 1.25 x 0.95
		0	1	5.5	12	15.4	35		30	0.1	
3.3	101			-	500	30	2	PESD3V3L1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95	
5	75			-	500	30	1	PESD5V0L1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95	
12	19			-	200	30	0.05	PESD12VL1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95	
15	16			-	200	30	0.05	PESD15VL1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95	
24	11			-	200	23	0.05	PESD24VL1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95	

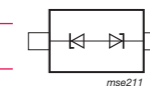
^[1] 8 / 20 μs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321

^[2] according to IEC 61000-4-2 (contact discharge)

In the spotlight

PESD5V0V1BSH – ESD protection in super small DSN0402-2 package

- Super small 0.4 x 0.2 CSP package
- Only 120 μm package height
- ESD protection of one 5V line
- Up to 20 kV ESD robustness



ESD protection, filtering and signal conditioning

Low-capacitance ESD protection devices – Part 2

types in **bold** represent new products

Number of protected lines		V _{revm} (V)	C _{line typ} (pF)	C _{line max} (pF)	P _{pp} ^[1] max (W)	ESD rating ^[2] max (kV)	I _r max (μA) @ V _{revm}	Configuration	Type	Package	Size (mm)
Unidirectional	Bidirectional										
0	1	5	5	7	35	25	25		PESD5V0V1BSH	DSN0402-2 (SOD992)	0.4 x 0.2 x 0.12
		5	11	13	45	30	0.01		PESD5V0V1BL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48
		5	11	13	45	30	0.01		PESD5V0V1BLD	DFN1006D-2 (SOD882D)	1.0 x 0.6 x 0.37
		5	11	13	45	30	0.01		PESD5V0V1BB	SOD523 (SC-79)	1.2 x 0.8 x 0.6
		5	11	13	45	30	0.01		PESD5V0V1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95
		5	5.3	6	10	20	0.1		PESD5V0V1BCSF	DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3
		5	5.3	6	20	25	0.1		PESD5V0V1BDSF		
		5.5	3.5	4.5	8	15	0.1		PESD5V0V1BSF	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48
		12	17	25	290	30	0.01		PESD12VV1BL	WLCSP2	0.7 x 0.52 x 0.40
		15	8	10	-	15	0.1		IP4302CX2/A	WLCSP2	0.7 x 0.52 x 0.40
		5	2.9	3.5	-	10	0.1		PESD5V0U1BL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48
									PESD5V0U1BLD	DFN1006D-2 (SOD882D)	1.0 x 0.6 x 0.37
									PESD5V0U1BB	SOD523 (SC-79)	1.2 x 0.8 x 0.6
									PESD5V0U1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95
PESD5V0U2BT	DFN1006-3 (SOT883)							1.0 x 0.6 x 0.48			
2	1	3.3	22	28	30	15	0.3		PESD3V3L2UM	DFN1006-3 (SOT883)	1.0 x 0.6 x 0.48
									PESD5V0L2UM	DFN1006-3 (SOT883)	1.0 x 0.6 x 0.48
									PESD5V0L2UMB	DFN1006B-3 (SOT883B)	1.0 x 0.6 x 0.37
									PESD5V0L2UU	SOT323 (SC-70)	2.0 x 1.25 x 0.95
									PESD6V0L2UU	SOT323 (SC-70)	2.0 x 1.25 x 0.95

^[1] 8 / 20 μs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321

^[2] according to IEC 61000-4-5 (contact discharge)

In the spotlight

PESD12VV1BL: Lowest capacitance ESD protection in DSN1006-2

Bidirectional protection for one data line

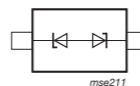
Very low line capacitance of 17 pF

High ESD robustness of 30 kV

AEC-Q101 qualified

Ultra-small package DFN1006-2 (SOD993) with a height of only 0.48 mm typ

Ideal for portable electronics, communication systems, or audio and video equipment



Low-capacitance ESD protection devices – Part 3

Number of protected lines		V _{revm} (V)	C _{line typ} (pF)	C _{line max} (pF)	P _{pp} ^[1] max (W)	ESD rating ^[2] max (kV)	I _r max (μA) @ V _{revm}	Configuration	Type	Package	Size (mm)							
Unidirectional	Bidirectional																	
0	2	3.3	101	-	350	30	2		PESD3V3L2BT	SOT23	2.9 x 1.3 x 1.0							
		5	75						30			1						
		12	19						30			0.05						
		15	16						30			0.05						
		24	11						23			0.05						
		5	2.9						3.5			-	10	0.1	PESD5V0U2BM	DFN1006-3 (SOT883)	1.0 x 0.6 x 0.48	
															PESD5V0U2BMB	DFN1006B-3 (SOT883B)	1.0 x 0.6 x 0.37	
										IP4303CX4/P	WLCSP4				0.76 x 0.76 x 0.40			
		4	3						3.3	22	28	30	20	0.3		PESD3V3L4UF	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
									5	16	19	30	20	0.025		PESD5V0L4UF	SOT665	1.6 x 1.2 x 0.55
									3.3	22	28	30	20	0.3		PESD3V3L4UW	SOT353 (SC-88A)	2.0 x 1.25 x 0.95
									5	16	19	30	20	0.025		PESD5V0L4UW	SOT665	1.6 x 1.2 x 0.55
									3.3	22	28	30	20	0.3		PESD3V3L4UG	SOT665	1.6 x 1.2 x 0.55
									5	16	19	30	20	0.025		PESD5V0L4UG	SOT665	1.6 x 1.2 x 0.55
3.3	13			17	25	10	1	PESD3V3V4UK	DFN1010-6 (SOT891)	1.0 x 1.0 x 0.48								
5	12			15	25	15	0.3	PESD5V0V4UK	SOT665	1.6 x 1.2 x 0.55								
9	6.5			10	28	8	0.1	PESD9V0V4UK	SOT665	1.6 x 1.2 x 0.55								
3.3	15			18	16	12	0.3	PESD3V3V4UW	SOT665	1.6 x 1.2 x 0.55								
5	12			15	16	12	0.025	PESD5V0V4UW	SOT665	1.6 x 1.2 x 0.55								
0	4			5.5	18	20	-	15	0.1		IP4343CX5/LF	WLCSP5	1.06 x 0.76 x 0.61					

^[1] 8 / 20 μs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321

^[2] according to IEC 61000-4-5 (contact discharge)

ESD protection, filtering and signal conditioning

Low-capacitance ESD protection devices – Part 4

Number of protected lines		V _{revm} (V)	C _{line typ} (pF)	C _{line max} (pF)	P _{pp} ^[1] max (W)	ESD rating ^[2] max (kV)	I _r max (μA) @ V _{revm}	Configuration	Type	Package	Size (mm)
Unidirectional	Bidirectional										
0	4	5	2.9	3.5	-	10	0.1		PESD5V0U4BF	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
		5	2.9	3.5	-	10	0.1		PESD5V0U4BW	SOT665	1.6 x 1.2 x 0.55
5	4	3.3	20	24	28	15	2		PESD3V3L5UK	DFN1010-6 (SOT891)	1.0 x 1.0 x 0.48
		5	18.5	22	30	20	0.5		PESD5V0L5UK		
		3.3	22	28	25	20	0.3		PESD3V3L5UF	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
		5	16	19	25	20	0.025		PESD5V0L5UF		
		3.3	22	28	25	20	0.3		PESD3V3L5UV	SOT666	1.6 x 1.2 x 0.55
		5	16	19	25	20	0.025		PESD5V0L5UV		
		3.3	22	28	25	20	0.3		PESD3V3L5UY	SOT363 (SC-88)	2.0 x 1.25 x 0.95
		5	16	19	25	20	0.025		PESD5V0L5UY		
0	5	5	2.9	3.5	-	10	0.1		PESD5V0U5BF	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
		5	2.9	3.5	-	10	0.1		PESD5V0U5BV	SOT666	1.6 x 1.2 x 0.55

^[1] 8 / 20 μs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321

^[2] according to IEC 61000-4-5 (contact discharge)

Standard ESD protection devices – Part I

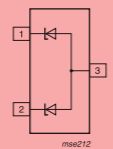

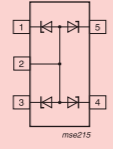
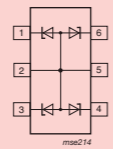
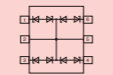
Number of protected lines		V _{revm} (V)	C _{line typ} (pF)	C _{line max} (pF)	P _{pp} ^[1] max (W)	ESD rating ^[2] max (kV)	I _r max (μA) @ V _{revm}	Configuration	Type	Package	Size (mm)		
Unidirectional	Bidirectional												
1	0	5	35	42	40	30	0.1		PESD5V0S1USF	DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3		
		3.3	207	300	150	30	2		PESD3V3S1UL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48		
		5	152	200	150	30	1		PESD5V0S1UL				
		12	38	75	150	30	0.05		PESD12VS1UL				
		15	32	70	150	30	0.05		PESD15VS1UL				
		24	23	50	150	23	0.05		PESD24VS1UL				
		36	18	30	150	30	0.01		PESD36VS1UL				
		5	152	200	150	30	1		PESD5V0S1ULD			DFN1006D-2 (SOD882D)	1.0 x 0.6 x 0.37
		12	38	75	150	30	0.05		PESD12VS1ULD				
		15	32	70	150	30	0.05		PESD15VS1ULD				
		24	23	50	150	23	0.05		PESD24VS1ULD				
		3.3	207	300	330	30	2		PESD3V3S1UB	SOD523 (SC-79)	1.2 x 0.8 x 0.6		
		5	152	200	260	30	1		PESD5V0S1UB				
		12	38	75	180	30	0.05		PESD12VS1UB	SOD323 (SC-76)	1.7 x 1.25 x 0.95		
		15	32	70	160	30	0.05		PESD15VS1UB				
		24	23	50	160	23	0.05		PESD24VS1UB				
		5	480	530	890	30	4		PESD5V0S1UA				
		12	160	180	600	30	0.1		PESD12VS1UA	SOD323F (SC-90)	1.7 x 1.25 x 0.7		
		24	23	50	160	23	0.05		PESD24VS1UA				
		5	480	530	890	30	4		PESD5V0S1UJ	SOD523 (SC-79)	1.2 x 0.8 x 0.6		
		12	160	180	600	30	0.1		PESD12VS1UJ				
		2.5	229	300	260	30	6		PESD5Z2.5	SOD523 (SC-79)	1.2 x 0.8 x 0.6		
		3.3	172	200	260	30	0.05		PESD5Z3.3				
		5	89	150	180	30	0.05		PESD5Z5.0				
6	78	150	180	30	0.01	PESD5Z6.0							
7	69	150	180	30	0.01	PESD5Z7.0							
12	35	75	200	30	0.01	PESD5Z12							
0	1	5.5	35	45	100	30	0.1		PESD5V0S1BSF	DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3		
		5	35	45	130	30	0.1		PESD5V0S1BL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48		
		5	35	45	130	30	0.1		PESD5V0S1BLD	DFN1006D-2 (SOD882D)	1.0 x 0.6 x 0.37		
		5	35	45	130	30	0.1		PESD5V0S1BB	SOD523 (SC-79)	1.2 x 0.8 x 0.6		
		5	35	45	130	30	0.1		PESD5V0S1BA	SOD323 (SC-76)	1.7 x 1.25 x 0.95		

^[1] 8 / 20 μs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321

^[2] according to IEC 61000-4-2 (contact discharge)

ESD protection, filtering and signal conditioning

Standard ESD protection devices – Part 2

Number of protected lines		V _{revM} (V)	C _{line typ} (pF)	C _{line max} (pF)	P _{pp} ^[1] max (W)	ESD rating ^[2] max (kV)	I _{rk} max (μA) @ V _{revM}	Configuration	Type	Package	Size (mm)			
Unidirectional	Bidirectional													
2	1	3.3	200	275	150	23	3		PESD3V3S2UQ	SOT663	1.6 x 1.2 x 0.55			
		5	150	215	150	30	0.3		PESD5V0S2UQ					
		12	38	100	150	30	0.03		PESD12VS2UQ					
		15	32	70	150	30	0.05		PESD15VS2UQ					
		24	23	50	150	23	0.05		PESD24VS2UQ					
		3.3	207	300	330	30	2		PESD3V3S2UT					
		2	1	5.2	152	200	260	30	1		PESD5V2S2UT	SOT23	2.9 x 1.3 x 1.0	
				12	38	75	180	30	1		PESD12VS2UT			
				15	32	70	160	30	1		PESD15VS2UT			
				24	23	50	160	23	1		PESD24VS2UT			
				36	17	35	160	30	1 (@ 30 V)		PESD36VS2UT			
				3.3	207	300	330	30	2		PESD3V3S2UAT			
				5	152	200	260	30	1		PESD5V0S2UAT			
				15	32	70	160	30	0.05		PESD15VS2UAT			
				24	23	50	160	23	0.05		PESD24VS2UAT			
				3.3	207	300	330	30	2		PESD3V3S4UF			
4	3	5	85	220	110	30	0.1 (@ 4.3 V)		PESD5V0S4UF	SOT665	1.6 x 1.2 x 0.55			
		3	107	125	-	8	1		BZA956A					
		4	90	105	-	8	0.5		BZA962A					
		4.3	78	90	-	8	0.1		BZA968A					
		3	200	240	-	8	2		BZA856A					
		3	200	240	-	8	2		BZA456A					
		4	3	4	165	200	-	15	0.7	BZA462A		BZA420A	SOT457 (SC-74)	2.9 x 1.5 x 1.0
				15	37	48	-	8	0.1	PESD3V3S4UD				
				3.3	215	300	200	30	0.8	PESD5V0S4UD				
				5	165	220	200	30	0.2	PESD24VS4UD				
				24	40	70	200	23	0.015	PESD3V3S5UD				
				3.3	215	300	200	30	0.8	PESD5V0S5UD				
				5	165	220	200	30	0.2	PESD12VS5UD				
				12	73	100	200	30	0.015	PESD15VS5UD				
				15	60	90	200	30	0.015	PESD24VS5UD				
				24	45	70	200	23	0.015	BZA408B				
0	4	5	45	75	-	15	0.1		BZA408B					

^[1] 8 / 20 μs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321

^[2] according to IEC 61000-4-2 (contact discharge)

USB 2.0 protection and filtering

types in **bold** represent new products

Baseband interface	Number of protected lines	R _{line}	C _{line} (pF)	Remark	Type	Package	Size (mm)
USB (CSP package)	3 + 2	47 Ω / 100 Ω	10	Integrated low- capacitance SIM-Card & USB passive filter array with ESD protection	IP4365CX11/P	WLCSP11	1.16 x 1.56 x 0.61
	2	-	0.8	MHL and USB2.0 high-speed ESD-protection	IP4369CX4	WLCSP4	0.76 x 0.76 x 0.47
USB2.0 (Plastic package)	2	0.5	2	>15 kV IEC contact ESD protection with pi-filter	IP4234CZ6	SOT457 (SC-74)	2.9 x 1.5 x 1.0
			1.0	ESD protection for up to 2 ultra high-speed datalines	PRTR5V0U2X	SOT143B	2.9 x 1.3 x 1.0
			1.8	ESD protection for up to 2 ultra high-speed datalines with 12 kV ESD robustness	PRTR5V0U2AX		
			0.7	ESD protection for ultra high-speed interfaces	IP4282CZ6	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
			-	ESD protection for up to 2 ultra high-speed datalines	PRTR5V0U2F	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
			0.8	Very low clamp ESD protection for USB2.0 high-speed with 12 kV IEC ESD protection	PUSB2X4X	SOT363 (SC-88)	2.0 x 1.25 x 0.95
	4	1	0.8	Very low clamp ESD protection for USB2.0 high-speed with 12 kV IEC ESD protection	PUSB2X4D	SOT457 (SC-74)	2.9 x 1.5 x 1.0
			0.8	Dual ESD protection for USB2.0 high-speed, SD-card, SIM card	IP4220CZ6		
			0.8	Dual ESD protection for USB2.0 high-speed, SD-card, SIM card	PRTR5V0U4D		
			0.8	Dual ESP protection for USB2.0 high-speed, SD-card, SIM card	PRTR5V0U4Y	SOT363 (SC-88)	2.0 x 1.25 x 0.95
			0.8	ESD protection for USB2.0 high-speed, SD-card, SIM card	IP4221CZ6-S	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
			0.8	Dual ESD protection for USB2.0 high-speed, SD-card, SIM-card	IP4221CZ6-XS	DFN1010-6 (SOT891)	1.0 x 1.0 x 0.48

ESD protection, filtering and signal conditioning

Common Mode Filter for USB 2.0

types in **bold** represent new products

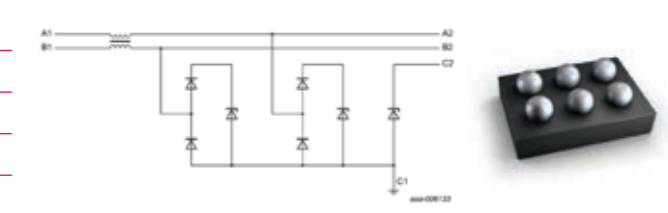
Baseband interface	Number of protected lines	C _{line} (pF)	ESD rating ^[1] max (kV)	Remark	Type	Package	Size (mm)
USB2.0	2	1.5	15	Common Mode filter with ESD protection for high-speed interfaces such as USB 2.0	IP3319CX6	WLCSP6	1.34 x 0.95 x 0.57

^[1] according to IEC 61000-4-2 (contact discharge)

In the spotlight

IP3319CX6 - Common Mode Filter for USB2.0

- Very wide differential pass band >1 GHz
- Very broadband Common Mode attenuation
- Very low clamping ESD protection, excellent SoC protection
- Very small WLCSP6 package (footprint area 1.34 x 0.95 mm)

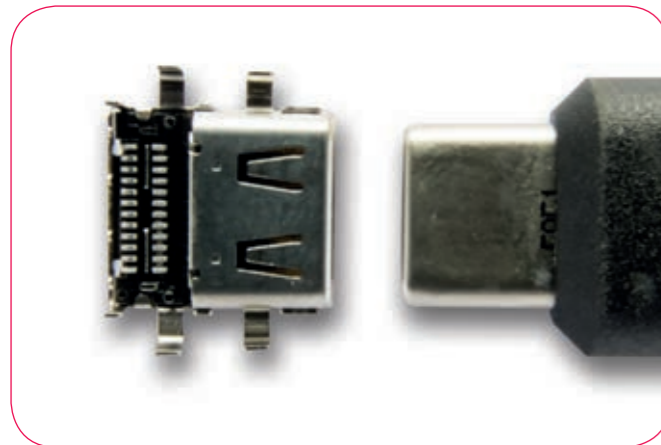


USB 3.x and eSATA protection and filtering

types in **bold** represent new products

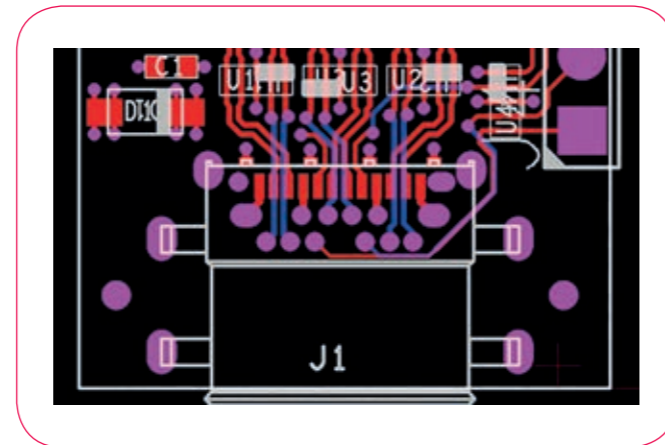
Baseband interface	Number of protected lines	C_{lim} (pF)	ESD rating max (kV)	R_{dyn} (Ω)	Remark	Type	Package	Size (mm)
USB3.0 - 5 Gbps	4	0.55	8	0.3 / 0.4	ESD protection for ultra high-speed interfaces	IP4292CZ10-TBR	DFN2510A-10 (SOT1176)	2.5 x 1.0 x 0.48
		0.5	10			IP4294CZ10-TBR		
		PUSB3F96						
USB3.1 - 10 Gbps	6	0.29	15	0.27		PUSB3FR6	DFN2111-7 (SOT1358)	2.1 x 1.1 x 0.48
		0.27	15	0.5		PUSB3TB6		
	4	0.29	15	0.27		PUSB3FR4		DFN2510A-10 (SOT1176)
		1	0.18	10	0.5	PESD5V0R1BSF	DSN0603-2 (SOD962)	
	0.22		15	0.36	PESD5V0H1BSF			
	0.26		20	0.35	PESD5V0C1BSF			
	0.35	20	0.18	PESD5V0C1USF				

NXP paves the way for USB Type-C connector

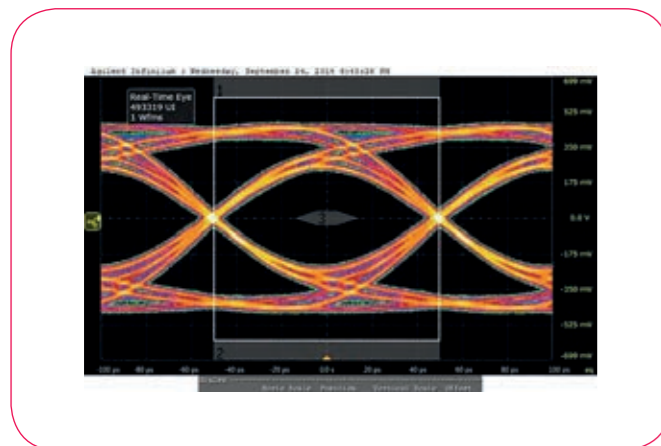


USB Type-C receptacle

USB Type-C plug



PUSB3FR4 routing diagram



PUSB3FR4 on standard FR4 testboard

PUSB3FR4 and the new Type-C connector

The perfect match. PUSB3FR4 supports protection and filtering for the new Type-C connector, in order to enable flawless direction-agnostic, faster charging and the smallest solution to support SuperSpeed USB.

USB 3.1 introduces data rates up to 10 Gbps

As shown in the eye diagram, NXP offers protection, which supports data rates up to 10 Gbps with low capacitance and optimized package layouts.

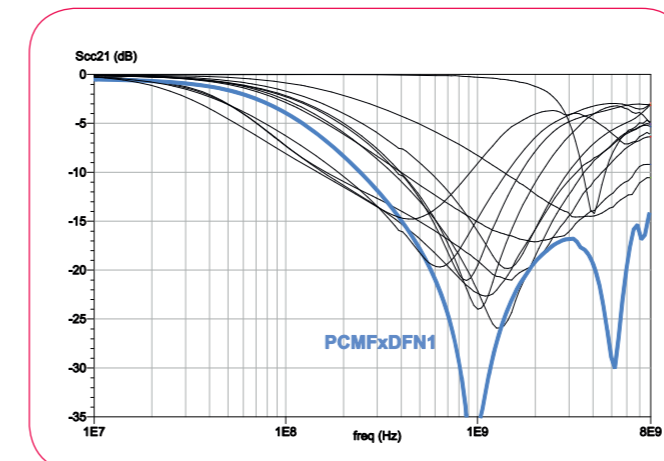
Common Mode Filter for USB 3.x

types in **bold** represent new products

Baseband interface	Number of protected line pairs	Type	Differential Mode 3dB frequency	Common Mode rejection 800 MHz - 2.4 GHz	C_d typical	V_{RWM}	ESD rating	Channel series resistance	Package	Size (mm)	
USB3.x	1	PCMF1USB30	>7 GHz	>12	0.3	5	15	3	WLCSP5	0.8 x 1.2 x 0.5	
	2								WLCSP10	1.6 x 1.2 x 0.5	
	3								WLCSP15	2.4 x 1.2 x 0.5	
	1	PESD1USB30							ESD protection only	WLCSP5	0.8 x 1.2 x 0.5
	2									WLCSP10	1.6 x 1.2 x 0.5
	3									WLCSP15	2.4 x 1.2 x 0.5

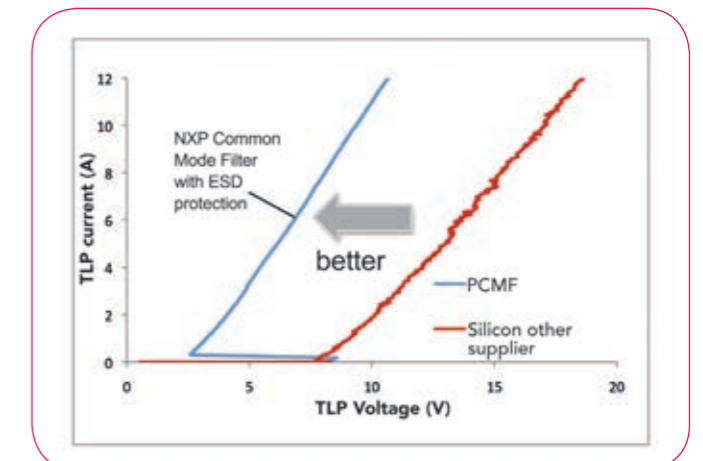
¹ according to IEC 61000-4-2 (contact discharge)

Common Mode suppression performance (for various ferrite and ceramic filters)



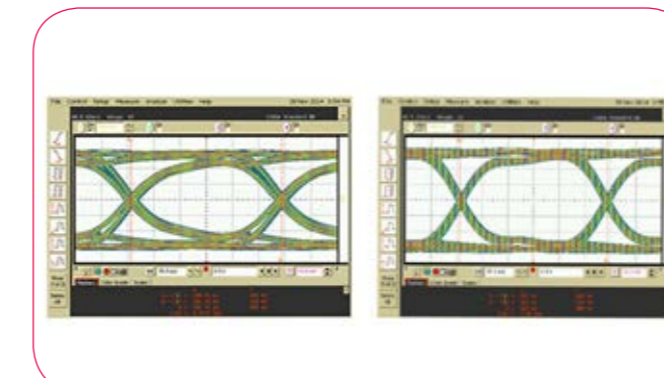
PCMFxDFN1 offers the largest bandwidth on Common Mode suppression

Clamping performance of PCMF compared to silicon



The superior system-level protection is shown in the lower TLP clamping voltage

USB 3.x 5 Gbps eye diagrams



PCMFxUSB30

Only test board

NXPs Common Mode Filter offer:

- ▶ Best in class system-level protection due to deep snap-back and very low dynamic resistance
- ▶ Very wide-band Common Mode rejection to cover all critical frequencies
- ▶ Improved RF performance and small footprint compared to separate ESD/CMF solutions
- ▶ Protection for MIPI CSI, DSI, USB3.x, and HDMI

ESD protection, filtering and signal conditioning

Common Mode Filter for video interfaces

types in **bold** represent new products

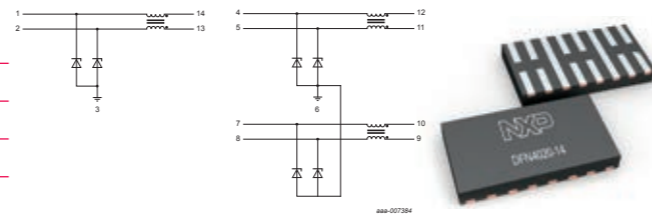
Baseband interface	Number of protected line pairs unidirectional	Number of protected line pairs bidirectional	Type	Differential Mode 3 dB frequency (typ.)	Common Mode insertion loss 800 MHz - 2.4 GHz	C _d pF typical	V _{RWM}	ESD rating ⁽¹⁾ max (kV)	Channel series resistance	Package	Size (mm)
MIPI D-PHY	2	0	PCMF2DFN1	>2 GHz	<-24 dB	0.8	5	15	5 Ω	DFN2520-9 (SOT1333)	2.5 x 2.0 x 0.48
	3		PCMF3DFN1	>2 GHz						DFN4020-14 (SOT1334)	4.0 x 2.0 x 0.48
MIPI, HDMI	2	0	PCMF2DFN2	<3 GHz	<- 20 dB	0.7	5	15	2 Ω	DFN2520-9 (SOT1333)	2.5 x 2.0 x 0.48
	3		PCMF3DFN2	<- 20 dB	DFN4020-14 (SOT1334)					4.0 x 2.0 x 0.48	

⁽¹⁾ according to IEC 61000-4-2 (contact discharge)

In the spotlight

PCMF-series: 2- and 3-line pair Common Mode filters for MIPI, HDMI

- Very wide differential pass band >2 GHz
- Very broadband Common Mode attenuation
- Very low clamping ESD protection, excellent SoC protection
- Very thin DFN plastic package (0.5 mm max)



Ethernet protection

types in **bold** represent new products

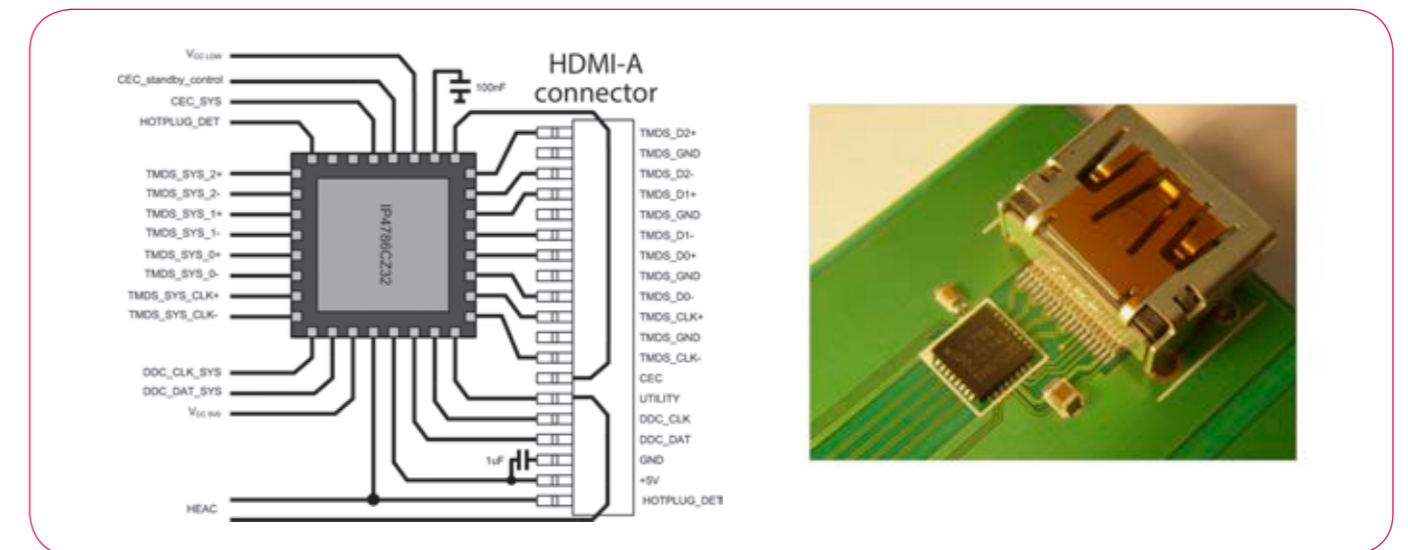
Baseband interface	Number of protected lines	C _{line} (pF)	Remark	Type	Package	Size (mm)
LAN	1	0.6	Ethernet ESD protection V _{RWM} = 3.3 V	PESD3V3U1UT	SOT23	2.9 x 1.3 x 1.0
			Ethernet ESD protection V _{RWM} = 5.0 V	PESD5V0U1UT		
			Ethernet ESD protection V _{RWM} = 12 V	PESD12VU1UT		
			Ethernet ESD protection V _{RWM} = 15 V	PESD15VU1UT		
			Ethernet ESD protection V _{RWM} = 24 V	PESD24VU1UT		
	4	1	Ethernet line-surge ESD protection	IP4233CZ6	SOT363 (SC-88)	2.0 x 1.25 x 0.95
		Ethernet ESD protection	IP4220CZ6	SOT457 (SC-74)	2.9 x 1.5 x 1.0	

HDMI and memory-card signal conditioning

types in **bold** represent new products

Interface	Number of protected lines	Buffer	Level shifter	C _{line} (pF)	Resistor (Ω)	LDO	Remark	Type	Package	Size (mm)
HDMI tx	5			-	internal	-	Fully integrated for HDMI control lines including buffer for DDC, CEC, and Hot Plug module	IP4791CZ12	DFN2521-12 (SOT1156)	2.5 x 2.1 x 0.48
				10	1.75 k, 100 k		HDMI, DDC, CEC, Hot Plug ESD protection and biasing	IP4310CX8/P	WLCSP8	1.16 x 1.16 x 0.61
	13	yes	yes	100 Ω differential impedance	internal	CEC LDO, 5 V LDO	Fully integrated HDMI source solution with current limiter, buffer, and level shifter for DDC, CEC, and Hot Plug	IP4786CZ32	DFN5050-32 (SOT617)	5.0 x 5.0 x 0.85
							Fully integrated HDMI sink solution with buffer, and level shifter for DDC, CEC, and Hot Plug			
HDMI2.0	13	yes	yes	100 Ω differential impedance	integrated	-	Fully integrated HDMI source solution with enhanced ESD protection, current limiter, buffer, and level shifter for DDC, CEC, and Hot Plug	IP4786CZ32S	DFN4040-32 (SOT1318-1)	4.0 x 4.0 x 0.50
							Fully integrated HDMI source solution with small package, current limiter, buffer, and level shifter for DDC, CEC, and Hot Plug			
							Fully integrated HDMI source solution with current limiter, buffer, and level shifter for DDC, CEC, and Hot Plug	IP4786CZ32S	DFN5050-32 (SOT617)	5.0 x 5.0 x 0.85
							Fully integrated HDMI source solution with enhanced ESD protection, current limiter, buffer, and level shifter for DDC, CEC, and Hot Plug			
							Fully integrated HDMI source solution in a small package with current limiter, buffer, and level shifter for DDC, CEC, and Hot Plug			
SD3.0	6	yes	yes	-	internal	1.8 V LDO	SD 3.0-compliant memory card with integrated dual voltage-level translator with EMI filter and ESD protection	IP4856CX25/C	WLCSP25	2.4 x 2.4 x 0.4
							Fully integrated SD 3.0 card level shifter with buffer technology, LDO, and EMI filter			
								IP4755CZ24	DFN5535-24 (SOT815)	3.5 x 5.5 x 0.85

ESD protection, filtering and signal conditioning

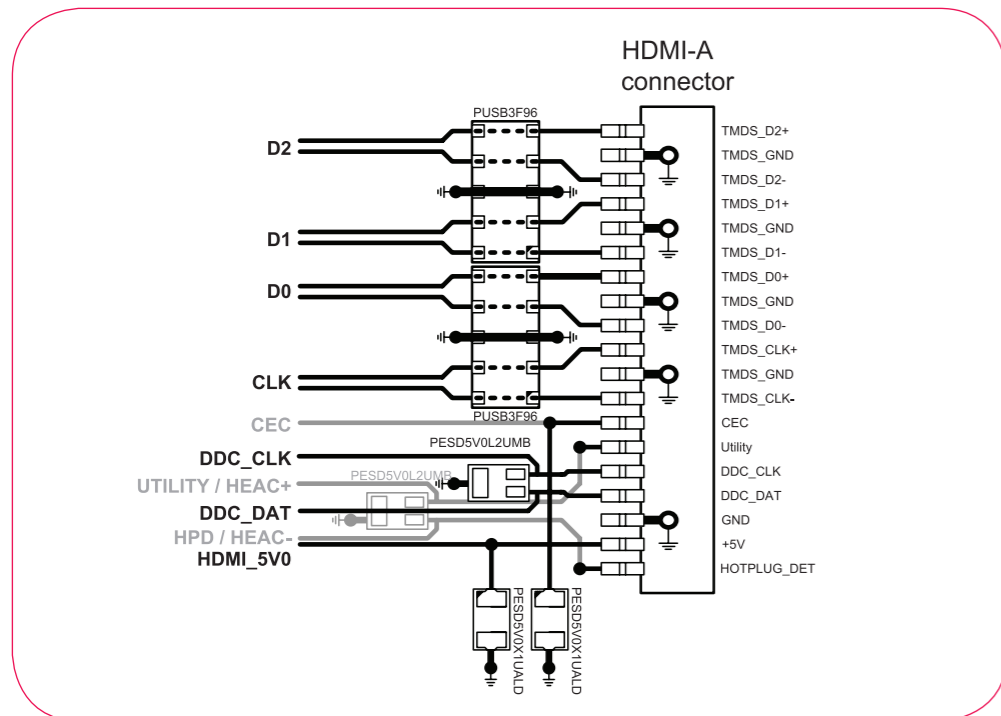


Video interface protection

types in **bold** represent new products

Baseband interface	Number of protected lines	C _{line} (pF)	Remark	Type	Package	Size (mm)
Display port	4	0.6	ESD protection for ultra high-speed interfaces	IP4283CZ10-TBR	DFN2510A-10 (SOT1176)	2.5 x 1.0 x 0.48
		0.55	ESD protection for ultra high-speed interfaces	IP4292CZ10-TBR		
		0.5	ESD protection for ultra high-speed interfaces	IP4294CZ10-TBR	PHDMI2F4	
			ESD protection for ultra high-speed interfaces			
		0.8	ESD protection for ultra high-speed interfaces	IP4285CZ9-TBB	DFN2110-9 (SOT1178)	2.1 x 1.0 x 0.48
HDMI	2	0.7	ESD protection for ultra high-speed interfaces	IP4282CZ6	DFN1410-6 (SOT886)	1.45 x 1.0 x 0.48
	4	0.6	ESD protection for ultra high-speed interfaces	IP4283CZ10-TBR	DFN2510A-10 (SOT1176)	2.5 x 1.0 x 0.48
		0.8	ESD protection for ultra high-speed interfaces	IP4285CZ9-TBB	DFN2110-9 (SOT1178)	
		0.55	ESD protection for ultra high-speed interfaces	IP4292CZ10-TBR	PHDMI2F4	2.5 x 1.0 x 0.48
			ESD protection for ultra high-speed interfaces			
0.5	ESD protection for ultra high-speed interfaces	IP4294CZ10-TBR				
	ESD protection for ultra high-speed interfaces					
LVDS	4	0.8	Very low clamp ESD protection with 12 kV IEC ruggedness	PUSB2X4D	SOT457 (SC-74)	2.9 x 1.5 x 1.0
		0.8	Very low clamp ESD protection with 12 kV IEC ruggedness	PUSB2X4Y	SOT363 (SC-88)	2.0 x 1.25 x 0.95

PHDMI2F4 PESD HDMI application schematic



NFC antenna protection

types in **bold** represent new products

Interface	Number of protected lines (Bidirectional)	V _{RWM} [V]	C _{line} typ [pF]	C _{line} max [pF]	ESD rating ⁽¹⁾ max [kV]	Configuration	Type	Package	Size
NFC Antenna	1	18	0.28	0.45	10		PESD18VF1BSF	DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3
			PESD18VF1BL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48				
		24	0.25	0.4	10		PESD24VF1BSF	DSN0603-2 (SOD962)	0.6 x 0.3 x 0.3
			0.3	0.45	10		PESD24VF1BL	DFN1006-2 (SOD882)	1.0 x 0.6 x 0.48

⁽¹⁾ according to IEC 61000-4-2 (contact discharge)

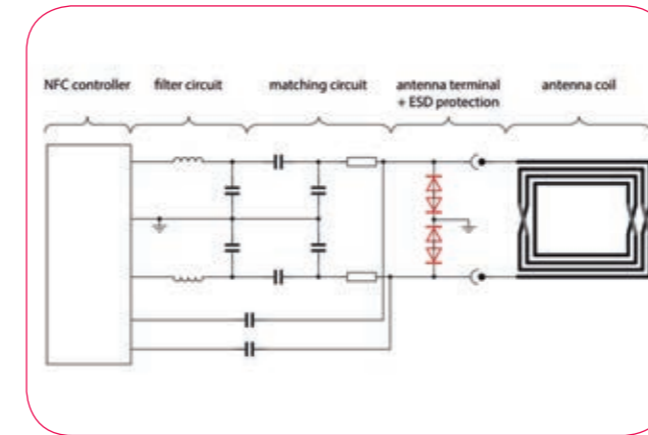
In the Spotlight

PESD24VF1BSF – NFC antenna protection in DSN0603-2 package

- High reverse standoff voltage V_{RWM}=24 V
- Ultra-low capacitance C_d typ = 0.25 pF
- Very small voltage dependency of the capacitance
- Ultra-small DSN0603-2 (SOD962) package (0.6 x 0.3 x 0.3 mm)

ESD protection, filtering and signal conditioning

Circuit diagram

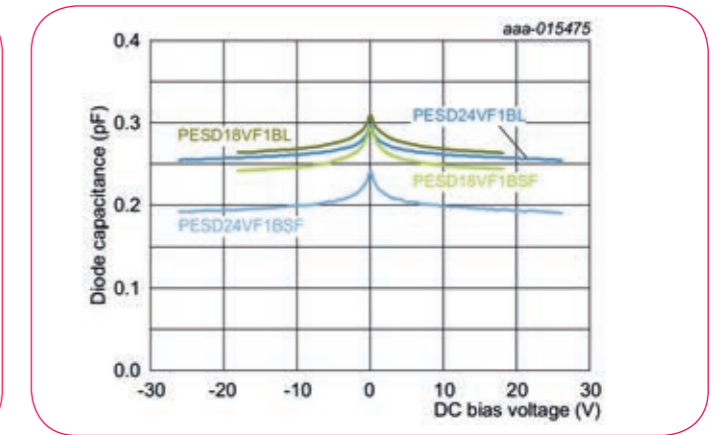


Using tiny packages makes PCB design more flexible

Features

- ▶ Bidirectional configuration, allowing operating voltages up to 18 or 24 V
- ▶ Very low capacitance, enabling easy design of the antenna-matching circuit
- ▶ Very small voltage dependency of the diode capacitance, avoiding intermodulation distortion
- ▶ Small form-factor packages of 1006 (0402 inch) and 0603 (0201 inch) standard size

Diode capacitance versus bias voltage













The highly linear diode capacitance, with very small variation, minimizes signal degradation

Benefits

- ▶ The phone's NFC antenna is often integrated into the battery cover or the battery itself and is connected to the NFC tags via small contacts on the phone, creating an entry point for ESD strikes that are potentially hazardous to the NFC IC. These new NXP devices are optimized for the requirements of the NFC system and ensure the best-possible protection of the NFC IC.

LCD and camera protection and filtering

types in **bold** represent new products

Baseband interface	Number of protected lines	Line small-signal equivalents			Digital interface clock speed (MHz)	Insertion loss S21 ~ -3 dB (MHz)	Type	Package	Size (mm)		
		R _{line} (Ω)	C _{line} (pF)	L _{line} (nH)							
LCD display, camera, keypad	2	45	40	-	~50	145	PEMI2STD/HT		1.6 x 1.2 x 0.5		
			15	-	~125	376	PEMI2STD/HE				
		200	40	-	~40	119	PEMI2STD/WT				
	4	15	43	18	~60	175	IP3253CZ8-4-TTL		1.7 x 1.35 x 0.52		
			50	18	~50	145	IP3254CZ8-4-TTL				
		40	18	-	~100	300	IP4252CZ8-4-TTL				
		100	45	-	~40	130	IP4254CZ8-4-TTL				
		15	-	~110	330	IP4251CZ8-4-TTL					
		200	45	-	~35	110	IP4253CZ8-4-TTL				
	6	100	54	-	~35	98	PEMI4CSP/RW		1.56 x 1.05 x 0.61		
			15	50	18	~50	145			IP3254CZ12-6-TTL	
		40	43	18	~60	175	IP3253CZ12-6-TTL		2.5 x 1.35 x 0.53		
			18	-	~100	300	IP4252CZ12-6-TTL				
		100	45	-	~40	130	IP4254CZ12-6-TTL		2.36 x 1.05 x 0.61		
			15	-	~110	330	IP4251CZ12-6-TTL				
		200	45	-	~35	110	IP4253CZ12-6-TTL				
		7	70	25	-	~75	220	IP4337CX18/LF		1.96 x 1.61 x 0.61	
				15	43	18	~60	175			IP3253CZ16-8-TTL
		8	40	18	-	~100	300	IP4252CZ16-8-TTL		3.3 x 1.35 x 0.53	
	100			45	-	~40	130	IP4254CZ16-8-TTL			
	15		-	~110	330	IP4251CZ16-8-TTL					
	200		45	-	~35	110	IP4253CZ16-8-TTL				
	100		54	-	~35	98	PEMI8CSP/RW/P				3.16 x 1.05 x 0.61
			70	25	-	~75	220				
	10	1000	50	-	~7	22	IP4035CX24/LF		2.41 x 2.41 x 0.65		
			200	50	-	~35	105			IP4041CX25/LF	
		200	50	-	~35	105	IP4041CX25/LF		2.41 x 2.41 x 0.65		




In the Spotlight

IP3253CZ8-4TTL – LCD and camera display protection in DFN1714-8

- Very wide pass-band 175 MHz
- Filters and protects 4, 6 or 8 data lines
- Very low clamping ESD protection, 15 kV IEC ESD ruggedness
- Very low series resistance of only 8 Ω
- Leadless DFN1714-8 (SOT1166) package with a height of only 0.52 mm














Audio interface protection and filtering

Baseband interface	Number of protected lines	Line small-signal equivalents		Remark	Type	Package	Size (mm)
		R _{line}	C _{line} (pF)				
Audio	2	0.9 Ω	290	Low-ohmic speaker (<~8 Ω)	IP4047CX6/LF		1.56 x 1.01 x 0.65
		10 Ω	200	Low-ohmic speaker (>~8 Ω)	IP4048CX5/LF		0.91 x 1.28 x 0.65
	68 Ω	110	Single-ended or differential microphone	IP4049CX5/LF			
	5	2.9 kΩ, 1 kΩ / 10 Ω	-	5-channel filter interface with integrated RC filters and biasing network for audio interfaces	IP4327CX15		1.05 x 2.36 x 0.61






Memory- and SIM-card protection and filtering

types in **bold** represent new products

Baseband interface	Number of protected lines	Line small-signal equivalents		Digital interface clock speed (MHz)	Remark	Type	Package	Size (mm)	
		R _{line}	C _{line} (pF)						
SIM card	3 + 2	-	10	~20	Integrated low capacitance SIM-card passive filter array & USB ESD protection	IP4365CX11		1.16 x 1.56 x 0.61	
		47 Ω / 100 Ω	20	~20	Integrated SIM-card EMI filter and ESD protection	IP4064CX8/LF/P		1.41 x 1.41 x 0.65	
	3	47 Ω / 100 Ω	10	-	Smaller size, integrated SIM-card EMI filter and ESD protection	IP4364CX8/LF/P		1.16 x 1.16 x 0.61	
			20	-	Smaller size, low-capacitance integrated SIM-card EMI filter and ESD protection	IP4366CX8/P			
	4	-	1	~240	Integrated SIM-card EMI filter and ESD protection	IP4264CZ8-20-TTL		1.7 x 1.35 x 0.52	
					Quad-channel, low-capacitance ESD protection	IP4221CZ6-S		1.0 x 1.0 x 0.48	
	4	-	1	~240	Quad-channel, low-capacitance ESD protection	IP4221CZ6-XS		1.0 x 1.0 x 0.48	
					MMC ESD protection, pull-up resistors	IP4051CX11/LF		1.44 x 1.96 x 0.65	
	SD-card / MMC	6	40 Ω	12	>52	(Mini) SD card/trans flash ESD protection, EMI filter	IP4252CZ12-6-TTL		2.5 x 1.35 x 0.53
					-	6-channel Micro-SD memory-card interface ESD protection filter	IP4340CX15		1.56 x 1.56 x 0.5
6 + 2		40 Ω	12	>52	(Mini) SD card/trans flash ESD protection, EMI filter	IP4252CZ16-8-TTL		3.3 x 1.35 x 0.53	
SD 3.0	6	-	0.27	5000	6-line bidirectional ESD protection for ultra high-speed interfaces	PUSB3TB6		2.1 x 1.1 x 0.5	

ESD protection, filtering and signal conditioning

Battery and charger protection

Baseband interface	Number of protected lines	C _{line} (pF)	Diode voltage	Remark	Type	Package	Size (mm)
Battery & charger protection	1	180	Breakdown 16 V	Power diode	IP4085CX4		0.91 x 0.91 x 0.65
		160	Breakdown 16 V	Power diode	IP4386CX4		0.76 x 0.76 x 0.61
		290	Breakdown 10 V	Power diode	IP4387CX4		1.7 x 1.25 x 0.7
		160	V _{RWM} = 12 V	Power diode	PESD12VS1UJ		1.7 x 1.25 x 0.95
		160	V _{RWM} = 12 V	Power diode	PESD12VS1UA		1.7 x 1.25 x 0.95
		480	V _{RWM} = 5 V	Power diode	PESD5V0S1UJ		1.7 x 1.25 x 0.7
		480	V _{RWM} = 5 V	Power diode	PESD5V0S1UA		1.7 x 1.25 x 0.95

Automotive high-speed network protection

types in **bold** represent new products

Number of protected lines	V_{RWM} (V)	C_{line} typ (pF)	I_{rev} max @3V (μ A)	ESD rating ⁽¹⁾ max (kV)	Configuration	Type	Package	Size (mm)
4	5.5	0.5	1	10		PESD2LVDS	DFN2510A-10 (SOT1176) 	2.5 x 1.0 x 0.5
	5.5	0.6	1	8		PESD1LVDS	DFN2510-10 (SOT1165) 	2.5 x 1.0 x 0.48
	5.5	0.6	1	8		PRTR5V0U4D	SOT457 	2.9 x 1.5 x 1.0

⁽¹⁾ according to IEC 61000-4-2 (contact discharge)

Automotive in-vehicle network bus line protection

types in **bold** represent new products

Number of protected lines bidirectional	V_{RWM} (V)	C_{line} typ (pF)	C_{line} max (pF)	P_{PP} ⁽¹⁾ max (W)	ESD rating ⁽²⁾ max (kV)	I_r max [μ A] @ V_{RWM}	Configuration	Type	Package	Size (mm)
1	15 (diode 1) 24 (diode 2)	13	17	160	23	0.05		PESD1LIN	SOD323 (SC-76) 	1.7 x 1.25 x 0.95
2	24	11	17	200	23	0.05		PESD1CAN	SOT23 	2.9 x 1.3 x 1.0
		25	30	230	30	0.01		PESD2CAN		
		11	17	200	23	0.05		PESD1FLEX		
		9.3	12	150	23	0.05		PESD1CAN-U	SOT323 	2.0 x 1.25 x 0.95
1	26.5	9.3	11	150	23	0.05		PESD1IVN-U	SOT323 	2.0 x 1.25 x 0.95
2								PESD2IVN-U		

⁽¹⁾ 8 / 20 μ s surge pulse according to IEC 61000-4-5

⁽²⁾ according to IEC 61000-4-2 (contact discharge)

In the spotlight

PESD2IVN-U: CAN bus protection in very small SOT323 package

Protection for 2 in-vehicle network BUS lines

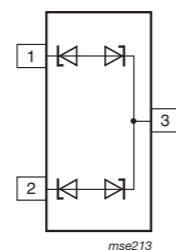
High reverse standoff voltage $V_{RWM} = 26.5$ V

Very small SOT323 package (2.0 x 1.25 x 0.95 mm)

AEC-Q101 compliant

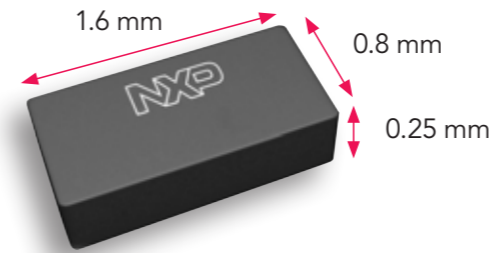
ESD robustness of up to 23 kV (contact)

Very good capacitance matching



1200 W surge protection for charger ports in mobile devices

A new 1200 W surge protection device in a 1.6 x 0.8 mm small, and 0.25 mm low package for slim mobiles



DSN1608-2

Features and benefits

- ▶ 7 types from $V_{RWM} = 5$ to 26 V
- ▶ High surge rating:
 - ▶ $P_{PPM} = 1200$ W 8/20 μ s pulse (IEC61000-4-5)
 - ▶ $P_{PPM} = 200$ W 10/1000 μ s pulse (IEC61643-321)
- ▶ Very compact and thin package
- ▶ Low leakage current: down to 1 nA, reduces power consumption
- ▶ Dynamic resistance down to 0.1 Ω
- ▶ High ESD robustness: $V_{ESD} = 30$ kV (IEC61000-4-2)



Surge pulses from the power supply, e.g. via a car charger, are a severe threat for the charger port VBUS line of smart phones and other portables. Supply voltages of these chargers often exceed the 5 V level – requiring high reverse standoff voltages.

NXP's PTVSxZ1USK series is ideally suited to protect the charger port and offers

- ▶ Superior electrical performance
- ▶ A high PCB design flexibility and,
- ▶ Easy routing

TVS diodes, 1200 W – selection guide

Type	V_{RWM} (V)	$V_{br, min}$ (V)	$V_{br, max}$ (V)	V_d @ I_{ppm} 8/20 μ s (V)	I_{ppm} 8/20 μ s (A)	P_{ppm} 8/20 μ s (W)	I_{ppm} 10/1000 μ s (A)	V_d @ I_{ppm} 10/1000 μ s (V)	P_{ppm} 10/1000 μ s (W)	I_{rm} typ @ V_{RWM} (μ A)	I_{rm} max @ V_{RWM} (μ A)
PTVS5V0Z1USK	5	6.4	7.80	18	80	1200	20	12	200	0.025	4
PTVS7V5Z1USK	7.5	8.33	9.65	23	70	1200	12.4	16.1	200	0.025	4
PTVS10VZ1USK	10	11.1	12.9	29	60	1200	9.44	21.2	200	0.025	4
PTVS12VZ1USK	12	13.3	15.4	32	53	1200	8.08	24.8	200	0.025	4
PTVS15VZ1USK	15	16.7	19.4	40	44	1200	6.56	30.5	200	0.025	2
PTVS18VZ1USK	18	20	23.2	43	40	1200	5.52	36.2	200	0.025	1
PTVS26VZ1USK	26	28.9	33.4	60	25	1200	3.76	53.2	200	0.025	0.5

TVS diodes, 24/40 W

Power (W) (10 / 1000 μ s waveform) ⁽¹⁾	V_{RWM} (V)	$V_{BR\ min}$ (V) @ I_R	$V_{BR\ typ}$ (V) @ I_R	$V_{BR\ max}$ (V) @ I_R	I_R (mA)	ESD rating ⁽¹⁾ max (kV)	C_{line} typ (pF)	$V_{CL\ max}$ ⁽¹⁾ (V) @ I_{pp}	I_{pp} ⁽¹⁾ (A)	$I_{RWM\ max}$ (μ A) @ V_{RWM}	Configuration	Type	Package	Size (mm)
24	3	5.32	5.6	5.88	20	30	210	8	3	5		MMBZ5V6AL	SOT23	2.9 x 1.3 x 1.0
	3	5.89	6.2	6.51	1	30	175	8.7	2.76	0.2		MMBZ6V2AL		
	4.5	6.48	6.8	7.14	1	30	150	9.6	2.5	0.3		MMBZ6V8AL		
	6	8.65	9.1	9.56	1	30	155	14	1.7	0.1		MMBZ9V1AL		
	6.5	9.5	10	10.5	1	30	130	14.2	1.7	0.02		MMBZ10VAL		
40	8.5	11.4	12	12.6	1	30	110	17	2.35	0.005	MMBZ12VAL			
	12	14.25	15	15.75	1	30	85	21	1.9	0.005	MMBZ15VAL			
	14.5	17.1	18	18.9	1	30	70	25	1.6	0.005	MMBZ18VAL			
	17	19	20	21	1	30	65	28	1.4	0.005	MMBZ20VAL			
	22	25.65	27	28.35	1	30	48	40	1	0.005	MMBZ27VAL			
	26	31.35	33	34.65	1	30	45	46	0.87	0.005	MMBZ33VAL			
	8.5	11.4	12	12.6	1	30	110	17	2.35	0.005	MMBZ12VDL			
	12.8	14.3	15	15.8	1	30	85	21.2	1.9	0.005	MMBZ15VDL			
	14.5	17.1	18	18.9	1	30	70	25	1.6	0.005	MMBZ18VCL			
	17	19	20	21	1	30	65	28	1.4	0.005	MMBZ20VCL			
	22	25.65	27	28.35	1	30	48	38	1	0.005	MMBZ27VCL			
	26	31.35	33	34.65	1	30	45	46	0.87	0.005	MMBZ33VCL			

⁽¹⁾ 10 / 1000 μ s according to IEC 61643-321 ⁽²⁾ according to IEC 61000-4-2 (contact discharge)

In the spotlight

PTVSxU1UPA series: 300 W surge protection in DFN2020-3 package

Series of 6 types from $V_{RWM} = 7.5$ to 26 V

Peak pulse power of 300 W for 10 / 1000 μ s pulse

Small package size of 2.0 x 2.0 mm

Very low package height of 0.62 mm typ

Charger-port protection in mobile devices



TVS diodes for mobile applications

Power (W) (10 / 1000 μ s waveform) ⁽¹⁾	V_{RWM} (V)	$V_{BR\ min}$ (V) @ I_R	$V_{BR\ typ}$ (V) @ I_R	$V_{BR\ max}$ (V) @ I_R	I_R (mA)	$V_{CL\ max}$ ⁽¹⁾ (V) @ I_{pp}	I_{pp} ⁽¹⁾ (A)	$I_{RWM\ typ}$ (μ A) @ V_{RWM}	$I_{RWM\ max}$ (μ A) @ V_{RWM}	Type	Package	Size (mm)
300	7.5	8.33	8.77	9.21	1	12.9	23.3	0.3	50	PTVS7V5U1UPA	DFN2020-3 (SOT1061)	2.0 x 2.0 x 0.62
	10	11.1	11.7	12.3	1	17	17.6	0.008	2.5	PTVS10VU1UPA		
	12	13.3	14	14.7	1	19.9	15.1	0.005	2.5	PTVS12VU1UPA		
	15	16.7	17.6	18.5	1	24.4	12.3	0.001	0.1	PTVS15VU1UPA		
	18	20	21	22.1	1	29.2	10.3	0.001	0.1	PTVS18VU1UPA		
	26	28.9	30.4	31.9	1	42.1	7	0.001	0.1	PTVS26VU1UPA		

⁽¹⁾ 10 / 1000 μ s according to IEC 61643-321

TVS diodes, 400 W

Power (W) (10/1000 μ s waveform) ⁽¹⁾	V_{RWM} (V)	$V_{BR\ min}$ (V) @ I_R	$V_{BR\ typ}$ (V) @ I_R	$V_{BR\ max}$ (V) @ I_R	I_R (mA)	$V_{CL\ max}$ ⁽¹⁾ (V) @ I_{pp}	I_{pp} ⁽¹⁾ (A)	$I_{RWM\ typ}$ (μ A) @ V_{RWM}	$I_{RWM\ max}$ (μ A) @ V_{RWM}	Type ($T_j\ max = 150\ ^\circ C$)	Type ($T_j\ max = 185\ ^\circ C$)	Package	Size (mm)
350	3.5	5.20	5.60	6.00	10	8.0	43.8	5	600	PTVS3V3S1UR	PTVS3V3S1UTR	SOD123W	2.6 x 1.7 x 1.0
400	5.0	6.40	6.70	7.00	10	9.2	43.5	5	400	PTVS5V0S1UR	PTVS5V0S1UTR		
	6.0	6.67	7.02	7.37	10	10.3	38.8	5	400	PTVS6V0S1UR	PTVS6V0S1UTR		
	6.5	7.22	7.60	7.98	10	11.2	35.7	5	250	PTVS6V5S1UR	PTVS6V5S1UTR		
	7.0	7.78	8.20	8.60	10	12.0	33.3	3	100	PTVS7V0S1UR	PTVS7V0S1UTR		
	7.5	8.33	8.77	9.21	1	12.9	31.0	0.2	50	PTVS7V5S1UR	PTVS7V5S1UTR		
	8.0	8.89	9.36	9.83	1	13.6	29.4	0.03	25	PTVS8V0S1UR	PTVS8V0S1UTR		
	8.5	9.44	9.92	10.40	1	14.4	27.8	0.01	10	PTVS8V5S1UR	PTVS8V5S1UTR		
	9.0	10.00	10.55	11.10	1	15.4	26.0	0.005	5	PTVS9V0S1UR	PTVS9V0S1UTR		
	10	11.10	11.70	12.30	1	17.0	23.5	0.005	2.5	PTVS10V5S1UR	PTVS10V5S1UTR		
	11	12.20	12.85	13.50	1	18.2	22.0	0.005	2.5	PTVS11V5S1UR	PTVS11V5S1UTR		
	12	13.30	14.00	14.70	1	19.9	20.1	0.005	2.5	PTVS12V5S1UR	PTVS12V5S1UTR		
	13	14.40	15.15	15.90	1	21.5	18.6	0.001	0.1	PTVS13V5S1UR	PTVS13V5S1UTR		
	14	15.60	16.40	17.20	1	23.2	17.2	0.001	0.1	PTVS14V5S1UR	PTVS14V5S1UTR		
	15	16.70	17.60	18.50	1	24.4	16.4	0.001	0.1	PTVS15V5S1UR	PTVS15V5S1UTR		
	16	17.80	18.75	19.70	1	26.0	15.4	0.001	0.1	PTVS16V5S1UR	PTVS16V5S1UTR		
17	18.90	19.90	20.90	1	27.6	14.5	0.001	0.1	PTVS17V5S1UR	PTVS17V5S1UTR			
18	20.00	21.00	22.10	1	29.2	13.7	0.001	0.1	PTVS18V5S1UR	PTVS18V5S1UTR			
20	22.20	23.35	24.50	1	32.4	12.3	0.001	0.1	PTVS20V5S1UR	PTVS20V5S1UTR			
22	24.40	25.60	26.90	1	35.5	11.3	0.001	0.1	PTVS22V5S1UR	PTVS22V5S1UTR			
24	26.70	28.10	29.50	1	38.9	10.3	0.001	0.1	PTVS24V5S1UR	PTVS24V5S1UTR			
26	28.90	30.40	31.90	1	42.1	9.5	0.001	0.1	PTVS26V5S1UR	PTVS26V5S1UTR			
28	31.10	32.80	34.40	1	45.4	8.8	0.001	0.1	PTVS28V5S1UR	PTVS28V5S1UTR			
30	33.30	35.10	36.80	1	48.4	8.3	0.001	0.1	PTVS30V5S1UR	PTVS30V5S1UTR			
33	36.70	38.70	40.60	1	53.3	7.5	0.001	0.1	PTVS33V5S1UR	PTVS33V5S1UTR			
36	40.00	42.10	44.20	1	58.1	6.9	0.001	0.1	PTVS36V5S1UR	PTVS36V5S1UTR			
40	44.40	46.80	49.10	1	64.5	6.2	0.001	0.1	PTVS40V5S1UR	PTVS40V5S1UTR			
43	47.80	50.30	52.80	1	69.4	5.8	0.001	0.1	PTVS43V5S1UR	PTVS43V5S1UTR			
45	50.00	52.65	55.30	1	72.7	5.5	0.001	0.1	PTVS45V5S1UR	PTVS45V5S1UTR			
48	53.30	56.10	58.90	1	77.4	5.2	0.001	0.1	PTVS48V5S1UR	PTVS48V5S1UTR			
51	56.70	59.70	62.70	1	82.4	4.9	0.001	0.1	PTVS51V5S1UR	PTVS51V5S1UTR			
54	60.00	63.15	66.30	1	87.1	4.6	0.001	0.1	PTVS54V5S1UR	PTVS54V5S1UTR			
58	64.40	67.80	71.20	1	93.6	4.3	0.001	0.1	PTVS58V5S1UR	PTVS58V5S1UTR			
60	66.70	70.20	73.70	1	96.8	4.1	0.001	0.1	PTVS60V5S1UR	PTVS60V5S1UTR			
64	71.10	74.85	78.60	1	103.0	3.9	0.001	0.1	PTVS64V5S1UR	PTVS64V5S1UTR			

ESD protection, filtering and signal conditioning

TVS diodes, 600 W

Power (W) (10 / 1000 µs waveform) ⁽¹⁾	V _{revm} (V)	V _{BR min} (V) @ I _r	V _{BR typ} (V) @ I _r	V _{BR max} (V) @ I _r	I _r (mA)	V _{CL max} ⁽¹⁾ (V) @ I _{pr}	I _{pr} ⁽¹⁾ (A)	I _{pr typ} (µA) @ V _{revm}	I _{rev max} (µA) @ V _{revm}	Type (T _{j max} = 150 °C)	Type (T _{j max} = 185 °C)	Package	Size (mm)
3.5	5.20	5.60	6.00	10	8	75	5	600	PTVS3V3P1UP	PTVS3V3P1UTP	SOD128	3.8 x 2.6 x 1.0	
5	6.40	6.70	7.00	10	9.2	65.2	5	400	PTVS5V0P1UP	PTVS5V0P1UTP			
6	6.67	7.02	7.37	10	10.3	58.3	5	400	PTVS6V0P1UP	PTVS6V0P1UTP			
6.5	7.22	7.60	7.98	10	11.2	53.6	5	250	PTVS6V5P1UP	PTVS6V5P1UTP			
7	7.78	8.20	8.60	10	12	50	3	100	PTVS7V0P1UP	PTVS7V0P1UTP			
7.5	8.33	8.77	9.21	1	12.9	46.5	0.2	50	PTVS7V5P1UP	PTVS7V5P1UTP			
8	8.89	9.36	9.83	1	13.6	44.1	0.03	25	PTVS8V0P1UP	PTVS8V0P1UTP			
8.5	9.44	9.92	10.40	1	14.4	41.7	0.01	10	PTVS8V5P1UP	PTVS8V5P1UTP			
9	10.00	10.55	11.10	1	15.4	39	0.005	5	PTVS9V0P1UP	PTVS9V0P1UTP			
10	11.10	11.70	12.30	1	17	35.3	0.005	2.5	PTVS10VP1UP	PTVS10VP1UTP			
11	12.20	12.85	13.50	1	18.2	33	0.005	2.5	PTVS11VP1UP	PTVS11VP1UTP			
12	13.30	14.00	14.70	1	19.9	30.2	0.005	2.5	PTVS12VP1UP	PTVS12VP1UTP			
13	14.40	15.15	15.90	1	21.5	27.9	0.001	0.1	PTVS13VP1UP	PTVS13VP1UTP			
14	15.60	16.40	17.20	1	23.2	25.9	0.001	0.1	PTVS14VP1UP	PTVS14VP1UTP			
15	16.70	17.60	18.50	1	24.4	24.6	0.001	0.1	PTVS15VP1UP	PTVS15VP1UTP			
16	17.80	18.75	19.70	1	26	23.1	0.001	0.1	PTVS16VP1UP	PTVS16VP1UTP			
17	18.90	19.90	20.90	1	27.6	21.7	0.001	0.1	PTVS17VP1UP	PTVS17VP1UTP			
18	20.00	21.00	22.10	1	29.2	20.5	0.001	0.1	PTVS18VP1UP	PTVS18VP1UTP			
20	22.20	23.35	24.50	1	32.4	18.5	0.001	0.1	PTVS20VP1UP	PTVS20VP1UTP			
22	24.40	25.60	26.90	1	35.5	16.9	0.001	0.1	PTVS22VP1UP	PTVS22VP1UTP			
24	26.70	28.10	29.50	1	38.9	15.4	0.001	0.1	PTVS24VP1UP	PTVS24VP1UTP			
26	28.90	30.40	31.90	1	42.1	14.2	0.001	0.1	PTVS26VP1UP	PTVS26VP1UTP			
28	31.10	32.80	34.40	1	45.4	13.2	0.001	0.1	PTVS28VP1UP	PTVS28VP1UTP			
30	33.30	35.10	36.80	1	48.4	12.4	0.001	0.1	PTVS30VP1UP	PTVS30VP1UTP			
33	36.70	38.70	40.60	1	53.3	11.3	0.001	0.1	PTVS33VP1UP	PTVS33VP1UTP			
36	40.00	42.10	44.20	1	58.1	10.3	0.001	0.1	PTVS36VP1UP	PTVS36VP1UTP			
40	44.40	46.80	49.10	1	64.5	9.3	0.001	0.1	PTVS40VP1UP	PTVS40VP1UTP			
43	47.80	50.30	52.80	1	69.4	8.6	0.001	0.1	PTVS43VP1UP	PTVS43VP1UTP			
45	50.00	52.65	55.30	1	72.7	8.3	0.001	0.1	PTVS45VP1UP	PTVS45VP1UTP			
48	53.30	56.10	58.90	1	77.4	7.8	0.001	0.1	PTVS48VP1UP	PTVS48VP1UTP			
51	56.70	59.70	62.70	1	82.4	7.3	0.001	0.1	PTVS51VP1UP	PTVS51VP1UTP			
54	60.00	63.15	66.30	1	87.1	6.9	0.001	0.1	PTVS54VP1UP	PTVS54VP1UTP			
58	64.40	67.80	71.20	1	93.6	6.4	0.001	0.1	PTVS58VP1UP	PTVS58VP1UTP			
60	66.70	70.20	73.70	1	96.8	6.2	0.001	0.1	PTVS60VP1UP	PTVS60VP1UTP			
64	71.10	74.85	78.60	1	103	5.8	0.001	0.1	PTVS64VP1UP	PTVS64VP1UTP			

⁽¹⁾ 10 / 1000 µs according to IEC 61643-321

In the spotlight

High-temperature TVS series in FlatPower package

Available in 400 W (PTVSxS1UTR) and 600 W (PTVSxP1UTP) power classes with 35 devices each

Very high maximal junction temperature of 185 °C

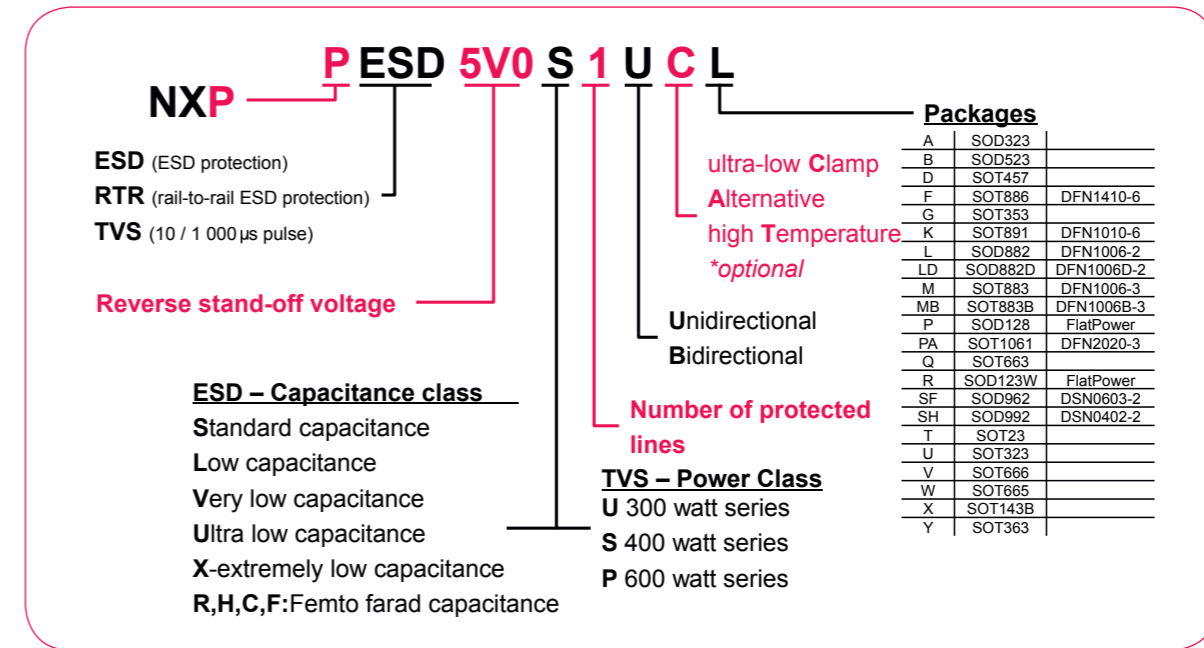
Reverse standoff voltages from 3.3 to 64 V

Low height, high performance - save board space by replacing SMA & SMB packages with low-profile SOD123W and SOD128 packages

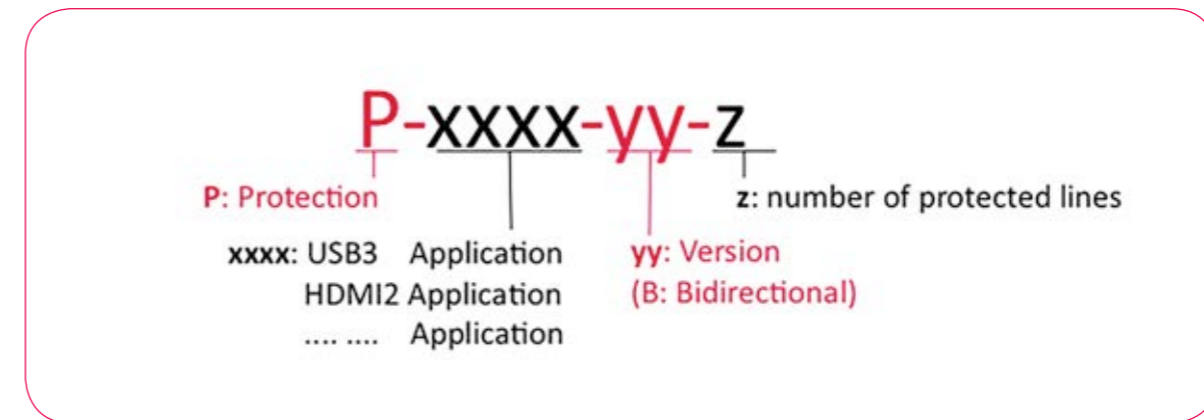
AEC-Q101 qualified



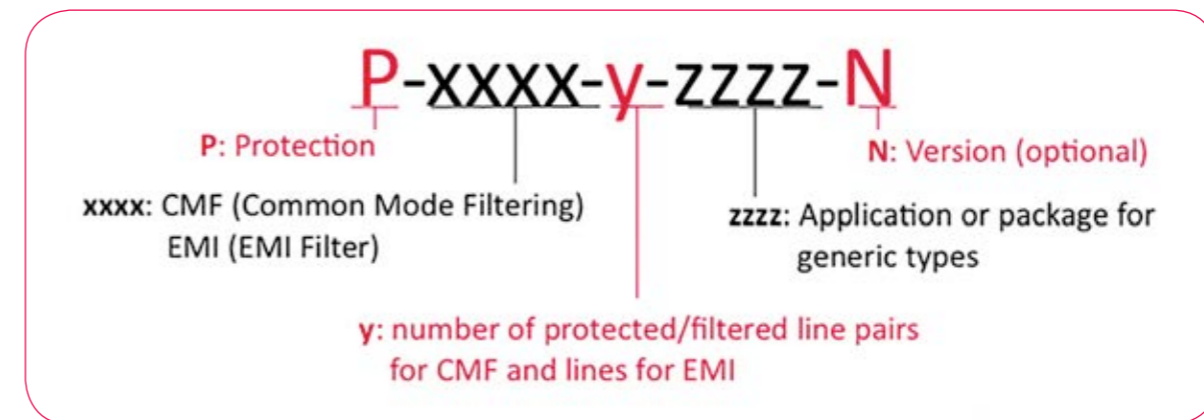
Protection and signal-conditioning nomenclature



Application specific protection nomenclature



Application specific filtering nomenclature



ESD protection, filtering and signal conditioning



MOSFETs

Small-signal MOSFETs

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Small-signal MOSFET portfolio overview

Small-signal MOSFET Portfolio structure

Leaded packages

Leadless packages

High R_{DSon}



- ▶ 2N7002 family
- ▶ NX7002AK family
- ▶ BSS84 family
- ▶ BSS138 family
- ▶ NX3008 family
- ▶ NX3020 family
- ▶ BSH ...



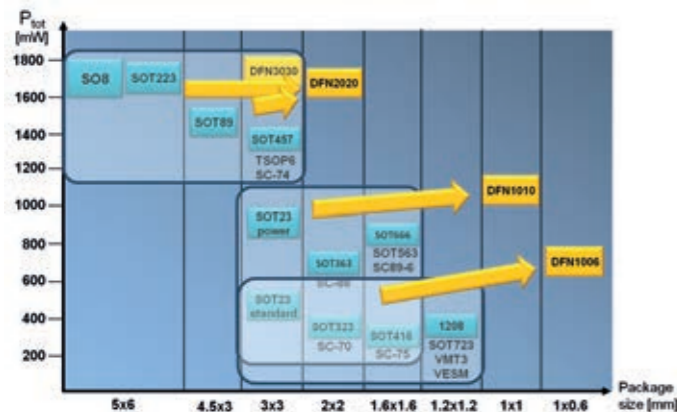
Low R_{DSon}

- ▶ PMT.../ PHT... SOT223
- ▶ PMV... SOT23
- ▶ PMN... SOT457
- ▶ PMF... SOT323
- ▶ PMG... SOT363

- ▶ PMPB... - single DFN2020
- ▶ PMDPB - dual DFN2020
- ▶ PMZ... single DFN1006
- ▶ PMXB... single DFN1010

- ▶ Broadliner in high to low ohmic MOSFETs down to 10 mΩ
- ▶ Package range from SOT223 package (5 x 6 mm footprint) down to DFN1006 leadless package (1 x 0.6 mm footprint)
- ▶ Addressing broad application range from portable to automotive
- ▶ Innovative DFN package portfolio for best power dissipation on smallest footprint for miniaturization

From leaded to leadless packages

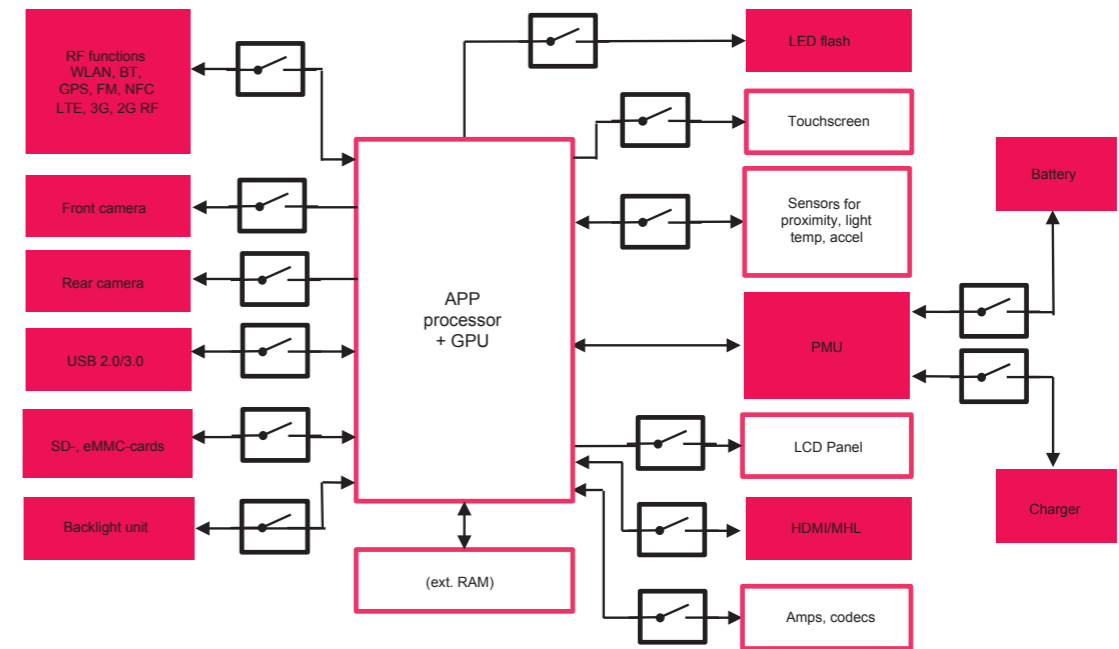


Leadless packages replace established leaded packages. They provide the same power capability compared to larger packages on a smaller size or provide a better thermal performance on the same footprint size.

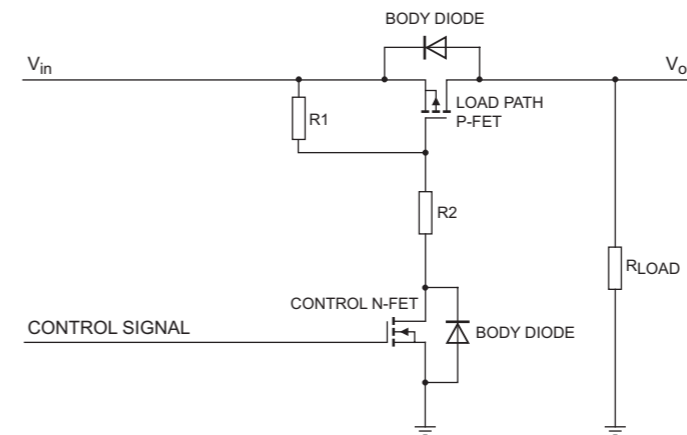
These features make them the ideal choice for space-constrained applications where size and performance matter.

The graph shows package replacement options, with improved power dissipation performance, for a dedicated R_{DSon} range of greater than 10 mΩ.

Enhanced switch application for low R_{DSon} MOSFETs



Load switch application for high R_{DSon} MOSFETs



▶ Further application examples for high R_{DSon} MOSFETs are discharger switch and the inverter

Small-signal MOSFETs portfolio for enhanced and standard switch applications

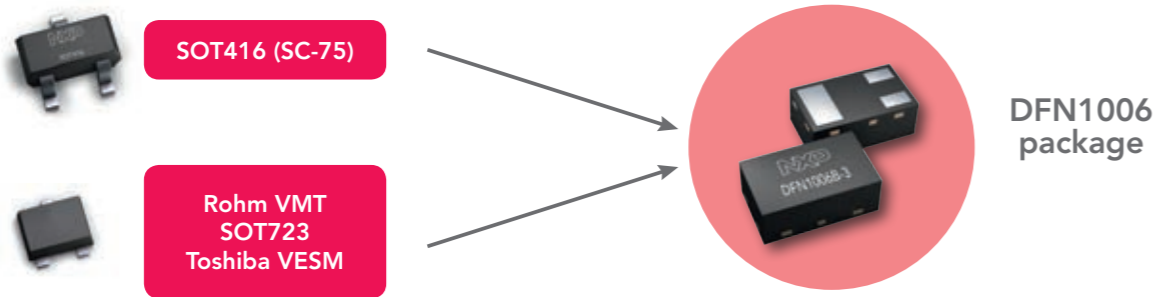
	Application	Package	V_{DS} range (in V)	R_{DSon} range (in Ω)	NXP portfolio
Portables	Enhanced switch	DFN2020MD-6 DFN2020-6 DFN1010d-3	12 - 30	10 - 100	PMPBx-series PMDPBx-series PMXB-series
	Standard switch	DFN1006-3 DFN1010B-6	12 - 30	> 100	PMZx-series PMDXBx-series NX30x-series
Computing / Consumer	Enhanced switch	SOT23	20 - 60	10 - 100	PMVx-series
	Standard switch	SOT23	20 - 60	> 100	NX7002x-series NX30x-series BSSx-series

DFN1006 – The new standard for portables



- ▶ DFN1006 is now the standard for portables
- ▶ Roughly 85% smaller than a SOT23, but delivers the same power dissipation (360 mW)
- ▶ DFN1006 replaces larger packages in the same R_{DSon} range of > 120 mΩ

Choose the next generation - DFN1006
Replace larger package types with R_{DSon} values > 120 mΩ



Types with similar thermal and electrical performance		
Package	SOT416	DFN1006-3
Package size	1.6 x 0.8 x 0.77 mm	1.0 x 0.6 x 0.48 mm
Solder footprint	2.2 x 2.0 mm = 4.4 mm ²	1.3 x 0.9 mm = 1.17 mm ²
N-channel > 1 Ω range	2N7002BKT	NX7002BKM
N-channel > 1 Ω range	NX3008NBKT	NX3008NBKM
P-channel > 1 Ω range	NX3008PBKT	NX3008PBKM
N-channel 300 mΩ range	PMR280UN	PMZ290UNE

DFN1006 – The ideal replacement for SOT416



75% size reduction!



Small-signal MOSFETs

Small-signal MOSFETs in ultra-small DFN1006 and DFN1006B packages

types in **bold** represent new products

Package		DFN1006-3 (SOT883)	DFN1006B-3 (SOT883B)															
Size (mm)		1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37															
P _{tot} (mW)		250	250															
Polarity	V _{DS} (V)	V _{GS} (V)	I _D (A)	V _{GS(th) min} (V)	V _{GS(th) max} (V)	t _{on} typ (ns)	t _{off} typ (ns)	Q _G typ (nC)	ESD protection (kV)	R _{DSon} typ (mΩ) @ V _{GS} =								
										10 V	4.5 V	2.5 V	1.8 V	1.5 V	1.2 V			
N-channel	20	8	1.9 / 1.6	0.45	0.95	5.3	16	1.6	2	-	120 / 155	155 / 190	195 / 235	255 / -	-	PMZ130UNE	PMZB150UNE	
			1	0.5	0.95	6	86	0.45	2	-	290	420	600	-	-	PMZ290UNE	PMZB290UNE	
		12	0.6	0.45	0.95	5.6	19	0.4	1	-	470	620	845	1125	2210	PMZ600UNE	PMZB600UNE	
			2.15	0.5	1.5	5	11	0.72	-	-	270	440	-	-	-	PMZ270XN		
		30	8	1.5	0.45	0.95	-	-	-	2	-	200	230	260	300	-	PMZ200UNE	PMZB200UNE
				1	0.45	0.95	4	12	0.8	2	-	380	450	520	600	-	PMZ390UNE	PMZB390UNE
	0.9			0.5	1.05	11	54	0.77	2	-	370	470	630	-	-	PMZ370UNE	PMZB370UNE	
	12		0.53	0.6	1.1	15	69	0.52	2	-	1000	1400	2000	-	-	NX3008NBKM	NX3008NBKMB	
			1.87	0.5	1.5	6.5	14	0.65	-	-	350	520	-	-	-	PMZ350XN		
			0.93	0.5	1.5	6.5	14	0.65	-	-	380	550	-	-	-		PMZB380XN	
	60	20	0.45	1.1	2.1	5	12	0.5	2	1000	1300	-	-	-	-	2N7002BKM	2N7002BKMB	
			0.35	1.1	2.1	4.7	6.9	1	2	2200	2500	-	-	-	-	NX7002BKM	NX7002BKMB	
30		8	1.4	0.45	0.95	4	26	1.3	1.8	-	330	420	520	-	-	PMZ350UPE	PMZB350UPE	
			0.68	0.5	1.3	18	80	0.76	2	-	670	1200	1800	-	-		PMZB670UPE	
		0.5	0.45	0.95	2.3	13.5	1.19	1	-	1020	1270	1700	2300	3500	PMZ950UPE	PMZB950UPE		
		1	0.45	0.95	2.9	22	1.45	2	-	400	480	600	760	-	PMZ320UPE	PMZB320UPE		
50	20	0.3	0.6	1.1	19	65	0.55	2	-	2800	5300	-	-	-	NX3008PBKM	NX3008PBKMB		
		0.23	1.1	2.1	13	48	0.26	1	4500	5700	-	-	-	-	BSS84AKM	BSS84AKMB		

In the spotlight

PMZ130UNE – smallest low R_{DSon} N-channel MOSFET in DFN1006

20 V N-channel with R_{DSon} of 120 mΩ @ V_{GS} = 4.5 V (typ)

I_D max of 1.9 A for medium current load switch

Ultra-small footprint: 1.0 x 0.6 x 0.48 mm

Low-voltage gate drive with V_{GS(th)} = 0.7 V (typ)

R_{DSon} specified to 1.5 V for low drive voltages



Key features

- ▶ N- and P-channel
- ▶ Low R_{DSon} down to 120 mΩ
- ▶ I_D up to 2.15 A
- ▶ Low voltage drive (V_{GS(th)} = 0.65 V typ)
- ▶ Voltage range of 20 to 60 V
- ▶ ESD protection of up to 2 kV

Package

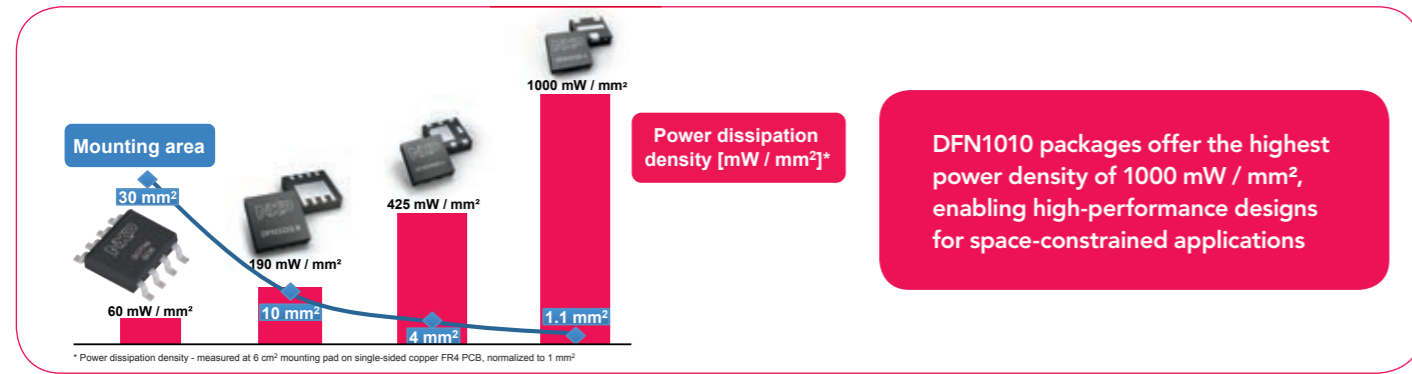
- ▶ 1.0 x 0.6 mm footprint
- ▶ Single package with different heights:
 - 0.5 mm for DFN1006 (SOT883)
 - 0.37 mm for DFN1006B (SOT883B)
- ▶ Power dissipation (P_{tot}) of 360 mW

Key applications

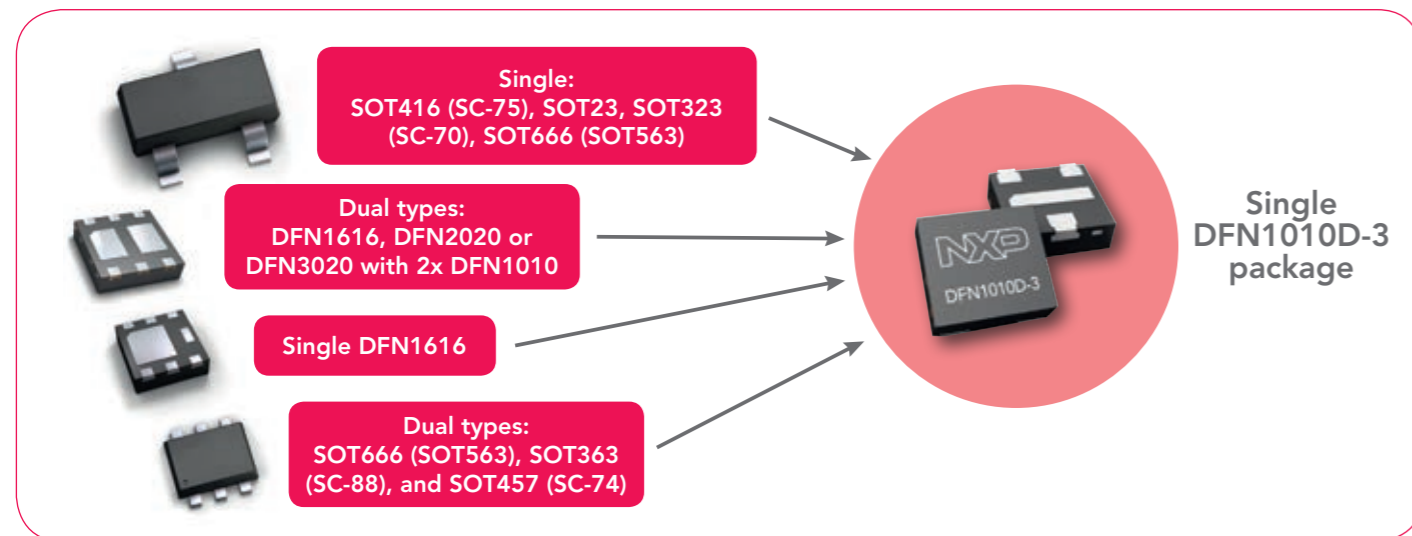
- ▶ Smartphones
- ▶ Wearables
- ▶ Tablets

DFN1010 – First 3 A MOSFETs on 1.1 mm² footprint

DFN1010 – Mounting area versus power density



The next generation of small packaging - Featuring currents up to 3 A on a 1.1 mm² footprint



The DFN1010 can be used for new designs in space-constrained applications and to replace larger packages in the same R_{DSon} range

Types with similar thermal and electrical performance		
Package	SOT363	DFN1010B-6
Package size	2.0 x 1.25 x 0.95 mm	1.1 x 1.0 x 0.37 mm
Solder footprint	2.2 x 2.0 mm = 4.4 mm ²	1.3 x 1.35 mm = 1.75 mm ²
N-channel > 1 Ω range	2N7002BKS	NX7002BKXB
N-channel > 1 Ω range	NX3008NBKS	NX3008NBKXB
P-channel > 1 Ω range	NX3008PBKS	NX3008PBKXB

DFN1010B-6 dual – The ideal replacement for SOT363



Small-signal MOSFETs

Small-signal MOSFETs in DFN1010D-3 single and DFN1010B-3 dual packages types in bold represent new products

Package																DFN1010D-3 (SOT1215)	DFN1010B-6 (SOT1216)	
Size (mm)																1.1 x 1.0 x 0.37	1.1 x 1.0 x 0.37	
P _{tot} (mW)																1000	350	
Configuration	Polarity	V _{DS} (V)	V _{GS} (V)	I _D (A)	V _{GS(th) min} (V)	V _{GS(th) max} (V)	t _{on} typ (ns)	t _{off} typ (ns)	Q _G typ (nC)	ESD protection (kV)	R _{DSon} typ (mΩ) @ V _{GS} =						PMXB40UNE	PMXB43UNE
											10 V	4.5 V	2.5 V	1.8 V	1.5 V	1.2 V		
Single	N-channel	12	8	1.1	0.4	0.9	6	18	6.6	1	-	34	39	46	50	121		
		20	8	3.2	0.5	0.9	6	17	5.7	1	-	42	48	56	64	-		
		30	20	3.2	1	2	3	11	3.6	-	49	56	-	-	-	-		
	P-channel	80	20	1.1	1.3	2.7	2	9	3	2	345	390	-	-	-	-		
		12	8	3.2	0.4	1	6.2	27	6.7	1.5	-	59	78	120	198	880		
		20	8	2.9	0.4	1	6	29	6.8	1.5	-	69	86	130	205	950		
Dual	N-ch	12	8	1.2	0.45	0.95	3	18	1.25	1.5	-	350	450	600	760	1200		
		30	20	2.4	1	2.5	4	16	6.2	1	100	125	-	-	-	-		
		60	20	0.35	1.1	2.1	4.7	6.9	1	2	2200	2500	-	-	-	-		
	P-ch	30	8	0.23	0.6	1.1	49	103	0.55	2	-	2800	5300	-	-	-		
		20	8	0.5	0.45	0.95	2.3	13.5	1.19	1	-	1020	1270	1700	2300	3500		
		20	8	0.6	0.45	0.95	5.6	19	0.4	1	-	470	620	845	1125	2210		
Complementary	N	20	8	0.6	0.45	0.95	5.6	19	0.4	1	-	470	620	845	1125	2210		
	P	20	8	0.5	0.45	0.95	2.3	13.5	1.19	1	-	1020	1270	1700	2300	3500		

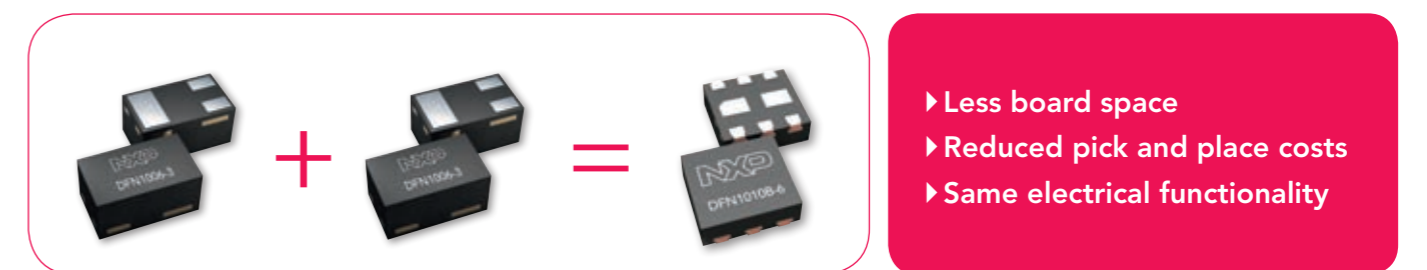
Key features

- ▶ N- and P-channel
- ▶ Low R_{DSon} to 34 mΩ
- ▶ I_D to 3.2 A
- ▶ Low voltage drive (V_{GS(th)} = 0.65 V typ)
- ▶ Voltage range of 12 to 80 V
- ▶ ESD protection to more than 1 kV

Package

- ▶ 1.1 x 1.0 x 0.37 mm package size
- ▶ Single and dual packages
- ▶ High power dissipation (P_{tot}) of 1000 mW single and 350 mW for dual package
- ▶ Single package with tin-plated, solderable side pads for improved mounting and automotive conformity

1+1 = 1: DFN1010B-6 dual equals two DFN1006



In the spotlight

PMXB40UNE – Low R_{DSon} of only 34 mΩ

Small and leadless ultrathin SMD package: 1.1 x 1.0 x 0.37 mm

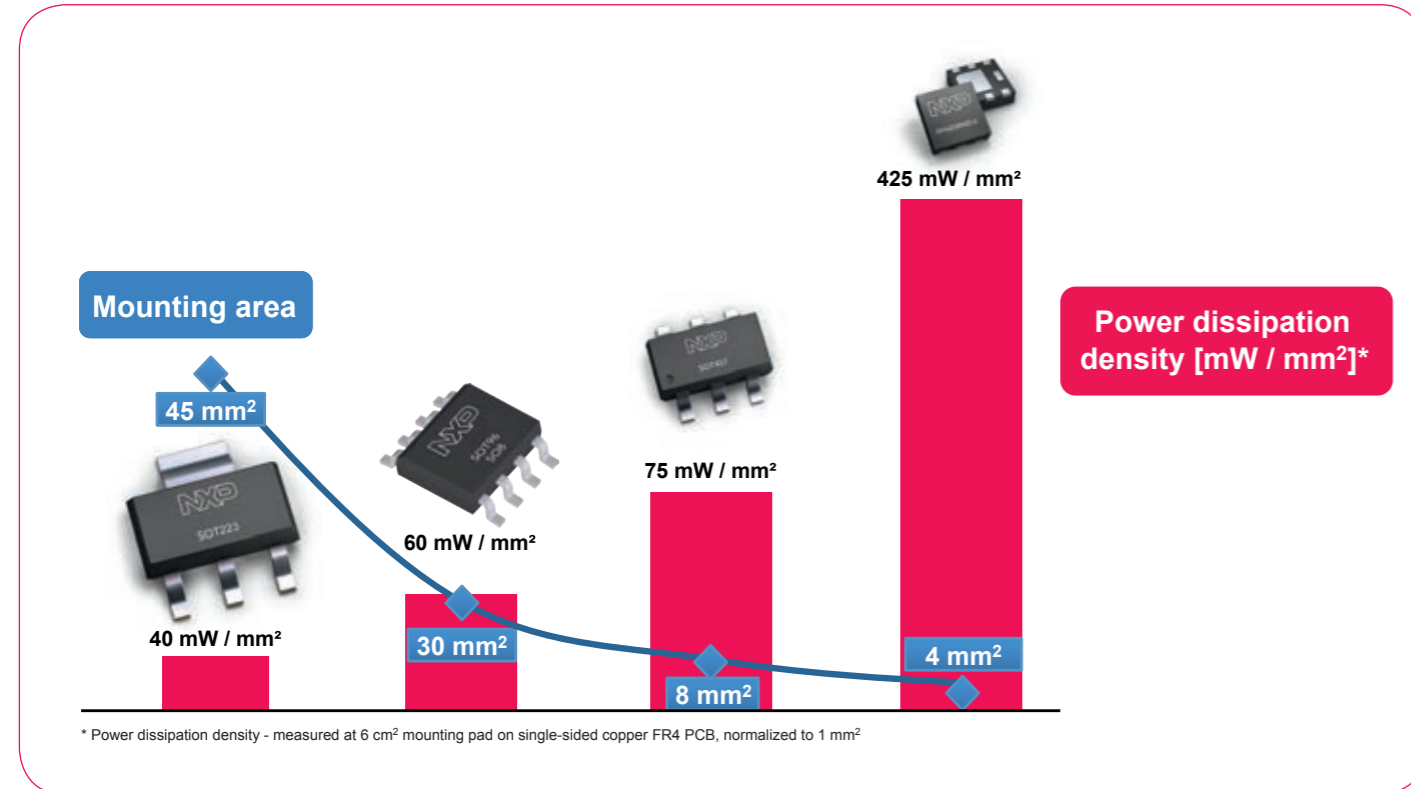
20 V N-channel with R_{DSon} of 34 mΩ @ V_{GS} = 4.5 V (typ)

Tin-plated 100% solderable side pads for optical solder inspection



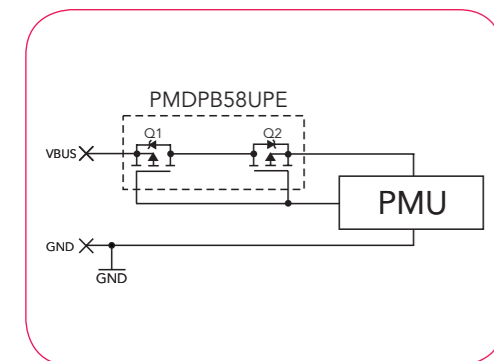
DFN2020 – The low $R_{DS(on)}$ choice for values $> 10\text{ m}\Omega$

DFN2020 – The must-have package for $R_{DS(on)}$ values of $> 10\text{ m}\Omega$



DFN2020 offers a power density of 425 mW / mm² on a footprint of only 4 mm², enabling high-performance designs for space-constrained applications

Low $R_{DS(on)}$ types for USB OTG Vbus protection



In the spotlight

PMPB15XP – Low $R_{DS(on)}$ P-channel MOSFET in DFN2020

- 12 V P-channel with $R_{DS(on)}$ of 15 m Ω @ $V_{GS} = 4.5\text{ V}$ (typ)
- I_D max of 11.8 A for medium current load switch
- Small and leadless ultrathin SMD plastic package: 2.0 x 2.0 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- $R_{DS(on)}$ specified to 1.8 V for low drive voltages

Key features

- ▶ N- and P-channel
- ▶ Low $R_{DS(on)}$ down to 10 m Ω
- ▶ I_D up to 13 A
- ▶ Low voltage drive ($V_{GS(th)} = 0.65\text{ V}$ typ)
- ▶ Voltage range of 12 to 100 V
- ▶ ESD protection of 3 kV

Package



- ▶ 2.0 x 2.0 x 0.65 mm package size
- ▶ Single and dual packages
- ▶ High power dissipation (P_{tot}) of 1250 mW for single and dual packages
- ▶ Single package with tin-plated, solderable side pads for improved mounting and automotive conformity

Small-signal MOSFETs in DFN2020MD-6 single and DFN2020-6 dual packages types in bold represent new products

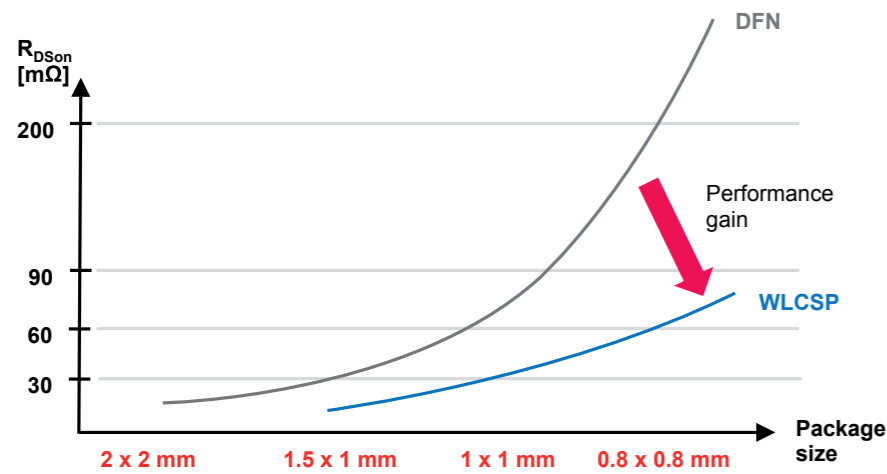
Package		DFN2020MD-6 (SOT1220)	DFN2020-6 (SOT1118)																							
Size (mm)		2.0 x 2.0 x 0.65	2.0 x 2.0 x 0.65																							
P_{tot} (mW)		1250	1250																							
Configuration	Polarity	V_{DS} (V)	V_{GS} (V)	I_D (A)	$V_{GS(th)}$ min (V)	$V_{GS(th)}$ max (V)	t_{on} typ (ns)	t_{off} typ (ns)	Q_g typ (nC)	ESD protection (kV)	$R_{DS(on)}$ typ (m Ω) @ $V_{GS} =$				Part Number											
											10 V	4.5 V	2.5 V	1.8 V												
Single	N-channel	8	11.3	0.4	1	9	26	8.8	2	-	14	17	21	PMPB12UNE												
														9.4	0.4	1	7	17	4.7	2	-	19	25	36	PMPB20UNE	
		20	12	12.9	0.4	0.9	13	54	23	2.2	-	10	12	16	PMPB10XNE											
															10.4	0.4	0.9	9	31	13.4	-	-	18	21	23	PMPB15XN
			12	10.1	0.4	0.9	9	31	11.6	2.1	-	19	23	31	PMPB23XNE											
															11.3	0.4	0.9	12	54	24	2.2	-	13	14	17	PMPB13XNE
		30	12	5	0.4	0.9	8	33	12.4	2.1	-	28	32	37	PMPB29XNE											
															5.5	0.45	1.2	6	21	5.1	-	-	37	55	-	PMPB33XN
			20	13	1	2	9	17	13.7	-	-	12	14	-	-	PMPB11EN										
																10.4	1	2	9	9	7.2	-	16.5	20.5	-	-
	60		20	12.9	1	3	9	12	12.1	-	-	34	40	-	-	PMPB40SNA										
																-	1.3	2.7	-	-	-	2	44	52	-	-
	80	20	3	1.3	2.7	4	10.5	6.2	2.7	-	72	85	-	-	PMPB85ENE											
															2.8	1.3	2.7	5	15	9.9	2.8	80	92	-	-	PMPB95ENE
		12	1.9	1.3	2.7	3.5	9.5	4.8	2	-	175	195	-	-	PMPB215ENE											
															12	12	11.8	0.47	0.9	18	85	67	-	-	15	17
		20	12	10.3	0.47	0.9	16	43	28.8	-	-	19	21	27	PMPB19XP											
															10.3	0.47	0.9	13	92	30	2.4	-	19	22	28	PMPB20XPE
															5	0.47	0.9	12	91	30	2.3	-	28	31	36	PMPB29XPE
			30	12	7.9	0.47	0.9	12	62	15	-	-	30	35	45	PMPB33XP										
5	0.47															0.9	9	57	15.6	2.3	-	39	45	56	PMPB43XPE	
5	0.47															0.9	15	28	14	-	-	47	54	74	PMPB47XP	
60	20	8.8	1	2.5	10	28	30	-	-	24	32	-	-	PMPB27EP												
														6.8	1	2.5	7.4	27	17	-	40	55	-	-	PMPB48EP	
Dual	N-ch	20	12	5.3	0.4	0.9	4	40	14.4	-	-	32	40	60	PMDPB30XN											
															4	0.5	1.5	8	12	1.9	2	-	55	86	-	PMDPB56XNE
		30	12	3.1	0.5	1.5	6	18	1.65	1.8	-	95	130	-	PMDPB95XNE2											
															4.5	0.45	0.95	7	41	6.3	2	-	58	74	97	PMDPB58UPE
	P-channel	8	3.7	0.45	0.95	6	47	5.4	2	-	82	107	142	PMDPB85UPE												
														-	0.75	1.25	-	-	-	2	-	44	60	-	PMDPB42XPE	
			20	12	4.5	0.47	0.9	4	135	16.5	-	-	55	75	110	PMDPB55XP										
																4.2	0.75	1.25	7	33	5	2	-	66	98	-
		30	12	3.7	0.4	1	6	120	5.7	-	-	80	95	120	PMDPB80XP											
															3.8	0.45	1	3	112	5.2	-	-	70	89	-	PMDPB70XP
			20	12	3.7	0.4	1	6	120	5.7	-	-	80	95	120	PMFPB8032XP										
																3.7	0.4	1	6	120	5.7	-	-	80	95	120
Pre-biased NPN	P	30	12	3.4	0.45	1	3	112	5.2	-	-	85	105	-	PMC85XP											
Complementary	N	20	12	5.3	0.4	0.9	4	40	14.4	-	-	26	33	50	-											
	P	20	12	4.5	0.4	0.9	4	40	8.1	-	-	55	75	110	PMCPB5530X											

MOSFETs

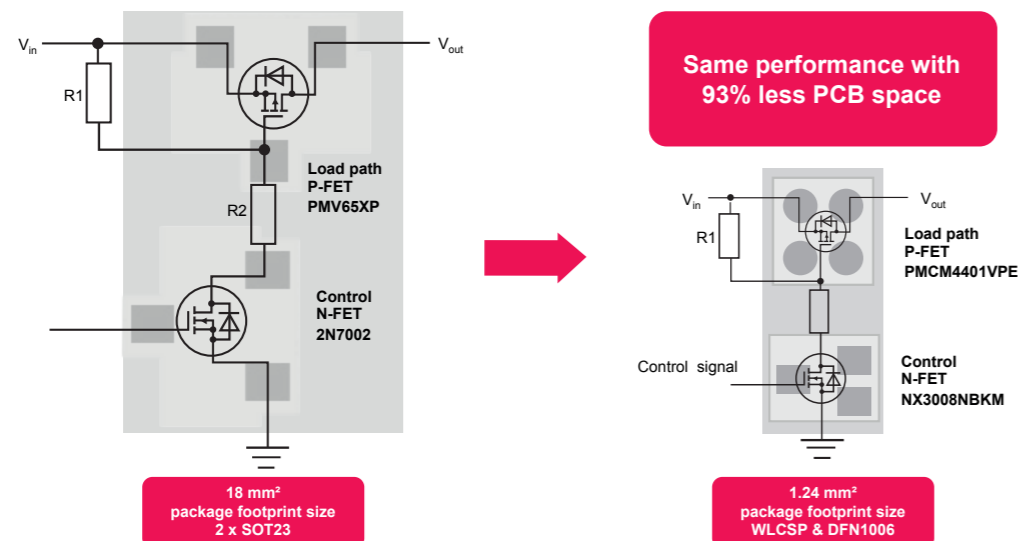
Small-signal MOSFETs in WLCSP4 and WLCSP6 packages

											WLCSP4	WLCSP6		
Package														
Size (mm)											0.78 x 0.78 x 0.35	1.48 x 0.98 x 0.35		
Ptot (mW)											1300	1300		
Polarity	V _{DS} (V)	V _{GS} (V)	I _D (A)	V _{GS(th) min} (V)	V _{GS(th) max} (V)	t _{on typ} (ns)	t _{off typ} (ns)	Q _{G typ} (nC)	ESD protection (kV)	R _{DSon typ} (mΩ) @ V _{GS} =				
										4.5 V	2.5 V	1.8 V	1.5 V	
N	12	8	3.2	0.4	1	-	-	-	2	57	65	77	-	PMCM440VNE
			4.1	0.4	1	-	-	-	2	34	40	55	-	PMCM4401VNE
P	12	8	3.3	0.5	1	-	-	-	2	55	100	120	-	PMCM4401VPE
N	12	8	7.8	0.4	1	-	-	-	2	20	23	28	-	PMCM650VNE
			9.8	0.4	1	-	-	-	2	13	16	19	-	PMCM6501VNE
P	12	8	7.8	0.5	1	-	-	-	2	20	25	35	-	PMCM6501VPE

WLCSP – MOSFETs with ultra-low R_{DSon}

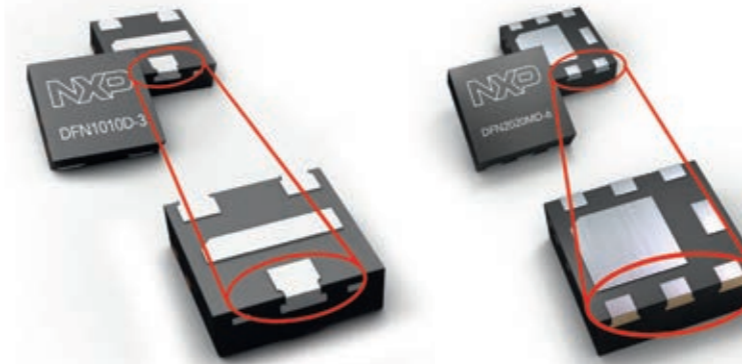


Loadswitch – WLCSP versus leaded packages



Small-signal MOSFETs for automotive

DFN1010 and DFN2020 with solderable side pads



- ▶ High-quality solder connections
- ▶ No complete wetting on side pad
- ▶ Reduction of production costs through optical visual solder inspection

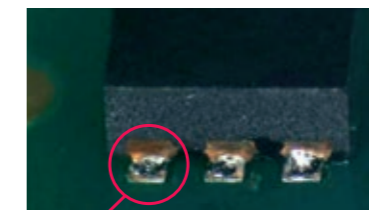
Comparison of solder capability

NXP package
100% solderable side pads



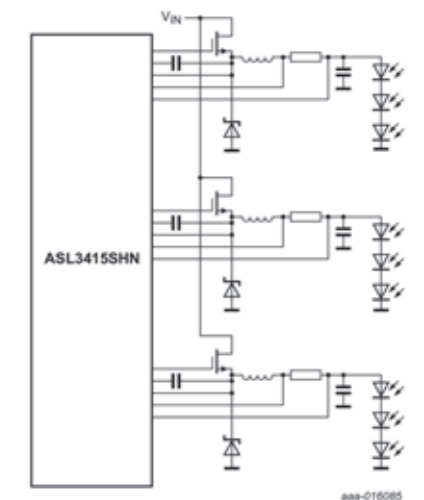
100% solder wetting solution
with new 2 x 2 mm leadless package DFN2020MD-6

Packages from other suppliers



- ▶ Quality of solder connection difficult to determine
- ▶ Very limited options for optical solder inspection

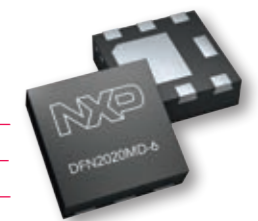
Reference design for LED lighting



In the spotlight

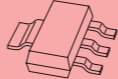
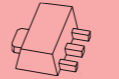


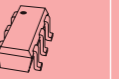



PMPB85ENEA - Automotive-compliant 60 V N-channel MOSFET with I_D max of 4.4 A in DFN2020MD-6 (SOT1220)

- 60 V N-channel with R_{DSon} of typ. 72mΩ @ V_{GS} = 10 V
- Small and leadless ultrathin SMD plastic package: 2.0 x 2.0 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- ESD protection to 2 kV HBM
- AEC-Q101 qualified




Small-signal MOSFETs single (P-channel)

types in **bold** represent new products

													SOT223	SOT89 (SC-62)	SOT457 (SC-74)	SOT23	SOT363 (SC-88)	SOT323 (SC-70)	DFN1006-3 (SOT883)	DFN1006B-3(SOT883B)
																				
Size (mm)													6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.5 x 1.0	2.9 x 1.3 x 1.0	2.0 x 1.25 x 0.95	2.0 x 1.25 x 0.95	1.0 x 0.6 x 0.48	1.0 x 0.6 x 0.37
P _{tot} (mW)													1700	1300	600	250	300	200	250	250
V _{DS} (V)	V _{GS} (V)	I _D (A)	V _{GS(th)} min (V)	V _{GS(th)} max (V)	t _{on} typ (ns)	t _{off} typ (ns)	Q _G typ (nC)	ESD protection (kV)	R _{DS(on)} typ (mΩ) @ V _{GS} =											
									10 V	4.5 V	2.5 V	1.8 V								
20	8	5.7	0.45	0.95	39	122	21	-	-	27	36	57								
		5.6	0.45	0.95	11	83	14.7	2	-	27	38	50								
		5.3	0.45	0.95	41	122	14.7	2	-	30	38	51								
		5.4	0.45	0.95	34	128	15.5	-	-	34	42	57								
		6	0.45	0.95	29	84	15.6	4	-	37	45	59								
		4	0.47	0.9	-	-	10.5	3	-	50	57	70								
		2	0.5	1.1	7	50	6	-	-	100	-	-								
		1.2	0.45	0.95	33	52	3.3	-	-	170	210	280								
		0.75	0.4	-	6.5	65	-	-	-	180	-	420								
	1.4	0.45	0.95	9	35	1.3	1.8	-	330	420	520									
	0.48	0.5	1.3	48	152	0.76	2	-	670	1200	1800									
	0.5	0.45	0.95	2.3	13.5	1.19	1	-	1020	1270	1700									
	4.4	0.75	1.25	-	-	-	2	-	26	-	-									
	5.7	0.75	1.25	37	66	15	2	-	27	39	-									
	5.7	0.75	1.25	44	60	11.5	2	-	41	56	-									
	4.1 / 3.5	0.75	1.25	24	84	8.5	-	-	48	71	-									
	4.4	0.47	0.9	7	135	7.7	-	-	48	60	82									
	3.9	0.55	0.95	28	101	7.6	-	-	65	90	-									
3.3	0.75	1.25	7	36	5	2	-	67	99	-										
4.1	0.75	1.25	20	57	5.2	2	-	70	101	-										
3.2	0.47	0.9	6	120	5	-	-	77	95	120										
3.2	0.45	1	20	170	5	-	-	80	95	120										
2	0.65	1.15	48	64	4.8	-	-	90	125	-										
2.2	0.75	1.25	-	-	-	2	-	93	-	-										
1	0.65	1.15	26	44	2.6	-	-	175	240	-										
1	0.45	0.95	2.9	22	1.45	2	-	400	480	600										
0.47	0.4	-	6.5	65	-	-	-	660	-	1100										
0.23	0.6	1.1	49	103	0.55	2	-	2800	5300	-										
4	1	3	6	38	18	3	23	39	-	-										
3	1	2.8	20	50	-	-	220	330	-	-										
0.52	1	-	6.5	65	-	-	630	890	-	-										
40	20	1.8	1	2.5	10	40	4.7	1	180	220	-	-								
50	20	0.2	1.1	2.1	24	73	0.26	1	5300	6000	-	-								
60	20	2.2	1	3	-	-	-	2	99	110	-	-								
		0.9	1	3	-	-	-	2	217	241	-	-								
		0.3	1	-	6.5	65	-	-	2100	-	2700	-	-							
70	20	2.3	1	3	-	-	-	2	156	177	-	-								
200	20	0.225	0.8	2.8	5	20	-	-	10000	-	-	-								
240	20	0.2	0.8	2.8	5	20	-	-	10000	-	-	-								
250	20	0.225	0.8	2.8	5	10	-	-	10000	-	-	-								
300	20	0.21	1.95	2.8	5	15	-	-	17000	-	-	-								

Small-signal MOSFET-Schottky combination

													DFN2020-6		
															
Size (mm)													2.0 x 2.0 x 0.65		
P _{tot} (mW)													1250		
Configuration	V _{DS} (V)	V _{GS} (V)	I _D (A)	V _{GS(th)} min (V)	V _{GS(th)} max (V)	t _{on} typ (ns)	t _{off} typ (ns)	Q _G typ (nC)	I _F (A)	V _R (V)	V _F typ. (mV)	R _{DS(on)} typ (mΩ) @ V _{GS} =			
												4.5 V	2.5 V	1.8 V	
Single + Schottky	20	8	3.7	0.4	1	20	170	5.7	2	30	455	80	95	120	PMFPB8040XP
			3.7	0.4	1	20	170	5.7	2.2	30	325	80	95	120	PMFPB8032XP

In the spotlight

PMV75UP – 20 V, 77 mΩ P-channel MOSFET

Cross of Si2301 types

Low-voltage gate drive with V_{GSth} = 0.68 V (typ)

Industry-standard SOT23 package





R_{DS(on)} specified to 1.8 V for low drive voltages



MOSFETs





Small-signal MOSFETs dual

types in **bold** represent new products

											SOT363 (SC-88)	SOT666	DFN2020-6 (SOT1118)	DFN1010B-6 (SOT1216)						
Package																				
Size (mm)											2.0 x 1.25 x 0.95	1.6 x 1.2 x 0.55	2.0 x 2.0 x 0.65	1.0 x 1.0 x 0.37						
P _{tot} (mW)											300	300	1250	350						
Polarity	V _{DS} (V)	V _{GS} (V)	I _D (A)	V _{GS(th)} min (V)	V _{GS(th)} max (V)	t _{on} typ (ns)	t _{off} typ (ns)	Q _G typ (nC)	ESD protection (kV)		R _{DS(on)} typ (mΩ) @ V _{GS} =									
											10 V	4.5 V	2.5 V	1.8 V						
N-channel	20	8	0.8	0.5	0.95	10	117	0.45	2		-	290	420	600						
			5.8	0.4	1	6	13	3.1	-			-	30	39	56					
			0.6	0.45	0.95	5.6	19	0.4	1			-	470	620	845					
			5.1	0.4	1	6	20	2	-			-	40	53	82					
			12	5.3	0.4	0.9	4	40	14.4	-		32	40	60						
			8	0.35	0.6	1.1	26	88	0.52	2		1000	1400	2000						
			12	4	0.5	1.5	8	12	1.9	2		55	86	-						
			30	3.1	0.5	1.5	6	18	1.65	1.8		95	130	-						
			20	1	0.5	1.5	6.5	14	0.7	2		170	240	-						
			60	0.18	0.8	1.5	10	51	0.34	Yes		2700	3000	4000						
			20	0.36	0.9	1.5	5	13	0.72	-		900	1000	-						
	P-channel	20	8	0.55	0.5	1.3	48	152	0.76	2		-	670	1200	1800					
4.5				0.45	0.95	7	41	6.3	2			-	58	74	97					
0.5				0.45	0.95	2.3	13.5	1.19	1			-	1020	1270	1700					
3.7				0.45	0.95	6	47	5.4	2			-	82	107	142					
			12	-	0.75	1.25	-	-	-	2		44	60	-						
			8	4.5	0.47	0.9	4	135	16.5	-		55	75	110						
			12	4.2	0.75	1	7	33	5	2		66	98	-						
			30	3.7	0.4	1	6	120	5.7	1		80	95	120						
			8	0.2	0.6	1.1	49	103	0.55	2		2800	5300	-						
			12	3.8	0.45	1	3	112	5.2	-		70	89	-						
			50	0.16	1.1	2.1	24	73	0.26	1		4500	5700	-						

MOSFETs

Small-signal MOSFETs complementary

Package	Type	Polarity	V _{DS} (V)	V _{GS} (V)	I _D (A)	V _{GS(th)} min (V)	V _{GS(th)} max (V)		t _{on} typ (ns)	t _{off} typ (ns)	Q _G typ (nC)	ESD protection (kV)	R _{DS(on)} typ (mΩ) @ V _{GS} =					
													10 V	4.5 V	2.5 V	1.8 V	1.5 V	1.2 V
 SOT666 (1.6 x 1.2 x 0.55)	NX1029X	N	60	20	0.33	1.1	2.1		11	19	0.5	2	1000	1300	-	-	-	-
	P	50	20	0.17	1.1	2.1		24	73	0.26	1	4500	5100	-	-	-	-	
	NX3008CBKV	N	30	8	0.4	0.6	1.1		26	88	0.52	2	-	1000	1400	2000	-	-
	P	30	8	0.22	0.6	1.1		49	103	0.55	2	-	2800	5300	-	-	-	
PMDT290UCE	N	20	8	0.8	0.5	20	0.95		10	117	0.45	2	-	290	420	600	-	-
	P	20	8	0.55	0.5	13.5	1.19		48	152	0.76	2	-	670	1200	1800	-	-
 SOT363 (SC-88) (2.0 x 1.25 x 0.95)	NX3008CBKS	N	30	8	0.35	0.6	1.1		26	88	0.52	2	-	1000	1400	2000	-	-
	P	30	8	0.2	0.6	1.1		49	103	0.55	2	-	2800	5300	-	-	-	
 DFN1010B-6 (1.1 x 1.0 x 0.37)	PMCXB900UE	N	20	8	0.6	0.45	0.95		5.6	19	0.4	1	-	470	620	845	1125	2210
	P	20	8	0.5	0.45	0.95		2.3	13.5	1.19	1	1	-	1020	1270	1700	2300	3500
 DFN2020-6 (2.0 x 2.0 x 0.65)	PMCPB5530X	N	20	12	5.3	0.4	0.9		19	56	14.4	-	-	26	33	50	-	-
	P	20	12	4.5	0.47	0.9		18	56	16.5	-	-	-	55	75	110	-	-

4 steps select a power MOSFET

High-performance power MOSFETs

- 1 Select a voltage, e.g. 40 V
- 2 Select a package, e.g. LFPAK56
- 3 Choose an R_{DSon} from our extensive range
- 4 Select a type and visit www.nxp.com/mosfets to download datasheets and models, and order samples

MOSFET package selection

Through-hole

Surface-mount

- TO220**
- ▶ Industry standard
 - ▶ Up to 150 A



- TO220F**
- ▶ Industry standard
 - ▶ Up to 75 A



- I²PAK**
- ▶ Industry standard
 - ▶ Up to 120 A



- LFPAK56**
- ▶ Power SO8
 - ▶ Up to 100 A



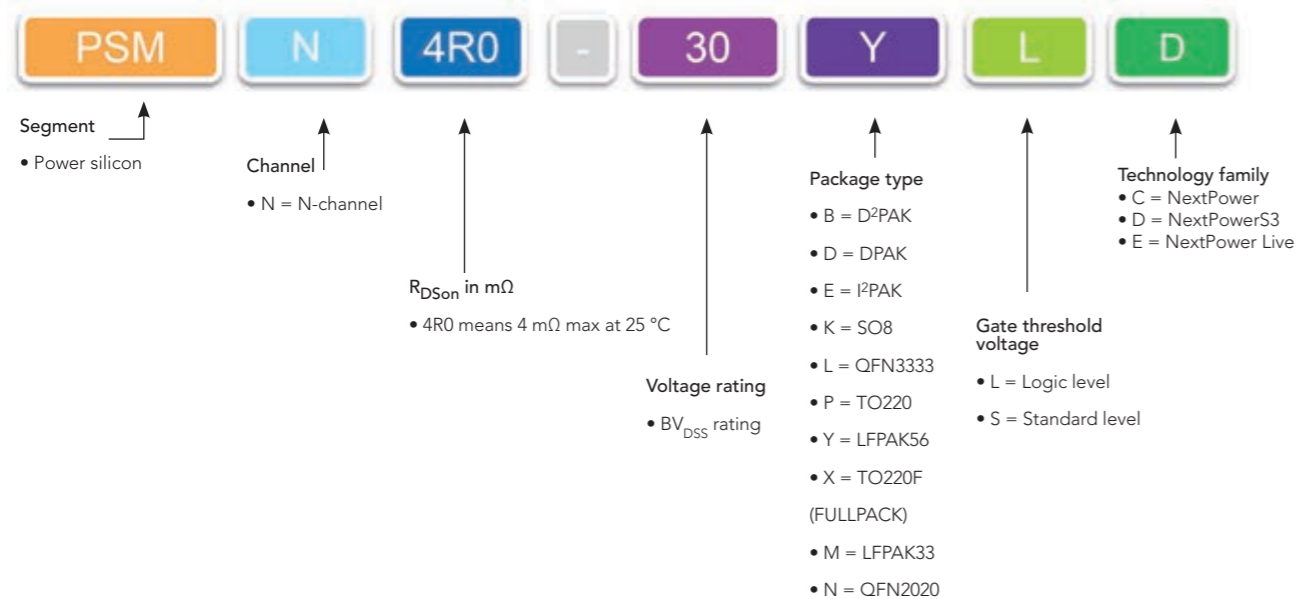
- LFPAK33**
- ▶ QFN/DFN3333 compatible
 - ▶ Up to 70 A



- D²PAK**
- ▶ Industry standard
 - ▶ Up to 120 A

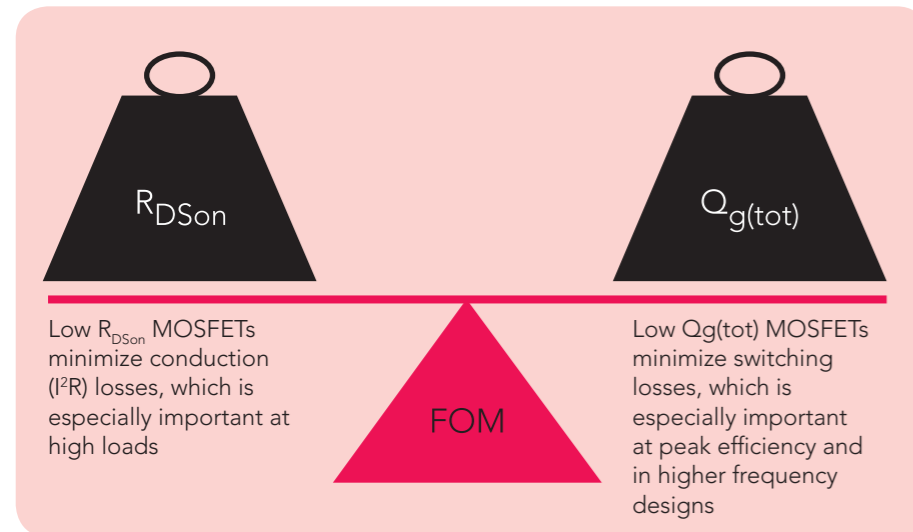


PSMN part numbering



Featured product: NextPowerS3

NextPowerS3 – perfectly balanced for DC/DC switching applications



The challenge

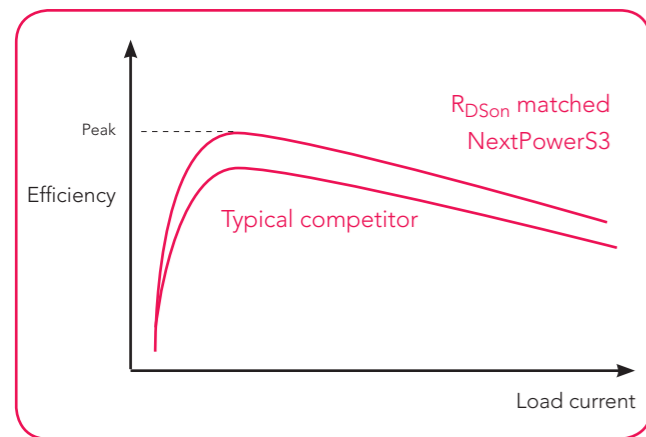
Low $R_{DS(on)}$ MOSFETs typically need a big die.

Low $Q_{g(tot)}$ MOSFETs typically need a small die.

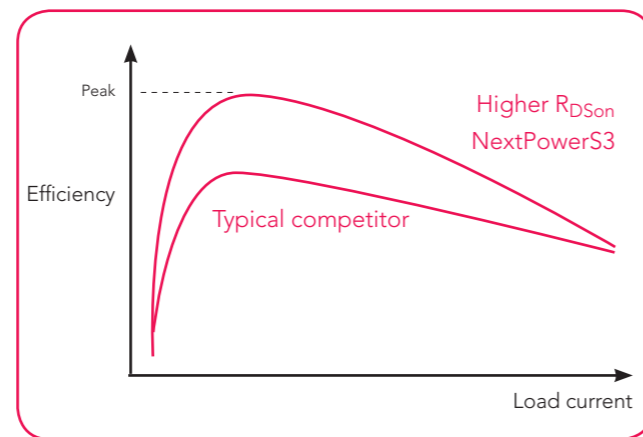
The challenge for manufacturers is to create optimized power MOSFETs that have both low $R_{DS(on)}$ and low $Q_{g(tot)}$.

Welcome to NextPowerS3.

The Figure of Merit (FOM) of a MOSFET is calculated as the product of the $R_{DS(on)}$ and $Q_{g(tot)}$. A low FOM indicates good MOSFET performance in switching applications.



Comparing the performance of a NextPowerS3 MOSFET with a competitor of similar $R_{DS(on)}$ typically shows an efficiency performance advantage across the load range. Since conduction losses are the same for both devices, the advantage is more noticeable at lower loads where switching losses contribute proportionally more.



Using a NextPowerS3 MOSFET, with a higher $R_{DS(on)}$ than a competitor device, reduces the $Q_{g(tot)}$ still further, resulting in an improved peak efficiency. At higher loads, increased conduction losses cancel out the switching advantages and the two parts show similar performance.

Featured product: NextPowerS3

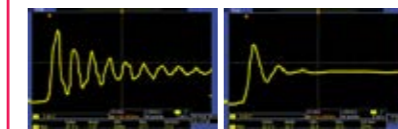
High switching frequencies



Increasing switching frequency from 300 KHz to 1 MHz allows a 70 - 80% reduction in inductor size. NextPowerS3's excellent switching performance enables such design choices with minimal loss of efficiency.

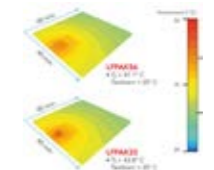
Low spiking

Typical competitor NextPowerS3



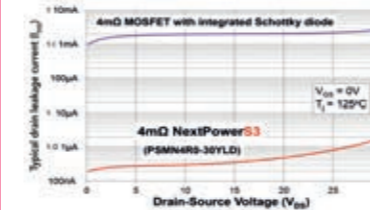
Thanks to optimised output capacitance, body diode and channel structure, NextPowerS3 MOSFETs exhibit "soft-recovery" switching behaviour, resulting in lower voltage spikes, faster decays and virtually no gate glitches.

Thermal efficiency



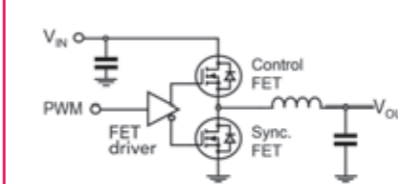
Packaged in the copper-clip based LFPACK package, NextPowerS3 features excellent thermal performance. As $R_{DS(on)}$ rises with temperature, keeping MOSFETs cool helps efficiency as well as reliability.

Low leakage



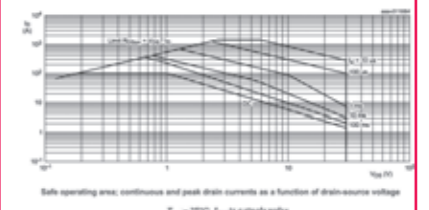
Unique SchottkyPlus technology offers the benefits of an integrated Schottky diode without the problems associated with leakage current.

Specialist high sides



The NextPowerS3 portfolio contains devices with multiple busbars and low R_g optimized for use as control FETs, further improving system efficiencies.

Improved SOA



A wide cell pitch makes NextPowerS3 an excellent choice for hot-swap, e-Fuse, and power OR-ing applications.

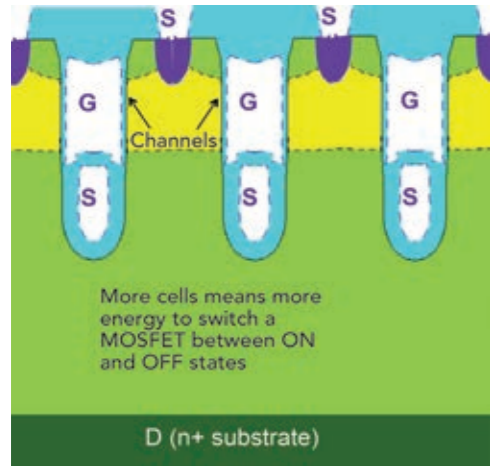
Package	Type number	V_{DS} [max] (V)	$R_{DS(on)}$ [max] @ $V_{GS} = 10$ V (m Ω)	$R_{DS(on)}$ [max] @ $V_{GS} = 4.5$ V (m Ω)	I_b [max] (A)	$Q_{g(tot)}$ [typ] (nC)
LFPACK33 (SOT1210)	30MLD	30	2.4	3.2	70	16
	PSMN4R2-30MLD	30	4.3	5.7	70	9.2
	PSMN7R5-30MLD	30	7.6	10.3	57	5.8
Power-SO (LFPACK56)	PSMN0R9-30YLD	30	0.87	1.09	100	51
	PSMN1R0-30YLD	30	1.02	1.3	100	38
	PSMN1R2-30YLD	30	1.24	1.6	100	32
	PSMN1R4-30YLD	30	1.42	1.85	100	27.6
	PSMN2R4-30YLD	30	2.4	3.1	100	18
	PSMN3R0-30YLD	30	3.1	4	100	14.5
	PSMN4R0-30YLD	30	4	5.5	95	9.6
	PSMN6R0-30YLD	30	6	8.35	66	6.7
	PSMN6R1-30YLD	30	6	8.35	66	6.8
	PSMN7R5-30YLD	30	7.5	10.2	51	5.8
	PSMN1R0-40YLD	40	1.1	1.4	100	54
	PSMN1R4-40YLD	40	1.4	1.8	100	45

Types in bold red represent new products

MOSFETs

Featured product: NextPowerS3 – the technology

Typical competitor



The importance of cell design

The outstanding performance of NextPowerS3 is largely attributable to NXP's unique "Super-junction" technology and optimization of cell structures.

Most manufacturers of low-voltage MOSFETs use "Split Gate" technology to achieve low R_{DSon} .

NextPowerS3 uses a different approach to its cell design.

The drive for R_{DSon}

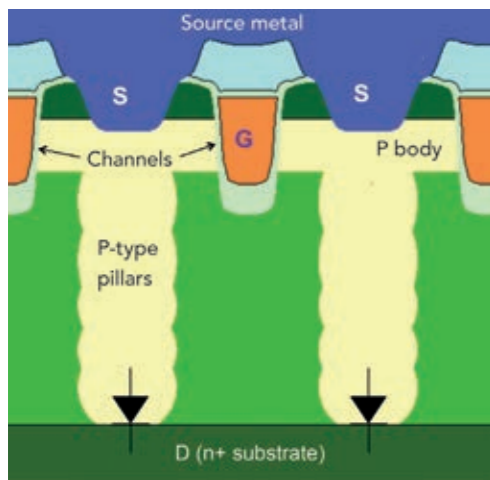
A MOSFET's R_{DSon} is given by the formula:

$$R_{DSon} = R_{channel} + R_{drift} + R_{substrate} + (R_{package})$$

Many manufacturers focus on reducing $R_{channel}$ to drive R_{DSon} down.

NXP's Super-junction allows for an optimization of all three components for reduction in R_{DSon} , while also enhancing switching performance and Safe Operating Area (SOA).

NextPowerS3



Maximizing switching performance

Switching losses result from the energy required to charge / discharge all the cell capacitances across the device. The total charge required is referred to as $Q_{g(tot)}$.

With NextPower S3, $Q_{g(tot)}$ is lower and switching losses are kept to a minimum. This is especially beneficial at peak efficiency and in higher-frequency designs, which have a higher number of switching events.

SOA and other benefits

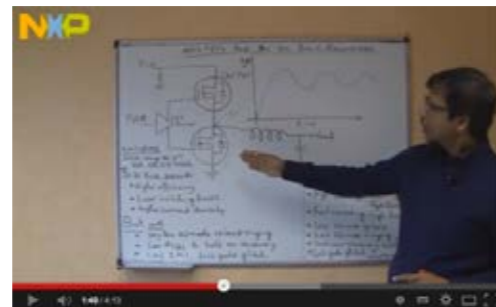
When a device is operating in its linear mode, the channel current generates localized heating effects, which can cause failure.

NXP has optimized the cell structure to keep this heating effect under control. As a result, NextPowerS3 enjoys a particularly strong SOA, which is important in hot-swap, e-Fuse, and power OR-ing designs.



Reverse recovery and diode leakage in SMPS

www.nxp.com/quicklearning33



NextPowerS3 MOSFETs for DC/DC buck regulators

www.nxp.com/quicklearning32

Featured product: NextPower Live



MOSFETs

NextPower Live! MOSFETs for a non-stop world

Reliable linear-mode performance AND low R_{DSon} efficiency in "hot-swap" and "soft-start" applications

Non-stop applications

- ▶ Cloud computing
- ▶ Network storage
- ▶ Communications infrastructure
- ▶ Industrial process control
- ▶ Transaction processing
- ▶ Traffic monitoring & signaling
- ▶ CCTV security

Non-stop equipment

- ▶ Blade and rack servers
- ▶ Routers, switches & base stations
- ▶ RAID arrays
- ▶ Industrial PCs
- ▶ Programmable Logic Controllers (PLCs)
- ▶ CCTV digital video recorders
- ▶ "Hot-swap" & "soft-start" systems

Featured product: NextPower Live

Mobile phones, ATMs, the internet, traffic signals – so much of our daily life depends on 24/7/365 computers, communications, and storage, made possible by rack-based systems that can be maintained with the power on. NextPower Live MOSFETs are designed specifically for such applications:

- ▶ When a replacement board is plugged into a live system, it is important that the in-rush current is carefully controlled, so as to protect the components on the board and ensure that other parts of the system experience no power disruption. This application requires MOSFETs with strong linear mode performance and a wide safe operating area (SOA) to manage current effectively and reliably.
- ▶ Once the replacement board is safely installed, the MOSFET is turned fully ON. In this mode of operation, a low R_{DSon} is of primary importance, helping to keep temperatures low while maximizing system efficiency.
- ▶ Only NextPower Live MOSFETs offer reliable linear mode performance **AND** low R_{DSon} efficiency.

NextPower Live portfolio

Package	30 V for 12 V supplies used in computing applications	100 V for 48 V supplies used in computing telecommunications
D ² PAK (SOT404)	PSMN1R5-30BLE PSMN3R4-30BLE	PSMN4R8-100BSE PSMN7R6-100BSE
TO220		PSMN4R8-100PSE PSMN7R8-100PSE
LFPAK56 (Power-SO8)	PSMN2R0-30YLE	PSMN013-100YSE
LFPAK33		(specifically for PoE applications) PSMN040-100MSE PSMN075-100MSE



Power MOSFET operation in linear mode
www.nxp.com/quicklearning34



MOSFETs for Power-over-Ethernet (PoE) PSE applications
www.nxp.com/quicklearning36



Next Power Live! MOSFETs for HOT SWAP and Power over Ethernet
www.nxp.com/quicklearning29

Featured product: NextPower Cordless

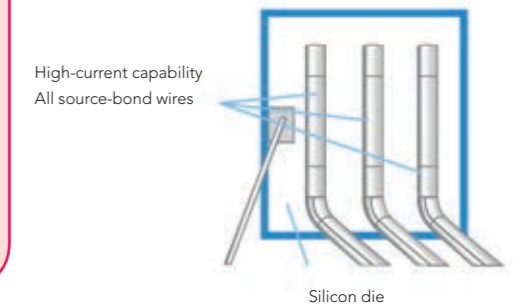
▶ Battery-powered tools, including everything from small engraving devices and screwdrivers to heavy-duty saws and agricultural tools, present a wide variety of requirements for driving the motor. The MOSFETs used in these systems have to perform at demanding levels and must have:

- ▶ Low on-resistance for optimum battery life
- ▶ Low thermal resistance for reduced junction temperature (for greater reliability)
- ▶ High current capability (when the motor stalls, for example)
- ▶ Choice of logic- and standard-level gate drives, depending on battery voltage
- ▶ Excellent avalanche ruggedness to withstand high-load conditions
- ▶ Environmental robustness (wide operating/storage temperatures, harsh vibrations)
- ▶ Competitive cost

Overall, the motor-control MOSFET needs to deliver automotive-grade performance at a commercially competitive price



Typical Power Tools MOSFET internal construction



NXP has developed a range of MOSFETs specifically aimed at motor-control applications. These are based on our highly reliable, automotive-qualified silicon, with specific package enhancements such as thicker wires and multiple bond points ("stitch bonding") to spread the current evenly over the die surface.

NXP's long history in automotive MOSFETs means we have the know-how to produce devices with excellent avalanche ruggedness. The same expertise deployed in power steering and ABS systems worldwide is put to use in our devices for motor control and that means performance you can count on.

Max current ($I_D[\max]$) depends largely on the number and diameter of the aluminium bond wires. The NXP Power Tools portfolio is typically based on a standard of three 500 μm wires, allowing for an $I_D[\max]$ rating of up to 150 A in a TO220 package.



Single-shot avalanche ruggedness
www.nxp.com/quicklearning35



NextPower Cordless MOSFETs for battery-powered tools
www.nxp.com/quicklearning28

NextPower Cordless portfolio

Type number	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	R _{DSon} [max] @ V _{GS} = 4.5 V (mΩ)	I _D [max] (A)	EAS at rated current [mJ]	Package	Gate threshold
PSMN2R0-30YL	30	2	2.63	100	151	LFPAK56	Logic Level
PSMN2R0-30YLE	30	2	3.5	100	370	LFPAK56	Logic Level
PSMN2R5-30YL	30	2.4	3.16	100	103	LFPAK56	Logic Level
PSMN2R6-30YLC	30	2.8	3.65	100	50	LFPAK56	Logic Level
PSMN1R9-40PL	40	1.7	1.94	150	1008	TO220 (SOT78)	Logic Level
PSMN2R1-40PL	40	2.2	2.6	150	622	TO220 (SOT78)	Logic Level
PSMN1R5-40PS	40	1.6	-	120	1400	TO220 (SOT78)	Standard Level
PSMN2R2-40PS	40	2.1	-	100	1240	TO220 (SOT78)	Standard Level
PSMN2R5-60PL	60	2.6	3.15	150	655	TO220 (SOT78)	Logic Level
PSMN2R6-60PS	60	2.9	-	150	519	TO220 (SOT78)	Standard Level
PSMN3R3-60PL	60	3.4	3.8	130	404	TO220 (SOT78)	Logic Level
PSMN3R9-60PS	60	3.9	-	130	372	TO220 (SOT78)	Standard Level
PSMN4R2-60PL	60	4.3	4.3	130	372	TO220 (SOT78)	Logic Level
PSMN7R6-60PS	60	7.8	-	92	110	TO220 (SOT78)	Standard Level

For the most current product information go to www.nxp.com/mosfets (updated daily!)



Heavy-duty tools with large batteries require MOSFETs that withstand higher currents. NXP's TO-220 NextPower Cordless devices handle up to 150A. The high-reliability LFPAK56 is ideal for smaller tools and space-constrained applications.

Power MOSFETs

Power MOSFETs 20 - 25 V

Package	Type number	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	R _{DSon} [max] @ V _{GS} = 4.5 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)
LFPAK56; Power-SO8 (SOT669)	PH3120L	20	2.65	3.7	100	48.5
	PH2520U	20		2.7	100	78
	PSMN0R9-25YLC	25	0.99	1.25	100	51
	PSMN1R1-25YLC	25	1.15	1.5	100	39
	PSMN1R2-25YL	25	1.2	1.85	100	50.6
	PSMN1R2-25YLC	25	1.3	1.7	100	31
	PSMN1R5-25YL	25	1.5	2.2	100	36
	PSMN2R2-25YLC	25	2.4	3.15	100	18
	PSMN2R9-25YLC	25	3.15	4.1	100	16
	PSMN4R0-25YLC	25	4.5	5.8	84	10.9
	PSMN6R0-25YLB	25	6.1	7.9	73	9
	PSMN6R5-25YLC	25	6.5	8.5	64	8.4
	PH2925U	25		3	100	92
	LFPAK33 (SOT1210)	PSMN2R8-25MLC	25	2.8	3.75	70
PSMN3R9-25MLC		25	4.15	5.55	70	9.7
PSMN9R0-25MLC		25	8.65	11.3	55	5.4
D ² PAK (SOT404)	PHB66NQ03LT	25	10.5		66	12
DPAK (SOT428)	PHD38N02LT	20			44.7	15.1
	PHD97NQ03LT	25	6.3	10.6	75	11.7
SO8 (SOT96-1)	PSMN006-20K	20		5	32	32

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Power MOSFETs 30V – Part 1

Package	Type number	V _{DS} [max] (V)	R _{DS(on)} [max] @ V _{GS} = 10 V (mΩ)	R _{DS(on)} [max] @ V _{GS} = 4.5 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)
LFPAK56; Power-SO8 (SOT669)	PSMN0R9-30YLD	30	0.87	1.09	100	51
	PSMN1R0-30YLD	30	1.02	1.3	100	38.2
	PSMN1R0-30YLC	30	1.15	1.4	100	50
	PSMN1R2-30YLD	30	1.24	1.6	100	32
	PSMN1R2-30YLC	30	1.25	1.65	100	38
	PSMN1R3-30YL	30	1.3	1.95	100	46.6
	PSMN1R4-30YLD	30	1.42	1.85	100	27.6
	PSMN1R5-30YL	30	1.5	1.9	100	36.2
	PSMN1R5-30YLC	30	1.55	2.05	100	30
	PSMN1R7-30YL	30	1.7	2.1	100	36.2
	PSMN2R0-30YL	30	2	2.63	100	30
	PSMN2R0-30YLE	30	2	3.5	100	87
	PSMN2R2-30YLC	30	2.15	2.8	100	26
	PSMN2R4-30YLD	30	2.4	3.1	100	18
	PSMN2R5-30YL	30	2.4	3.16	100	27
	PSMN2R6-30YLC	30	2.8	3.65	100	18
	PSMN3R0-30YL	30	3	4.04	100	21
	PSMN3R0-30YLD	30	3.1	4	100	14.5
	PSMN3R2-30YLC	30	3.5	4.55	100	14.2
	PSMN3R5-30YL	30	3.5	4.61	100	19
	PSMN4R0-30YL	30	4	5.25	100	17.6
	PSMN4R0-30YLD	30	4	5.5	95	9.6
	PSMN4R1-30YLC	30	4.35	5.7	92	11
	PSMN4R5-30YLC	30	4.8	6.1	84	9.6
	PSMN5R0-30YL	30	5	6.7	91	14.1
	PSMN6R0-30YL	30	6	7.87	79	11
	PSMN6R0-30YLD	30	6	8.35	66	6.7
	PSMN6R1-30YLD	30	6	8.35	66	6.4
	PSMN6R0-30YLB	30	6.5	8.1	71	9
	PSMN7R0-30YL	30	7	9.1	76	10
	PSMN7R0-30YLC	30	7.1	8.9	61	7.9
	PSMN7R5-30YLD	30	7.5	10.2	51	5.8
	PSMN9R1-30YL	30	9.1	13.6	57	8.4
	PSMN9R5-30YLC	30	9.8	12.1	44	5
	PSMN011-30YLC	30	11.6	14.5	37	4.9
	PSMN013-30YLC	30	13.6	16.9	32	4
LFPAK33 (SOT1210)	PSMN2R4-30MLD	30	2.4	3.2	70	16
	PSMN2R9-30MLC	30	2.95	3.8	70	16.7
	PSMN3R0-30MLC	30	3.15	4.05	70	16.1
	PSMN4R2-30MLD	30	4.3	5.7	70	9.2
	PSMN4R4-30MLC	30	4.65	6	70	10.6
	PSMN7R0-30MLC	30	7	9	67	8.2
	PSMN7R5-30MLD	30	7.6	10.3	57	5.8
	PSMN9R8-30MLC	30	9.8	12.4	50	5
	PSMN013-30MLC	30	13.6	16.9	39	3.7
	PSMN020-30MLC	30	18.1	27	31.8	4.6
D ² PAK (SOT404)	PSMNR90-30BL	30	1	1.4	120	118
	PSMN1R5-30BLE	30	1.5	1.85	120	228
	PSMN1R8-30BL	30	1.8	2.1	100	83
	PSMN1R6-30BL	30	1.9	2.2	100	101
	PSMN2R0-30BL	30	2.1	2.9	100	55
	PSMN2R7-30BL	30	3	3.7	100	32
	PSMN3R4-30BL	30	3.3	3.8	100	31
	PSMN3R4-30BLE	30	3.4	5	120	81
	PSMN4R3-30BL	30	4.1	5.2	100	19
	PSMN017-30BL	30	17	23.3	32	5.1
	PSMN022-30BL	30	22.6	29.6	30	4.4

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Power MOSFETs 30V – Part 2

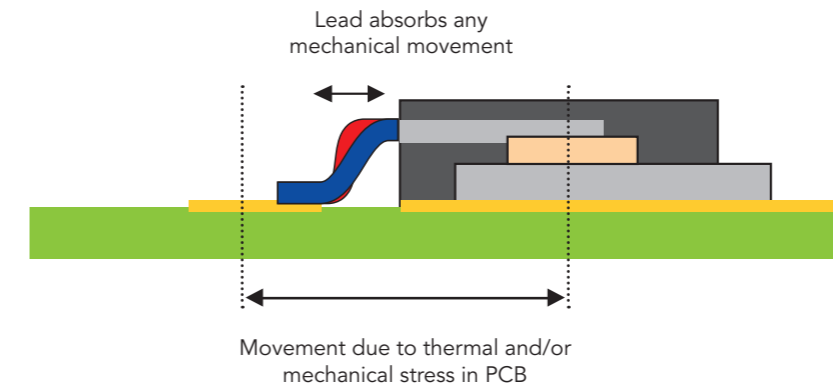
types in **bold** represent new products

Package	Type number	V _{DS} [max] (V)	R _{DS(on)} [max] @ V _{GS} = 10 V (mΩ)	R _{DS(on)} [max] @ V _{GS} = 4.5 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)
DPAK (SOT428)	PHD101NQ03LT	30	5.5		75	23
	PHD71NQ03LT	30	10		75	13.2
TO-220AB (SOT78)	PSMN1R1-30PL	30	1.3	1.6	120	118
	PSMN1R6-30PL	30	1.7	2.1	100	101
	PSMN1R8-30PL	30	1.8	2.3	100	83
	PSMN2R0-30PL	30	2.1	2.8	100	55
	PSMN2R7-30PL	30	2.7	3.6	100	32
	PSMN3R4-30PL	30	3.4	4.1	100	31
	PSMN4R3-30PL	30	4.3	6.2	100	19
	PHP36N03LT	30	17	22	43.4	18.5
	PSMN017-30PL	30	17	23.4	32	5.1
	PSMN022-30PL	30	22	34	30	4.4
IFPAK (SOT226)	PSMN1R1-30EL	30	1.3	1.6	120	118
	PSMN017-30EL	30	17	23.4	32	5.1
SO8 (SOT96-1)	PHK31NQ03LT	30	4.4	5.6	30.4	33
	PSMN005-30K	30	5.5	8		34
	PHK18NQ03LT	30	8.9	12.5	20.3	10.6
	PHK13N03LT	30	20	26	13.8	10.7
	PHK12NQ03LT	30		14	11.8	

For the most current product information go to www.nxp.com/mosfets (updated daily!)

LFPAK for mechanical and thermal ruggedness

NXP LFPAK



LFPAK pins provide compliance while allowing for thermal expansion due to temperature differences between the MOSFET and the PCB, and allowing for mechanical strain due to PCB bending and flexing

Power MOSFETs 40V

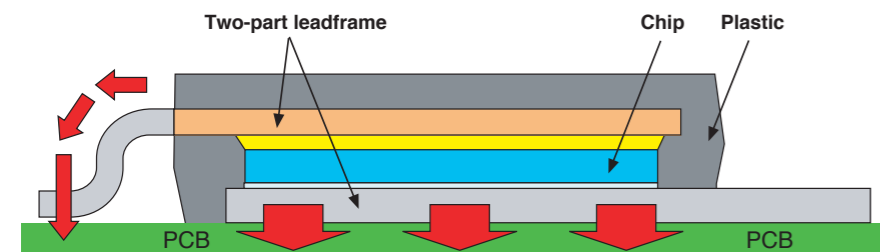
types in **bold** represent new products

Package	Type number	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	R _{DSon} [max] @ V _{GS} = 4.5 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)	
LFPAK56; Power-SO8 (SOT669)	PSMN1R0-40YLD	40	1.1	1.4	100	59	
	PSMN1R4-40YLD	40	1.4	1.85	100	45	
	PSMN1R6-40YLC	40	1.55	1.8	100	59	
	PSMN1R8-40YLC	40	1.8	2.1	100	45	
	PSMN2R6-40YS	40	2.8		100	63	
	PSMN3R3-40YS	40	3.3		100	49	
	PH4840S	40	4.1		94.5	67	
	PSMN4R0-40YS	40	4.2		100	38	
	PSMN5R8-40YS	40	5.7		90	28.8	
	PSMN8R3-40YS	40	8.6		70	20	
	PSMN014-40YS	40	14		46	12	
	D ² PAK (SOT404)	PSMN1R1-40BS	40	1.3		120	136
		PSMN2R2-40BS	40	2.2		100	130
		PSMN2R8-40BS	40	2.9		100	71
PSMN4R5-40BS		40	4.5		100	35	
PSMN8R0-40BS		40	7.6		77	21	
TO-220AB (SOT78)	PSMN1R5-40PS	40	1.6		150	136	
	PSMN1R9-40PL	40	1.7	1.94	150	230	
	PSMN2R1-40PL	40	2.2	2.6	150	168.9	
	PSMN2R2-40PS	40	2.1		100	110	
	PSMN2R8-40PS	40	2.8		100	71	
	PSMN4R5-40PS	40	4.6		100	35	
	PSMN8R0-40PS	40	7.6		77	17	
iPAK (SOT226)	PSMN1R5-40ES	40	1.6		120	136	

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Power-SO8 (LFPAK) Design

- ▶ Low thermal resistance
- ▶ Low electrical resistance
- ▶ Low inductance



Power MOSFETs 55 - 60V

Package	Type number	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)	
LFPAK56; Power-SO8 (SOT669)	PH955L	55	8.3	62.5	42	
	PSMN5R5-60YS	60	5.2	100	56	
	PSMN7R0-60YS	60	6.4	89	45	
	PSMN8R5-60YS	60	8	76	39	
	PSMN012-60YS	60	11.1	59	28.4	
	PSMN017-60YS	60	15.7	44	20	
	PSMN030-60YS	60	24.7	29	13	
	LFPAK33 (SOT1210)	PSMN011-60ML	60	11.3	61	37.2
PSMN011-60MS		60	11.3	61	23	
D ² PAK (SOT404)	PHB191N006LT	55	3.7	75	95.6	
	PHB21N06LT	55	70	19		
	PHB20N06T	55	75	20.3	11	
	PSMN1R7-60BS	60	2	120	137	
	PSMN3R0-60BS	60	3.2	100	130	
	PSMN004-60B	60	3.6	75	168	
	PSMN4R6-60BS	60	4.4	100	70.8	
	PSMN7R6-60BS	60	7.8	92	38.7	
	PSMN015-60BS	60	14.8	50	20.9	
	PHB32N06LT	60	37	34	17	
DPAK (SOT428)	PHD20N06T	55	77	18	11	
TO-220AB (SOT78)	PHP191N006LT	55	3.7	75	95.6	
	PHP20N06T	55	75	20.3	11	
	PSMN2R0-60PS	60	2.2	120	137	
	PSMN2R5-60PL	60	2.6	150	223	
	PSMN2R6-60PS	60	2.6	150	140	
	PSMN3R0-60PS	60	3	100	130	
	PSMN3R3-60PL	60	3.4	130	175	
	PSMN3R9-60PS	60	3.9	130	103	
	PSMN4R2-60PL	60	3.9	130	151	
	PSMN4R6-60PS	60	4.6	100	70.8	
	PSMN7R6-60PS	60	7.8	92	38.7	
	PSMN015-60PS	60	14.8	50	20.9	
	TO-220F (SOT186A)	PSMN3R9-60XS	60	4	75	103
	iPAK (SOT226)	PSMN2R0-60ES	60	2.2	120	137
PSMN3R0-60ES		60	3	100	130	

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Power MOSFETs 75 - 80V

Package	Type number	V _{DS} [max] (V)	R _{DS(on)} [max] @ V _{GS} = 10 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)	
LFPAK56; Power-SO8 (SOT669)	PSMN8R2-80YS	80	8.5	82	55	
	PSMN011-80YS	80	11	67	45	
	PSMN013-80YS	80	12.9	60	37	
	PSMN018-80YS	80	18	45	26	
	PSMN026-80YS	80	27.5	34	20	
	PSMN041-80YL	80	41	25	21.9	
	PSMN045-80YS	80	45	24	12.5	
	PSMN005-75B	75	5	75	165	
D ² PAK (SOT404)	PSMN008-75B	75	8.5	75	122.8	
	PHB110NQ08T	75	9	75	113.1	
	PHB29N08T	75		27	19	
	PSMN2R8-80BS	80	3	120	139	
	PSMN3R3-80BS	80	3.5	120	111	
	PSMN4R4-80BS	80	4.5	100	125	
	PSMN5R0-80BS	80	5.1	100	101	
	PSMN6R5-80BS	80	6.9	100	71	
	PSMN8R7-80BS	80	8.7	90	52	
	PSMN012-80BS	80	11	74	36	
	PSMN017-80BS	80	17	50	26	
	PSMN050-80BS	80	46	22	11	
	TO-220AB (SOT78)	PSMN005-75P	75	5	75	165
		PHP79NQ08LT	75	16	73	30
PHP29N08T		75		27	19	
PSMN3R3-80PS		80	3.3	120	139	
PSMN3R5-80PS		80	3.5	120	139	
PSMN4R4-80PS		80	4.1	100	112	
PSMN4R3-80PS		80	4.3	120	111	
PSMN5R0-80PS		80	4.7	100	87	
PSMN6R5-80PS		80	6.9	100	71	
PSMN8R7-80PS		80	8.7	90	52	
PSMN012-80PS		80	11	74	36	
PSMN017-80PS		80	17	50	26	
I ² PAK (SOT226)		PSMN3R3-80ES	80	3.3	120	139
		PSMN3R5-80ES	80	3.5	120	139
	PSMN4R3-80ES	80	4.3	120	111	

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Power MOSFETs 100V

Package	Type number	V _{DS} [max] (V)	R _{DS(on)} [max] @ V _{GS} = 10 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)	
LFPAK56; Power-SO8 (SOT669)	PSMN012-100YS	100	12	60	64	
	PSMN013-100YSE	100	13	82	75	
	PSMN016-100YS	100	16.3	51	54	
	PSMN020-100YS	100	20.5	43	41	
	PH20100S	100	23	34.3	39	
	PSMN028-100YS	100	27.5	42	33	
	PSMN038-100YL	100	37.5	30	21.6	
	PSMN039-100YS	100	39.5	28.1	23	
	PSMN069-100YS	100	72.4	17	14	
	LFPAK33 (SOT1210)	PSMN040-100MSE	100	36.6	30	30
PSMN075-100MSE		100	71	18	16.4	
D ² PAK (SOT404)	PSMN3R8-100BS	100	3.9	120	170	
	PSMN4R8-100BSE	100	4.8	120	196	
	PSMN5R6-100BS	100	5.6	100	141	
	PSMN7R0-100BS	100	6.8	100	125	
	PSMN7R6-100BSE	100	7.6	75	128	
	PSMN009-100B	100	8.8	75	156	
	PSMN9R5-100BS	100	9.6	89	82	
	PSMN013-100BS	100	13.9	68	59	
	PSMN015-100B	100	15	75	90	
	PSMN016-100BS	100	16	57	49	
	PHB45NQ10T	100	25	47	61	
	PSMN027-100BS	100	26.8	37	30	
	PHB47NQ10T	100	28	47	66	
	PSMN034-100BS	100	34.5	32	23.8	
	PHB27NQ10T	100	50	28	30	
	PHB18NQ10T	100	90	18	21	
	DPAK (SOT428)	PSMN025-100D	100	25	47	61
	TO-220AB (SOT78)	PSMN4R3-100PS	100	4.3	120	170
PSMN5R0-100PS		100	5	120	170	
PSMN5R6-100PS		100	5.6	100	141	
PSMN7R0-100PS		100	6.8	100	125	
PSMN8R5-100PS		100	8.5	100	111	
PSMN009-100P		100	8.8	75	156	
PSMN9R5-100PS		100	9.6	89	82	
PSMN013-100PS		100	13.9	68	59	
PSMN015-100P		100	15	75	90	
PSMN016-100PS		100	16	57	49	
PHP45NQ10T		100	25	47	61	
PSMN027-100PS		100	26.8	37	30	
PSMN034-100PS		100	34.5	32	23.8	
PHP18NQ10T		100	90	18	21	
TO-220F (SOT186A)	PSMN4R6-100XS	100	4.6	70.4	153	
	PSMN5R0-100XS	100	5	67.5	153	
	PSMN5R6-100XS	100	5.6	61.8	145	
	PSMN7R0-100XS	100	6.8	55	121	
	PSMN8R5-100XS	100	8.5	49	100	
	PSMN9R5-100XS	100	9.6	44.2	81.5	
	PSMN013-100XS	100	13.9	35.2	57.5	
	PSMN016-100XS	100	16	32.1	46.2	
	PSMN027-100XS	100	26.8	23.4	30	
	PSMN4R3-100ES	100	4.3	120	170	
I ² PAK (SOT226)	PSMN5R0-100ES	100	5	120	170	
	PSMN7R0-100ES	100	6.8	100	125	
	PSMN8R5-100ES	100	8.5	100	111	
	PSMN013-100ES	100	13.9	68	59	
SC-73 (SOT223)	PHT6NQ10T	100	90	6.5	21	
	PHT4NQ10T	100	250	3.5	7.4	
SO8 (SOT96-1)	PSMN038-100K	100	38		43	
	PHKD3NQ10T	100	90	3	21	

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Power MOSFETs 105 - 150 V

Package	Type number	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)	
LFPAK56; Power-SO8 (SOT669)	PSMN059-150Y	150	59	43	27.9	
	PSMN030-150B	150	30	55.5	98	
D ² PAK (SOT404)	PSMN035-150B	150	35	50	79	
	PHB45NQ15T	150	42	45.1	32	
	PSMN063-150D	150	63	29	55	
TO-220AB (SOT78)	PHP45NQ11T	105	25	47	60	
	PSMN015-110P	110	15	75	90	
	PHP27NQ11T	110	50	27.6	30	
	PHP23NQ11T	110	70	23	22	
	PHP18NQ11T	110	90	18	21	
	PSMN6R3-120PS	120	6.7	70	207.1	
	PSMN7R8-120PS	120	7.9	70	167	
	PSMN030-150P	150	30	55.5	98	
	PSMN035-150P	150	35	50	79	
	PHP30NQ15T	150	63	29	55	
	PHP28NQ15T	150	65	28.5	24	
	I ² PAK (SOT226)	PSMN6R3-120ES	120	6.7	70	207.1
		PSMN7R8-120ES	120	7.9	70	167
	SO8 (SOT96-1)	PHK5NQ15T	150	75	5	29
PSMN085-150K		150	85	-	40	

For the most current product information go to www.nxp.com/mosfets (updated daily!)

P-channel

Package	Type number	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	R _{DSon} [max] @ V _{GS} = 4.5 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)
SO8 (SOT96-1)	PMK30EP	-30	19	30	-14.9	50
	PMK35EP	-30	19	35	-14.9	42
	PHP225	-30	250	400	-	10
	PMK50XP	-20	-	50	-7.9	10
	PHK04P02T	-16	-	120	-4.66	7.2

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Multi-chip

Package	Type number	Channel type	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)
SO8 (SOT96-1)	PHP225	P	-30	250	-	10
	PHKD6N02LT	N	20	-	10.9	15.3
	PHKD13N03LT	N	30	20	10.4	10.7
	PHN203	N	30	30	6.3	14.6
	PHN210T	N	30	100	3.4	6
	PHC21025	N/P	30	250	-	10
	PHKD3NQ10T	N	100	90	3	21
	PHC2300	N/P	300	6000	-	6.24

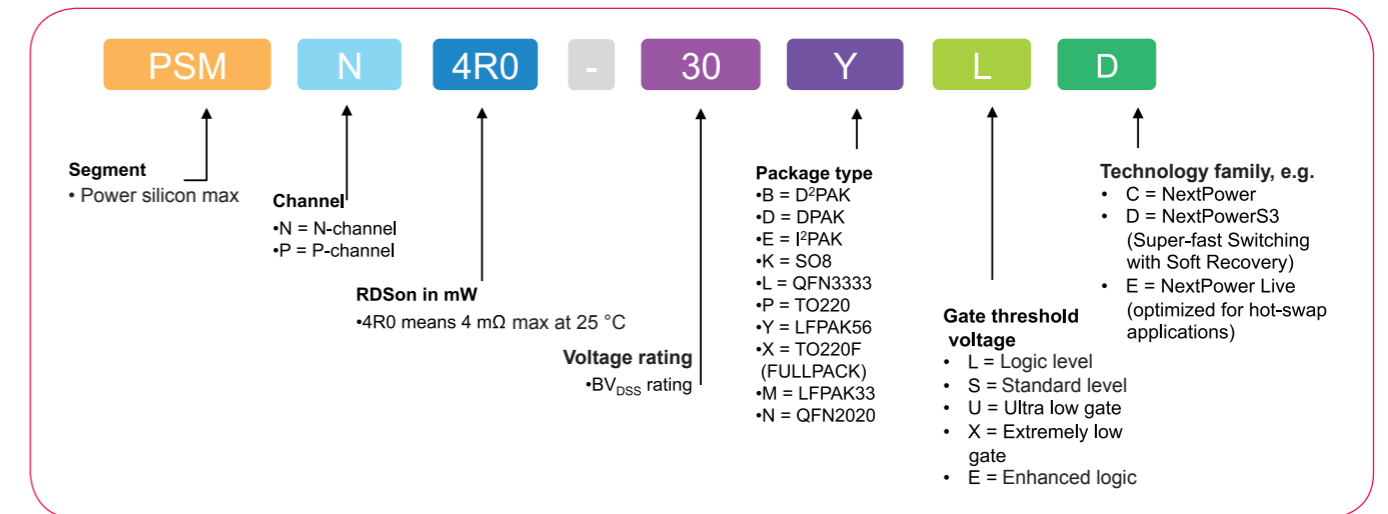
For the most current product information go to www.nxp.com/mosfets (updated daily!)

Power MOSFETs 200 V

Package	Type number	V _{DS} [max] (V)	R _{DSon} [max] @ V _{GS} = 10 V (mΩ)	I _D [max] (A)	Q _{G(tot)} [typ] (nC)
LFPAK56; Power-SO8 (SOT669)	PSMN102-200Y	200	102	21.5	30.7
	PSMN057-200B	200	57	39	96
D ² PAK (SOT404)	PSMN070-200B	200	70	35	77
	PHB33NQ20T	200	77	32.7	32.2
	PHB20NQ20T	200	130	20	65
DPAK (SOT428)	PSMN130-200D	200	130	20	65
	PHD9NQ20T	200	400	8.7	24
TO-220AB (SOT78)	PSMN057-200P	200	57	39	96
	PSMN070-200P	200	70	35	77
	PHP33NQ20T	200	77	32.7	32.2
	PHP20NQ20T	200	130	20	65
	PHP9NQ20T	200	400	8.7	24
SO8 (SOT96-1)	PSMN165-200K	200	165	-	40

For the most current product information go to www.nxp.com/mosfets (updated daily!)

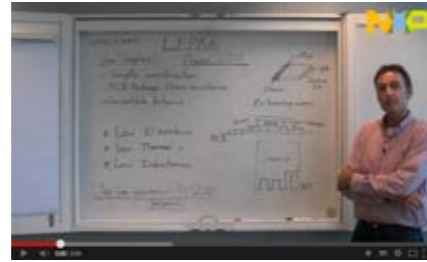
PSMN part numbering



Quick learning videos



Introduction to clip-bonding technology
www.nxp.com/quicklearning1



Introducing NXP LPAK
www.nxp.com/quicklearning5



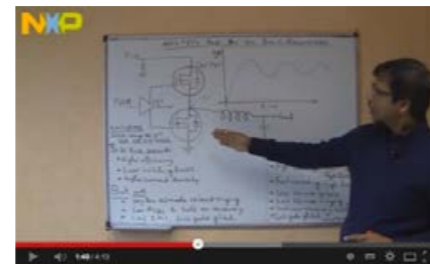
LPAK Power-SO8 vs. DPAK
www.nxp.com/quicklearning18



NextPower Cordless MOSFETs for battery-powered tools
www.nxp.com/quicklearning28



Next Power Live! MOSFETs for HOT SWAP and Power over Ethernet
www.nxp.com/quicklearning29



NextPowerS3 MOSFETs for DC/DC buck regulators
www.nxp.com/quicklearning32



Reverse recovery and diode leakage in SMPS
www.nxp.com/quicklearning33



Power MOSFET operation in Linear Mode
www.nxp.com/quicklearning34



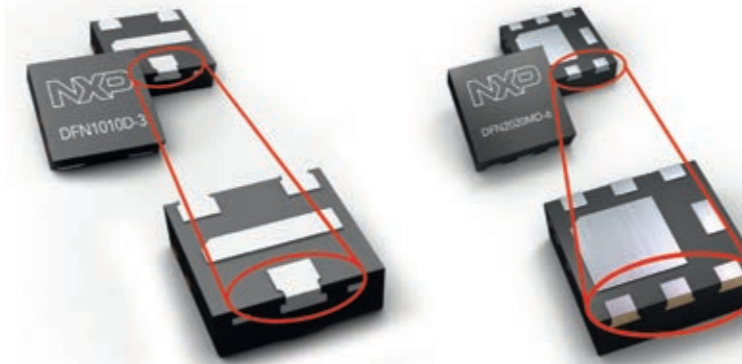
Single-shot avalanche ruggedness
www.nxp.com/quicklearning35



MOSFETs for Power-over-Ethernet (PoE) PSE applications
www.nxp.com/quicklearning36

Small-signal MOSFETs for automotive

DFN1010 and DFN2020 with solderable side pads



- ▶ High-quality solder connections
- ▶ No complete wetting on side pad
- ▶ Reduction of production costs through optical visual solder inspection

Comparison of solder capability

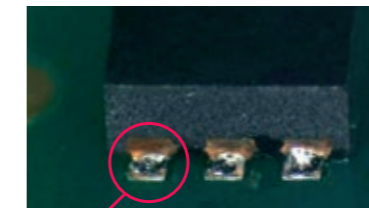
NXP package

100% solderable side pads



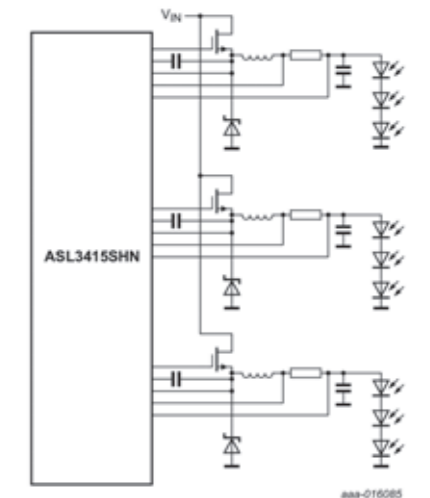
100% solder wetting solution with new 2 x 2 mm leadless package DFN2020MD-6

Packages from other suppliers



- ▶ Quality of solder connection difficult to determine
- ▶ Very limited options for optical solder inspection

Reference design for LED lighting



In the spotlight

PMPB85ENEA - Automotive-compliant 60 V N-channel MOSFET with I_D max of 4.4 A in DFN2020MD-6 (SOT1220)

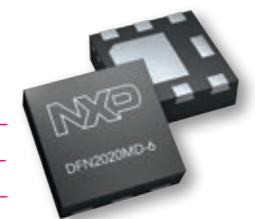
60 V N-channel with $R_{DS(on)}$ of typ. 72m Ω @ $V_{GS} = 10$ V

Small and leadless ultrathin SMD plastic package: 2.0 x 2.0 x 0.65 mm

Exposed drain pad for excellent thermal conduction

ESD protection to 2 kV HBM

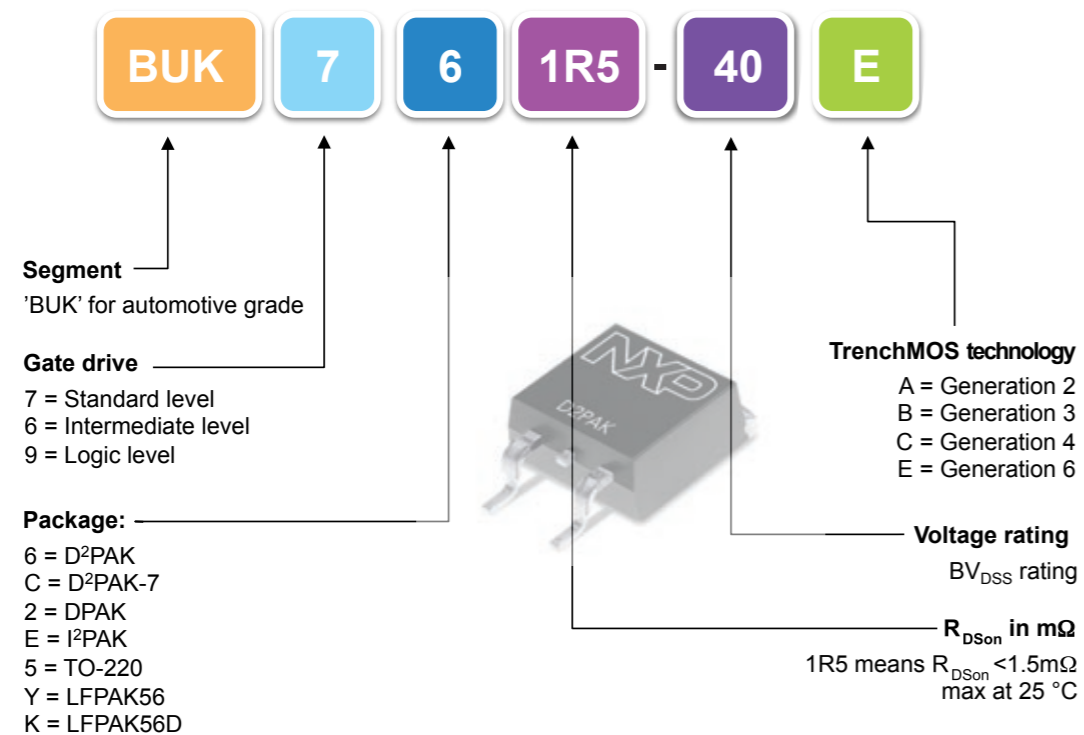
AEC-Q101 qualified



4 steps to select an automotive MOSFET

- 1 Select a voltage, e.g. 40 V
- 2 Select a package, e.g D²PAK
- 3 Choose an R_{DSon} from our extensive range
- 4 Select a 'BUK' type and visit www.nxp.com/automotivemosfets to download datasheets and models, and order samples

Automotive-grade MOSFET product numbering



High-performance automotive MOSFETs

MOSFET package selection

Through-hole

TO220
▶ Industry standard
▶ 120 A



I²PAK
▶ Industry standard
▶ 120 A



Surface-mount

Premium performance

D²PAK-7
▶ Highest performance
▶ 190 A



D²PAK
▶ Industry standard
▶ 120 A

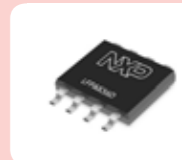


Space saving

LFPAK56
▶ PowerSO8
▶ 100 A



LFPAK56D
▶ Dual Power-SO8
▶ 40 A per channel



DPAK
▶ Industry standard
▶ Proven reliability
▶ 100 A



SOT223
▶ Industry standard
▶ Proven reliability

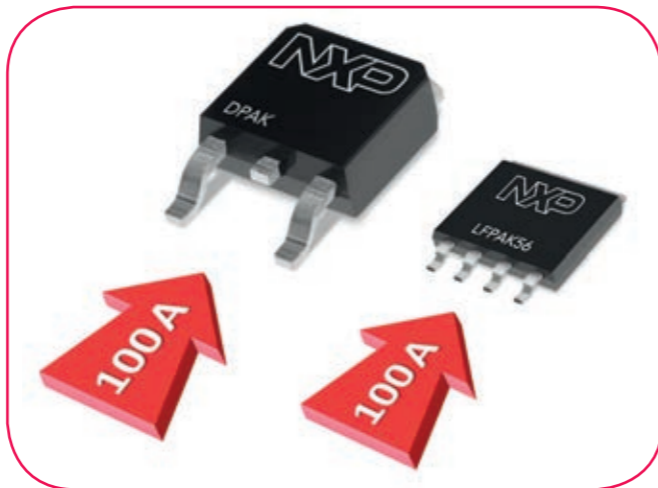


All packages are automotive AEC-Q101 qualified to 175 °C and RoHs compliant

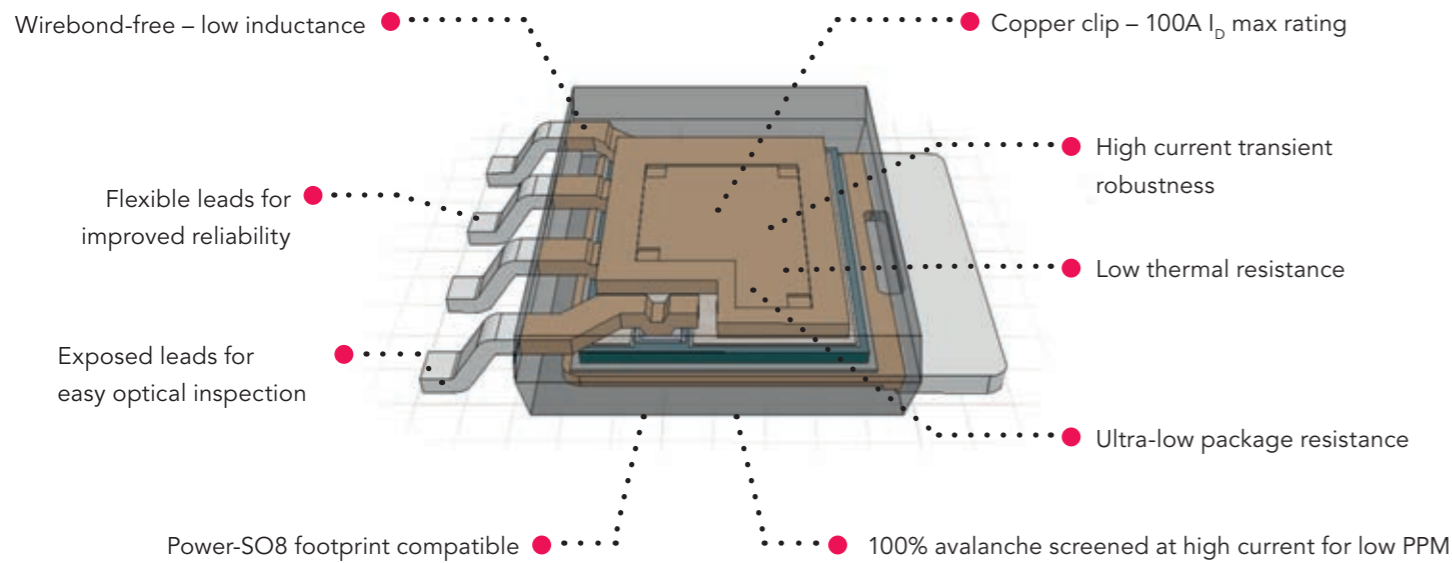
LFPAK56

LFPAK56 – the Power-SO8 that packs a punch

Providing a true alternative to DPAK, NXP's LFPAK56 portfolio gives industry-leading performance in a truly innovative, automotive-grade package. Saving a considerable amount of space compared to traditional DPAK solutions, the LFPAK56 offers designers flexibility and reliability without compromising thermal performance.



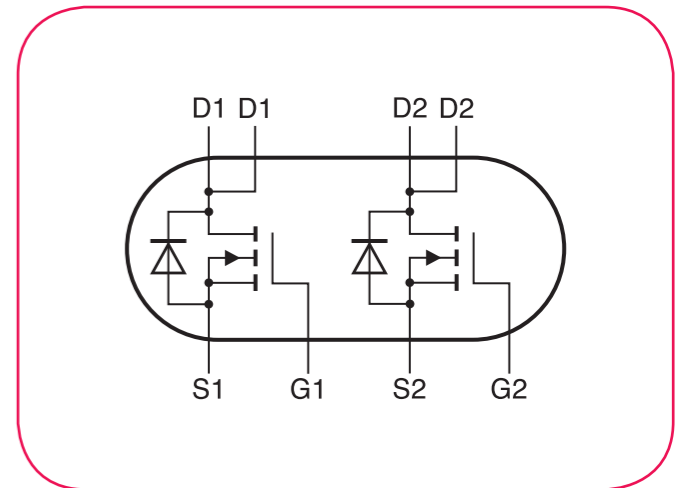
Fully AEC-Q101 qualified to 175 °C



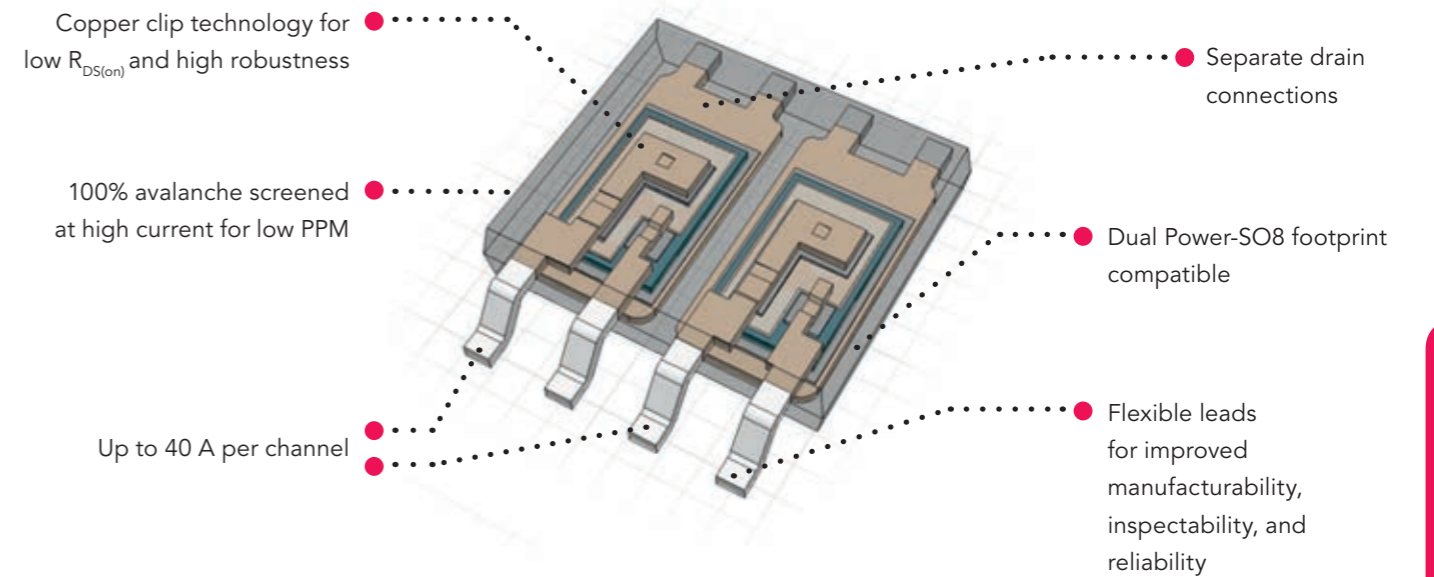
LFPAK56D

LFPAK56D – the ultimate dual MOSFET

Packing even more into the Power-SO8 footprint, the LFPAK56D fits two MOSFETs into one robust package without compromising on performance. NXP's cutting-edge copper-clip technology allows for exceptional current handling, ultra-low package resistance, and supreme robustness and reliability. Perfect for situations where space is at a premium, the LFPAK56D offers power performance.



Fully AEC-Q101 qualified to 175 °C



POWERTRAIN

- ▶ Engine management
- ▶ Gearbox / clutch
- ▶ Engine fan
- ▶ Fuel / water pump
- ▶ Auxiliary valves



CHASSIS & SAFETY

- ▶ Vertical stability (ESP)
- ▶ Braking systems (ABS)
- ▶ Airbag
- ▶ Electric Parking Brake (EPB)



BODY & SECURITY

- ▶ Body control module
- ▶ Climate control (HVAC)
- ▶ Wiper systems
- ▶ Electric windows
- ▶ Electric mirrors
- ▶ Electric seats
- ▶ Sunroof
- ▶ Lighting

LFPAK56D footprint comparison

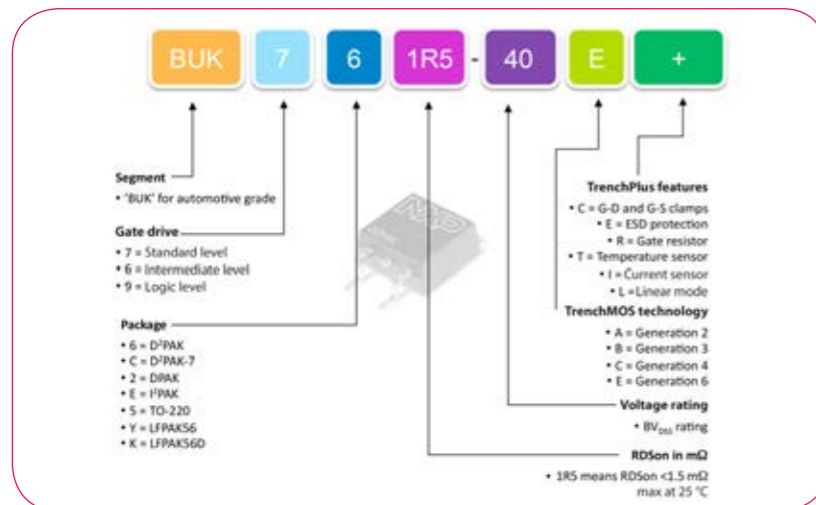
Product	Pad layout	Footprint area
		31 mm ²
		62 mm ²
		140 mm ²

30 V N-channel automotive TrenchMOS

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _D [max] @ 25 °C [A]	R _{th(j-mb)} [K/W]
LFPAK56; Power-SO8 (SOT669)	BUK9Y07-30B	30	6	7	75	1.42
	BUK7Y07-30B	30	7		75	1.42
	BUK9Y11-30B	30	9	11	59	2
	BUK7Y10-30B	30	10		67	1.76
	BUK9Y22-30B	30	19	22	37.7	2.53
	BUK7Y20-30B	30	20		39.5	2.53
LFPAK56D (SOT1205)	BUK7K5R1-30E	30			40	2.21
	BUK7K5R6-30E	30			40	2.36
D ² PAK (SOT404)	BUK962R8-30B	30	2.4	2.8	75	0.5
	BUK762R7-30B	30	2.7		75	0.5
	BUK763R4-30B	30	3.4		75	0.59
	BUK9605-30A	30	4.6	5	75	0.65
	BUK9607-30B	30	5	7	75	0.95
	BUK7607-30B	30	7		75	0.95
DPAK (SOT428)	BUK9214-30A	30	12	14	63	1.4
	BUK6213-30A	30	13		55	1.4
TO-220AB (SOT78A)	BUK952R8-30B	30	2.4	2.8	75	0.5
	BUK752R7-30B	30	2.7		75	0.5
	BUK9507-30B	30	5	7	75	0.95
	BUK7507-30B	30	7		75	0.95
I ² PAK (SOT226)	BUK7E2R7-30B	30	2.7		75	0.5
	BUK9E04-30B	30	3	4	75	0.59

For the most current product information go to www.nxp.com/mosfets (updated daily!)

Automotive TrenchMOS part numbering







40 V N-channel automotive TrenchMOS – Part I

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _D [max] @ 25 °C [A]	R _{th(j-mb)} [K/W]	
LFPAK56; Power-SO8 (SOT669)	BUK9Y3R0-40E	40	2.5	3	100	0.77	
	BUK7Y3R5-40E	40	3.5		100	0.9	
	BUK9Y3R5-40E	40	3.6	3.8	100	0.9	
	BUK9Y4R4-40E	40	3.7	4.4	100	1.02	
	BUK7Y4R4-40E	40	4.4		100	1.02	
	BUK9Y7R6-40E	40	6	7.6	79	1.58	
	BUK7Y7R6-40E	40	7.6		79	1.58	
	BUK9Y09-40B	40	8	9	75	1.42	
	BUK7Y08-40B	40	8		75	1.42	
	BUK9Y12-40E	40	10	12	52	2.31	
	BUK9Y14-40B	40	11	14	56	1.8	
	BUK7Y12-40E	40	12		52	2.31	
	BUK7Y13-40B	40	13		58	1.8	
	BUK9Y21-40E	40	17	21	33	3.33	
	BUK7Y21-40E	40	21		33	3.33	
	BUK9Y27-40B	40	24	27	34	2.53	
	BUK9Y29-40E	40	25	29	25	4.03	
	BUK7Y25-40B	40	25		35.3	2.53	
	LFPAK56D (SOT1205)	BUK7K6R2-40E	40	5.8			2.21
		BUK9K6R2-40E	40	6	6.2	40	2.21
BUK9K6R8-40E		40	6.1	7.2	40	2.36	
BUK7K6R8-40E		40	6.8			2.36	
BUK9K8R7-40E		40	8	9.4	30	2.84	
BUK7K8R7-40E		40	8.5			2.84	
BUK9K18-40E		40	16	19.5	30	3.96	
BUK7K18-40E		40	19		24.2	3.96	
BUK9K25-40E		40	24	29	18.2	4.68	
BUK7K25-40E		40	25			4.68	
D ² PAK (SOT404)		BUK961R6-40E	40	1.4	1.6	120	0.43
		BUK762R0-40E	40	2		120	0.51
		BUK962R6-40E	40	2.4	2.8	100	0.57
		BUK762R6-40E	40	2.6		100	0.57
		BUK963R1-40E	40	2.7	3.1	100	0.64
		BUK963R2-40B	40	2.8	3.2	100	0.5
		BUK762R9-40E	40	2.9		100	0.64
		BUK763R1-40B	40	3.1		75	0.5
		BUK964R1-40E	40	3.5	4.1	75	0.82
		BUK9604-40A	40	4	4.4	75	0.5

For the most current product information go to www.nxp.com/mosfets (updated daily!)




MOSFETs

40V N-channel automotive TrenchMOS – Part 2

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _b [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]
D ² PAK (SOT404) 	BUK964R4-40B	40	4	4.4	75	0.59
	BUK764R0-40E	40	4		75	0.82
	BUK965R4-40E	40	4.4	5.4	75	1.09
	BUK7604-40A	40	4.5		75	0.5
	BUK765R3-40E	40	4.9		75	1.09
	BUK9606-40B	40	5	6.4	75	0.74
	BUK765R2-40B	40	5.2		75	0.74
	BUK9609-40B	40	7	9	75	0.95
	BUK768R1-40E	40	7.2		75	1.56
	BUK7608-40B	40	8		75	0.95
	BUK761R6-40E	40	1.57		120	0.43
	BUK761R7-40E	40	1.6		120	0.46
	DPAK (SOT428) 	BUK9209-40B	40	7	9	75
BUK7208-40B		40	8		75	0.95
TO-220AB (SOT78A) 	BUK751R8-40E	40	1.8		120	0.43
	BUK752R3-40E	40	2.3		120	0.51
	BUK953R2-40B	40	2.8	3.2	100	0.5
	BUK753R1-40E	40	3.1		100	0.64
	BUK9504-40A	40	4	4.4	75	0.5
	BUK954R4-40B	40	4	4.4	75	0.59
	BUK754R3-40B	40	4.3		75	0.59
	BUK9506-40B	40	5	6.4	75	0.74
	BUK755R2-40B	40	5.2		75	0.74
	BUK9509-40B	40	7	9	75	0.95
	BUK758R3-40E	40	7.4		75	1.56
I ² PAK (SOT226) 	BUK7E1R8-40E	40	1.8		120	0.43
	BUK7E1R9-40E	40	1.9		120	0.46
	BUK7E2R3-40E	40	2.3		120	0.51
	BUK9E3R2-40B	40	2.8	3.2	100	0.5
	BUK7E3R1-40E	40	3.1		100	0.64
	BUK9E04-40A	40	4	4.4	75	0.5
	BUK9E4R4-40B	40	4	4.4	75	0.59
	BUK7E04-40A	40	4.5		75	0.5
	BUK7E8R3-40E	40	7.4		75	1.56




For the most current product information go to www.nxp.com/mosfets (updated daily!)

55 - 60V N-channel automotive TrenchMOS – Part I

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _b [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]	
L ² PAK56; Power-SO8 (SOT669) 	BUK9Y12-55B	55	11	12	61.8	1.42	
	BUK7Y12-55B	55	12		61.8	1.42	
	BUK9Y19-55B	55	17.3	19	46	1.8	
	BUK7Y18-55B	55	18		47.4	1.76	
	BUK9Y40-55B	55	36	40	26	2.5	
	BUK9Y4R8-60E	60	4.1	4.8	100	0.63	
	BUK7Y4R8-60E	60	4.8		100	0.63	
	BUK9Y6R0-60E	60	5.2	6	100	0.77	
	BUK9Y7R2-60E	60	5.6	7.2	100	0.9	
	BUK7Y6R0-60E	60	6		100	0.77	
	BUK7Y7R2-60E	60	7.2		100	0.9	
	BUK9Y8R7-60E	60	7.5	8.7	86	1.02	
	BUK7Y8R7-60E	60	8.7		87	1.02	
	BUK9Y15-60E	60	13	15	53	1.58	
	BUK7Y15-60E	60	15		53	1.59	
	BUK9Y25-60E	60	21.5	25	34	2.31	
	BUK7Y25-60E	60	25		34	2.31	
	BUK9Y43-60E	60	38	43	22	3.33	
	BUK7Y43-60E	60	43		22	3.33	
	BUK9Y59-60E	60	52	59	16.7	4.03	
	BUK7Y59-60E	60	59		17	4.03	
	L ² PAK56D (SOT1205) 	BUK7K12-60E	60	9.3			2.21
		BUK9K12-60E	60	10.7	11.5	35	2.21
BUK7K17-60E		60	14			2.84	
BUK9K17-60E		60	15.6	17	26	2.84	
BUK7K35-60E		60	30		20.7	3.96	
BUK9K35-60E		60	32	35	22	3.96	
BUK7K52-60E		60	45		15.4	4.68	
BUK9K52-60E		60	49	55	16	4.68	
D ² PAK (SOT404) 		BUK964R2-55B	55	3.7	4.2	75	0.5
		BUK764R0-55B	55	4		75	0.5
	BUK9606-55B	55	5.4	6	75	0.58	
	BUK9606-55A	55	5.8	6.3	75	0.5	
	BUK7606-55B	55	6		75	0.59	
	BUK7606-55A	55	6.3		75	0.5	
	BUK9608-55B	55	7	8.4	75	0.74	
	BUK7607-55B	55	7.1		75	0.74	
	BUK9608-55A	55	7.5	8	75	0.59	
	BUK7608-55A	55	8		75	0.59	
BUK9612-55B	55	10	12	75	0.95		





For the most current product information go to www.nxp.com/mosfets (updated daily!)

55 - 60 V N-channel automotive TrenchMOS – Part 2

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _b [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]
D ² PAK (SOT404) 	BUK7610-55AL	55	10		75	0.5
	BUK7611-55A	55	11		75	0.9
	BUK7611-55B	55	11		75	0.95
	BUK9614-55A	55	13	14	73	1
	BUK7614-55A	55	14		73	0.9
	BUK9616-55A	55	15	16	66	
	BUK9620-55A	55	18	20	54	1.2
	BUK7620-55A	55	20		54	1.2
	BUK9624-55A	55	21.7	24	46	1.4
	BUK7624-55A	55	24		47	
	BUK9628-55A	55	25	28	42	1.5
	BUK7628-55A	55	28		42	
	BUK9635-55A	55	32	35	34	1.8
	BUK7635-55A	55	35		35	1.7
	BUK9675-55A	55	68	75	20	2.4
	BUK7675-55A	55	75		20.3	2.4
	BUK962R5-60E	60	2.3	2.5	120	0.43
	BUK762R4-60E	60	2.4		120	0.43
	BUK962R8-60E	60	2.5	2.8	120	0.46
	BUK762R6-60E	60	2.6		120	0.46
	BUK963R3-60E	60	3	3.3	120	0.51
	BUK763R1-60E	60	3.1		120	0.51
	BUK964R2-60E	60	3.9	4.2	100	0.57
	BUK763R9-60E	60	3.9		100	0.57
	BUK964R8-60E	60	4.4	4.8	100	0.64
	BUK764R4-60E	60	4.5		100	0.64
	BUK966R5-60E	60	5.9	6.5	75	0.82
	BUK766R0-60E	60	6		75	0.82
	BUK969R0-60E	60	8	9	75	1.09
	BUK768R3-60E	60	8.3		75	1.09
BUK9614-60E	60	12.8	14	56	1.56	
BUK7613-60E	60	13		58	1.56	
D ² PAK-7 (SOT427) 	BUK9C10-55BIT	55	9	10	75	0.78
DPAK (SOT428) 	BUK9212-55B	55	10	12	75	0.95
	BUK7210-55B	55	10		75	0.95
	BUK7212-55B	55	12		75	0.95
	BUK9215-55A	55	13.6	15	62	1.3
	BUK7215-55A	55	15		62	1.3
	BUK9219-55A	55	17.6	19	55	1.3
	BUK7219-55A	55	19		55	1.3
	BUK9222-55A	55	20	22	48	1.5
	BUK9225-55A	55	22	25	43	1.6
	BUK7222-55A	55	22		48	1.5



For the most current product information go to www.nxp.com/mosfets (updated daily!)

55 - 60 V N-channel automotive TrenchMOS – Part 3

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _b [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]
DPAK (SOT428) 	BUK7230-55A	55	30		38	1.7
	BUK9237-55A	55	33	37	32	1.94
	BUK7237-55A	55	37		32.3	1.9
	BUK9245-55A	55	40	45	28	2.1
	BUK9277-55A	55	69	77	18	2.93
	BUK7277-55A	55	77		18	2.9
	BUK92150-55A	55	125	140	11	4.1
	BUK72150-55A	55	150		11	4.1
TO-220AB (SOT78A) 	BUK954R2-55B	55	3.7	4.2	75	0.5
	BUK754R0-55B	55	4		75	0.5
	BUK7506-55A	55	6.3		75	0.5
	BUK9508-55B	55	7	8.4	75	0.74
	BUK7507-55B	55	7.1		75	0.74
	BUK7508-55A	55	8		75	0.59
	BUK7509-55A	55	9		75	0.71
	BUK9511-55A	55	10	11	75	0.9
	BUK9512-55B	55	10	12	75	0.95
	BUK7511-55B	55	11		75	0.95
	BUK9514-55A	55	13	14	73	1
	BUK9518-55A	55	16	18	61	1.1
	BUK7516-55A	55	16		65.7	1.1
	BUK7520-55A	55	20		54	1.2
	BUK9524-55A	55	21.7	24	46	1.4
	BUK7528-55A	55	28		42	1.5
	BUK9535-55A	55	32	35	34	1.8
	BUK7535-55A	55	35		35	1.7
	BUK9575-55A	55	68	75	20	2.4
	BUK7575-55A	55	75		20.3	2.4
BUK953R5-60E	60	3.4	3.7	120	0.51	
BUK954R8-60E	60	4.5	4.9	100	0.64	
FPAK (SOT226) 	BUK9E06-55B	55	5.4	6	75	0.58
	BUK9E06-55A	55	5.8	6.3	75	0.5
	BUK9E08-55B	55	7	8.4	75	0.74
	BUK7E07-55B	55	7.1		75	0.74
	BUK7E2R6-60E	60	2.6		120	0.43
	BUK7E3R5-60E	60	3.5		120	0.51
SC-73 (SOT223) 	BUK7E4R6-60E	60	4.6		100	0.64
	BUK7E13-60E	60	13		58	1.56
	BUK9832-55A	55	29	32	12	
	BUK9880-55A	55	73	80	7	
	BUK7880-55A	55	80		7	
	BUK98150-55A	55	137	150	5.5	
BUK78150-55A	55	150		5.5		



For the most current product information go to www.nxp.com/mosfets (updated daily!)

75 - 80 V N-channel automotive TrenchMOS – Part 1

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _D [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]
LFPAK56; Power-SO8 (SOT669) 	BUK9Y19-75B	75	18	19	48.2	1.42
	BUK7Y18-75B	75	18		49	1.42
	BUK9Y30-75B	75	28	30	34	1.8
	BUK7Y28-75B	75	28		35.5	1.76
	BUK9Y58-75B	75	53	58	20.73	2.53
	BUK7Y7R8-80E	80	7.8		100	0.63
	BUK9Y8R5-80E	80	8	8.5	100	0.63
	BUK7Y9R9-80E	80	9.9		89	0.77
	BUK9Y11-80E	80	10	11	84	0.77
	BUK9Y14-80E	80	14	15	62	1.02
	BUK7Y14-80E	80	14		65	1.02
	BUK9Y25-80E	80	25	27	37	1.58
	BUK7Y25-80E	80	25		39	1.58
	BUK9Y41-80E	80	41	45	24	2.33
	BUK7Y41-80E	80	41		25	2.31
	BUK9Y72-80E	80	72	78	15	3.33
	BUK7Y72-80E	80	72		16	3.33
	BUK9Y107-80E	80	98	107	11.8	4.03
	BUK7Y98-80E	80	98		12.3	4.03
	D ² PAK (SOT404) 	BUK9606-75B	75	5.5	6.1	75
BUK7606-75B		75	5.6		75	0.5
BUK9609-75A		75	8.5	9	75	0.65
BUK7609-75A		75	9		75	0.65
BUK7613-75B		75	13		75	0.95
BUK9616-75B		75	14	16.4	67	0.95
BUK9623-75A		75	22	23	53	1.1
BUK7623-75A		75	23		53	1.1
BUK763R8-80E		80	3.8		120	0.43
BUK964R2-80E		80	4	4.2	120	0.43
BUK764R2-80E		80	4.2		120	0.46
BUK964R7-80E		80	4.5	4.7	120	0.46
BUK769R6-80E		80	9.6		75	0.82
BUK9611-80E		80	10	11	75	0.82

For the most current product information go to www.nxp.com/mosfets (updated daily!)




75 - 80 V N-channel automotive TrenchMOS – Part 2

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _D [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]
DPAK (SOT428) 	BUK7214-75B	75	14		69	0.95
	BUK9217-75B	75	15	17	64	0.95
	BUK9226-75A	75	24.6	26	45	1.3
	BUK7226-75A	75	26		45	1
TO-220AB (SOT78A) 	BUK9506-75B	75	5.5	6.1	75	0.5
	BUK7506-75B	75	5.6		75	0.5
	BUK7509-75A	75	9		75	0.65
	BUK7513-75B	75	13		75	0.95
	BUK9516-75B	75	14	16.4	67	0.95
	BUK753R8-80E	80	4		120	0.43

For the most current product information go to www.nxp.com/mosfets (updated daily!)

100V N-channel automotive TrenchMOS – Part 1






types in **bold** represent new products

Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _D [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]
LFPAK56, Power-SO8 (SOT669) 	BUK9Y12-100E	100	11.9	12	85	0.63
	BUK7Y12-100E	100	12		85	0.63
	BUK9Y15-100E	100	14.7	15	69	0.77
	BUK7Y15-100E	100	15		68	0.77
	BUK9Y19-100E	100	18	19	56	0.9
	BUK7Y19-100E	100	19		56	0.9
	BUK9Y22-100E	100	21.5	22	49	1.02
	BUK7Y22-100E	100	22		49	1.02
	BUK9Y38-100E	100	37.5	38	30	1.58
	BUK7Y38-100E	100	38		30	1.58
	BUK9Y53-100B	100	49	53	23	2
	BUK7Y53-100B	100	53		24.8	1.76
	BUK9Y65-100E	100	63.3	65	19	2.31
	BUK7Y65-100E	100	65		19	2.31
	BUK9Y104-100B	100	99	104	14.8	2.53
	BUK7Y102-100B	100	102		15	2.53
	BUK9Y113-100E	100	110	113	12	3.33
	BUK7Y113-100E	100	113		12	3.33
	BUK9Y153-100E	100	146	153	9.4	4.03
	BUK7Y153-100E	100	153		9.4	4.03
LFPAK56D (SOT1205) 	BUK9K29-100E	100	27	29	30	2.21
	BUK9K32-100E	100	31	33	26	2.36
	BUK9K45-100E	100	42	45	21	2.84
	BUK9K89-100E	100	85	89	12.5	3.96
	BUK9K134-100E	100	154	159	8.5	4.68
D ² PAK (SOT404) 	BUK765R0-100E	100	5		120	0.43
	BUK965R8-100E	100	5.6	5.8	120	0.43
	BUK768R1-100E	100	8.1		100	0.57
	BUK969R3-100E	100	8.9	9.3	100	0.57
	BUK9610-100B	100	9.7	10	75	0.5
	BUK7610-100B	100	10		75	0.5
	BUK7613-100E	100	13		72	0.82
	BUK9615-100E	100	14	15	66	0.82
	BUK9615-100A	100	14.4	15	75	0.65
	BUK9620-100B	100	18.5	20	63	0.75
	BUK7619-100B	100	19		64	
	BUK7620-100A	100	20		63	0.75
	BUK7626-100B	100	26		49	0.95
	BUK9628-100A	100	27	28	49	0.9
	BUK9629-100B	100	27	29	46	0.95
	BUK7628-100A	100	28		47	0.9
	BUK7631-100E	100	31		34	1.56
	BUK7635-100A	100	35		41	1
	BUK9637-100E	100	36	37	31	1.56
	BUK9640-100A	100	39	40	39	0.95
	BUK7640-100A	100	40		37	1.1
	BUK9660-100A	100	58	60	26	1.4
	BUK7660-100A	100	60		26	1.4

For the most current product information go to www.nxp.com/mosfets (updated daily!)

100V N-channel automotive TrenchMOS – Part 2

types in **bold** represent new products




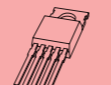
Package name	Type number	V _{DS} [max] [V]	R _{DSon} [max] @ 10 V [mΩ]	R _{DSon} [max] @ 5 V [mΩ]	I _D [max] @ 25 °C [A]	R _{th(j-mb)} [max] [K/W]
D ² PAK (SOT404) 	BUK9675-100A	100	72	75	23	1.5
	BUK7675-100A	100	75		23	1.5
	BUK96180-100A	100	173	180	11	2.8
DPAK (SOT428) 	BUK7227-100B	100	27		48	0.95
	BUK9230-100B	100	28	30	47	0.95
	BUK9240-100A	100	38.6	40	33	1.3
	BUK7240-100A	100	40		34	1.3
	BUK9275-100A	100	72	75	21.7	1.7
	BUK7275-100A	100	75		21.7	1.7
TO-220AB (SOT78A) 	BUK755R4-100E	100	5.2		120	0.43
	BUK9510-100B	100	9.7	10	75	0.5
	BUK7510-100B	100	10		75	0.5
	BUK9515-100A	100	14.4	15	75	0.65
	BUK7515-100A	100	15		75	0.5
	BUK9520-100B	100	18.5	20	63	0.75
	BUK9520-100A	100	19	20	63	0.75
	BUK7520-100A	100	20		63	0.75
	BUK7526-100B	100	26		49	0.95
	BUK9529-100B	100	27	29	46	0.95
	BUK7528-100A	100	28		47	0.9
	BUK9535-100A	100	34	35	41	1
	BUK7535-100A	100	35		41	1
	BUK7540-100A	100	40		37	1.1
	BUK9575-100A	100	72	75	23	1.5
	BUK7575-100A	100	75		23	1.5
	P ² PAK (SOT226) 	BUK7E5R2-100E	100	5.2		120
SC-73 (SOT223) 		BUK9875-100A	100	72	75	7
	BUK98180-100A	100	173	180	4.6	

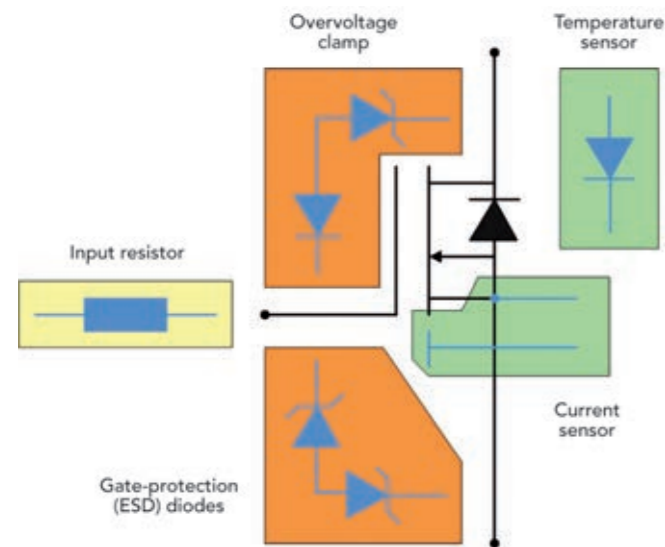
For the most current product information go to www.nxp.com/mosfets (updated daily!)

TrenchPLUS MOSFETs

TrenchPLUS is a range of standard MOSFETs with additional protection features, such as current and temperature sensing components, overvoltage clamps, and gate-protection (ESD) diodes. The system microcontroller can use data gathered from these

sensors to implement cost-effective protection features, thus eliminating the need to design with protected power devices. All the standard products listed below offer one or more "PLUS" features. Custom versions can be developed for high-volume applications.

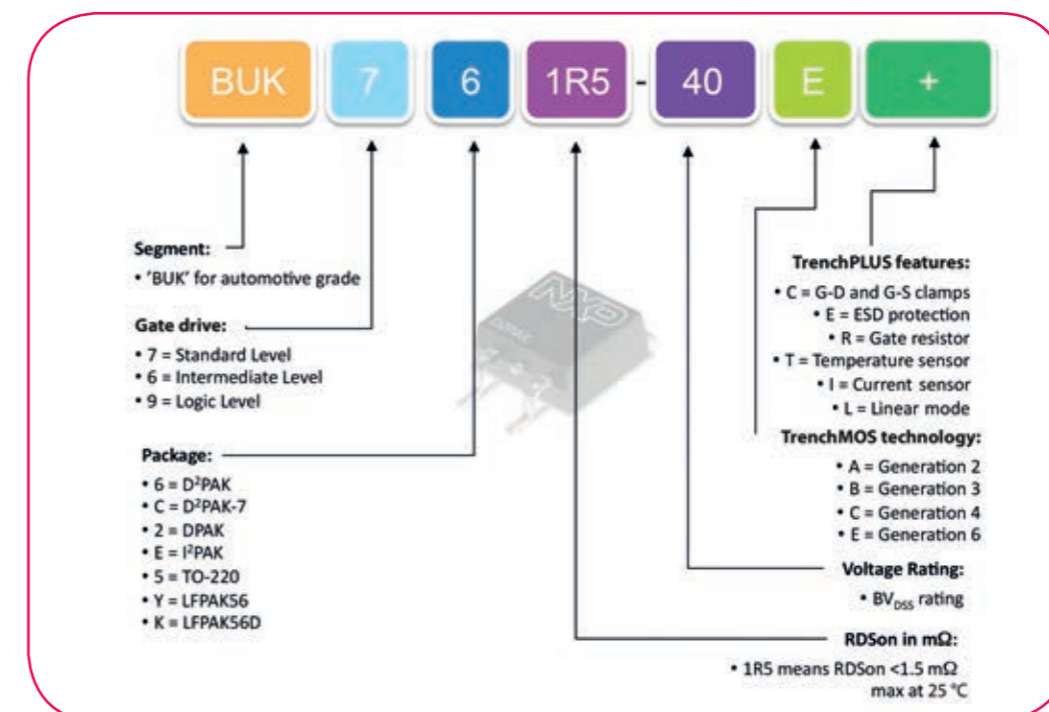
V_{DS} (V)	$R_{DS(on)}$ (max) @ 10 V (mΩ)	$R_{DS(on)}$ (max) @ 5 V (mΩ)	I_b (max) @ 25 °C (A)	Temperature sensing	Current sensing	Gate source clamps	Gate drain clamps	Gate resistor	Surface-mount package		Leaded package	
									7-pin D ² PAK (SOT427)	5-pin D ² PAK (SOT426)	TO220AB (SOT78C)	5-pin TO220 (SOT263B-01)
												
34	6		75			•	•	•			BUK7L06-34ARC	
34	11		75			•	•	•			BUK7L11-34ARC	
40	4.1		75	•							BUK714R1-40BT	BUK794R1-40BT
40	5		75		•	•					BUK7105-40AIE	BUK7905-40AIE
40	5		75	•		•					BUK7105-40ATE	BUK7905-40ATE
40	5		75									BUK7905-40AI
40	6		75	•	•	•			BUK7C06-40AITE			



TrenchPLUS MOSFETs

V_{DS} (V)	$R_{DS(on)}$ (max) @ 10 V (mΩ)	$R_{DS(on)}$ (max) @ 5 V (mΩ)	I_b (max) @ 25 °C (A)	Temperature sensing	Current sensing	Gate source clamps	Gate drain clamps	Gate resistor	Surface-mount package		Leaded package	
									7-pin D ² PAK (SOT427)	5-pin D ² PAK (SOT426)	TO220AB (SOT78C)	5-pin TO220 (SOT263B-01)
												
40	6.6	7	75	•		•	•				BUK9107-40ATC	BUK9907-40ATC
40	8		75	•		•	•				BUK7107-40ATC	BUK7907-40ATC
40	8		75		•	•					BUK7108-40AIE	BUK7908-40AIE
55	6.6	7	75	•		•					BUK9107-55ATE	BUK9907-55ATE
55	7		75		•	•					BUK7107-55AIE	BUK7907-55AIE
55	7		75	•		•					BUK7107-55ATE	BUK7907-55ATE
55	8		75	•	•	•			BUK7C08-55AITE			
55	9	10	75	•	•				BUK9C10-55BIT			
75	9		75		•	•					BUK7109-75AIE	BUK7909-75AIE
75	9		75	•		•					BUK7109-75ATE	BUK7909-75ATE
75	10		75	•	•	•			BUK7C10-75AITE			

Automotive TrenchPLUS part numbering





Thyristors

AC Thyristor Triacs / AC Thyristors / TOPTriacs 142

AC Thyristor Triacs 142

AC Thyristors 142

Temperature and Overload Protected Triacs (TOPTriacs) 142

3-quadrant Hi-Com 143

4-quadrant triacs 144

Silicon Controlled Rectifiers 145

AC Thyristor Triacs

(3Q Hi-Com power switches, overvoltage protection)

types in **bold** represent new products

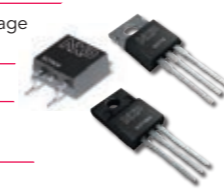
$I_{T(RMS)}$ (A)	V_{DRM} (V)	I_{GT} (max) (mA)	SOT78 (TO220AB)	SOT186A (isolated TO220AB)	SOT226 (I ² PAK)	SOT404 (D ² PAK)	SOT428 (DPAK)
2	800	E					ACTT2S
4	800	C/E		ACTT4X			ACTT4S
6	800	E	ACTT6	ACTT6X	ACTT6G	ACTT6B	
8	800	C0/COT	ACTT8	ACTT8X		ACTT8B	
10	800	C/CT	ACTT10	ACTT10X			
12	800	C/CT	ACTT12	ACTT12X		ACTT12B	

I_{GT} key: C = 35 mA; C0 = 5 - 30 mA; E = 10 mA
T: High $T_{j(max)}$ 150 °C

In the spotlight

AC Thyristor Triac ACTT10 series, ACTT12 series

- Planar passivated with overvoltage clamping function
- High-energy surge handling
- Very high dV_o/dt for maximum immunity to false triggering
- High $T_{j(max)}$ to 150 °C



AC Thyristors

(2Q Hi-Com power switches, exclusive negative gate triggering, overvoltage protection; SMD with "Common" mounting base.)

types in **bold** represent new products


$I_{T(RMS)}$ (A)	V_{DRM} (V)	I_{GT} (max) (mA)	SOT54 (TO92)	SOT223	SO8
0.2	600	D			ACT102H
0.8	600	D/E	ACT108	ACT108W	
0.8	800	E	ACT108	ACT108W	

I_{GT} key: D = 5 mA; E = 10 mA

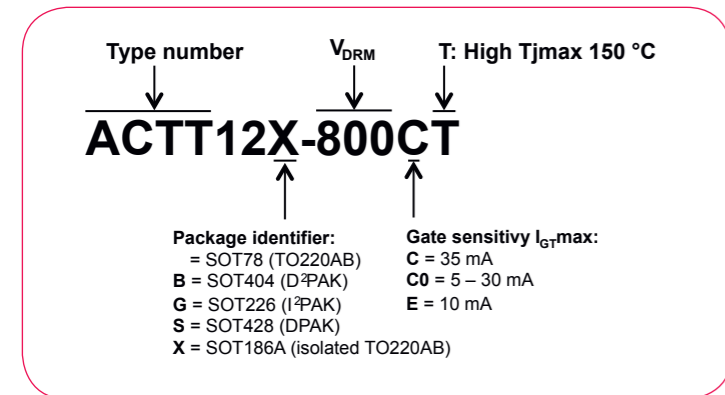
In the spotlight

AC Thyristor ACT108W-800E

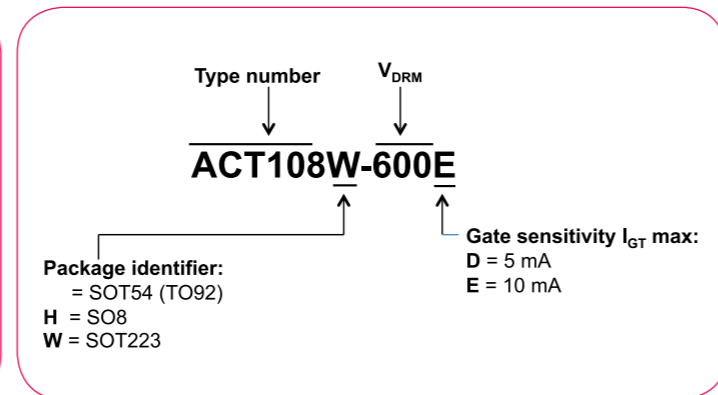
- Planar passivated with overvoltage clamping function
- Enhanced working voltage with enhanced overvoltage clamping capability
- Very high false-trigger immunity
- Exclusive negative gate triggering
- "Common" terminal on mounting base for multiple ACTs on shared cooling pad



AC Thyristor Triac part numbering



AC Thyristor part numbering



Temperature and Overload Protected Triacs (TOPTriacs)

(2Q Hi-Com power switches, exclusive negative gate triggering, over-temperature protection)

types in **bold italic underlined** represent products in development

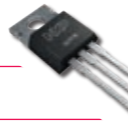
$I_{T(RMS)}$ (A)	V_{DRM} (V)	I_{GT} (max) (mA)	SOT78 (TO220)
12	800	C0	<u>TOPT12</u>
16	800	C0	<u>TOPT16</u>

I_{GT} key: C0 = 5 - 35 mA

In the spotlight

TOPTriac TOPT12-800C0

- Planar passivated for voltage ruggedness and reliability
- Over-temperature safety shutdown feature
- Hi-Com technology with min I_{GT} spec for highest noise immunity
- Exclusive negative gate triggering



3-quadrant Hi-Com

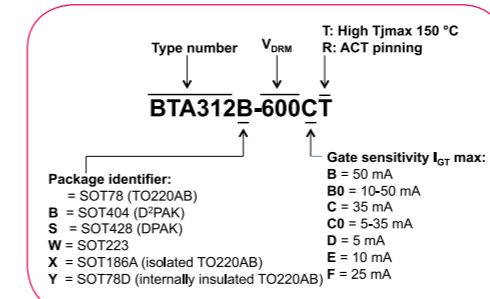
3-quadrant Hi-Com

types in **bold** represent new products
types in **bold italic underlined** represent products in development

$I_{T(RMS)}$ (A)	V_{DRM} (V)	I_{GT} (max) (mA)	SOT54 (TO92)	SOT78 (TO220AB)	SOT78D (internally insulated TO220AB)	SOT186A (isolated TO220AB)	SOT223	SOT404 (D ² PAK)	SOT428 (DPAK)
0.8	600 / 800	D					BTA2008W		
	1000	D	BTA2008						
1	600 / 800	B/E/ER	BTA201						
	600	E					BTA201W		
	800	B/C/D/E/F					BTA204W*		
2	600 / 800	D/E							
	600	B/C/D/E/F		BTA204		BTA202X			
4	800	B/C/E		BTA204		BTA204X			BTA204S
	1000	C				BTA204X			BTA204S
	600	CT/ET		BTA206		BTA206X			
6	600	D		BTA208		BTA208X			BTA208S
	600 / 800	B/E/F		BTA208		BTA208X			BTA208S
	800	B0/C0				BTA308X			
	1000	B				BTA208X			
8	600	C				BTA208X		BTA208B	
	800	C0				BTA208X			
	600 / 800	C/D/E		BTA310		BTA310X			
	800	BT/CT/ET		BTA410*	BTA410Y*	BTA410X*			
10	600	CT		BTA312					BTA312B
	800	D		BTA312		BTA312X			BTA312B
	600 / 800	B/C/E		BTA312		BTA312X			BTA312B
	800	C			BTA312Y				
12	600 / 800	B/C			BTA412Y*				
	800	CT		BTA312					BTA312B
	600	ET		BTA312					BTA312B
	800	BT		BTA316					BTA316B
16	600	B0		BTA316					BTA316B
	800	D		BTA316					
	600 / 800	B/C/E		BTA316		BTA316X			BTA316B
	800	ET		BTA316					
20	600	B/C				BTA416Y*			
	800	B0		BTA316		BTA316X			
	600 / 800	BT/CT		BTA420*	BTA420Y*	BTA420X*			
	800	B		BTA225					BTA225B
25	600 / 800	B		BTA225					
	800	BT/CT				BTA425Y*			
30	600	B/BT							
	800	BT		BTA330		BTA330X			

* Large chip / high surge I_{TSM}
 I_{GT} key: B = 50 mA, B0 = 10 - 50 mA, C = 35 mA, C0 = 5 - 35 mA, D = 5 mA, E = 10 mA, F = 25 mA
T: High $T_{j(max)}$ 150 °C R: ACT pinning


3-quadrant triac part numbering



In the spotlight

3-quadrant Hi-Com triac BTA316-600B0, BTA316B-600B0

- Planar passivated for voltage ruggedness and reliability
- Minimum I_{GT} spec of 10 mA for high noise immunity guarantee
- High commutation, high dV_o/dt for maximum immunity to false triggering



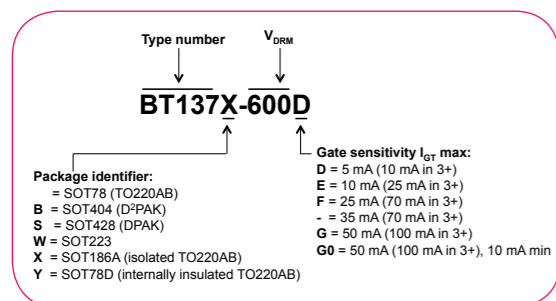
4-quadrant triacs

types in **bold** represent new products

I _{T(RMS)} (A)	V _{DRM} (V)	I _{GT} (max) (mA)	SOT54 (TO92)	SOT78 (TO220AB)	SOT78D (internally insulated TO220AB)	SOT82	SOT186A (isolated TO220AB)	SOT223	SOT404 (D ² PAK)	SOT428 (DPAK)	
0.6	400	5/5/5/7	MAC97A6								
	600	5/5/5/7	MAC97A8								
1	600	3/3/3/7						BT131W			
	600 / 800	3/3/3/7	BT131								
		5/5/5/7	BT131-D								
		10/10/10/10	BT131-E								
		3/3/3/5	Z0103MA/NA					Z0103MN/NN			
		5/5/5/7	Z0107MA/NA					Z0107MN/NN			
		10/10/10/10	Z0109MA/NA					Z0109MN/NN			
		3/3/3/5	Z0103MA0/NA0**					Z0103MNO/NN0**			
		5/5/5/7	Z0107MA0/NA0**					Z0107MNO/NN0**			
	10/10/10/10	Z0109MA0/NA0**					Z0109MNO/NN0**				
	600	5/5/5/10	BT132-D*								
	800	D/E/-						BT134W*			
	800	-						BT134W*			
	600	D/E/-/G									
	800	E/-						BT134			
600 / 800	D/E						BT234*				
4	600	D/-					BT136X			BT136S	
	600 / 800	F					BT136X			BT136S	
	600 / 800	E					BT136X		BT136B	BT136S	
	800	F								BT136S	
	800	-					BT136X			BT136S	
	800	F/-/G					BT236X				
6	600	F/-/G					BT236X				
	800	-/G					BT236X				
	600 / 800	D/-/G					BT137X			BT137S	
		E					BT137X		BT137B	BT137S	
		F					BT137X		BT137B	BT137S	
	8	600 / 800	G0/GOT								
800		E					BT137X			BT137S	
		F							BT137B	BT137S	
		-					BT137X		BT137B	BT137S	
600		D					BT138X				
		-/G					BT138X		BT138B		
	F					BT138X		BT138B			
12	600 / 800	G0/GOT									
	800	E					BT138X		BT138B		
	800	-					BT138X				
	800	G									
	600	D					BT138X				
		-/G					BT138X		BT138B		
F						BT138X		BT138B			
16	600	E/-					BT139X		BT139B		
	600 / 800	F/G					BT139X		BT139B		
		G0/GOT									
		E							BT139B		
	800	F							BT139B		
		-					BT139X		BT139B		
G								BT139B			
20	600	50/50/50/75					MAC223A8X				
25	400	50/50/50/75									
	600 / 800	G0/GOT									

I_{GT} key:
D = 5 mA (10 mA in 3+) E = 10 mA (25 mA in 3+) F = 25 mA (70 mA in 3+) - = 35 mA (70 mA in 3+) G = 50 mA (100 mA in 3+) G0 = 50 mA (100 mA in 3+), 10 mA min
T: High T_{jmax} 150°C * Large chip / high I_{TSM} ** Enhanced immunity to false triggering

4Q triac part numbering



In the spotlight

4-quadrant triac BT137-G0(T) series

- Planar passivated for voltage ruggedness and reliability
- Optimized I_{GT} with min spec for highest noise immunity
- Highest false-trigger immunity for a 4Q triac
- The first 4Q triac to offer high T_{j(max)} capability



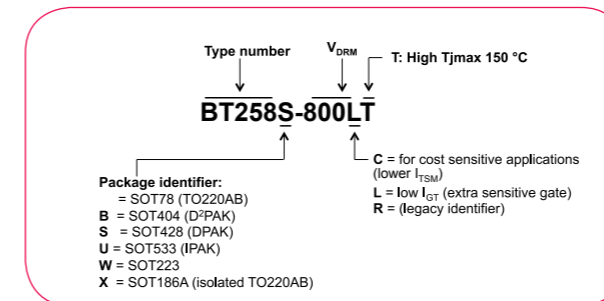
Silicon Controlled rectifiers

types in **bold** represent new products
types in ***bold italic underlined*** represent products in development

I _{T(RMS)} (A)	V _{DRM} & V _{RRM} (V)	I _{GT} (max) (mA)	SOT23	SOT54 (TO92)	SOT78 (TO220AB)	SOT82	SOT186A (isolated TO220AB)	SOT223	SOT404 (D ² PAK)	SOT428 (DPAK)	SOT533 (IPAK)
0.6	200	0.2									
	400	0.012						MCR08BT1			
	600	0.5µA min - 7µA max						EC103D1W			
	200 / 400 / 600	0.2									
		0.2									
	400	0.015 min - 0.05 max									
		0.02 min - 0.2 max									
	600	0.015 min - 0.05 max	<i>NCR100-8L</i>								
		0.1	<i>NCR100-8M</i>								
	800	0.1									
0.015 min - 0.05 max											
850	0.015 min - 0.05 max										
	0.1										
	0.015 min - 0.05 max										
	0.1										
1000	0.015 min - 0.05 max										
	0.1										
1	600	0.02 min - 0.2 max									
	0.07 min - 0.45 max										
4	400 / 500 / 600	0.2									
	500	0.2									
	600	0.2									
	500 / 600 / 800	0.2									
	600	0.2									
	800	0.2									
8	600	0.2									
	5										
	0.05										
	0.2										
	650	0.2									
	500 / 650	5									
12	650	15									
	500 / 650 / 800	15									
	500 / 1000	15									
	600	15									
	600 / 800	25									
	400 / 600 / 800	32									
20	500	32									
	600	32									
25	800	32									
	35										

* Large chip / high I_{TSM} ** Hi-Com / fast turn-off T: high T_{j(max)} 150 °C

Silicon Controlled Rectifiers part numbering



In the spotlight

Silicon Controlled Rectifiers TYN16 series, TYN20 series

- Planar passivated for voltage ruggedness and reliability
- High T_{j(max)} of 150 °C
- High thermal cycling capability



Our extensive package range provides maximum flexibility

Miniaturization

>>

Medium Power

2 Pins



3 Pins



4/5 Pins



6 Pins

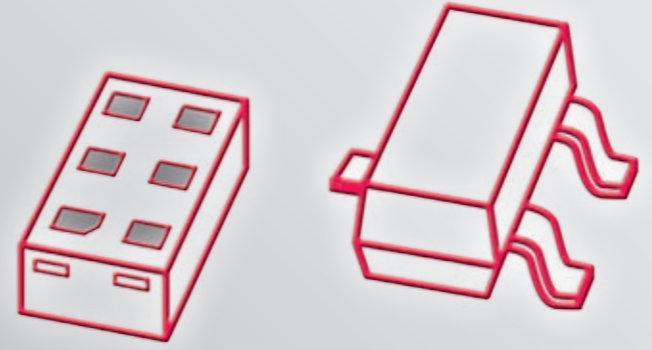


≥ 7 Pins



* The exact position of the balls and package dimensions vary.



























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Packages

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Package details and packing methods WLCSP – Part 2

Basic Type	Length x width x height	# of balls	Pitch	Package	Package name
IP4340CX15	1.56 x 1.56 x 0.47	15	0.4		WLCSP15
IP4342CX5	1.06 x 0.76 x 0.20	5	0.4		WLCSP5
IP4343CX5	0.93 x 0.93 x 0.61	5	0.4		WLCSP5
IP4352CX24	2.02 x 2.01 x 0.61	24	0.4		WLCSP24
IP4353CX15	2.36 x 1.06 x 0.61	15	0.4		WLCSP15
IP4355CX6	1.16 x 0.76 x 0.61	6	0.4		WLCSP6
IP4357CX17	2.4 x 1.1 x 0.61	17	0.4		WLCSP17
IP4359CX4	0.76 x 0.76 x 0.61	4	0.4		WLCSP4
IP4364CX8	1.41 x 1.41 x 0.65	8	0.4		WLCSP8
IP4365CX11	1.56 x 1.16 x 0.61	11	0.4		WLCSP11
IP4366CX8	1.41 x 1.41 x 0.65	8	0.4		WLCSP8
IP4369CX4	0.76 x 0.76 x 0.5	4	0.4		WLCSP4
IP4386CX4	0.91 x 0.91 x 0.65	4	0.4		WLCSP4
IP4387CX4	0.91 x 0.91 x 0.65	4	0.4		WLCSP4
PEM14CSP-RT	1.56 x 1.05 x 0.61	10	0.4		WLCSP10
PEM14CSP-RW	1.56 x 1.05 x 0.61	10	0.4		WLCSP10
PEM16CSP-RT	2.36 x 1.05 x 0.61	15	0.4		WLCSP15
PEM16CSP-RW	2.36 x 1.05 x 0.61	15	0.4		WLCSP15
PEM18CSP-RT-P	3.16 x 1.05 x 0.61	20	0.4		WLCSP20
PEM18CSP-RW-P	3.16 x 1.05 x 0.61	20	0.4		WLCSP20
PMCM440VNE	0.78 x 0.78 x 0.35	4	0.4		WLCSP4
PMCM4401VNE	0.78 x 0.78 x 0.35	4	0.4		WLCSP4
PMCM650VNE	1.48 x 0.98 x 0.35	6	0.5		WLCSP6
PMCM440VPE	0.78 x 0.78 x 0.35	4	0.4		WLCSP4
PMCM4401VPE	0.78 x 0.78 x 0.35	4	0.4		WLCSP4
PMCM650VPE	1.48 x 0.98 x 0.35	6	0.5		WLCSP6




Single Ended and Through Hole Packages

2 Pins




SOD59
15.7 x 9.98 x 4.5




SOD113
15.5 x 10.0 x 4.3


3 Pins




SOT54
4.6 x 3.9 x 5.1




SOT82
10.8 x 7.5 x 2.55




SOT226
11.0 x 10.0 x 4.3



SOT533
6.1 x 6.6 x 2.3



SOT186A
15.5 x 10.0 x 4.3



SOT78
15.6 x 10.0 x 4.4

Packing details glass diodes, single ended and through hole packages

Pins / leads	Package	Packing method and tape/reel/tube dimensions	Package	Ordering code (12 NC ending)	Packing quantity
2	SOD27	26 mm tape ammo pack, axial		-143	5000 pcs
		52 mm tape ammo pack, axial		-133	10000 pcs
		52 mm reel pack, axial		-113	10000 pcs
	SOD59	Rail packing, 50 pcs/tube, tube length = 520 mm		-127	20 tubes x 50 pcs
		SOD66		52 mm tape ammo pack, axial	-133
	SOD66	52 mm reel pack, axial		-113	10000 pcs
		SOD68		26 mm tape ammo pack, axial	
	52 mm reel pack, axial		-113	10000 pcs	
	SOD68	52 mm tape ammo pack, axial		-133	10000 pcs
		SOD113		Rail packing, 50 pcs/tube, tube length = 520 mm	
	SOD141		52 mm tape ammo pack, axial		
		Bulk pack, 500 pcs. per carrier	-112		20 carriers x 500 pcs
3	SOT54	Bulk pack, 1000 pcs/carrier		-112	5 carriers x 1000 pcs
		55 mm reel packing, 2000 pcs/reel, reel dimensions = 380 x 55 mm		-116	5 reels x 2000 pcs
		Ammo packing, 18 mm tape, 2000 pcs/carrier, reel dimensions = 350 x 55 mm		-126	5 carriers x 2000 pcs
		Bulk pack, 1000 pcs/carrier		-412	5 carriers x 1000 pcs
SOT78 (TO-220)	Rail packing, 50 pcs/tube, tube length = 520 mm		-127	20 tubes x 50 pcs	
	SOT78D		Rail packing, 50 pcs/tube, tube length = 520 mm	-127	20 tubes x 50 pcs
SOT82	Rail packing, 50 pcs/tube, tube length = 390 mm		-127	20 tubes x 50 pcs	
	SOT186A (TO-220F)		Rail packing, 50 pcs/tube, tube length = 520 mm	-127	20 tubes x 50 pcs
I2PAK (SOT226)	Rail packing, 50 pcs/tube, tube length = 520 mm		-127	20 tubes x 50 pcs	
	SOT533		Rail packing	-127	75 tubes x 50 pcs
5	SOT263B-1	Rail packing		-127	20 tubes x 50 pcs

Package cross reference list – Part 1

Type	Competitor	NXP	Pins / Leads	Type	Competitor	NXP	Pins / Leads
µQFN-10L	ST	DFN2510A-10 (SOT1176)	10	Micro 3	Int. Rectifier	SOT23	3
µQFN-10L	ST	DFN2520-9 (SOT1333)	9	Micro 6	Int. Rectifier	SOT457	6
µQFN-2L	ST	DFN1006-2 (SOD882)	2	MICRO FOOT 0.8 x 0.8*	Vishay	DFN1010D-3 (SOT1215)	3
6 Lead DFN	ON Semi	DFN2020-6 (SOT1118)	6	MICRO FOOT 1 x 1.2*	Vishay	DFN1010D-3 (SOT1215)	3
CLP0603	Vishay	DSN0603-2 (SOD962)	2	MICRO FOOT 1 x 1.5*	Vishay	DFN1010D-3 (SOT1215)	3
CMAK/ CMAK	Renesas	SOT323	3	MICRO FOOT 1.6 x 1.6*	Vishay	DFN2020MD-6 (SOT1220)	6
CMAK/ CMAK	Renesas	SOT323	3	MICRO FOOT 1 x 1*	Vishay	DFN1010D-3 (SOT1215)	3
CMPAK-5(T)	Renesas	SOT353	5	MICRO FOOT*	Vishay	DFN2020MD-6 (SOT1220)	6
CMPAK-6	Renesas	SOT363	6	MicroFET	Fairchild	DFN2020MD-6 (SOT1220)	6
CP4	Toshiba	SOT143B	4	MicroFET 1.6 x 1.6*	Fairchild	DFN2020MD-6 (SOT1220)	6
CS6	Toshiba	DFN1010-6 (SOT891)	6	MiniMelf	Diodes Inc.	SOD80C	2
CST3	Toshiba	DFN1006-3 (SOT883)	3	MiniMelf	ST	SOD80C	2
CST3	Toshiba	DFN1006B-3 (SOT883B)	3	MiniMelf	Vishay	SOD80C	2
CTS2 (fSC)	Toshiba	DFN1006-2 (SOD882)	2	MP6	Renesas	DSN0603-2 (SOD962)	2
CTS2 (fSC)	Toshiba	DFN1006D-2 (SOD882D)	2	MPAK	Renesas	SOT23	3
D ² PAK	ON Semi	D ² PAK (SOT404)	3	MPAK	Renesas	SOT23	3
D ² PAK	Vishay	D ² PAK (SOT404)	3	MPAK-4R	Renesas	SOT143B	4
D ² PAK 3	ON Semi	D ² PAK (SOT404)	3	MPT3	Rohm	SOT89	3
D ² PAK*	Diodes Inc.	D ² PAK (SOT404)	3	MSOP-10L	Semtech	SOT552	10
DFN1006-3	Diodes Inc.	DFN1006-3 (SOT883)	3	PG-TD SON-8	Infineon	LFPK (SOT669)	5
DFN1006H4-3	Diodes Inc.	DFN1006-3 (SOT883)	3	PMDT	Rohm	SOD128	2
DFN1411*	Diodes Inc.	DFN1010D-3 (SOT1215)	3	PMDU	Rohm	SOD123W	2
DFN2	ST	DSN0603-2 (SOD962)	2	PowerDI123	Diodes Inc.	SOD123F	2
DPAK	ON Semi	DPAK (SOT428)	3	PowerDI123	Diodes Inc.	SOD123W	2
DSO14	Infineon	SOT108	14	PowerDI323	Diodes Inc.	SOD323F	2
DSN2	ON Semi	DSN0603-2 (SOD962)	2	PowerDi5	Diodes Inc.	CFP15 (SOT1289)	3
DSN2, 1.0 x 0.6	ON Semi	DFN1006D-2 (SOD882D)	2	PowerFLAT (6 x 5)	ST	LFPK (SOT669)	5
DSN2, 1.6 x 0.8	ON Semi	DFN1608D-2 (SOD1608)	2	PowerFLAT (6 x 5)	ST	LFPK56D (SOT1205)	6
EMD2	Rohm	SOD523	2	PowerPAK SC-70	Vishay	DFN2020-6 (SOT1118)	6
EMD3/EMT3	Rohm	DFN1006-3 (SOT883)	3	PowerPAK SC-70	Vishay	DFN2020MD-6 (SOT1220)	6
EMD5/EMT5	Rohm	SOT665	5	PowerPAK SC-70	Vishay	DFN2020MD-6 (SOT1220)	6
EMD6/EMT6/WEMT6	Rohm	SOT666	6	PowerPAK SC706L	Vishay	DFN2020-3 (SOT1061)	3
EMT3	Rohm	DFN1006-3 (SOT883)	3	PowerPak SC-70-6L	Vishay	DFN2020-6 (SOT1118)	6
EMT3/EMD3	Rohm	DFN1006-3 (SOT883)	3	PowerPAK SC-75*	Vishay	DFN2020MD-6 (SOT1220)	6
EMT3F*	Rohm	DFN1006-3 (SOT883)	3	PowerPak SC-75-6L*	Vishay	DFN2020MD-6 (SOT1220)	6
EMT5*	Rohm	SOT666	6	PowerPAK SO-8	Vishay	LFPK (SOT669)	5
EMT5/EMD5	Rohm	SOT665	5	PW-Mini	Toshiba	SOT89	3
EMT6	Rohm	SOT666	6	S08	Vishay	SOT96	8
EMT6/EMD6/WEMT6	Rohm	SOT666	6	SC2	Toshiba	DSN0603-2 (SOD962)	2
ES6	Toshiba	SOT666	6	SC59	Diodes Inc.	SOT23	3
ES6 ESV	Toshiba	SOT666	6	SC70	ON Semi	SOT323	3
ESC/TESC	Toshiba	SOD523	2	SC-70	ON Semi	SOT323	3
ESM	Toshiba	DFN1006-3 (SOT883)	3	SC-70, 3 leads	Vishay	SOT323	3
ESV	Toshiba	SOT665	5	SC70-3	Vishay	SOT323	3
ESV	Toshiba	SOT666	6	SC70-3	AOS	SOT323	3
FM8	Toshiba	SOT96	8	SC70-5L	Semtech	SOT353	5
FS6*	Toshiba	DFN1010B-6 (SOT1216)	6	SC70-6	Vishay	SOT363	6
GMD2	Rohm	DSN0603-2 (SOD962)	2	SC70-6	AOS	SOT363	6
HUML2020L8 (Dual)	Rohm	DFN2020-6 (SOT1118)	6	SC70-6	Fairchild	SOT363	6
HUML2020L8 (Single)	Rohm	DFN2020MD-6 (SOT1220)	6	SC70-6L	Semtech	SOT363	6
KMD2	Rohm	DFN1608D-2 (SOD1608)	2	SC74 TSOP6	Infineon	SOT457	6
LDPK(S)-1)	Renesas	D ² PAK (SOT404)	3	SC-74 TSOP-6	ON Semi	SOT457	6
LFPK	Renesas	LFPK (SOT669)	5	SC75	Infineon	DFN1006-3 (SOT883)	3
LG A 1.0 x 0.6mm	Texas Instruments	DFN1006B-3 (SOT883B)	3	SC75	ON Semi	DFN1006-3 (SOT883)	3
LLD	Renesas	SOD80C	2	SC-75	ON Semi	DFN1006-3 (SOT883)	3
LLDS	Rohm	SOD80C	2	SC-75	Semtech	DFN1006-3 (SOT883)	3
LLP1006-2L	Vishay	DFN1006-2 (SOD882)	2	SC75A	Vishay	DFN1006-3 (SOT883)	3
LLP1006-2L	Vishay	DFN1006D-2 (SOD882D)	2	SC-75A	Vishay	DFN1006-3 (SOT883)	3
LLP1006-2M	Vishay	DFN1006-2 (SOD882)	2	SC79	Infineon	SOD523	2
LLP1006-2M	Vishay	DFN1006D-2 (SOD882D)	2	SC-88	ON Semi	SOT363	6
LLP75-7L	Vishay	DFN1616-6 (SOT1189)	6	SC88/SC 7 0-6/SOT 363 6 LEAD	ON Semi	SOT363	6
LPDS/LPTS	Rohm	D ² PAK (SOT404)	3	SC-88A	ON Semi	SOT353	5
LPTS/LPDS	Rohm	D ² PAK (SOT404)	3	SC89	Fairchild	SOT666	6
M-Flat	Toshiba	SOD128	2	SC-89	ON Semi	SOT666	6
Micro 10	ON Semi	SOT552	10		Semtech	SOT666	6

Types with * show footprint compability only

Package cross reference list – Part 2

Type	Competitor	NXP	Pins / Leads	Type	Competitor	NXP	Pins / Leads
SC89-3	Vishay	DFN1006-3 (SOT883)	3	SOT 143	Infineon	SOT143B	4
SC89-3	ON Semi	DFN1006-3 (SOT883)	3	SOT063*	ON Semi	DFN101 OB-6 (SOT1216)	6
SC89-3	Fairchild	DFN1006-3 (SOT883)	3	SOT-143	Semtech	SOT143B	4
SC89-6	Vishay	SOT666	6	SOT-143	Diodes Inc.	SOT143B	4
SC89-6	AOS	SOT666	6	SOT223	Vishay	SOT223	4
SC89-6	Fairchild	SOT666	6	SOT223	Infineon	SOT223	4
SC89-6lead	Vishay	SOT666	6	SOT223	Fairchild	SOT223	4
S-Flat	Toshiba	SOD123F	2	SOT223	ON Semi	SOT223	4
S-Flat	Toshiba	SOD123W	2	SOT223	Diodes Inc.	SOT223	4
SLP1006P2	Semtech	DFN1006-2 (SOD882)	2	SOT-223	ON Semi	SOT223	4
SLP1006P2T	Semtech	DFN1006D-2 (SOD882D)	2	SOT-223	Diodes Inc.	SOT223	4
SLP1006P3	Semtech	DFN1006-3 (SOT883)	3	SOT23	Infineon	SOT23	3
SLP1006P3T	Semtech	DFN1006B-3 (SOT883B)	3	SOT23	ST	SOT23	3
SLP1510N6	Semtech	DFN1410-6 (SOT886)	6	SOT23	Vishay	SOT23	3
SLP1610N2	Semtech	DFN1608D-2 (SOD1608)	2	SOT23	Semtech	SOT23	3
SLP1610P4	Semtech	DFN2510A-10 (SOT1176)	10	SOT23	Diodes Inc.	SOT23	3
SLP1610P4	Semtech	DFN2520-9 (SOT1333)	9	SOT23	AOS	SOT23	3
SLP1616P6	Semtech	DFN1616-6 (SOT1189)	6	SOT23	ON Semi	SOT23	3
SLP1713P8	Semtech	DFN1714-8 (SOT1166)	8	SOT-23	ON Semi	SOT23	3
SLP1713P8	Semtech	DFN1714U-8 (SOT983)	8	SOT-23	Diodes Inc.	SOT23	3
SLP2010P8T	Semtech	DFN2110-9 (SOT1178)	9	SOT23-3	Diodes Inc.	SOT23	3
SLP2513P12	Semtech	DFN2512-12 (SOT1158)	12	SOT23-3	AOS	SOT23	3
SLP2513P12	Semtech	DFN2514-12 (SOT1167)	12	SOT23-3	ON Semi	SOT23	3
SLP2513P12	Semtech	DFN2514U-12 (SOT984)	12	SOT23-5	AOS	SOT457	6
SLP2626P10	Semtech	DFN2626-10 (SOT1197)	10	SOT23-5	Diodes Inc.	SOT457	6
SLP3313P16	Semtech	DFN3314-16 (SOT1168)	16	SOT23-6	Diodes Inc.	SOT457	6
SLP3313P16	Semtech	DFN3314U-16 (SOT985)	16	SOT23-6	ST	SOT457	6
SM6 VS-6	Toshiba	SOT457	6	SOT23-6	Diodes Inc.	SOT457	6
SMA flat	ST	SOD128	2	SOT23-6L	Semtech	SOT457	6
SMD TO-263	Renesas	D ² PAK (SOT404)	3	SOT23F	Toshiba	SOT23	3
SMD6/SMT6	Rohm	SOT457	6	SOT23F	Diodes Inc.	SOT23	3
SMD6/SMZ6	Rohm	SOT457	6	SOT26	Diodes Inc.	SOT457	6
SMFPAK-6	Renesas	SOT666	6	SOT323	Infineon	SOT323	3
S-Mini	Toshiba	SOT23	3	SOT323	Diodes Inc.	SOT323	3
S-Mini TSM	Toshiba	SOT23	3	SOT323	Fairchild	SOT323	3
SMPAK	Renesas	DFN1006-3 (SOT883)	3	SOT323	Diodes Inc.	SOT323	3
SMPC TO-277A	Vishay	CFP15 (SOT1289)	3	SOT323	ST	SOT323	3
SMT3	Rohm	SOT23	3	SOT353	Diodes Inc.	SOT353	5
SMT5*	Rohm	SOT457	6	SOT353	Vishay	SOT353	5
SMT6	Rohm	SOT457	6	SOT353	Diodes Inc.	SOT363	6
SMZ6/SMD6	Rohm	SOT457	6	SOT363	Infineon	SOT363	6
SO-8 FL	ON Semi	LFPK (SOT669)	5	SOT363	Diodes Inc.	SOT363	6
SOD-123	ST	SOD123F	2	SOT-363	Diodes Inc.	SOT363	6
SOD-123-FL	ON Semi	SOD123F	2	SOT523	Diodes Inc.	DFN1006-3 (SOT883)	3
SOD-123-FL	ON Semi	SOD123W	2	SOT523F	Fairchild	DFN1006-3 (SOT883)	3
SOD323	Infineon	SOD323	2	SOT553	ON Semi	SOT665	5
SOD323	Vishay	SOD323	2	SOT563	Diodes Inc.	SOT666	6
SOD323	Semtech	SOD323	2	SOT563	ON Semi	SOT666	6
SOD-323	ON Semi	SOD323	2	SOT563-6	ON Semi	SOT666	6
SOD-323	Diodes Inc.	SOD323	2	SOT563F	Fairchild	SOT666	6
SOD-323	ST	SOD323	2	SOT666	Infineon	SOT666	6
SOD523	Diodes Inc.	SOD523	2	SOT723*	ON Semi	DFN1010D-3 (SOT1215)	3
SOD523	Vishay	SOD523	2	SOT723-3*	ON Semi	DFN1010D-3 (SOT1215)	3
SOD523	Semtech	SOD523	2	SOT89	Infineon	SOT89	3
SOD-523	ON Semi	SOD523	2	SOT89	Diodes Inc.	SOT89	3
SOD-523	ST	SOD523	2	SOT-89	ON Semi	SOT89	3
SOD882	ST	DFN1006-2 (SOD882)	2	SOT89-3L	Diodes Inc.	SOT89	3
SOD882T	ST	DFN1006D-2 (SOD882D)	2	SOT963	ON Semi	DFN1010-6 (SOT891)	6
SOD923-2*	ON Semi	DFN1006-2 (SOD882)	2	SOT963*	Diodes Inc.	DFN1010B-6 (SOT1216)	6
SOIC-8 NB	ON Semi	SOT96	8	SOT963*	ON Semi	DFN1010E-6 (SOT1202)	6
SON 2x2	Texas Instruments	DFN2020MD-6 (SOT1220)	6	SRP-F	Renesas	SOD123W	2
SON 3x3*	Texas Instruments	DFN2020MD-6 (SOT1220)	6	SS CSP2	Toshiba	DFN1006-3 (SOT883)	3
SOP8	Rohm	SOT96	8	SSD3/SST3	Rohm	SOT23	3
SOP-8	Renesas	SOT96	8	SSM	Toshiba	DFN1006-3 (SOT883)	3
SOPH	Rohm	SOT 108	14	SSOT3	Fairchild	SOT23	3

Types with * show footprint compability only

Package cross reference list – Part 3

Type	Competitor	NXP	Pins / Leads	Type	Competitor	NXP	Pins / Leads
SSOT6	Fairchild	SOT457	6	UDFN-6 WDFN6	ON Semi	DFN2020MD-6 (SOT1220)	6
SSOT6 FLMP	Fairchild	SOT457	6	UDFN6B	Toshiba	DFN2020MD-6 (SOT1220)	6
SST3	Rohm	SOT23	3	UDFN8, 1.8 x 1.2, 0.4P	ON Semi	DFN1712-8 (SOT1157)	8
SST3/SSD3	Rohm	SOT23	3	UDRN 16 4 x 2	ON Semi	DFN4020-14 (SOT1334)	14
ST01005	STM	DSN0402-2 (SOD992)	2	UF6	Toshiba	SOT363	6
Strmite flat	ST	SOD123W	2	UF6/ USV/ US6	Toshiba	SOT363	6
T0263	Diodes Inc.	D ² PAK(SOT404)	3	UFP	Renesas	SOD523	2
T0263-3	Infineon	D ² PAK (SOT404)	3	UMD2	Rohm	SOD323F	2
Thin PowerPAK SC70	Vishay	DFN2020MD-6 (SOT1220)	6	UMD3/UMT3	Rohm	SOT323	3
Thin PowerPAK SC-70	Vishay	DFN2020-6 (SOT1118)	6	UMD5/UMT5	Rohm	SOT353	5
Thin PowerPAK SC-70	Vishay	DFN2020MD-6 (SOT1220)	6	UMD6/ UMT6	Rohm	SOT363	6
Thin PowerPAK SC75*	Vishay	DFN2020MD-6 (SOT1220)	6	UMLP 1.6 x 1.6*	Fairchild	DFN2020MD-6 (SOT1220)	6
TLSP-6-1	Infineon	DFN1010E-6 (SOT1202)	6	UMT3	Rohm	SOT323	3
TO-220S	Renesas	D ² PAK (SOT404)	3	UMT3F*	Rohm	SOT323	3
TO-220SM	Toshiba	D ² PAK (SOT404)	3	UMT5/ UMD5	Rohm	SOT353	5
TO-252 (MP-3ZK)	Renesas	DPAK (SOT428)	3	UMT6	Rohm	SOT363	6
TO-252 reverse, TO-252	Vishay	DPAK (SOT428)	3	UMT6/ UMD6	Rohm	SOT363	6
TO-252, TO-252 reverse	Vishay	DPAK (SOT428)	3	UPAK (SOT89)	Renesas	SOT89	3
TO-252-3/-3-23	Infineon	DPAK (SOT428)	3	URP	Renesas	SOD323	2
TO-263 3-lead	Vishay	D ² PAK (SOT404)	3	US6	Toshiba	SOT363	6
TO-263AB	Vishay	D ² PAK (SOT404)	3	US6/ UF6/ USV	Toshiba	SOT363	6
TSLP-2-1	Infineon	DFN1006-2 (SOD882)	2	use	Toshiba	SOD323	2
TSLP-2-7/-17	Infineon	DFN1006D-2 (SOD882D)	2	US-Flat	Toshiba	SOD323F	2
TSLP-3-1, -15	Infineon	DFN1006B-3 (SOT883B)	3	USM	Toshiba	SOT323	3
TSLP-3-4	Infineon	DFN1006-3 (SOT883)	3	USV	Toshiba	SOT353	5
TSLP-9-1	Infineon	DFN2510A-10 (SOT 1176)	10	USV	Toshiba	SOT363	6
TSLP-9-1	Infineon	DFN2520-9 (SOT1333)	9	USV/ US6/ UF6/	Toshiba	SOT363	6
TSMT5*	Rohm	SOT457	6	VESM*	Toshiba	DFN1010D-3 (SOT1215)	3
TSMT6	Rohm	SOT457	6	VML0806*	Rohm	DFN1006B-3 (SOT883B)	3
TSNP-2-2	Infineon	DFN1608D-2 (SOD 1608)	2	VMN2*	Rohm	DFN1006-2 (SOD882)	2
TSON Advance	Toshiba	DFN3333-8 (SOT873-1)	8	VMN2*	Rohm	DFN1006D-2 (SOD882D)	2
TSOP6	Vishay	SOT457	6	VMN3*	Rohm	DFN1006-3 (SOT883)	3
TSOP6	AOS	SOT457	6	VMT3*	Rohm	DFN1010D-3 (SOT1215)	3
TSOP6	ON Semi	SOT457	6	VMT6*	Rohm	DFN101 OB-6 (SOT1216)	6
TSOP-6	Renesas	SOT457	6	VS6	Toshiba	SOT457	6
TSOP-6/ TSOP6	Vishay	SOT457	6	VSON-5	Renesas	SOT665	5
TSSLP-2-1	Infineon	DSN0603-2 (SOD962)	2	WDFN 10 2.5 x 2	ON Semi	DFN2520-9 (SOT1333)	9
TSSOP10	Infineon	SOT552	10	WDFN 16 4 x 2	ON Semi	DFN4020-14 (SOT1334)	14
TSSOP20	Toshiba	SOT360	20	WDFN3	ON Semi	DFN2020-3 (SOT1061)	3
TSSOP20	Renesas	SOT360	20	W-DFN3020-8*	Diodes Inc.	DFN2020-6 (SOT1118)	6
TSSOP38	Infineon	SOT510	38	WDFN6	ON Semi	DFN2020-6 (SOT1118)	6
TSSOP-8	ON Semi	SOT505	8	WDFN6	ON Semi	DFN2020MD-6 (SOT1220)	6
TSST8*	Rohm	DFN2020MD-6 (SOT1220)	6	WEMT6	Rohm	SOT666	6
TUMT3	Rohm	SOT323	3	WEMT6/ EMT6/ EMD6	Rohm	SOT666	6
TUMT5*	Rohm	DFN2020-6 (SOT1118)	6	WLCSP 1 x 1*	Fairchild	WLCSP4	3
TUMT6*	Rohm	DFN2020-6 (SOT1118)	6	WLCSP1.6 x 1.6*	AOS	WLCSP6	6
UDFN 1.6 x 1.6	ON Semi	DFN1616-6 (SOT1189)	6	WLCSP2	ON Semi	DSN0603-2 (SOD962)	2
UDFN 1.7 x 1.35, 0.4P	ON Semi	DFN1714U-8 (SOT983)	8	WLCSP-4*	Fairchild	WLCSP4	3
UDFN 10 2.5 x 1, 0.5P	ON Semi	DFN2520-9 (SOT1333)	9	WLCSP-4*	ON Semi	WLCSP4	3
UDFN 10 2.5 x 2	ON Semi	DFN2520-9 (SOT1333)	9	WLL-2-2	Infineon	DSN0402-2 (SOD992)	2
UDFN10 2.5 x 1, 0.5P	ON Semi	DFN2510A-10 (SOT1176)	10	WLP1.5x 1.5*	Texas Instruments	DFN2020MD-6 (SOT1220)	6
UDFN10 2.6 x 2.6, 0.5P	ON Semi	DFN2626-10 (SOT1197)	10	WLP1.Ox 1.0*	Texas Instruments	DFN1010D-3 (SOT1215)	3
UDFN12, 2.5 x 1.2, 0.4P	ON Semi	DFN2512-12 (SOT1158)	12	WLP1.Ox 1.5*	Texas Instruments	DFN2020MD-6 (SOT1220)	6
UDFN12, 2.5 x 1.35, 0.4P	ON Semi	DFN2512-12 (SOT1158)	12	X1 -DFN 1006-3	Diodes Inc.	DFN1006-3 (SOT883)	3
UDFN12, 2.5 x 1.35, 0.4P	ON Semi	DFN2514-12 (SOT1167)	12	X1-DFN1212-3*	Diodes Inc.	DFN1010D-3 (SOT1215)	3
UDFN16, 3.3 x 1.35, 0.4P	Toshiba	DFN3314U-16 (SOT985)	16	X1-DFN1616-6*	Diodes Inc.	DFN2020MD-6 (SOT1220)	6
UDFN16, 3.5 x 1.2, 0.4P	ON Semi	DFN3312-16 (SOT1159)	16	X2-DFN0806-3	Diodes Inc.	DFN1006-3 (SOT883)	3
U-DFN2020-3 Type B 2.0 x 2.0 x 0.6	Diodes Inc.	DFN2020-3 (SOT1061)	3	X2-DFN1006-2	Diodes Inc.	DFN1006D-2 (SOD882D)	2
U-DFN2020-6	Diodes Inc.	DFN2020MD-6 (SOT1220)	6	X2-DFN1006-3	Diodes Inc.	DFN1006B-3 (SOT883B)	3
UDFN2020-6 Type B	Diodes Inc.	DFN2020-6 (SOT1118)	6	X2-DFN1310-6*	Diodes Inc.	DFN1010B-6 (SOT1216)	6
UDFN2020-6 Type E	Diodes Inc.	DFN2020MD-6 (SOT1220)	6	X2-DFN2015-3*	Diodes Inc.	DFN2020MD-6 (SOT1220)	6
U-DFN2523-6*	Diodes Inc.	DFN2020MD-6 (SOT1220)	6	X2-DFN2020-6	Diodes Inc.	DFN2020MD-6 (SOT1220)	6
UDFN6	Toshiba	DFN2020-6 (SOT1118)	6	X3-DFN0603-2	Diodes Inc.	DSN0603-2 (SOD962)	2
UDFN6	ON Semi	DFN2020MD-6 (SOT1220)	6	X3DFN-2	ON Semi	DSN0603-2 (SOD962)	2
				XI-DFN1006-2	Diodes Inc.	DFN1006-2 (SOD882)	2

Types with * show footprint compatibility only

Package cross reference matrix – Part I

Pins / leads	NXP	Industry standard names	Size (l x w x h) (mm)	P _{tot} (mW)	Package	Competitor synonyms									
						Rohm	Toshiba	ON Semi	Renesas	Infineon	Diodes Inc	ST	Vishay	Semtech	
2	DSN0402-2 (SOD992)		0.4 x 0.2 x 0.12							WLL-2-2		ST01005			
	DSN1006-2 (SOD993)		1.0 x 0.6 x 0.3												
	DSN1006U-2 (SOD995)		1.0 x 0.6 x 0.3												
	DFN1006-2 (SOD882)		1.0 x 0.6 x 0.48	250		(VMN2)	CTS2 (fsc)	(SOD923-2)		TSLP-2-1	XI-DFN1006-2	SOD 882 uQFN-2L	LLP1006-2M LLP1006-2L	SLP1006P2	
	DFN1006D-2 (SOD882D)		1.0 x 0.6 x 0.37	250		(VMN2)	CTS2 (fsc)	DSN2, 1.Ox 0.6		TSLP-2-7/ -17	X2-DFN1006-2	SOD882T	LLP1006-2L LLP1006-2M	SLP1006P2T	
	DFN1608D-2 (SOD1608)		1.6 x 0.8 x 0.37	780		KMD2		DSN2 1.6 x 0.8		TSNP-2-2				SLP1610N2	
	DSN0603-2 (SOD962)		0.6 x 0.3 x 0.3	525		GMD2	SC2	DSN2, X3DFN-2 WLCSP2	MP6	TSS-LP-2-1	X3-DFN0603-2	DFN2	CLP0603	SLP0603P2X3	
	SOD80C	Mini-Melf		3.5 x 1.5 x 1.5	300		LLDS			LLD		MiniMelf	MiniMelf	MiniMelf	
	SOD123F			2.6 x 1.6 x 1.1	830			S-Flat	SOD-123-FL			PowerDI123	SOD-123		
	SOD123W			2.6 x 1.7 x 1.0	900		PMDU	S-Flat	SOD-123-FL	SRP-F		PowerDI123	Strmite flat		
	SOD128			3.8 x 2.5 x 1.0	1000		PMDT	M-Flat					SMA flat		
	SOD323	SC-76		1.7 x 1.25 x 0.95	400			USC	SOD-323	URP	SOD323	SOD-323	SOD-323	SOD323	
	SOD323F	SC-90		1.7 x 1.25 x 0.7	830		UMD2	US-Flat				PowerDI323			
	SOD523	SC-79		1.2 x 0.8 x 0.6	500		EMD2	ESC/TESC	SOD-523	UFP	SC79	SOD523	SOD-523	SOD523	
	3	CFP15 (SOT1289)		5.8 x 4.3 x 0.78	1200							PowerDi5		SMPC TO-277A	
		DFN1006-3 (SOT883)	SC-101	1.0 x 0.6 x 0.48	250			SS CSP2			TSLP-3-4	X1 -DFN 1006-3		SLP1006P3	
		DFN1006B-3 (SOT883B)		1.0 x 0.6 x 0.37	250				CST3		TSLP-3-1, -15	X2-DFN1006-3		SLP1006P3T	
		DFN1010D-3 (SOT1215)		1.1 x 1.0 x 0.37	325		(VMT3)	(VESM)	(SOT723)				(DFN1411)		
		DFN2020-3 (SOT1061)	HU-SON3		2.0 x 2.0 x 0.62	1300				WDFN3			U-DFN2020-3 Type B 2.0 x 2.0 x 0.6	PowerPAK SC706L	
		DFN2020D-3 (SOT1061D)			2.0 x 2.0 x 0.62	1300				WDFN3			U-DFN2020-3 Type B 2.0 x 2.0 x 0.6	PowerPAK SC706L	
		DPAK (SOT428)			6.6 x 6.1 x 2.3					DPAK	TO-252 (MP-3ZK)	TO-252-3/-3-2 3		TO-252, TO-252 reverse	
		D2PAK (SOT404)			11.0 x 11.0 x 4.3				LPDS/ LPTS	TO-220SM	D2PAK D2PAK 3	TO-220S / SMD TO-263 LDPK(S)-1)	T0263-3	T0263 (D2PAK)	TO-263 3-lead TO-263AB / D2PAK
SOT23				2.9 x 1.3 x 1.0	250		SSD3/ SST3	S-Mini TSM	SOT-23	MPAK	SOT23	SOT-23	SOT23	SOT23	
SOT89		SC-62		4.5 x 2.5 x 1.5	1300		MPT3	PW-Mini	SOT-89	UPAK (SOT89)	SOT89	SOT89		SC-75	
SOT323		SC-70		2.0 x 1.25 x 0.95	200		UMD3/ UMT3 TUMT3	USM	SC-70	CMAK/ CMPAK	SOT323	SOT-323	SOT-323	SC-70 3 leads	
4		LFPK56 (SOT669)	Power-S08	4.9 x 4.45 x 1.0	3000					SO-8 FL	LFPK	PG-TD-SON-8	Power-Di5060-8	PowerFLAT (6x5)	PowerPAK SO-8
	SOT143B		2.9 x 1.3 x 1.0	250					CP4		MPAK-4R	SOT143	SOT-143	SOT-143	
	SOT223	SC-73	6.5 x 3.5 x 1.65	1700						SOT-223		SOT223	SOT-223	SOT223	

Types in brackets (...) show footprint compatibility only

Package cross reference matrix – Part 2

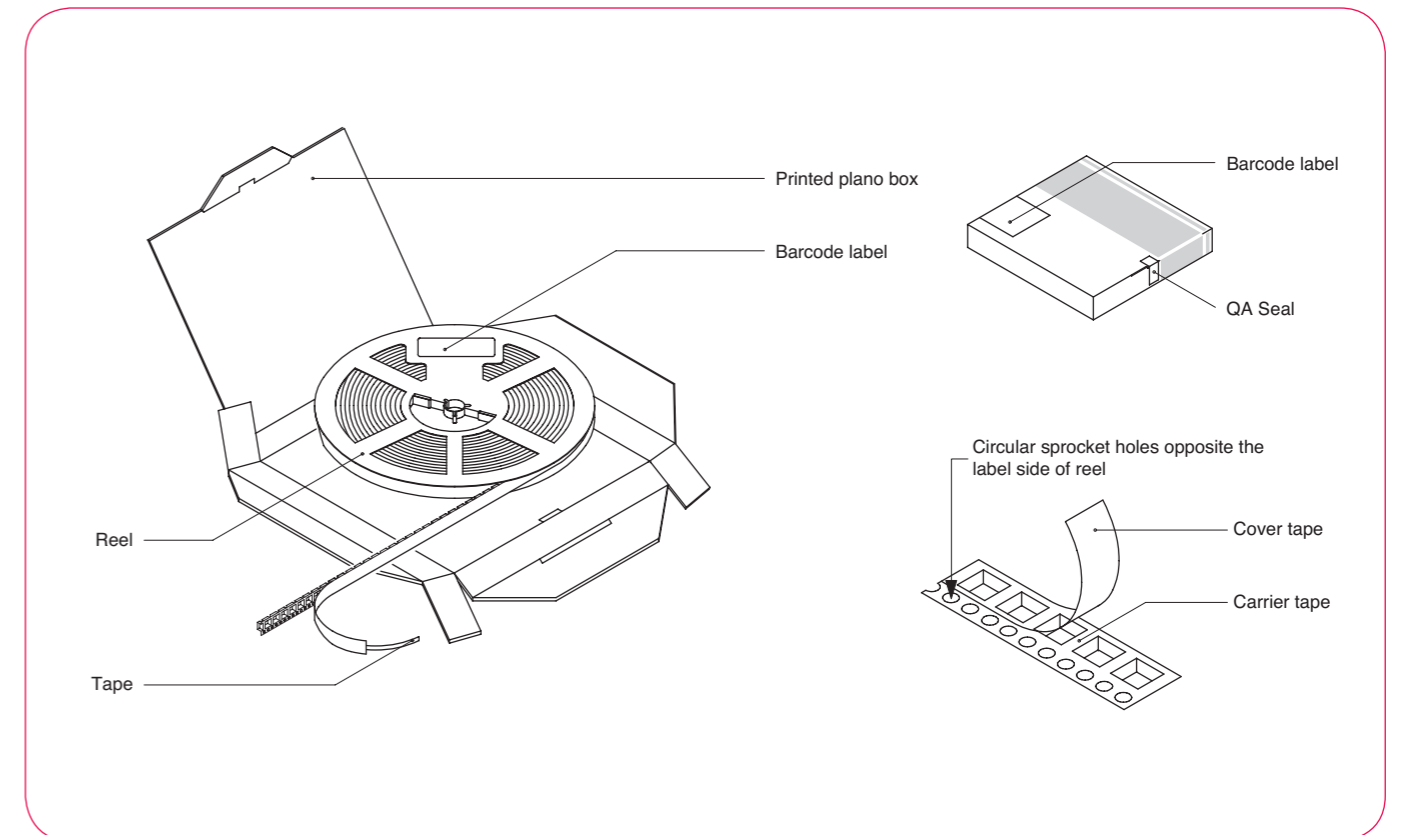
Pins / leads	NXP	Industry standard names	Size (l x w x h) (mm)	P _{tot} (mW)	Package	Competitor synonyms											
						Rohm	Toshiba	ON Semi	Renesas	Infineon	Diodes Inc	ST	Vishay	Semtech			
5	SOT753		2.9 x 1.5 x 1.0														
	SOT353	SC-88 A	2.0 x 1.25 x 0.95	300		UMD5/UMT5	USV	SC-88 A	CMPAK-5C0		SOT353		SOT353		SC70-5L		
	SOT665		1.6 x 1.2 x 0.55	300		EMD5/EMT5	ESV	SOT-553	VSON-5								
6	DFN1010-6 (SOT891)	x SON6	1.0 x 1.0 x 0.48				CS6	SOT963									
	DFN1010B-6 (SOT1216)		1.1 x 1.0 x 0.37	350		VMT6)	(FS6)	(SOT063)			(SOT963)						
	DFN1010E-6 (SOT1202)							(SOT963)		TLSP-6-1							
	DFN1410-6 (SOT886)	x SON6	1.45 x 1.0 x 0.48	250											SLP1510N6		
	DFN1616-6 (SOT1189)	H x SON6	1.6 x 1.6 x 0.48					UDFN 1.6 x 1.6					LLP75-/L		SLP1616P6		
	DFN2020-6 (SOT1118)		2.0 x 2.0 x 0.62	1300		HU-ML2020L8 (Dual)	UDFN6	6 Lead DFN WDFN6			UDFN2020-6 Type B		PowerPAK SC-70 Thin PowerPAK SC-70				
	DFN2020D-6 (SOT1118D)		2.0 x 2.0 x 0.62	1300		HU-ML2020L8 (Dual)	UDFN6	6 Lead DFN WDFN6			UDFN2020-6 Type B		PowerPAK SC-70 Thin PowerPAK SC-70				
	DFN2020MD-6 (SOT1220)		2.0 x 2.0 x 0.62	1250		HU-ML2020L8 (Single)	UDFN6B	UDFN-6 WDFN6			UDFN2020-6 Type E		PowerPAK SC-70 Thin PowerPAK SC-70				
	LFPK56D (SOT1205)		4.9 x 4.45 x 1.0	3000								PowerFLAT (6x5)					
	SOT363	SC-88	2.0 x 1.25 x 0.95	300		UMD6/UMT6	US6 UF6 USV	SC-88	CMPAK-6	SOT363	SOT-363		SC70-6		SC70-6L		
	SOT457	SC-74	2.9 x 1.5 x 1.0	750		SMD6/SMT6	SM6 VS-6	SC-74 TSOP-6	TSOP-6	SC74 TSOP6	SOT23-6 SOT26		TSOP6 TSOP-6		SOT23-6L		
	SOT666		1.6 x 1.2 x 0.55	300		EMD6/EMT6 WEMT6	ES6 ESV	SOT-563	SMFPAK-6	SOT666	SOT563		SC89-6lead		SC-89		
	8	SOT96	S08	4.9 x 3.9 x 1.75	1500		SOP8	FM8	SOIC-8 NB	SOP-8				S08			
		SOT505	TSSOP8	3.0 x 3.0 x 1.1					TSSOP-8								
		DFN1712-8 (SOT1157)	H x SON8	1.7 x 1.2 x 0.48					UDFN8, 1.8 x 1.2, 0.4P								
		DFN1714-8 (SOT 1166)	HUSON8	1.7 x 1.35 x 0.52												SLP1713P8	
9	DFN1714U-8 (SOT983)	H x SON8	1.7 x 1.35 x 0.48					UDFN 1.7 x 1.35, 0.4P							SLP1713P8		
	DFN2110-9 (SOT1178)	x SON9	2.1 x 1.0 x 0.48												SLP2010P8T		
10	DFN2510-10 (SOT 1165)	x SON10	2.5 x 1.0 x 0.48					WDFN 10 2.5 x 2 UDFN10 2.5 x 2									
	DFN2510A-10 (SOT1176)	x SON10	2.5 x 1.0 x 0.48					UDFN10 2.5 x 1, 0.5P		TSLP-9-1		pQFN-10L		SLP1610P4			
	SOT552	TSSOP10	3.0 x 3.0 x 1.1					Micro 10		TSSOP10				MSOP-10L			
	DFN2626-10 (SOT 1197)		2.6 x 2.6 x 0.48					UDFN10 2.6 x 2.6, 0.5P							SLP2626P10		

Package cross reference matrix – Part 3

Pins / leads	NXP	Industry standard names	Size (l x w x h) (mm)	P _{tot} (mW)	Package	Competitor synonyms										
						Rohm	Toshiba	ON Semi	Renesas	Infineon	Diodes Inc	ST	Vishay	Semtech		
12	DFN2512-12 (SOT 1158)	H x -SON12	2.5 x 1.2 x 0.48					UDFN12, 2.5 x 1.2, 0.4P								
	DFN2514-12 (SOT 1167)	HU-SON12	2.5 x 1.35 x 0.53					UDFN12, 2.5 x 1.35, 0.4P							SLP2513P12	
	DFN2514U-12 (SOT984)	H x -SON12	2.5 x 1.35 x 0.48												SLP2513P12	
14	DFN4020-14 (SOT 1334)		4.0 x 2.0 x 0.48					WDFN 16 4 x 2 UDRN 16 4 x 2								
	SOT 108	S014	8.65 x 3.9 x 1.75			SOP 14				DS014						
16	DFN3312-16 (SOT 1159)	H x -SON16	3.3 x 1.2 x 0.48					UDFN 16, 3.5 x 1.2, 0.4P								
	DFN3314-16 (SOT 1168)	HU-SON16	3.3 x 1.35 x 0.53												SLP3313P16	
	DFN3314U-16 (SOT985)	H x -SON16	3.3 x 1.35 x 0.48					UDFN 16, 3.3 x 1.35, 0.4P							SLP3313P16	
20	SOT360	TSSOP20	6.5 x 4.4 x 1.1					TSSOP20		TSSOP20						
38	SOT510	TSSOP38	9.7 x 4.4 x 1.1							TSSOP38						

Types in brackets (...) show footprint compatibility only

Tape and reel pack for SMD and WLCSP packages



Product orientation (tape and reel pack)

Orientation in tape	Package	Packing 12NC ending
	DFN1006-2 (SOD882)	315
	DFN1006D-2 (SOD882D)	315
	DFN1608D-2 (SOD1608)	315
	DSN0603-2 (SOD962)	315
	DSN0402-2 (SOD992)	315
	DSN1006-2 (SOD993)	315
	DSN1006U-2 (SOD995)	315
	SOD80	115, 135
	SOD123F	115
	SOD123W	115
	SOD128	115
	SOD523	115, 135, 315, 335

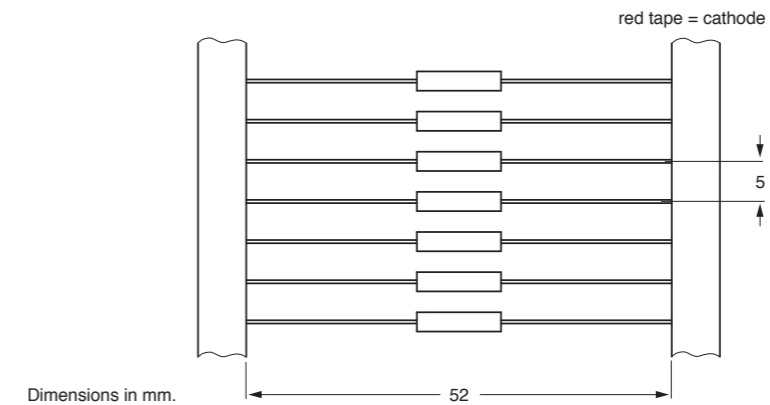
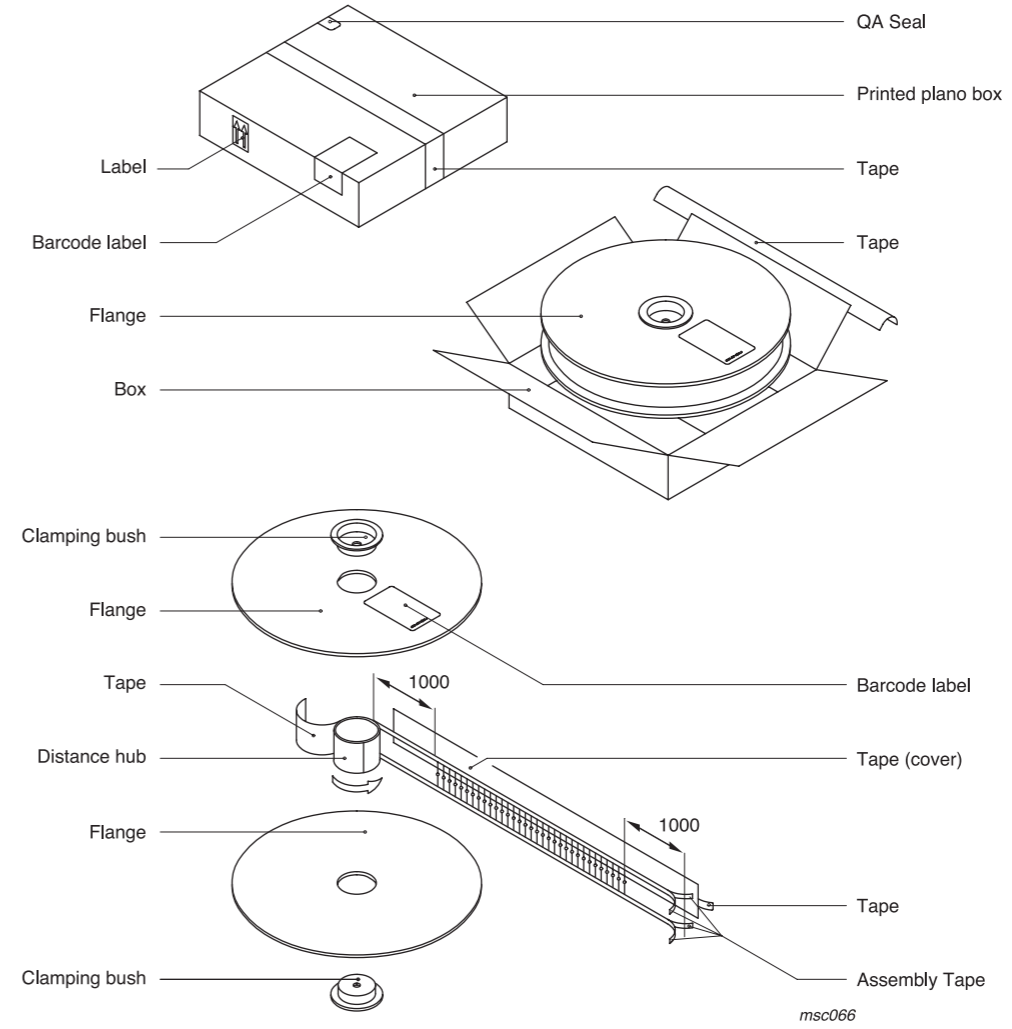
Orientation in tape	Package	Packing 12NC ending	Orientation in tape	Package	Packing 12NC ending
	SOT89	146		DFN1010D-3 (SOT1215)	147
				DFN2020-3 (SOT1061)	115, 135
				DFN2020D-3 (SOT1061D)	115, 135
				SOT89	115, 135
				SOT663	115
				CFP15 (SOT1289)	139, 145
	DFN1006-3 (SOT883)	315		DPAK (SOT428)	118
	DFN1006B-3 (SOT883B)	315		D2PAK (SOT404)	118
	SOT23	185, 215, 235			
	SOT323	115, 135			
	SOT416	115, 135			

Orientation in tape	Package	Packing 12NC ending	Orientation in tape	Package	Packing 12NC ending
	LFPAK33 (SOT1210)	115			
	LFPAK56 (SOT669)	115			
	SOT143B	215, 235			
	SOT223	115, 135			
	DFN1010-4 (SOT1194)	115			

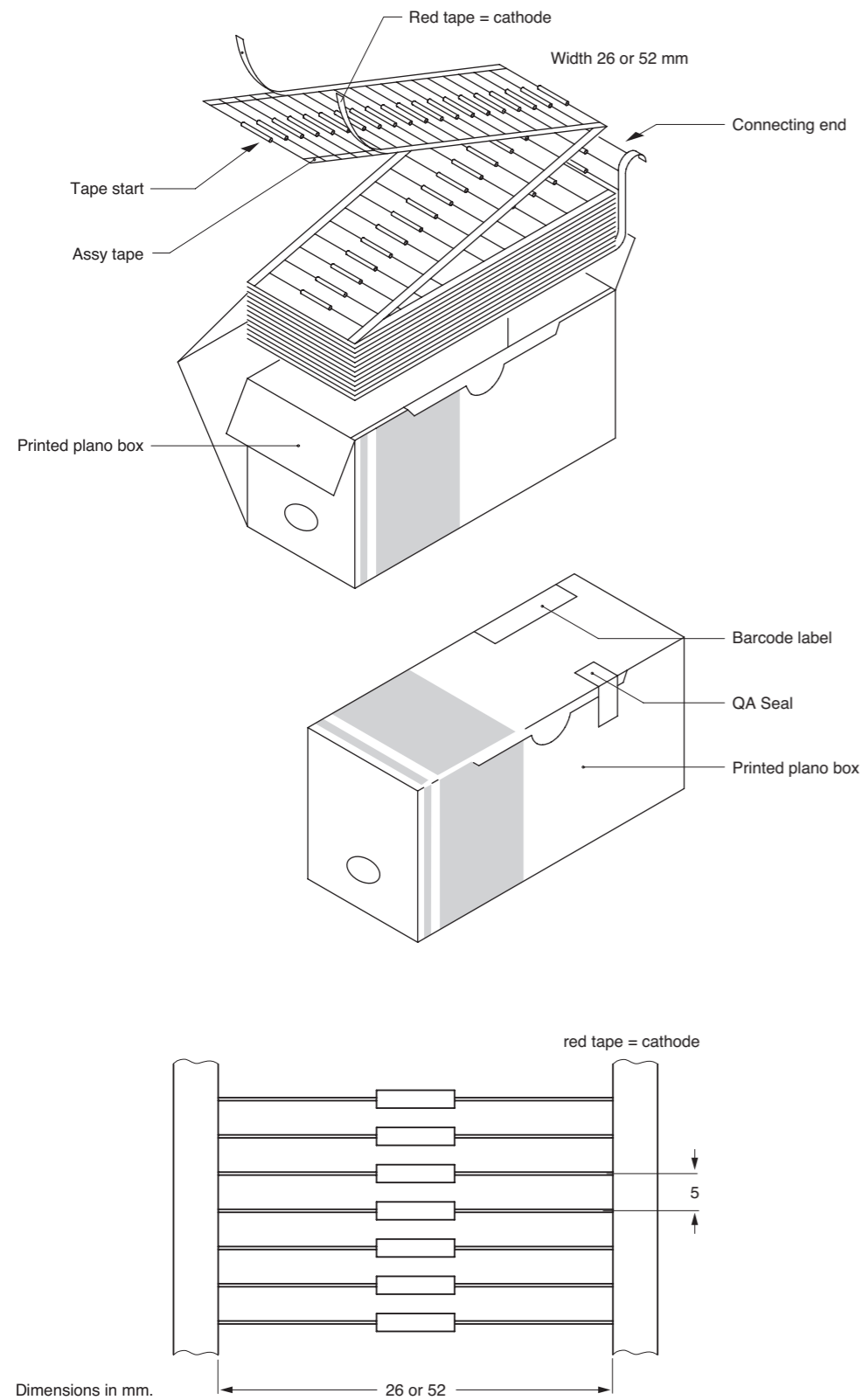
Orientation in tape	Package	Packing 12NC ending	Orientation in tape	Package	Packing 12NC ending
				SOT353	115, 135
				SOT665	115
	SOT753	125			

Orientation in tape	Package	Packing 12NC ending	Orientation in tape	Package	Packing 12NC ending
	DFN1410-6 (SOT886)	115		DFN2020-6 (SOT1118)	115
	DFN1616-6 (SOT1189)	115		DFN2020D-6 (SOT1118D)	115
	DFN2020MD-6 (SOT1220)	184		DFN2020MD-6 (SOT1220)	115
	LFPAK56D (SOT1205)	115		SOT363	115, 135
				SOT457	115, 135
	DFN1010-6 (SOT891)	132		SOT666	115, 315
	DFN1010E-6 (SOT1202)	132			
	DFN1410-6 (SOT886)	132			
	DFN2020MD-6 (SOT1220)	125			
	SOT363	125, 165			
	SOT457	125, 165			

Reel pack axial tape for glass diodes



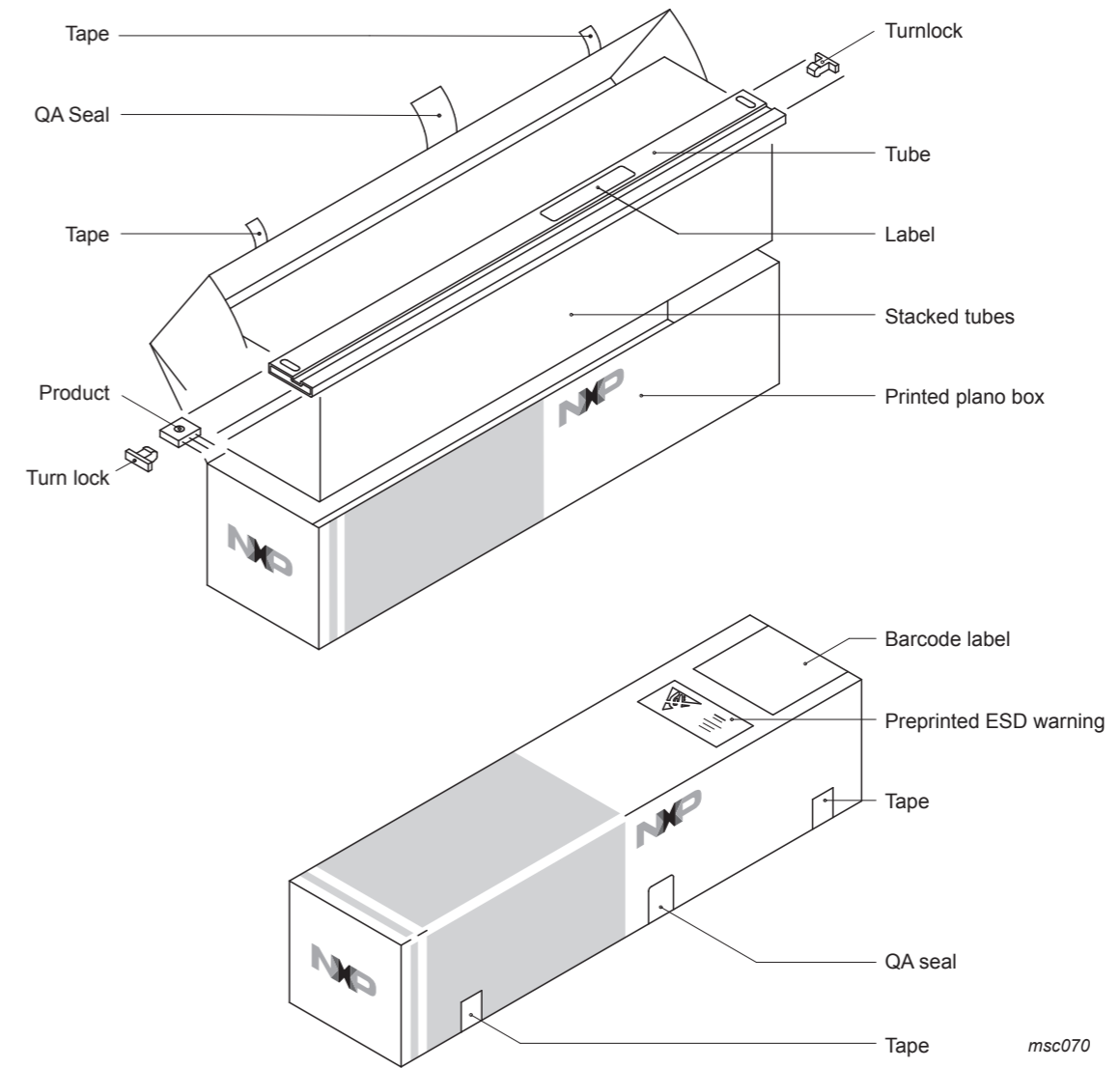
Ammo pack axial tape for glass diodes



Tube pack for through hole packages

Item	Material	Weight ⁽¹⁾ (g)
Printed plano box	Cardboard carbon coated	155.00
Tape	Polypropylene	0.10
Labels	Paper	28.71
Tube	Polyvinylchloride	720.00
Turnlock	Polyamide	24.00
Seal	Acrylate	0.15

(1) For SOT78

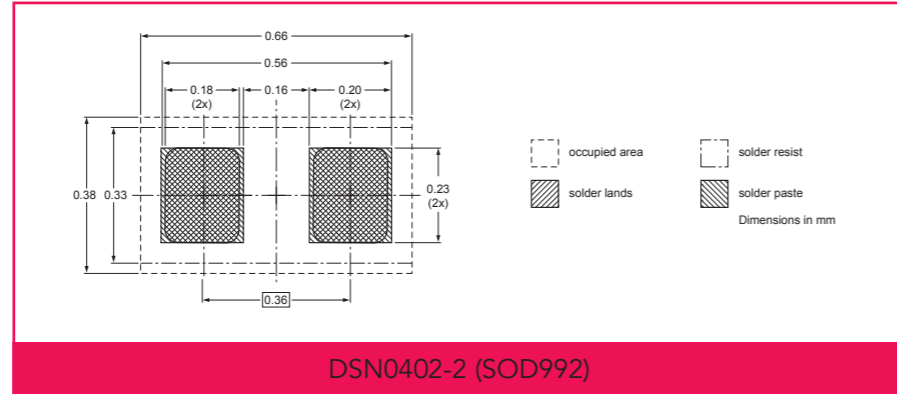
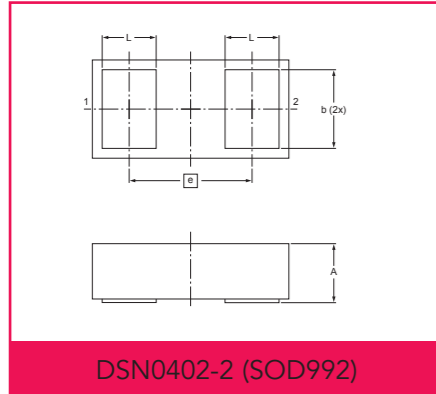


Outline and footprint drawings

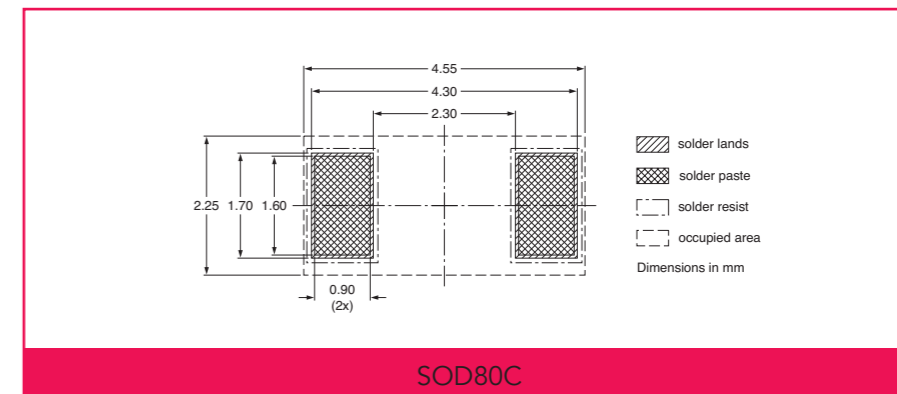
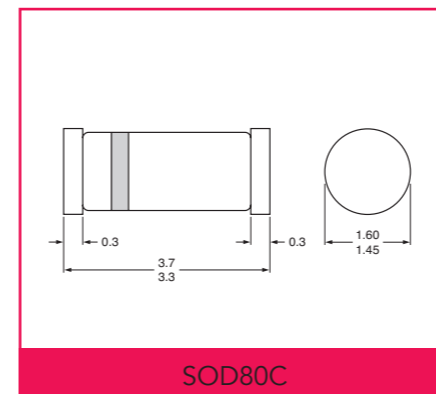
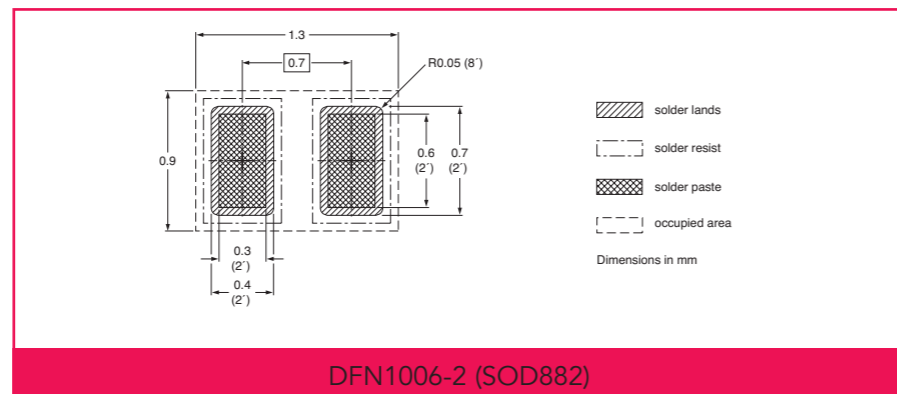
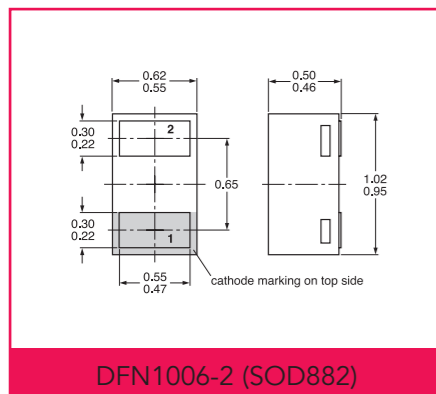
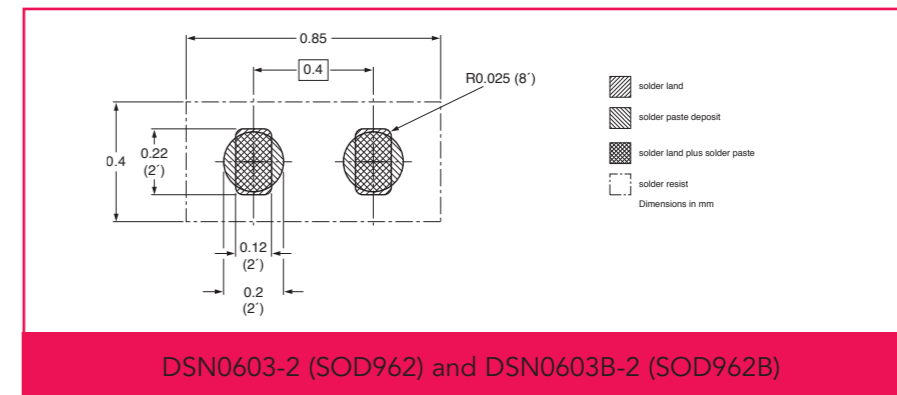
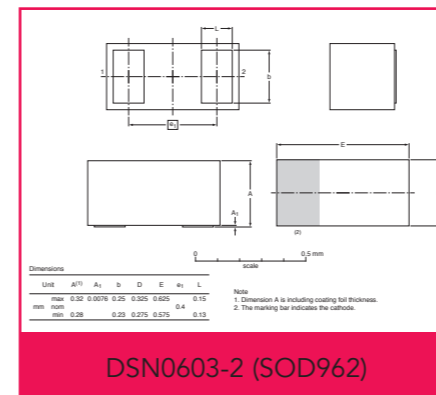
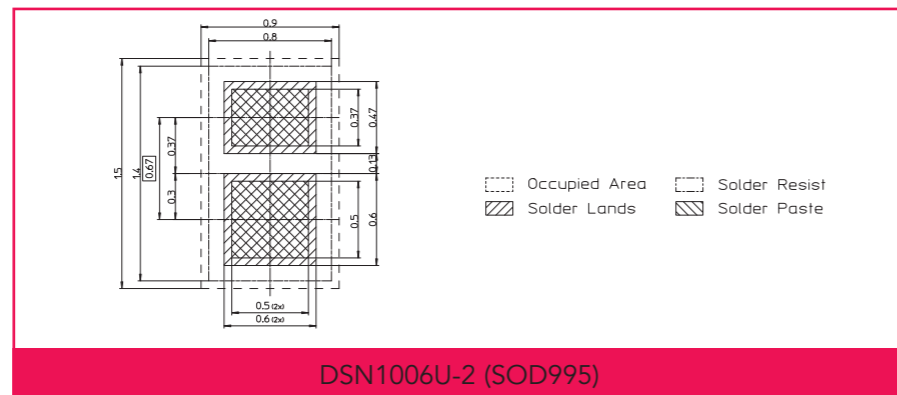
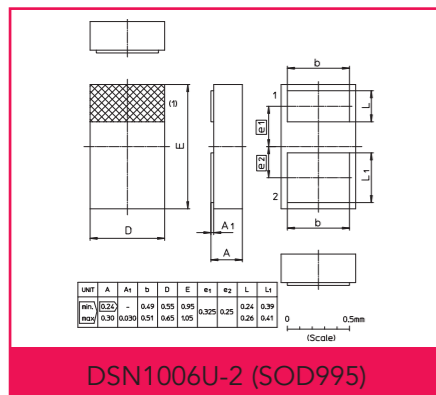
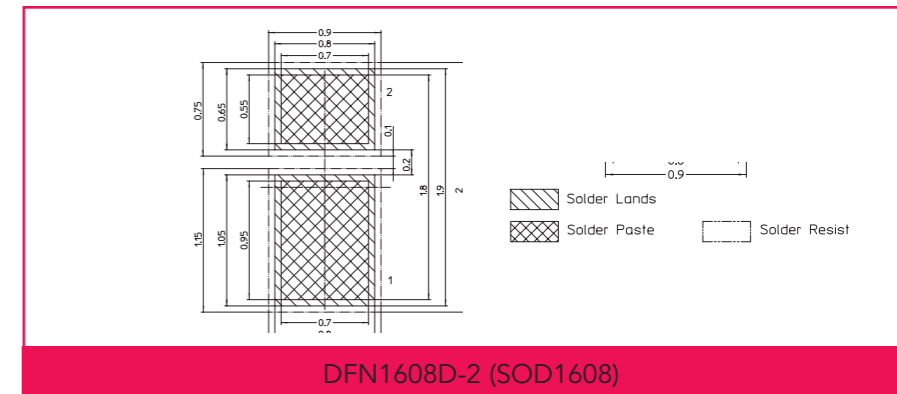
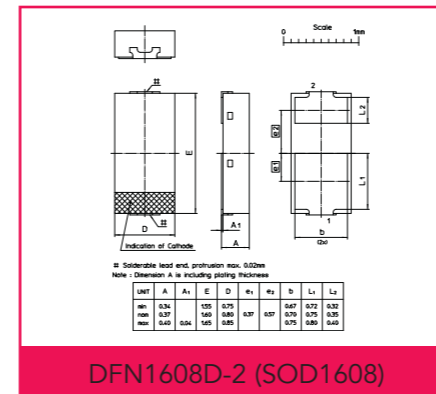
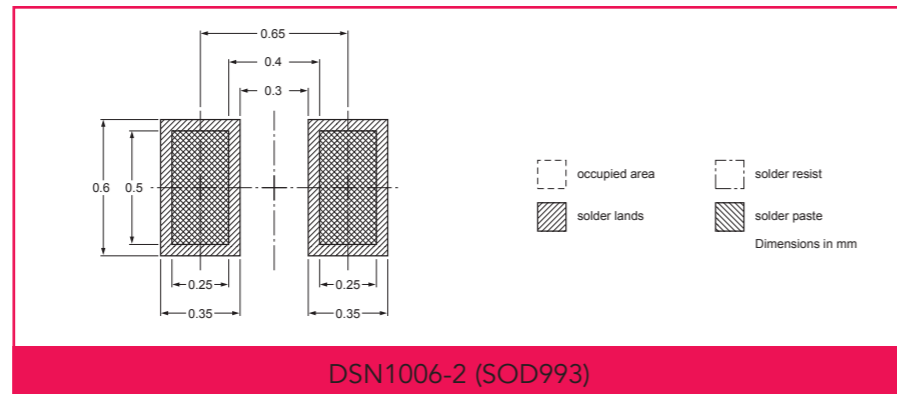
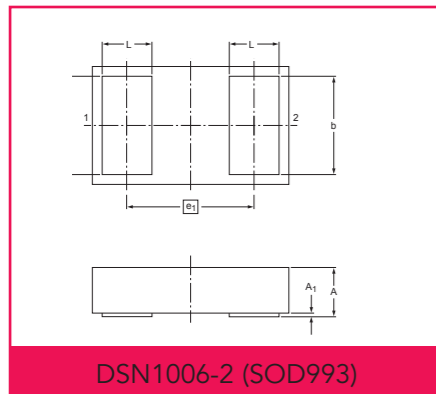
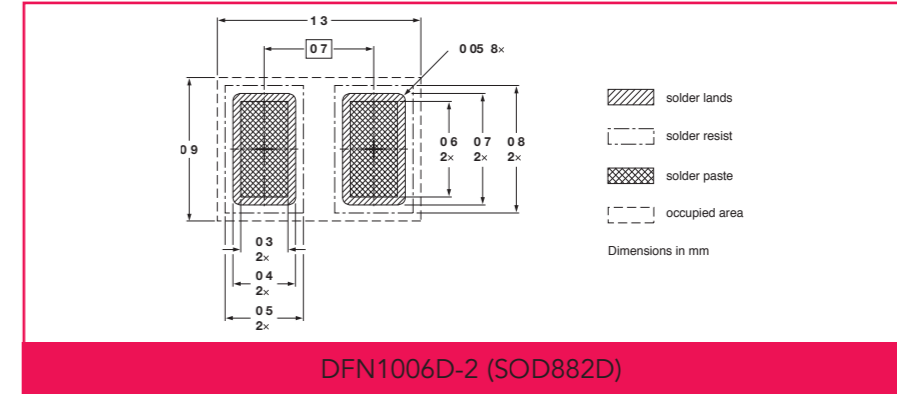
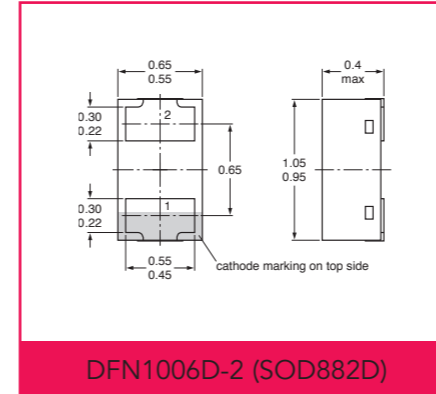
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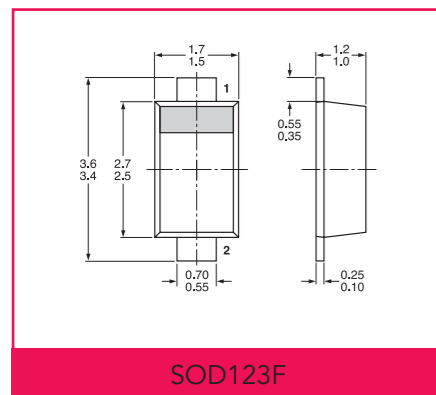
2-pin SMD packages



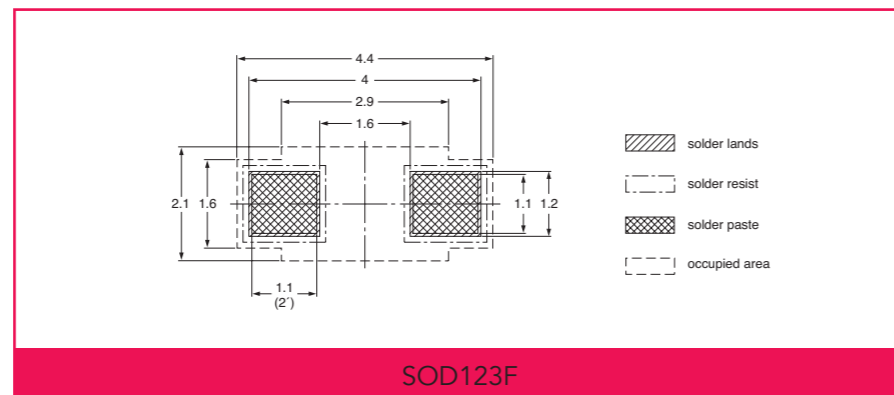
2-pin SMD packages



2-pin SMD packages

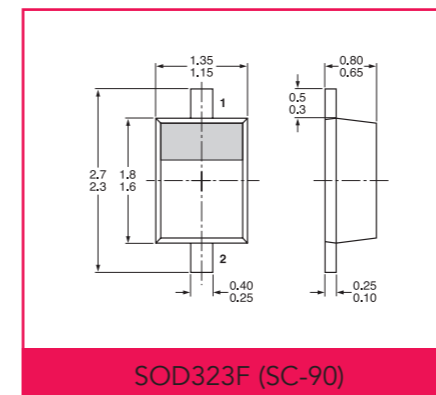


SOD123F

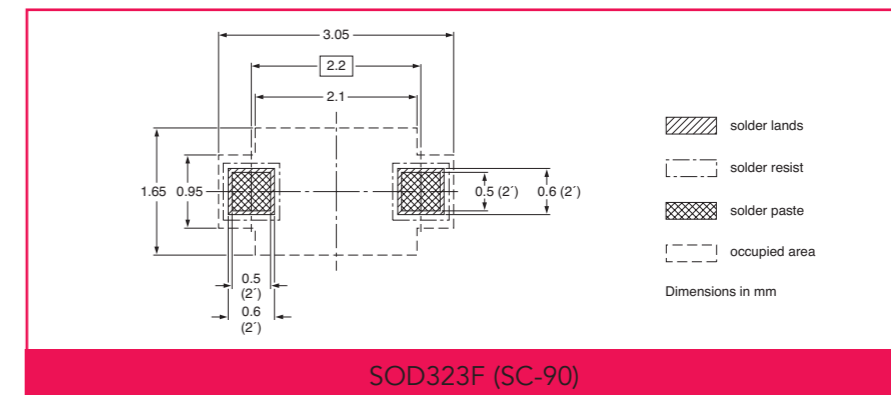


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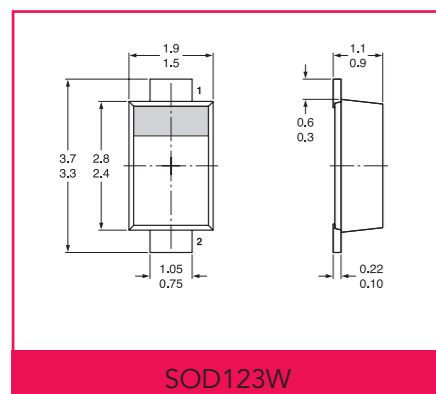
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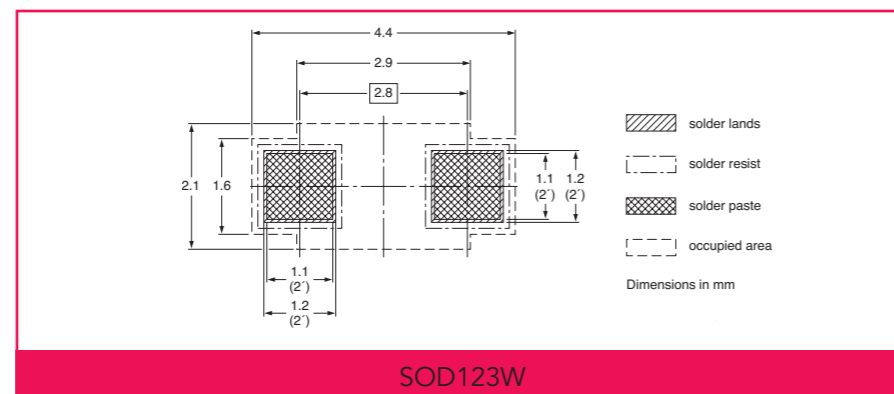
SOD323F (SC-90)



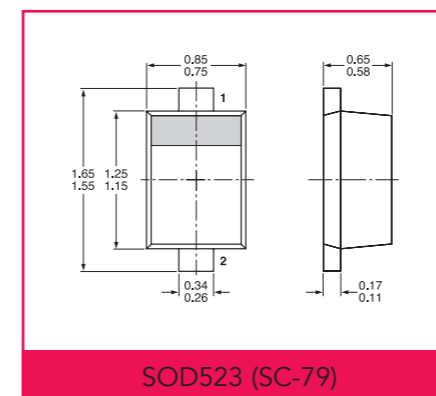
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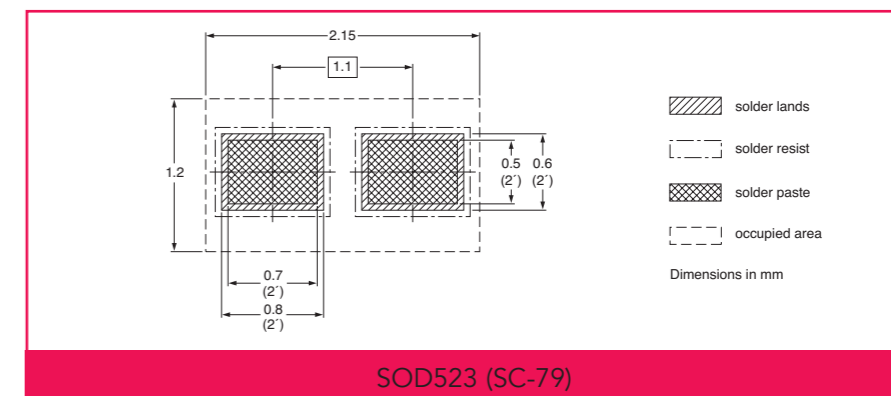
SOD123W



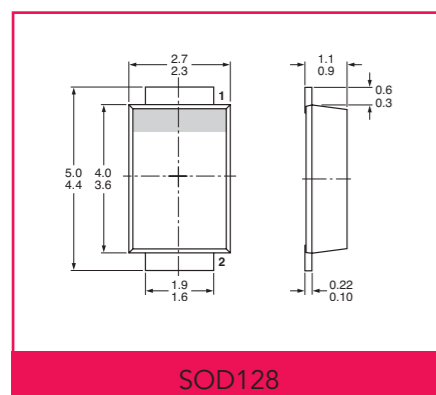
SOD123W



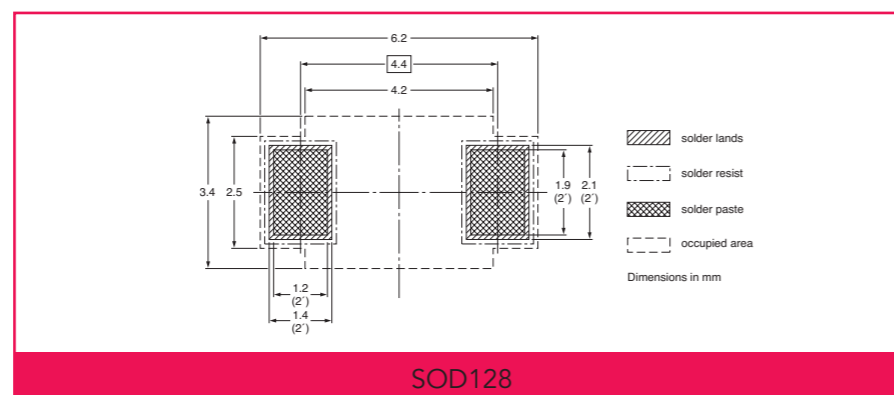
SOD523 (SC-79)



SOD523 (SC-79)

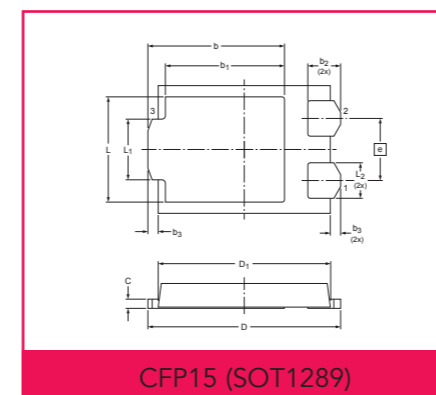


SOD128

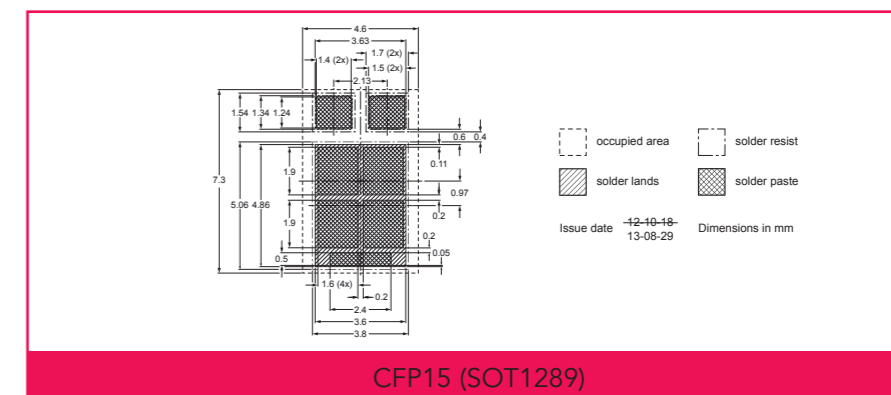


SOD128

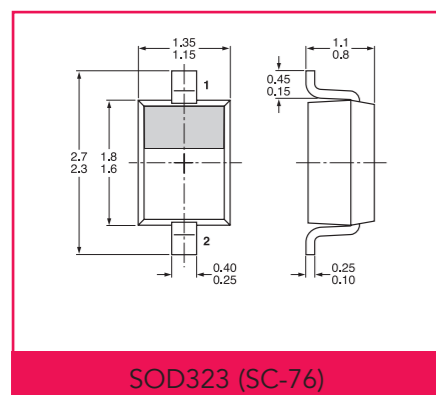
3-pin SMD packages



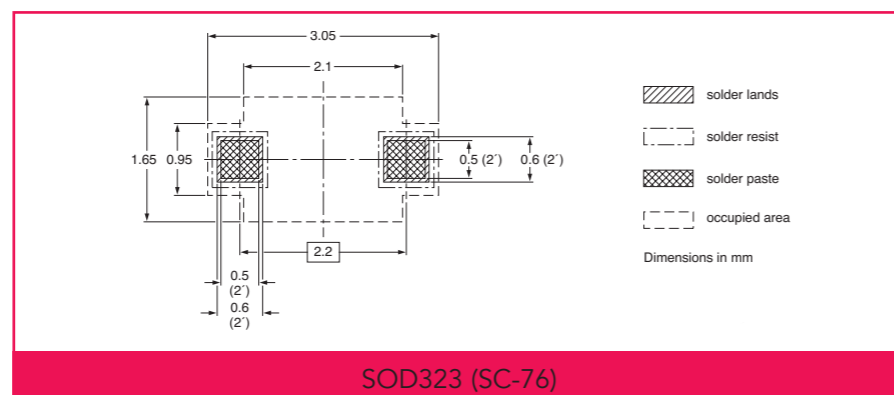
CFP15 (SOT1289)



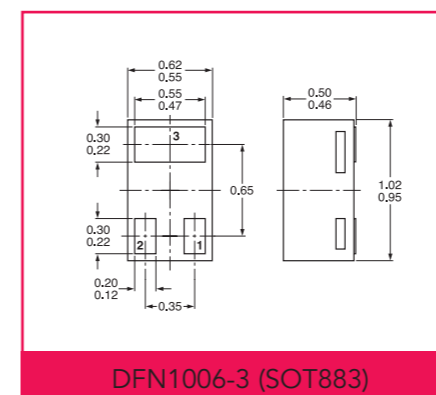
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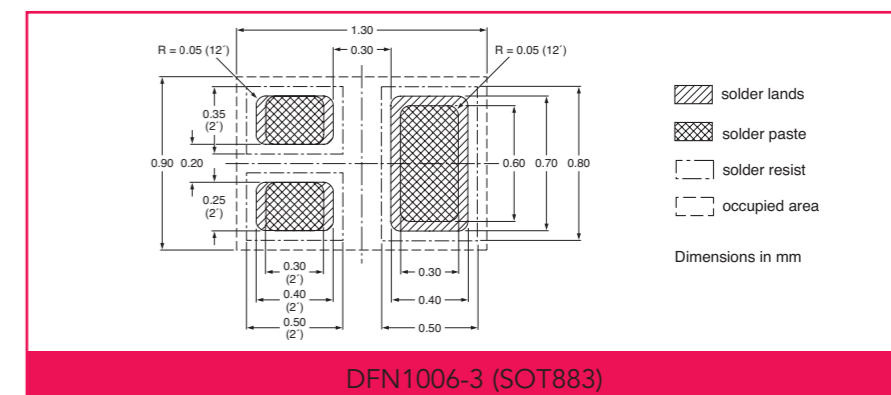
SOD323 (SC-76)



SOD323 (SC-76)

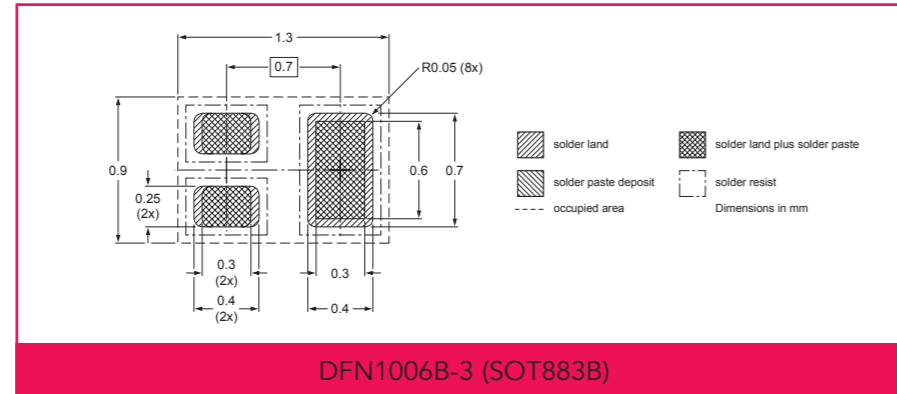
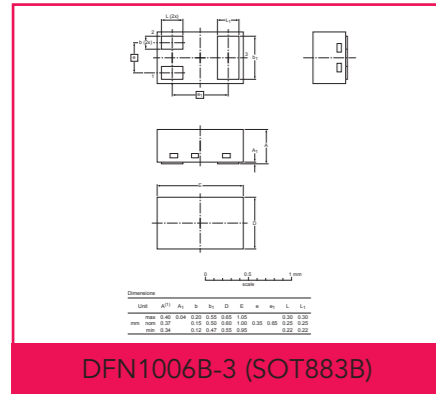


DFN1006-3 (SOT883)

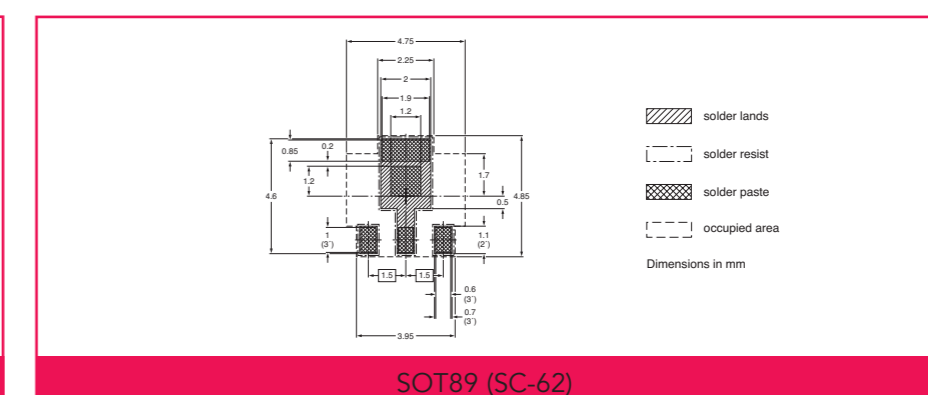
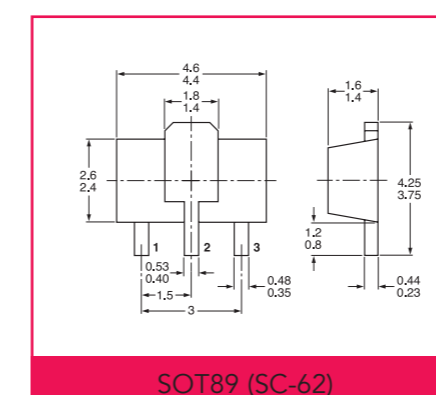
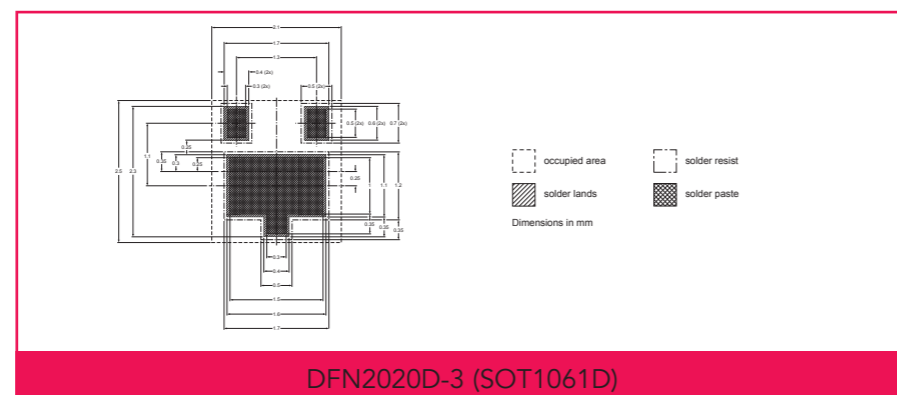
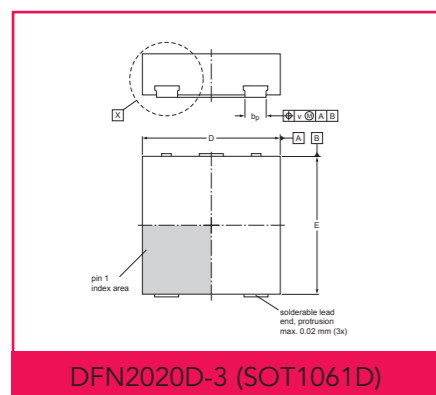
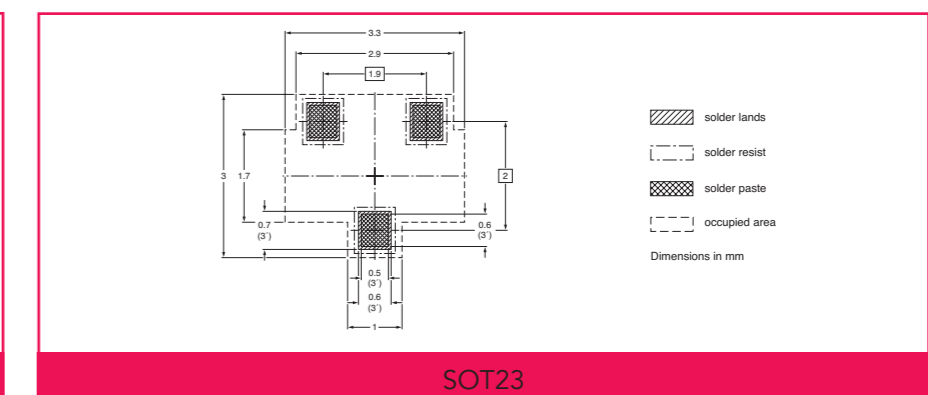
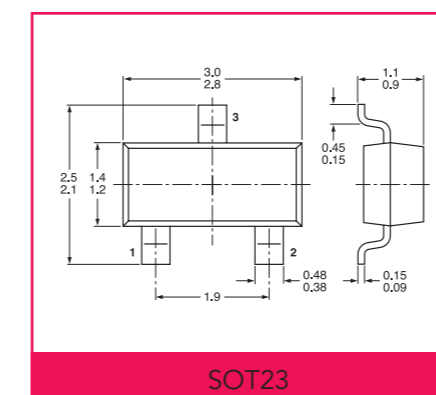
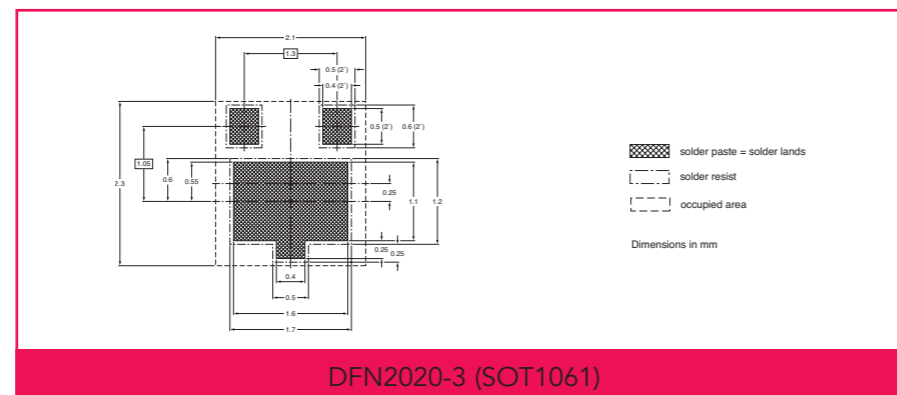
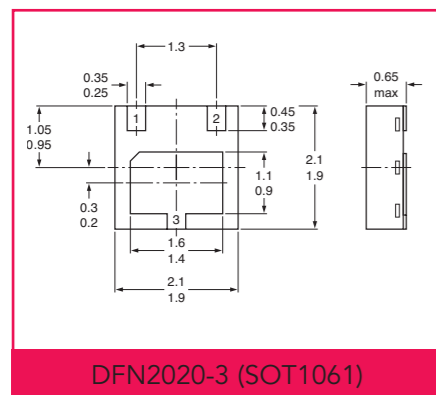
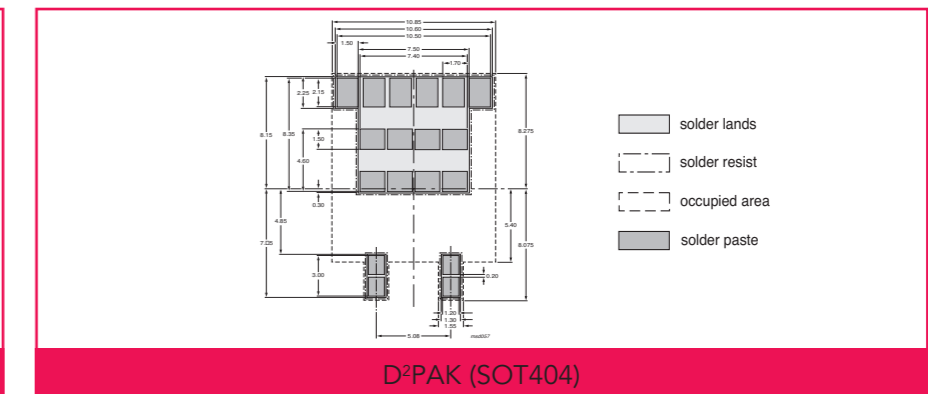
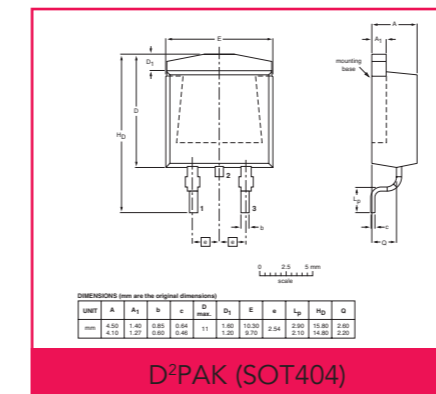
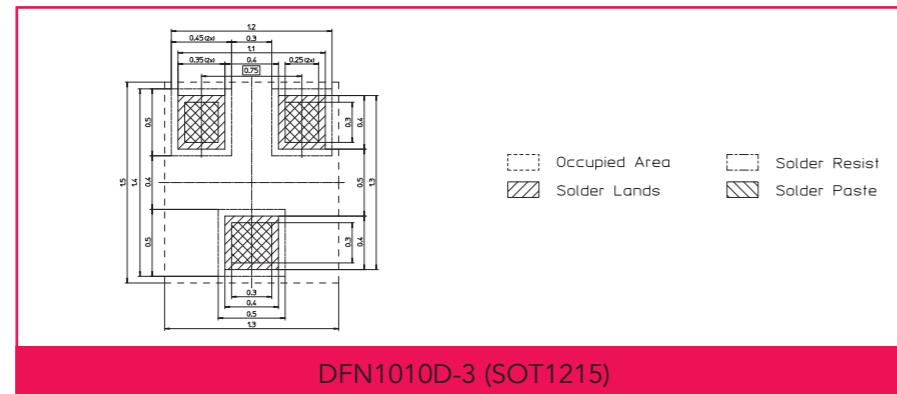
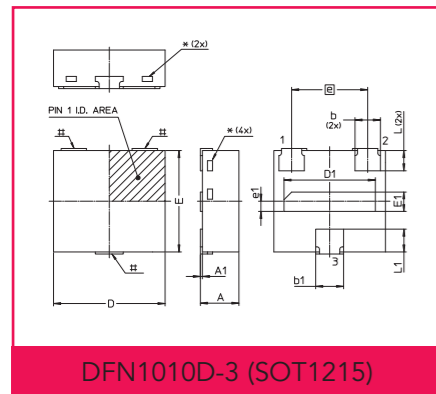
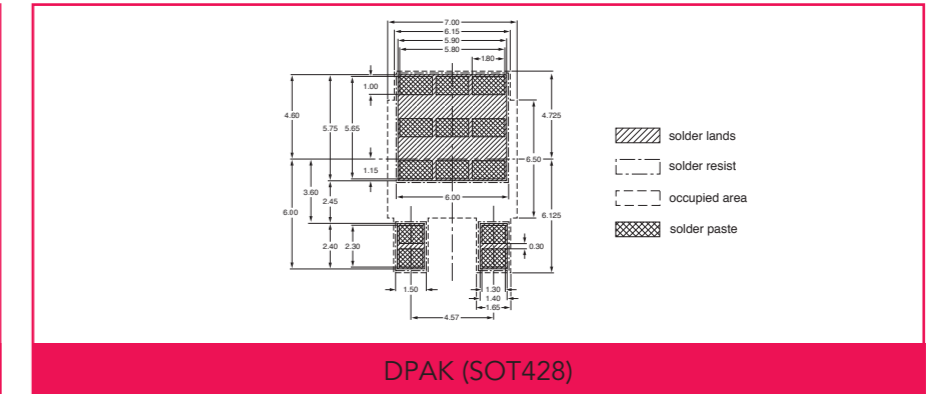
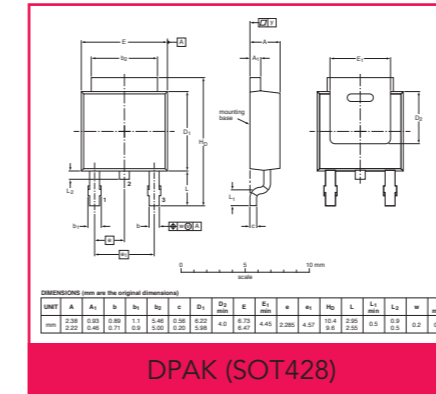


DFN1006-3 (SOT883)

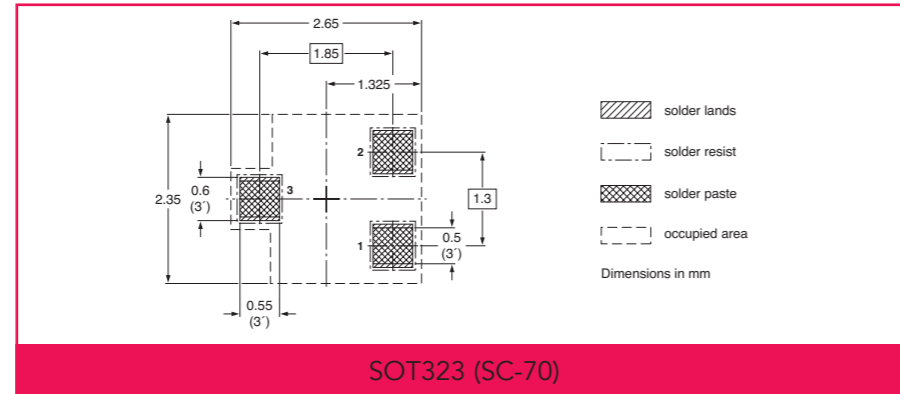
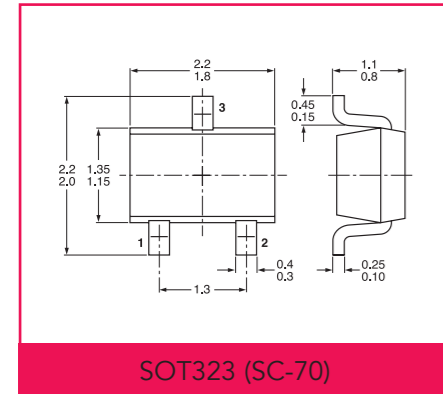
3-pin SMD packages



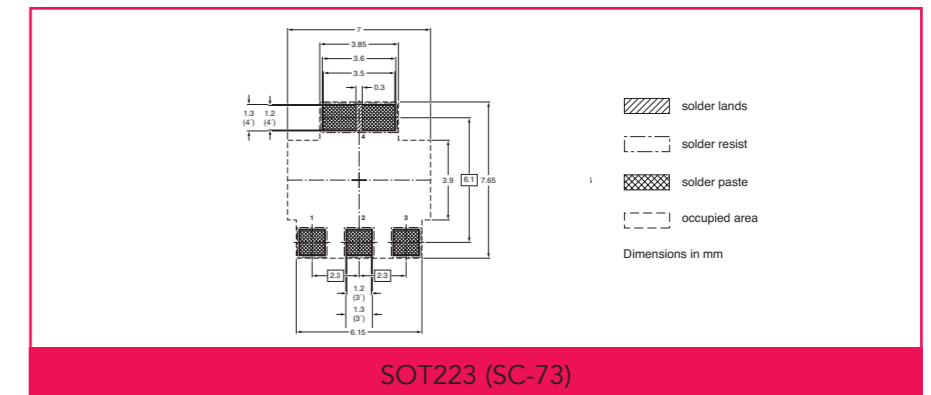
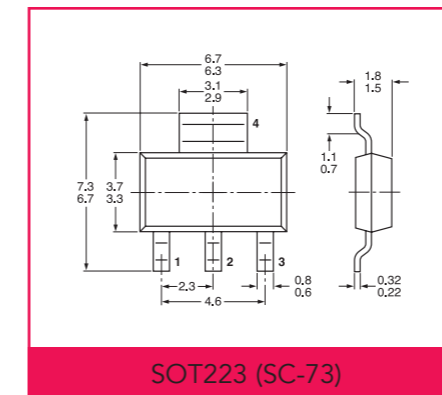
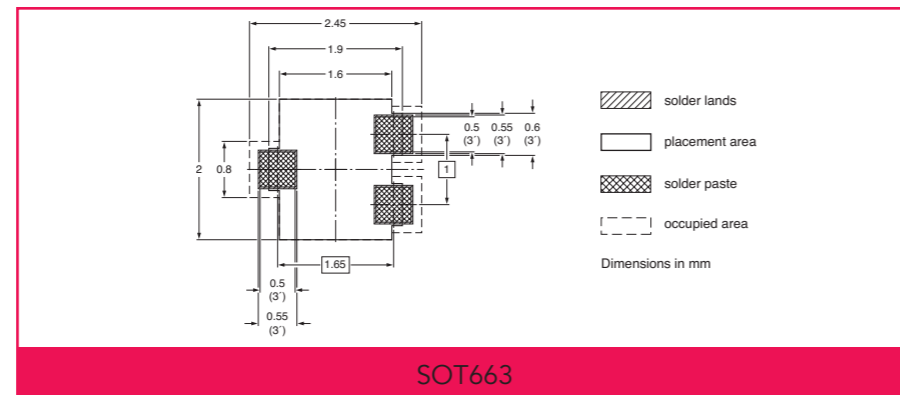
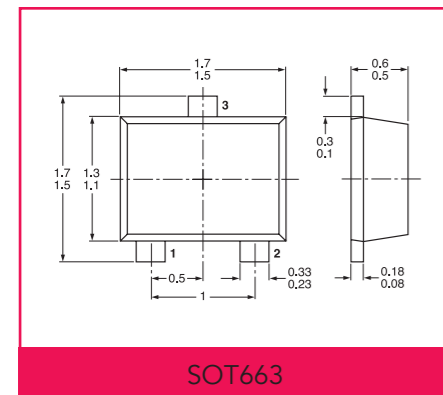
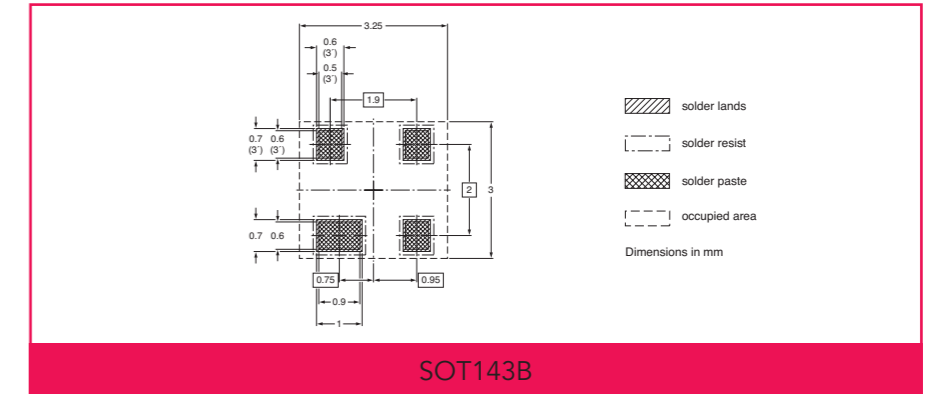
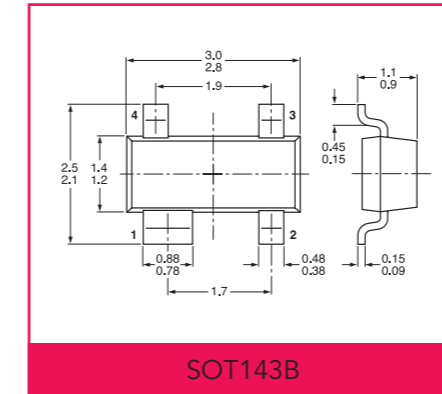
3-pin SMD packages



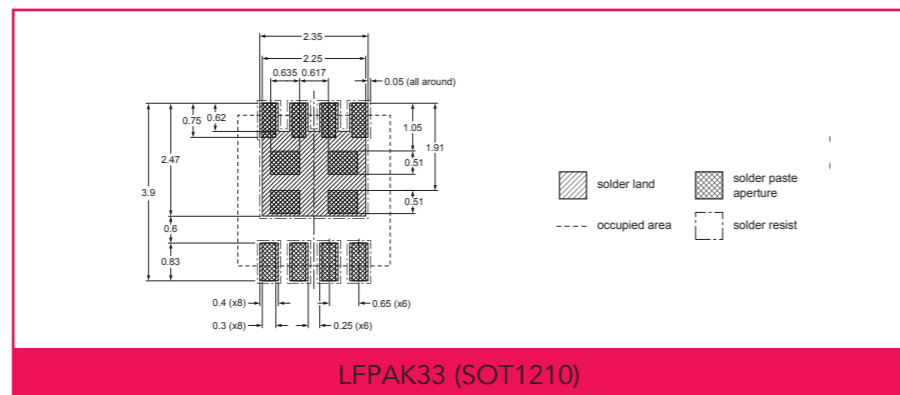
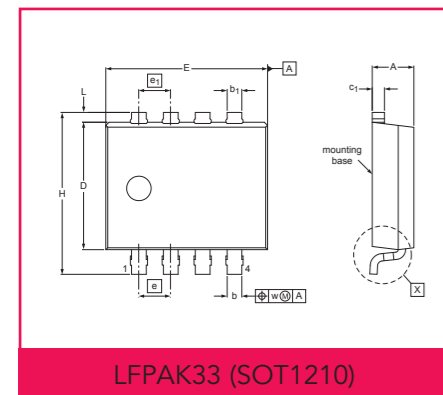
3-pin SMD packages



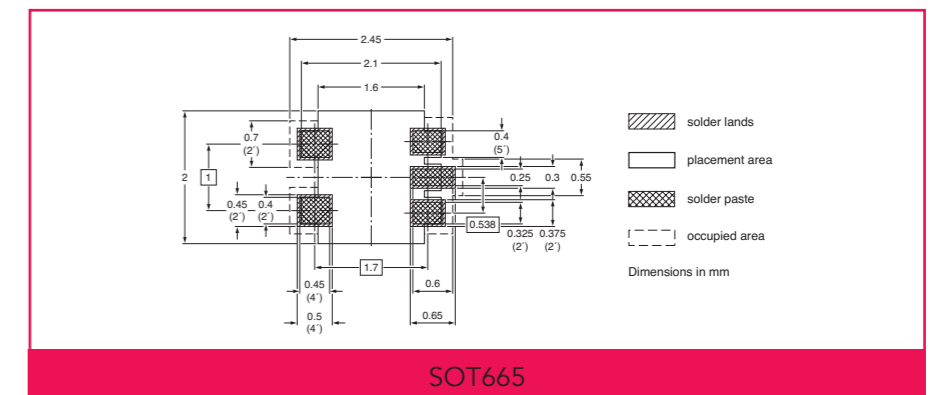
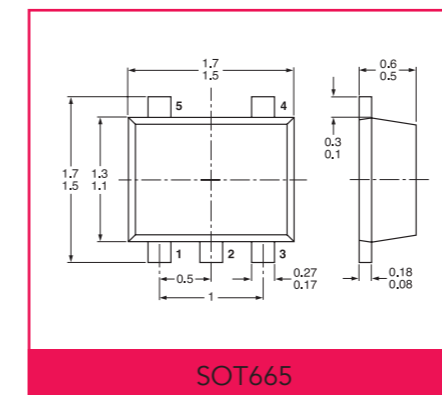
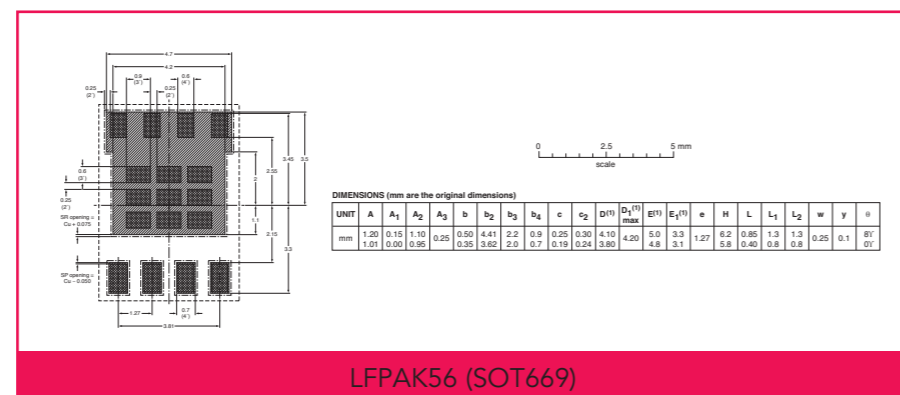
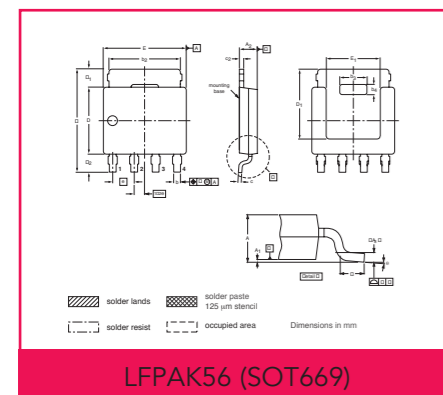
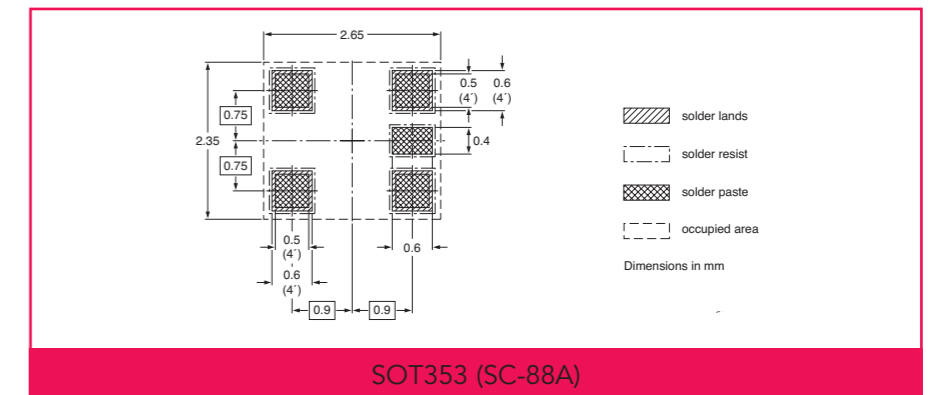
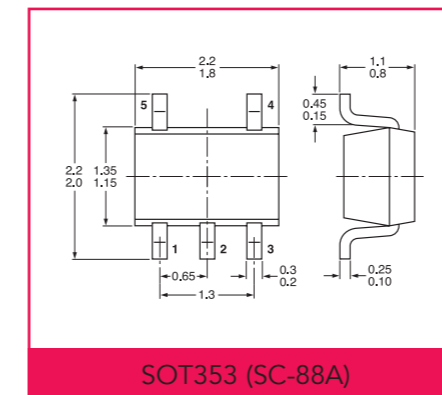
4-pin SMD packages



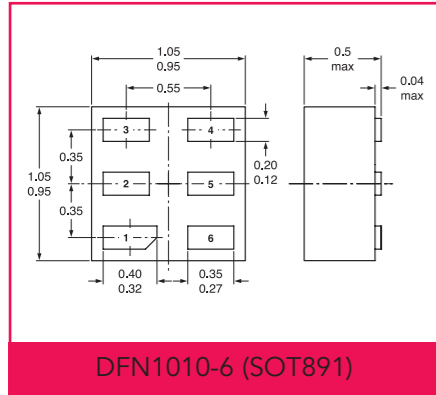
4-pin SMD packages



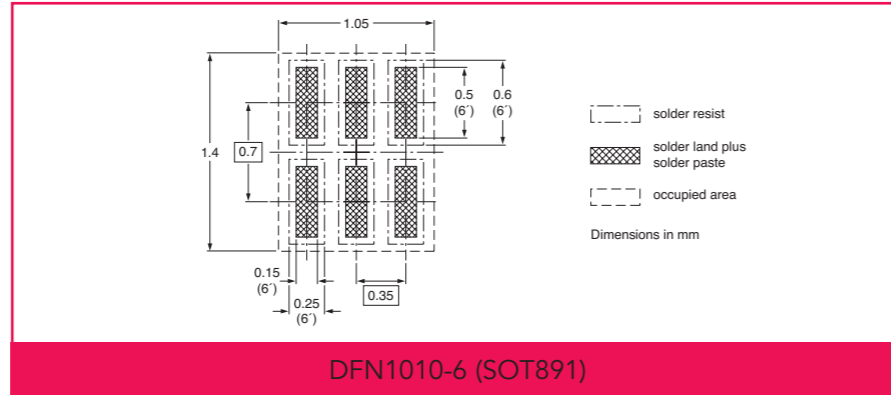
5-pin SMD packages



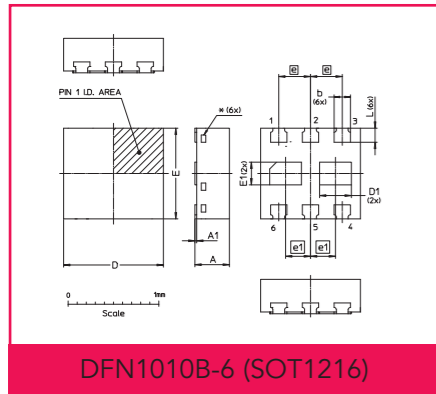
6-pin SMD packages



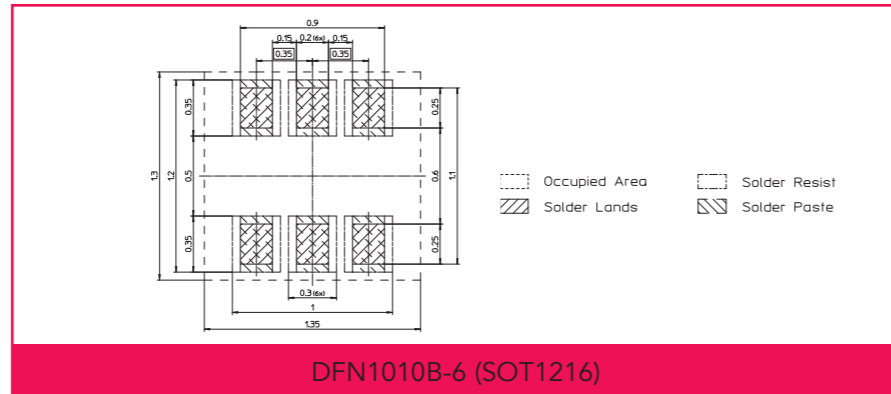
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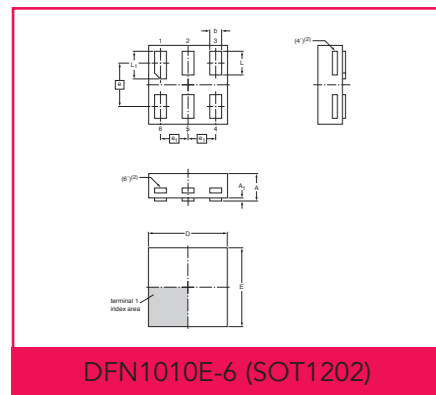
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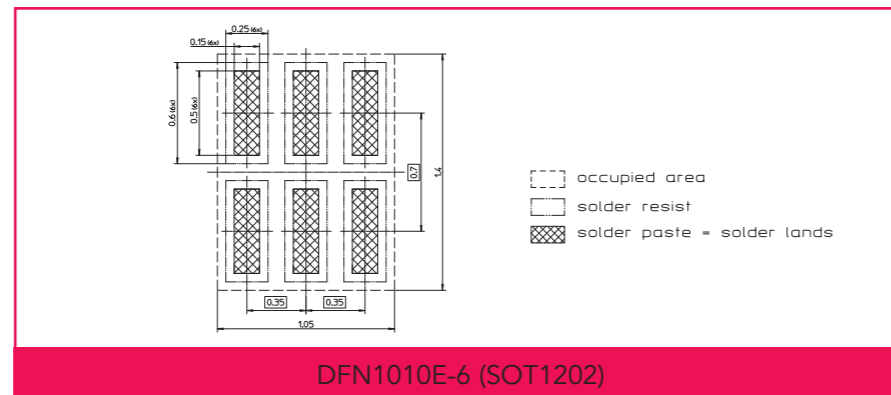
DFN1010B-6 (SOT1216)



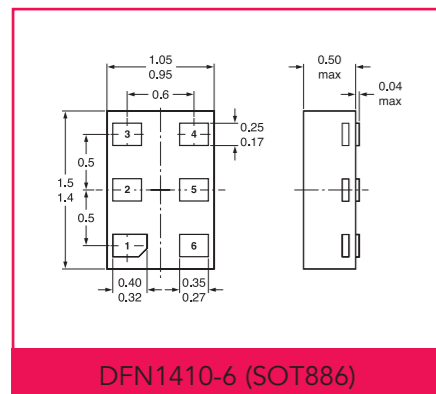
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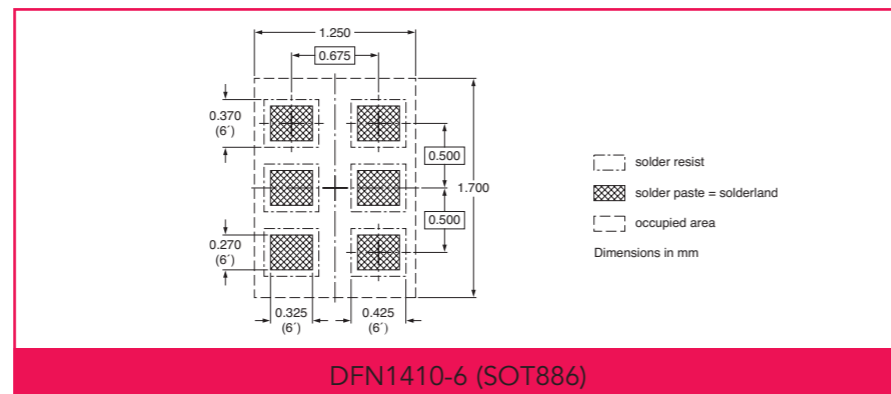
DFN1010E-6 (SOT1202)



DFN1010E-6 (SOT1202)



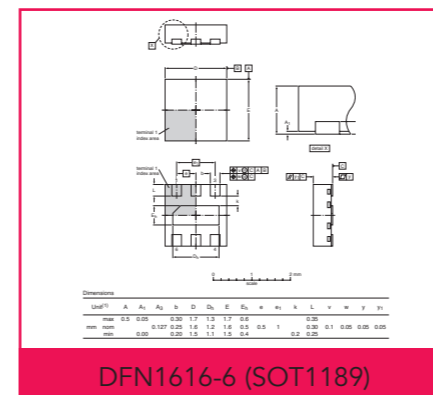
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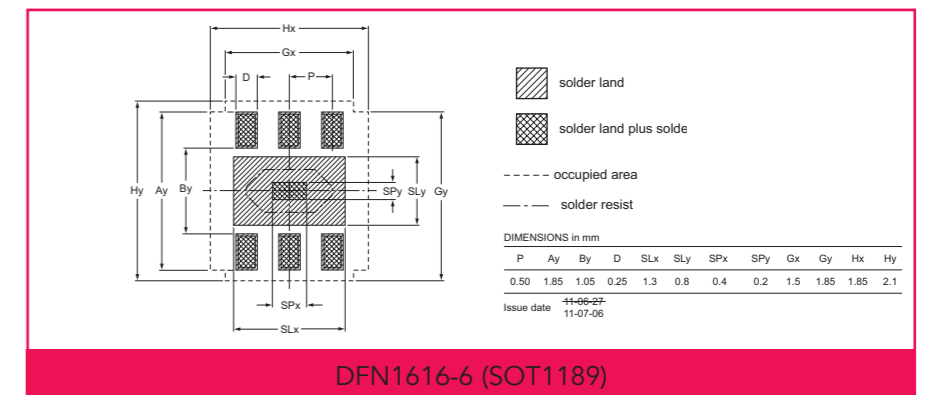
DFN1410-6 (SOT886)

Dimensions in mm

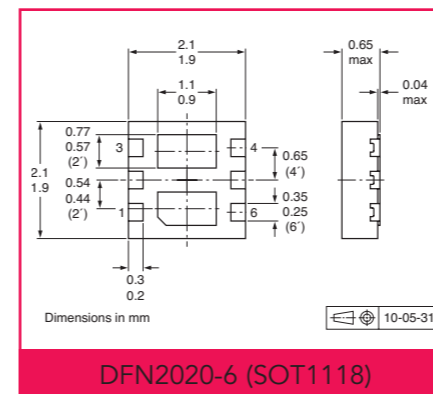
6-pin SMD packages



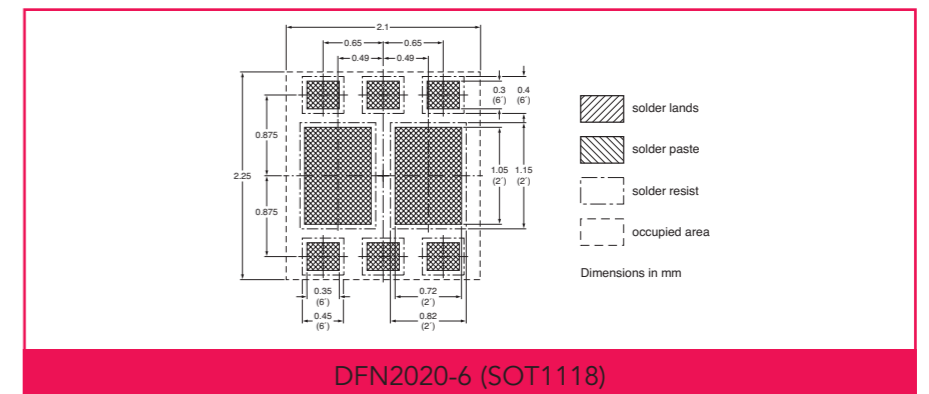
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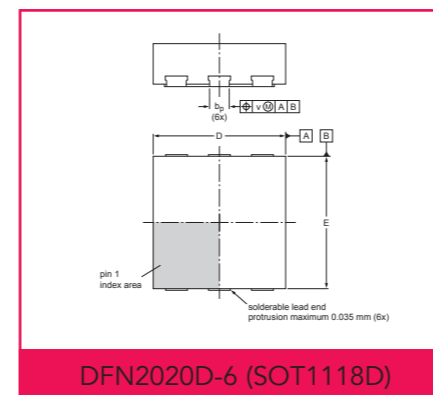
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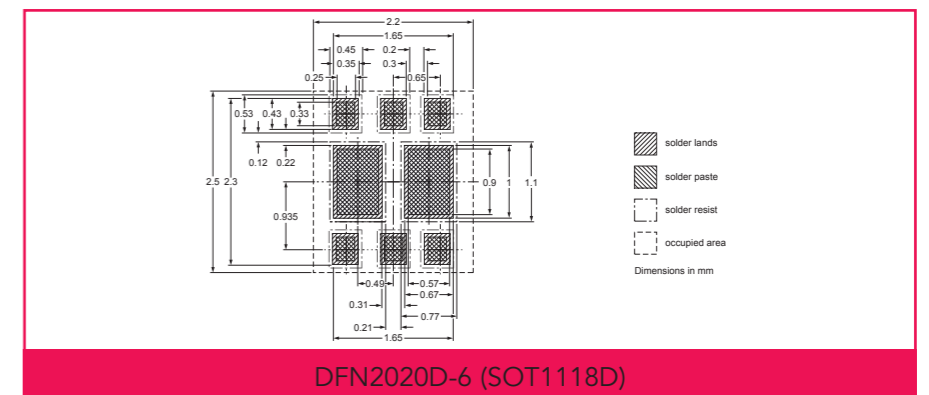
DFN2020-6 (SOT1118)



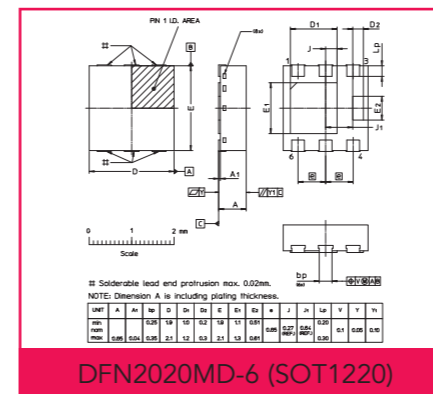
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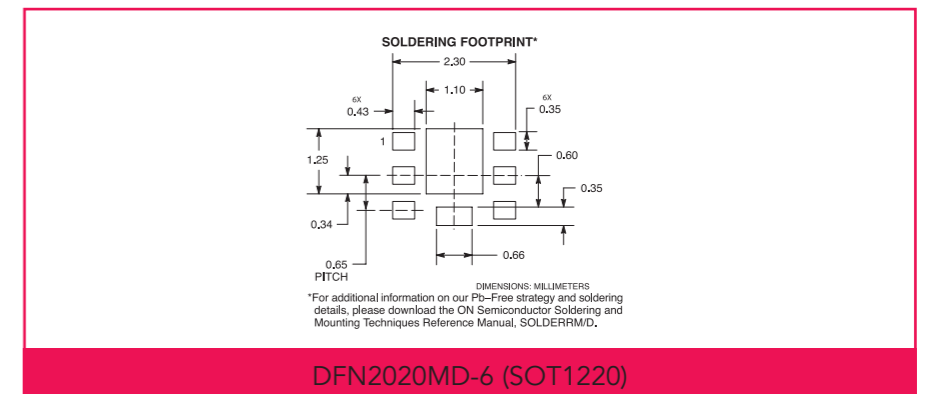
DFN2020D-6 (SOT1118D)



DFN2020D-6 (SOT1118D)



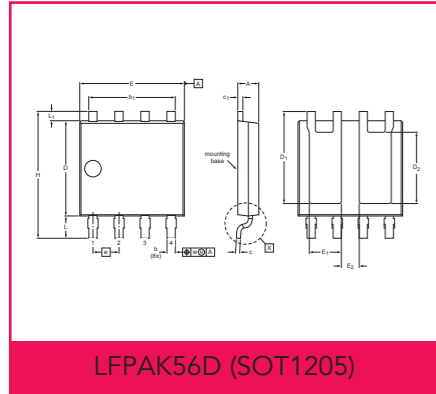
DFN2020MD-6 (SOT1220)



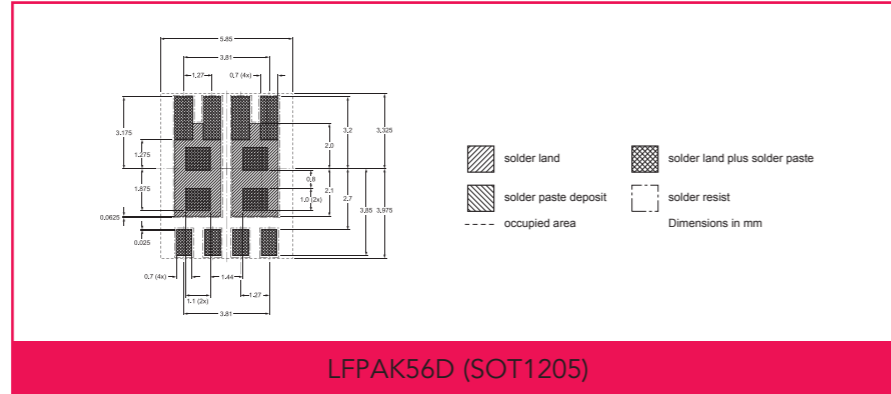
DFN2020MD-6 (SOT1220)

Dimensions in mm

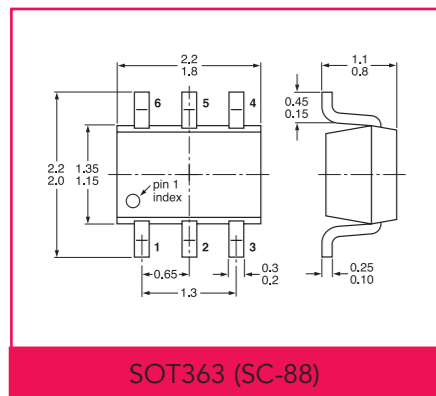
6-pin SMD packages



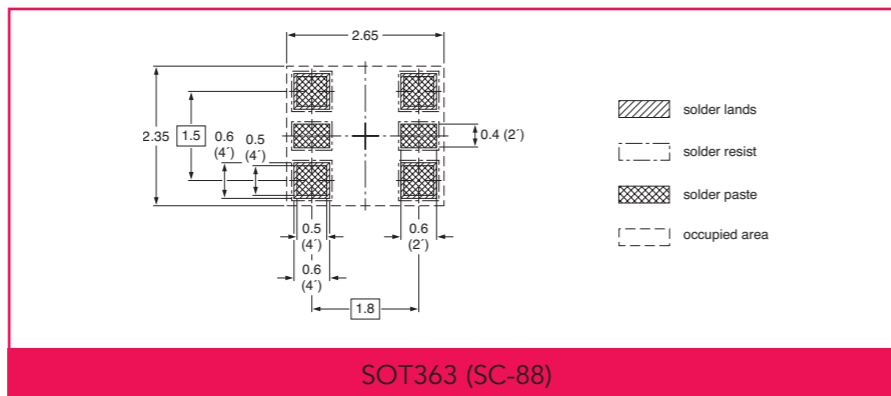
LFPAK56D (SOT1205)



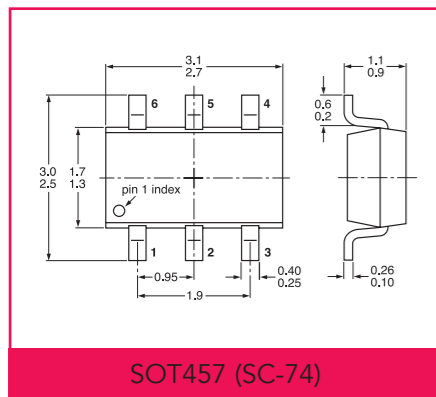
LFPAK56D (SOT1205)



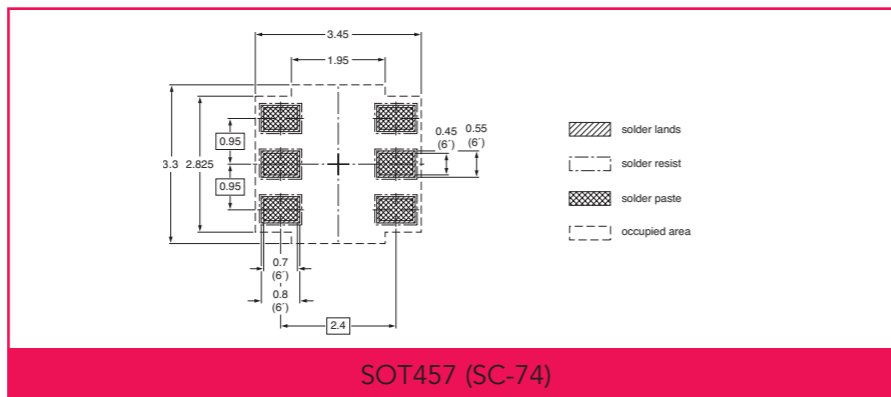
SOT363 (SC-88)



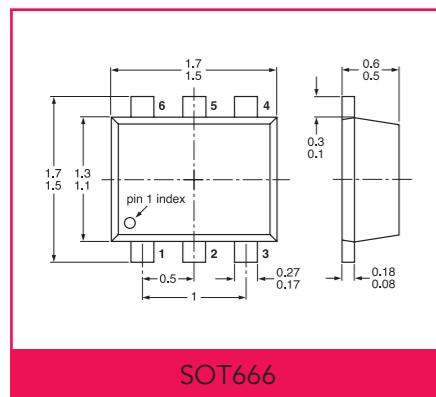
SOT363 (SC-88)



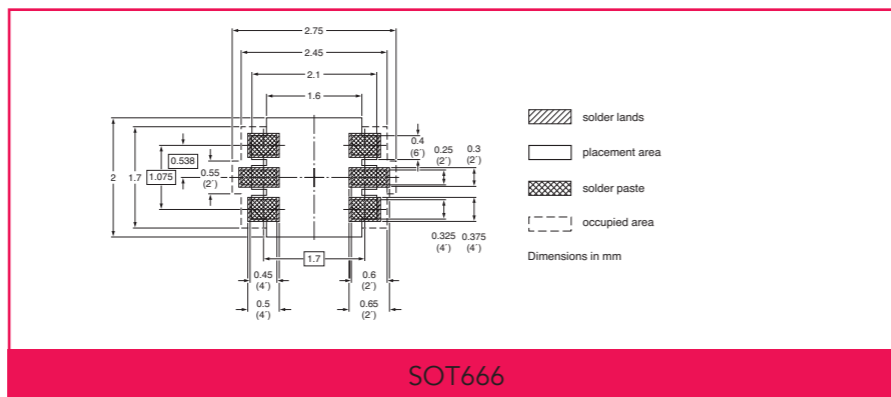
SOT457 (SC-74)



SOT457 (SC-74)



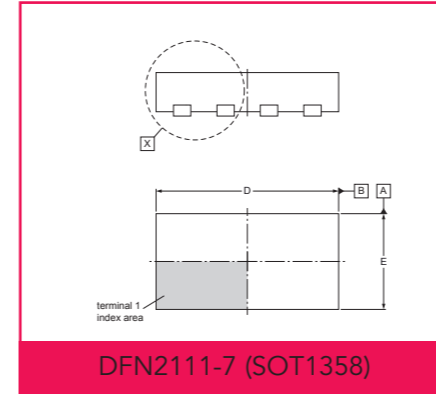
SOT666



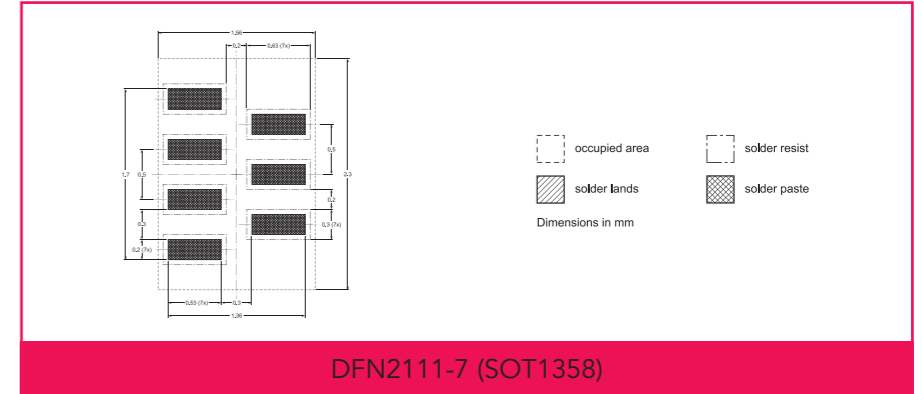
SOT666

Dimensions in mm

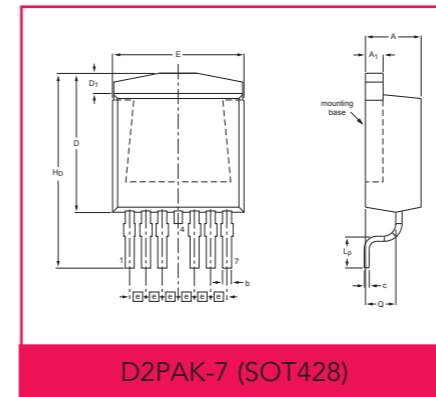
7-pin SMD packages



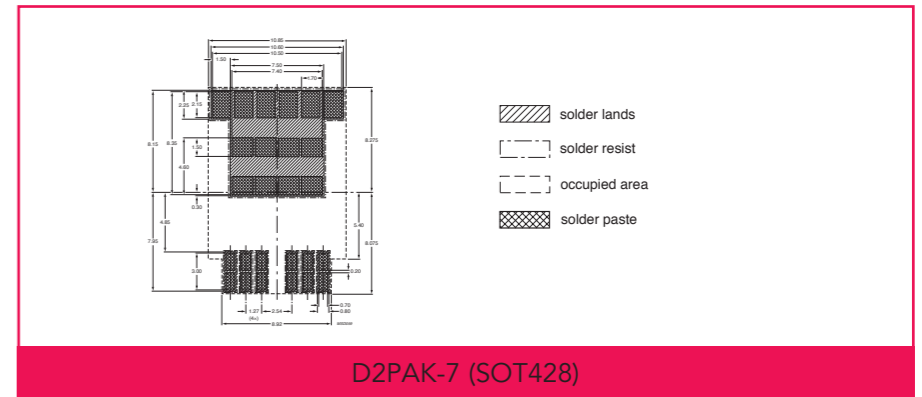
DFN2111-7 (SOT1358)



DFN2111-7 (SOT1358)

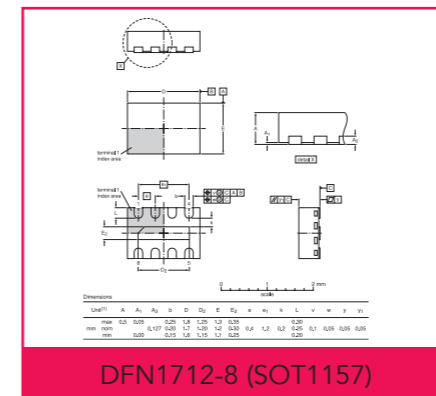


D2PAK-7 (SOT428)

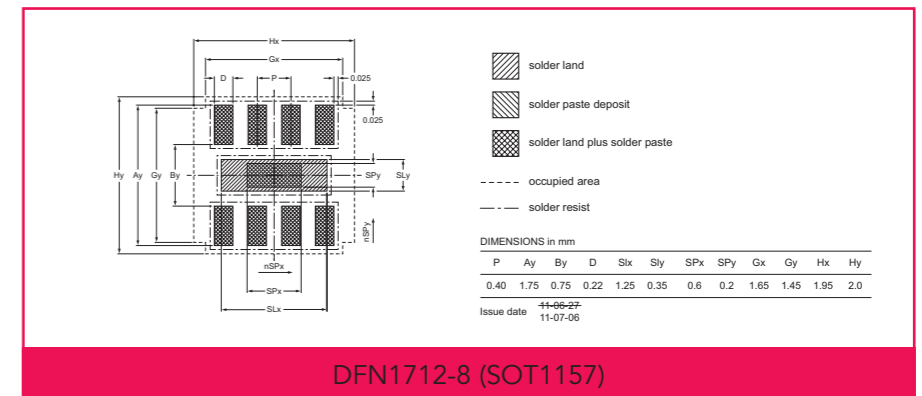


D2PAK-7 (SOT428)

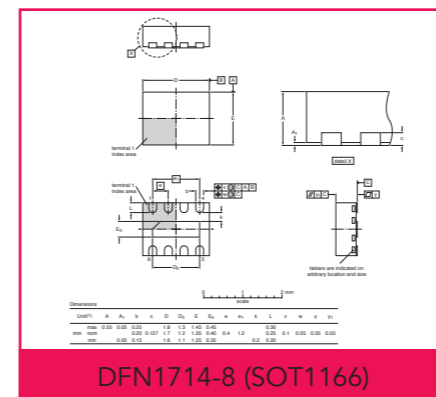
8-pin SMD packages



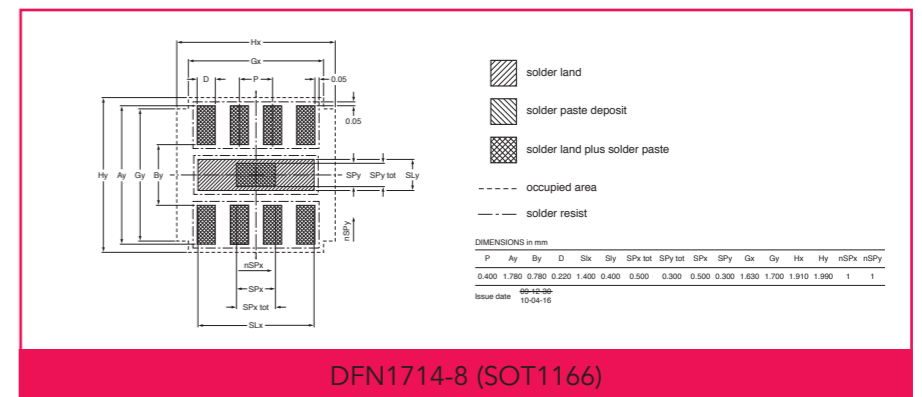
DFN1712-8 (SOT1157)



DFN1712-8 (SOT1157)



DFN1714-8 (SOT1166)

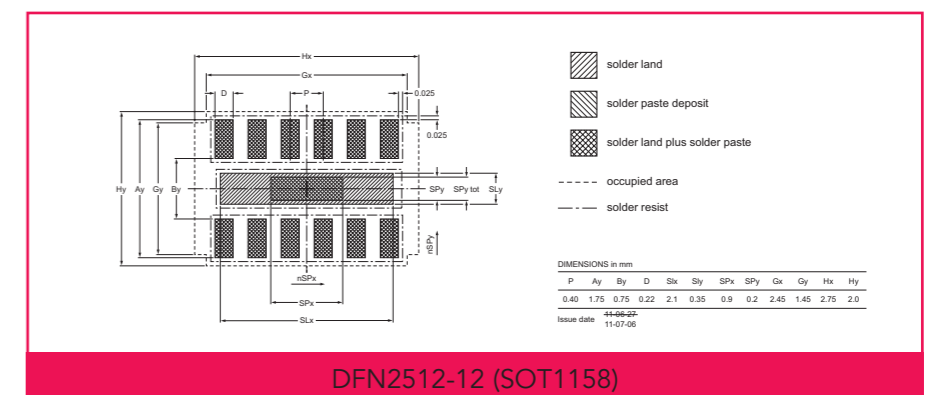
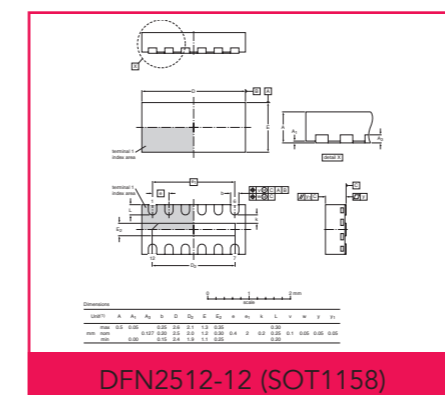
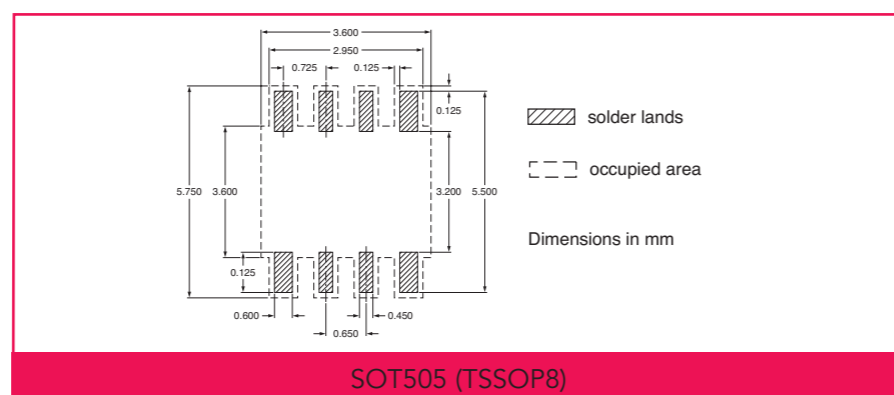
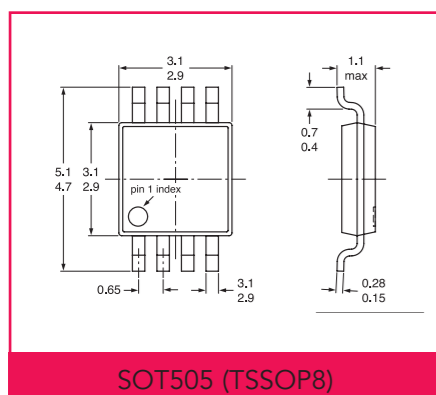
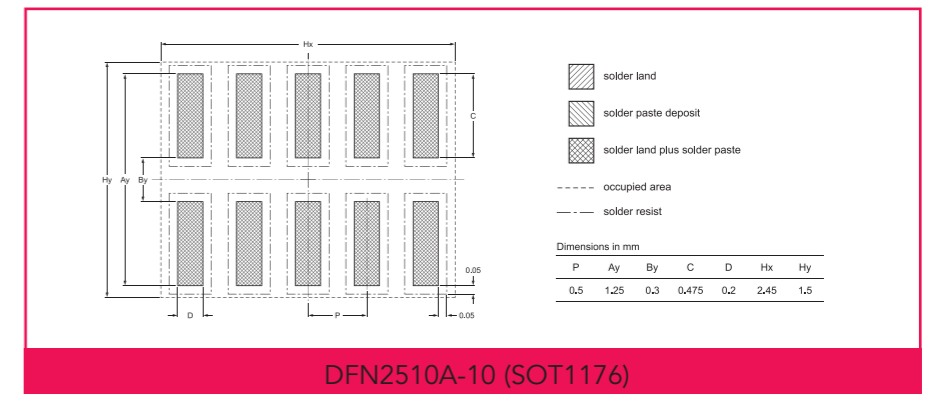
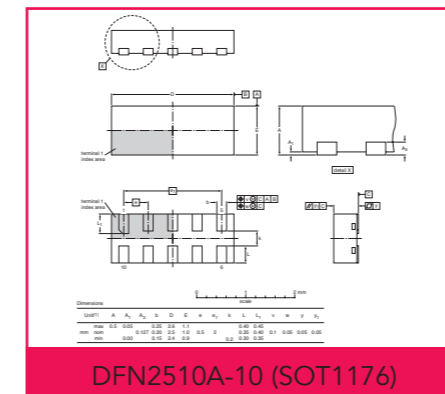
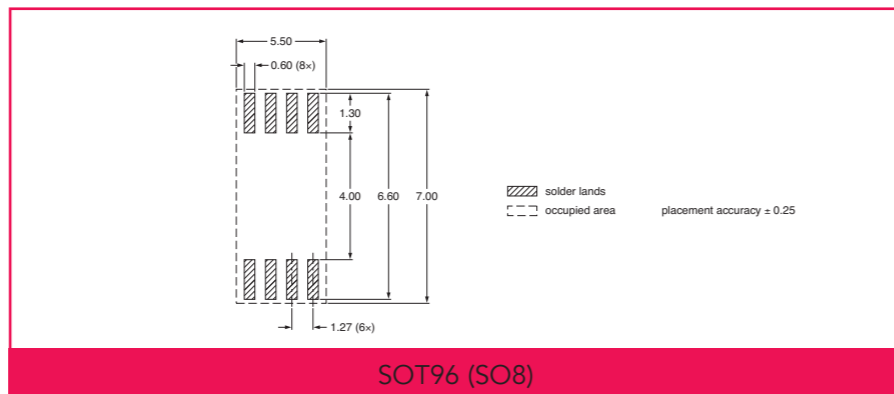
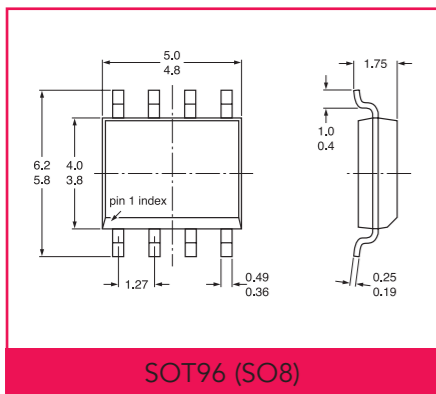
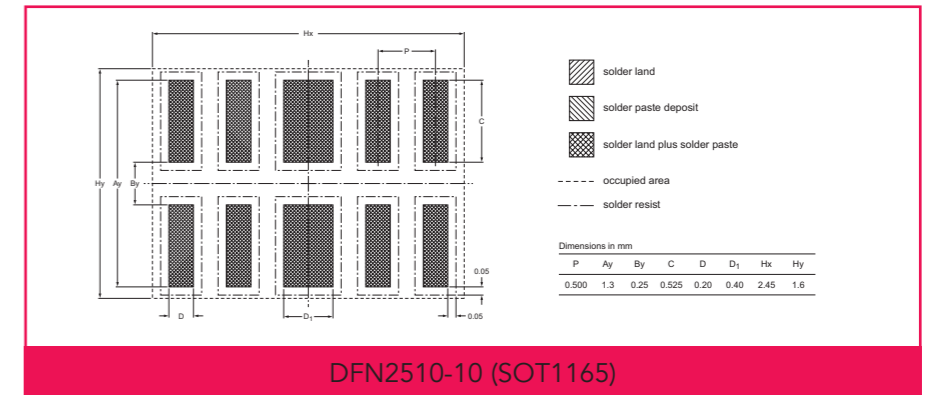
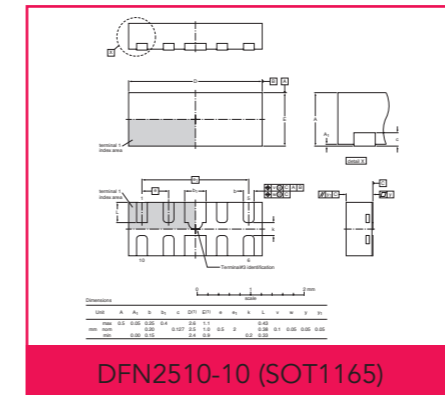
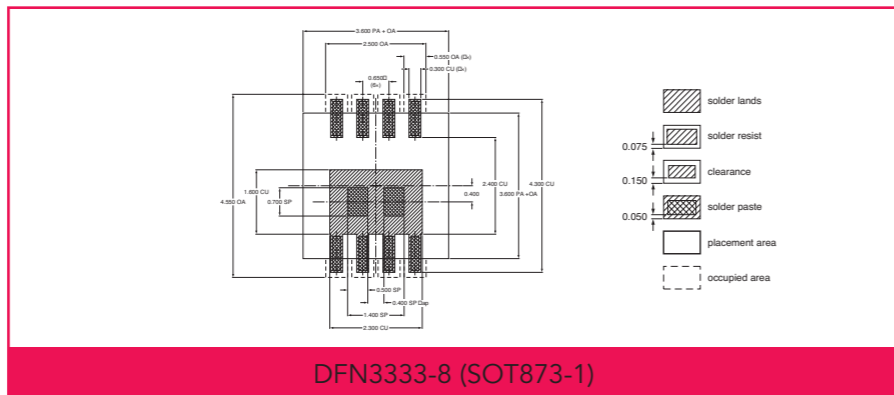
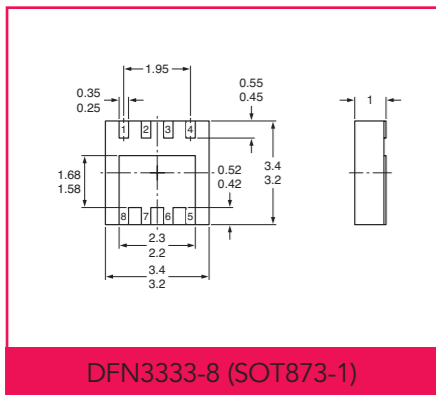
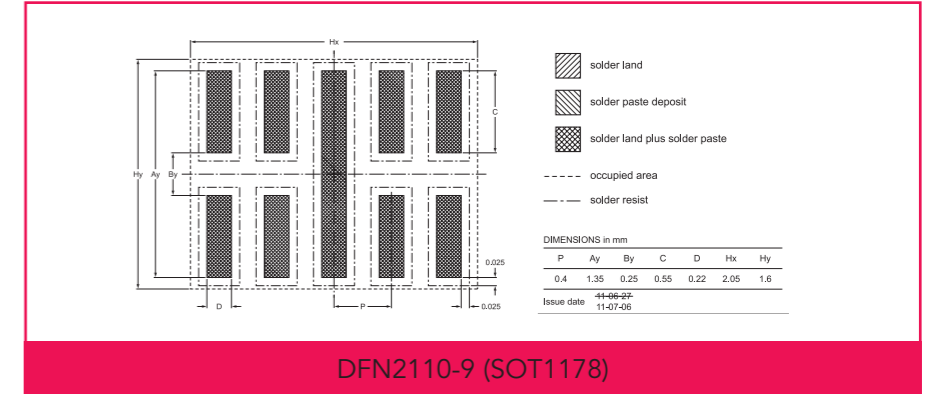
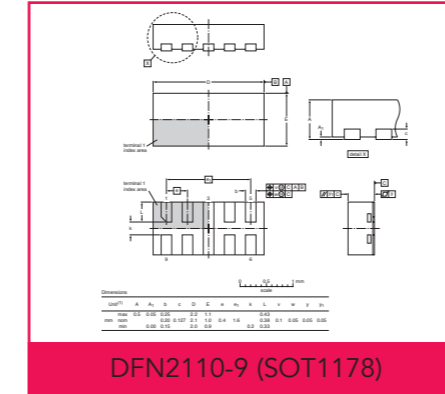
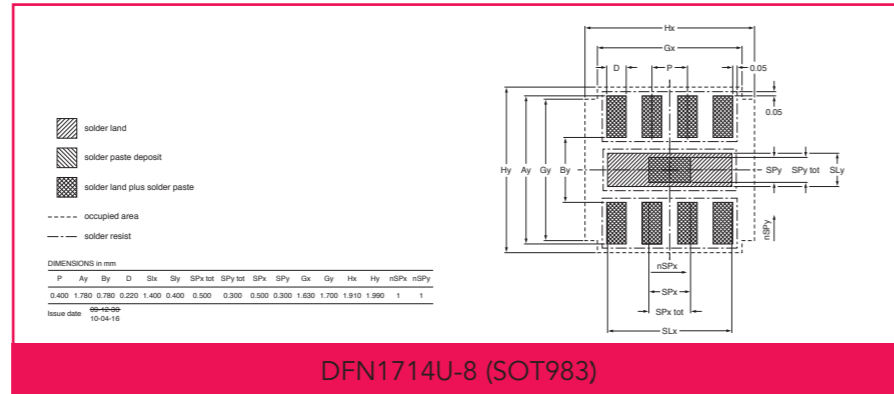
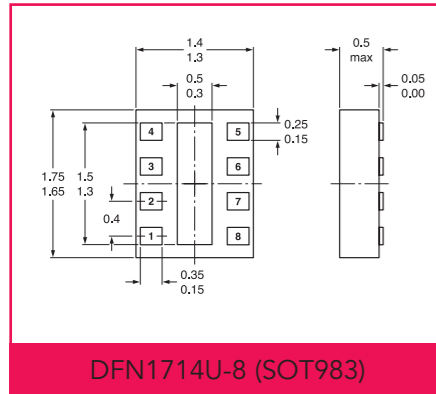


DFN1714-8 (SOT1166)

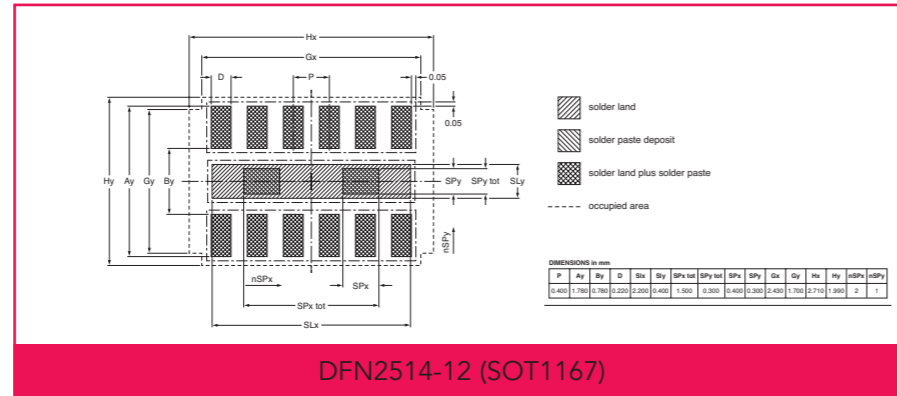
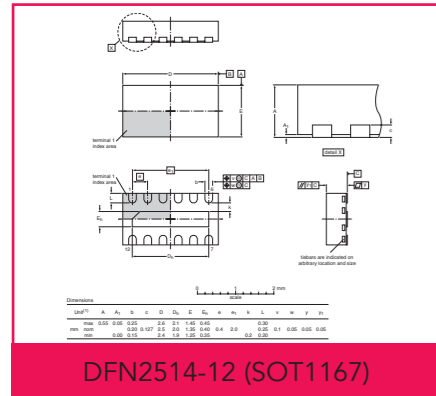
Dimensions in mm

8-pin SMD packages

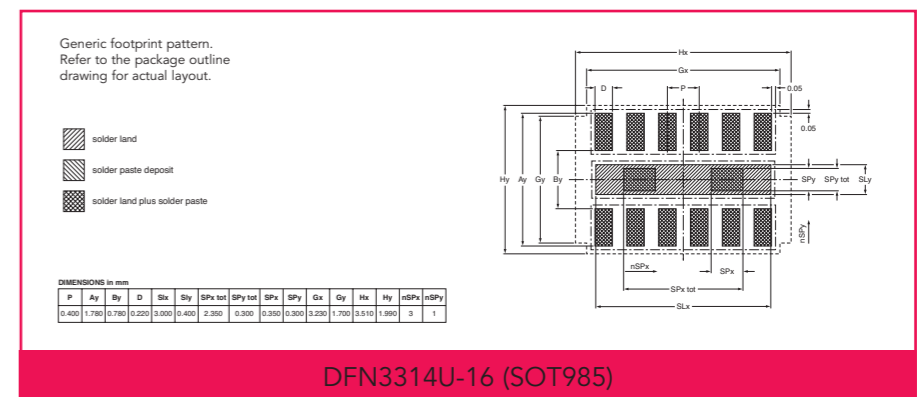
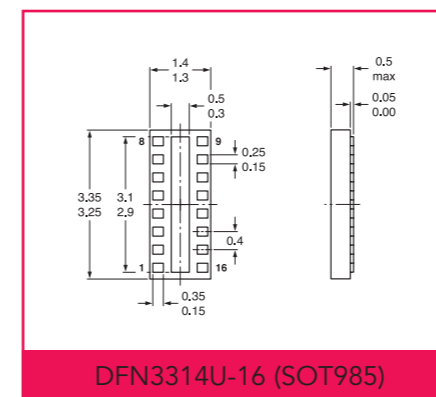
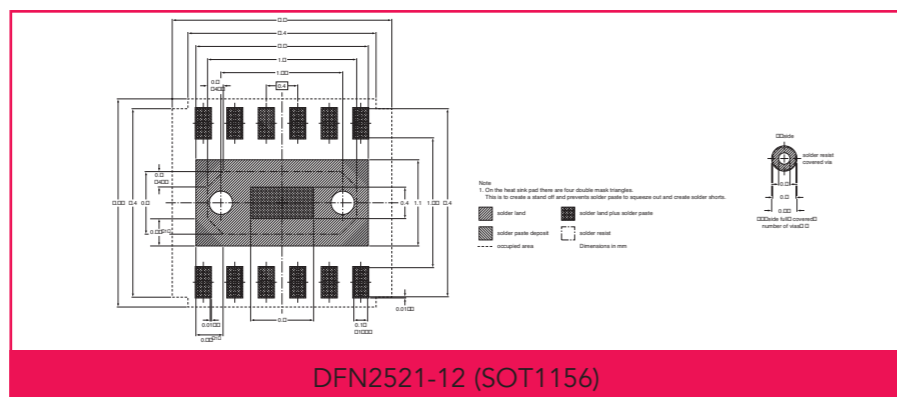
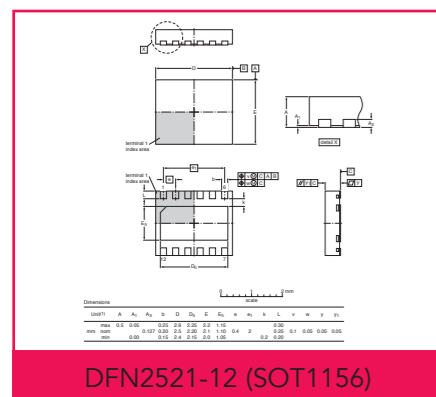
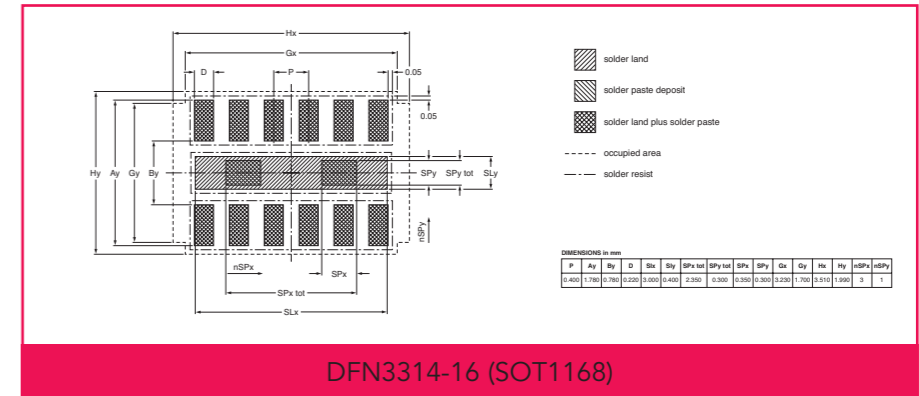
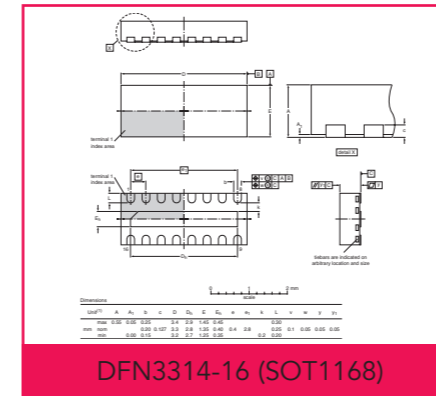
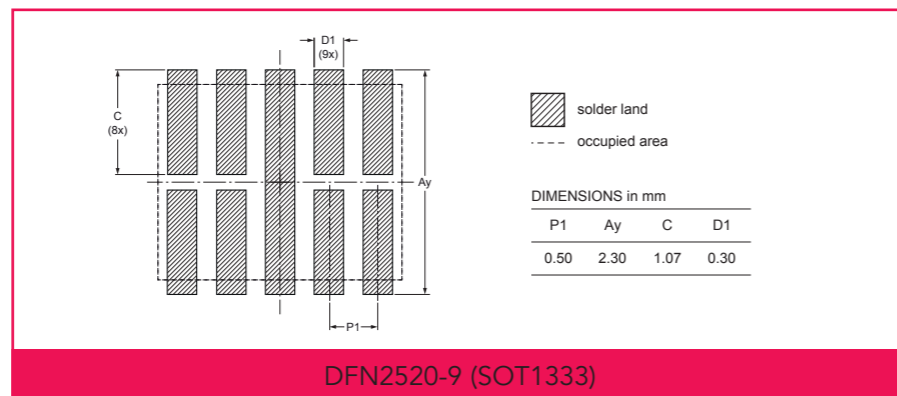
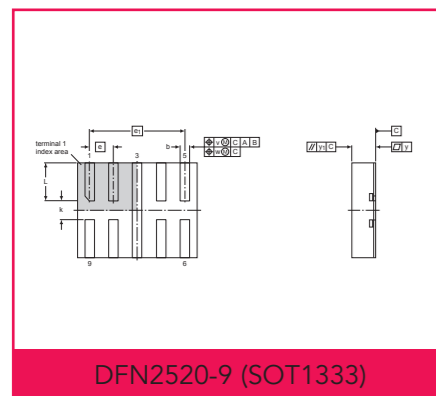
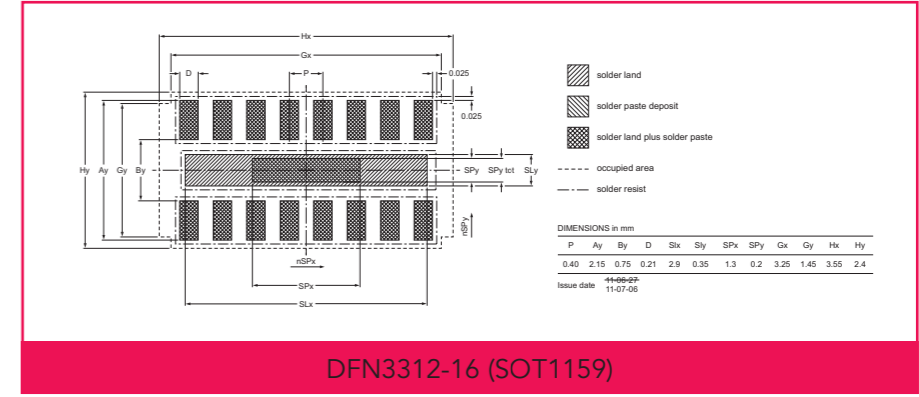
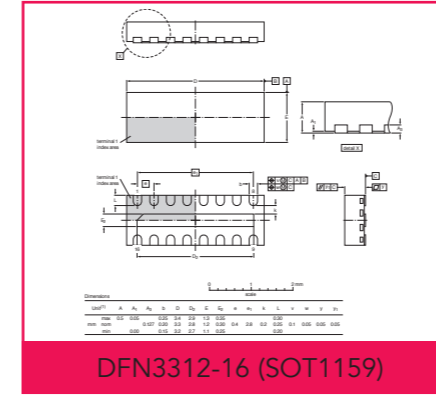
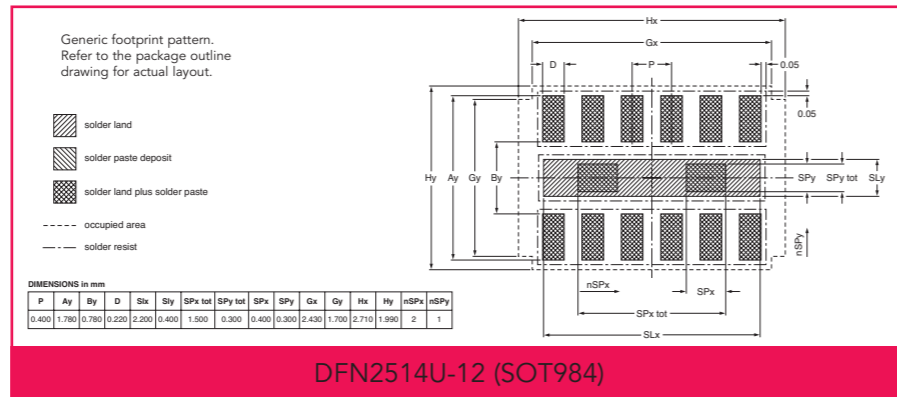
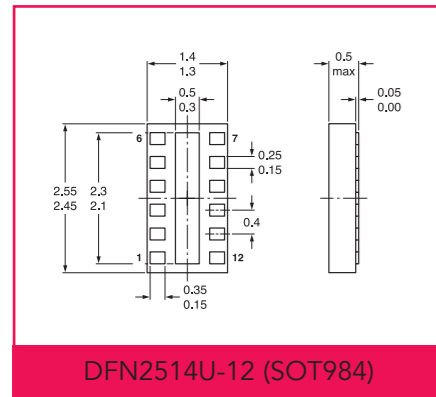
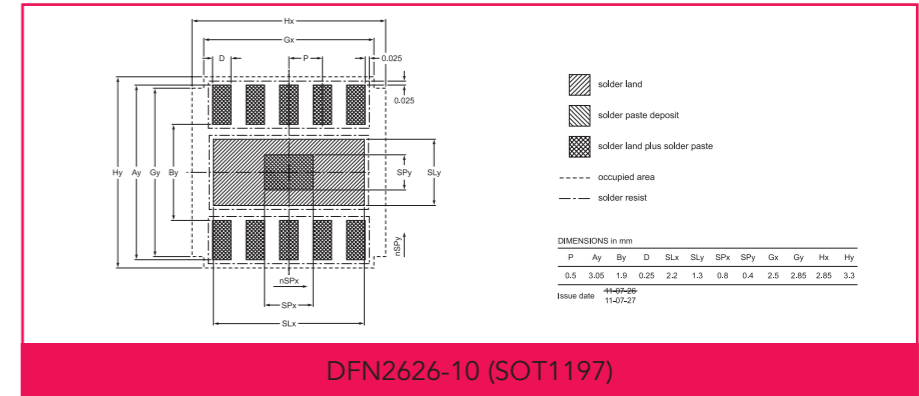
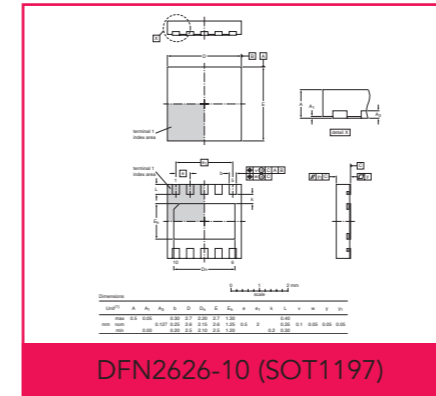
More than 8-pin SMD packages



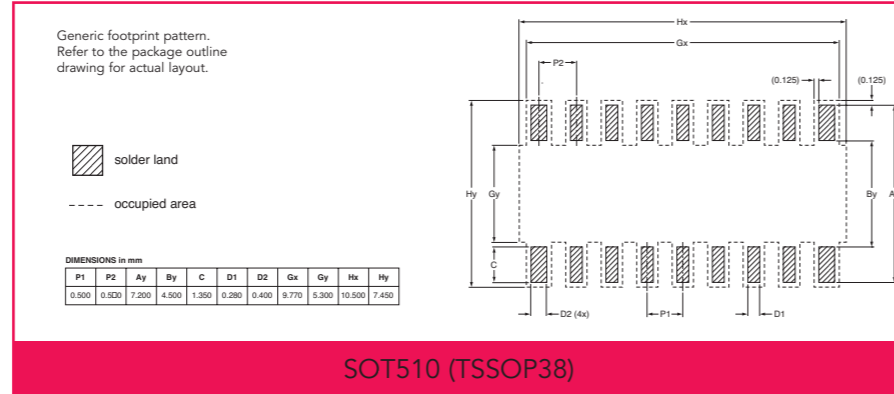
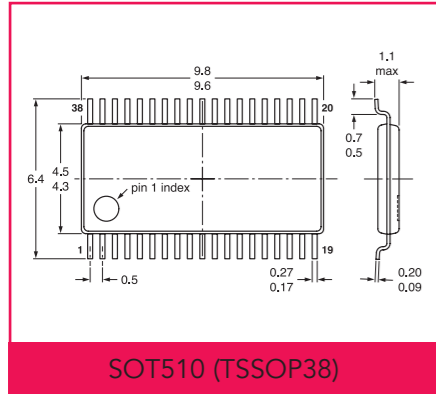
More than 8-pin SMD packages



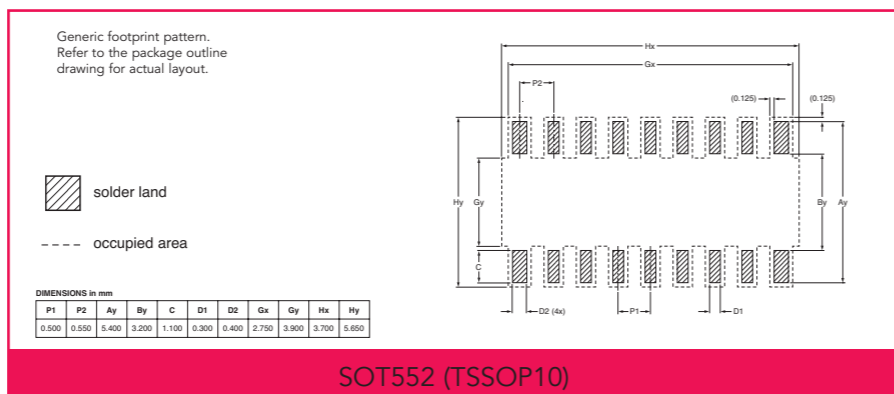
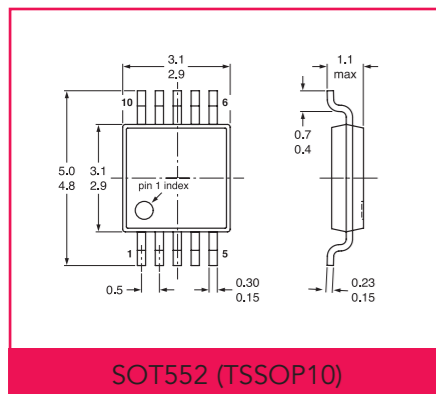
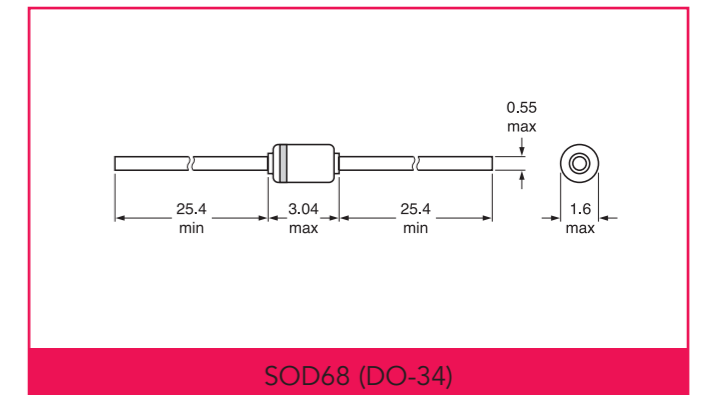
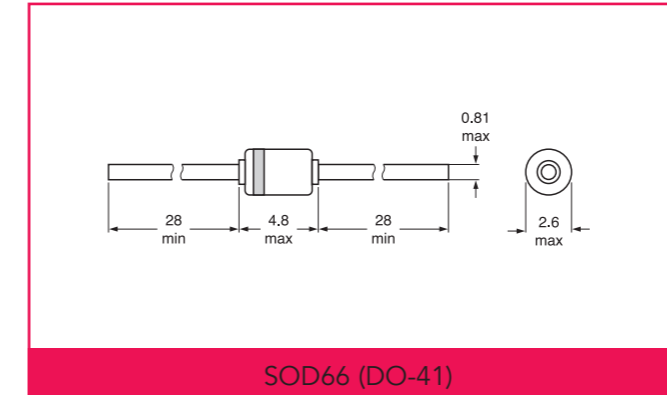
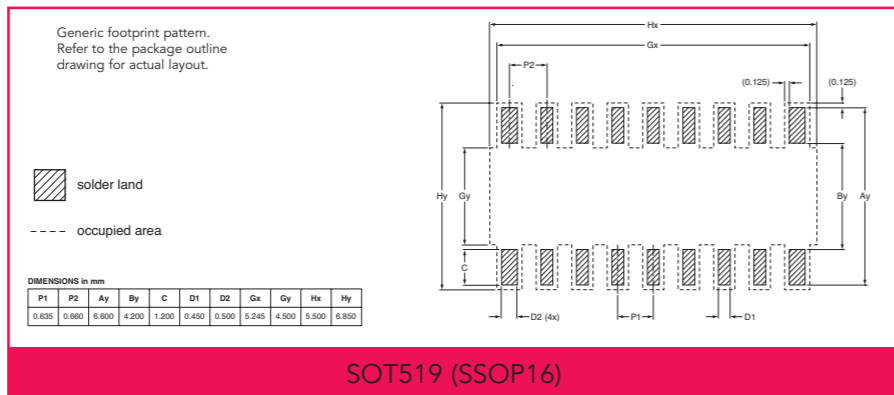
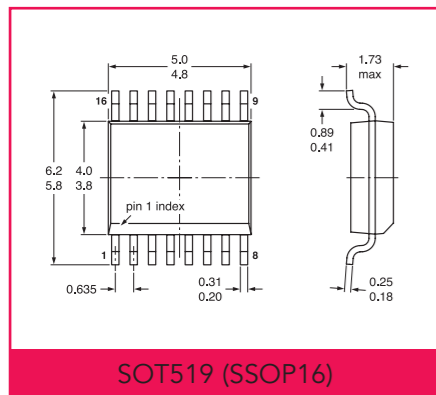
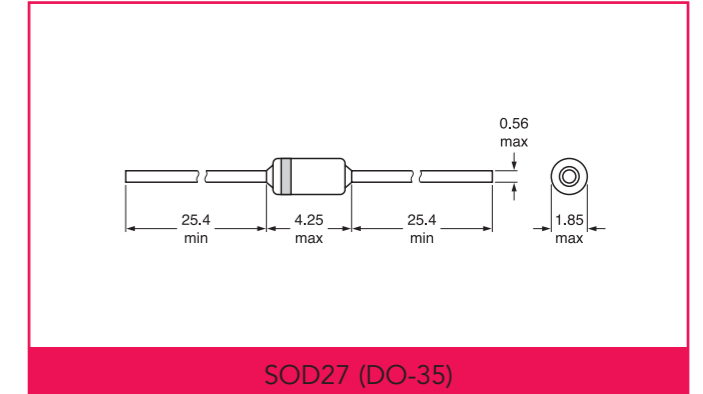
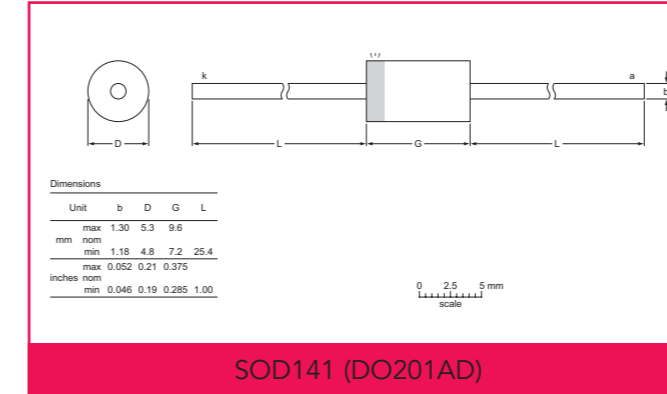
More than 8-pin SMD packages



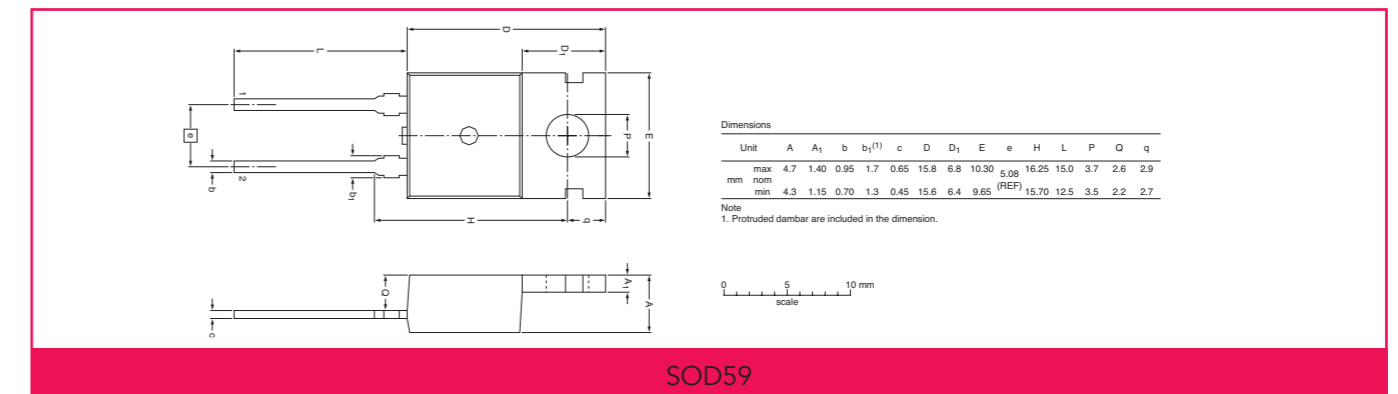
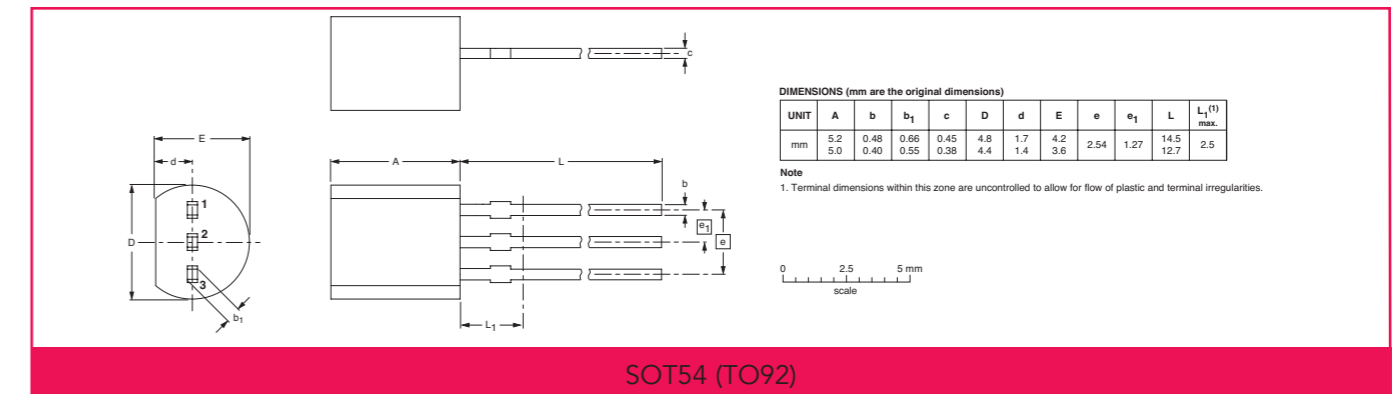
More than 8-pin SMD packages



Glass diodes



Single-ended and through-hole packages



Single-ended and through-hole packages

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7	1.40	0.9	1.6	1.3	0.7	16.0	6.6	10.3	2.54	15.0	3.30	3.0	3.8	3.0	2.6
	4.1	1.25	0.6	1.0	1.0	0.4	15.2	5.9	9.7		12.8	2.79		3.5	2.7	2.2

Notes
 1. Lead shoulder designs may vary.
 2. Dimension includes excess dambar.

0 5 10 mm scale

SOT78 (TO220AB)

Single-ended and through-hole packages

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	c	D	D ₁	E	e	L	L ₁	L ₂	p	q	Q	
mm	2.0	0.0	1.1	1.0	0.0	16.8	0.5	10.0	2.50	5.08	2.0	0.0	0.0	10.0	0.0
	2.5	0.0	0.0	1.0	0.0	15.2	0.0	10.0	2.00	1.0	0.0	0.0	0.0	2.0	0.0

Notes
 1. Terminal dimensions within this zone are uncontrolled.
 2. Both recesses are $\pm 2.5^\circ$ 0.8 max. depth

0 5 10 mm scale

SOT186A (isolated TO220AB)

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	b ₂	c	D	D ₁ ref	E	e	L	L ₁ ref	p	Q	q	w
mm	4.7	1.40	0.9	1.4	1.72	0.6	16.0	6.5	10.3	2.54	14.0	3.7	2.6	3.0	2.7	0.2
	4.3	1.25	0.6	1.1	1.32	0.4	15.2	6.5	9.7		12.8	3.0	3.5	2.2	2.7	0.2

0 5 10 mm scale

SOT78D

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	D ₁	E	e	L	L ₁	Q
mm	4.5	1.40	0.85	1.3	0.7	11	1.6	10.3	2.54	15.0	3.30	2.6
	4.1	1.27	0.60	1.0	0.4		1.2	9.7		13.5	2.79	2.2

0 5 10 mm scale

SOT226

DIMENSIONS (mm are the original dimensions)

UNIT	A	b	c	D	E	e	e ₁	L	L ₁ (1) max.	P	Q	q	w
mm	2.8	0.88	0.58	11.1	7.8	2.29	4.58	16.5	2.54	3.1	1.5	3.9	0.254
	2.3	0.65	0.47	10.5	7.2			15.3	2.5	0.9	3.5		

Note
 1. Terminal dimensions within this zone are uncontrolled to allow for body and terminal irregularities.

0 2.5 5 mm scale

SOT82

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	c	D	D ₁	E	e	L	L ₁	L ₂	L ₃ (1)	L ₄ (2) max.	m	p	p ₁	q	Q	Q ₁	Q ₂	R	w
mm	4.5	1.39	0.85	0.7	15.8	6.4	10.3	1.7	9.8	5.9	5.2	2.4	0.5	0.8	3.8	4.3	3.0	2.0	4.5	8.2	0.5	0.4
	4.1	1.27	0.70	0.4	15.2	5.9	9.7		9.7	5.3	5.0	1.6		0.6	3.6	4.1	2.7					

0 5 10 mm scale

SOT263B-1

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	E	e	He max	j	k	L	L ₁ (1)	L ₂ max	m	p	Q	q	T	w
mm	4.8	2.9	0.8	1.1	0.7	15.8	10.2	5.08	19.0	2.7	0.8	14.4	3.3	0.5	6.5	3.2	2.6	2.6	2.55	0.4
	4.0	2.5	0.7	0.9	0.4	15.2	9.7		17.7	0.4	13.5	2.8	0.5	6.0	3.0	2.5				

Notes
 1. Terminals are uncontrolled within zone L₁.
 2. z is depth of T.

0 10 20 mm scale

SOD113

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	c	D ₁	D ₂	E	E ₁	e	e ₁	L	L ₁ (2) max.	Q	w
mm	2.38	0.93	0.89	0.56	1.10	6.22	6.73	5.21	4.57	2.285	9.6	2.7	1.1	0.3
	2.22	0.46	0.71	0.46	0.96	5.98	6.47	5.00	BSC(1)	BSC(1)	9.2		1.0	

Notes
 1. Basic spacing between centers.
 2. Terminal dimensions are uncontrolled within zone L₁.

0 2.5 5 mm scale

SOT533

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CURRENT PACKAGE TECHNOLOGY

POWER PACKAGES



TO-220 / SOT78
15.6 x 10.0 x 4.4 mm

DPAK / SOT428
6.6 x 6.1 x 2.3 mm

SMB
5.3 x 3.6 x 2.3 mm

SMA
5.2 x 2.6 x 2.2 mm

SOT8 / SOT96
5.0 x 6.0 x 1.8 mm

LOW-POWER PACKAGES



1.6 x 1.6 mm size
SOT416 – SC75/
SOT666 – SOT563

2 x 2 mm size
SOT323 – SC70
SOT363 – SC88

3 x 3 mm size
SOT23
SOT457 – SC74

Boost power

Save system costs

Optimize energy efficiency

Minimize board space

NEW PACKAGE TECHNOLOGY

CLIP-BOND PACKAGES

Miniaturization of power



LFBPAK56
SOT669
4.9 x 4.5 x 1.0 mm

LFBPAK33
SOT1210
3.3 x 3.3 x 0.85 mm

CEP15
SOT1289
6.3 x 4.5 x 0.8 mm

CEP3
SOD123W
2.6 x 1.7 x 1.0 mm

CEP5
SOD128
3.8 x 2.8 x 1.0 mm

LEADLESS DFN AND WLCSFP PACKAGES

Highest performance with minimal size



DFN2020
2.0 x 2.0 x 0.6 mm

DFN1010
1.1 x 1.0 x 0.37 mm

DFN1006
1.0 x 0.9 x 0.37 mm

WLCSFP6
p-lead 6 Ball

WLCSFP4
p-lead 4 Ball



GET ON BOARD, NAVIGATE YOUR PACKAGE FUTURE



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